

CATALOGUE 2019/2020

Welcome to the World of Power Electronics



HIGHLIGHTS

1

POWER MODULES

2

IGBT DRIVER

3

STACKS

4

SYSTEMS

5

DISCRETES
ACCESSOIRES

6

INFORMATION
SERVICE & CONTACT

7

OVERVIEW

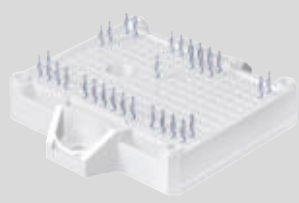
Product Range

2 POWER MODULES

CHAPTER



MiniSKiiP Page 22



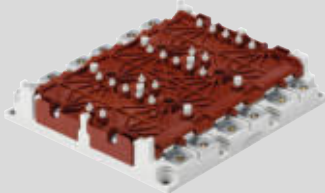
SEMITOP Page 24



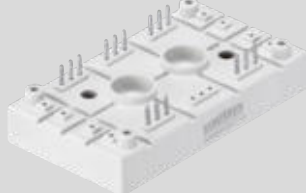
SEMiX Page 26



SEMITRANS Page 28



SKiM Page 30



SEMIPONT Page 32



SEMI PACK Page 34



SEMiSTART Page 36

Intelligent Power Modules



SKiiP Page 140

Product Classes	
IGBT Modules	38
Full Silicon Carbide Modules, Hybrid Silicon Carbide Modules	78, 88
MOSFET Modules	98
Thyristor / Diode Modules	104
Bridge Rectifier Modules	120

3 IGBT DRIVERS

CHAPTER



SKYPER Page 156

5 SYSTEMS

CHAPTER



SKAI Page 186

6 DISCRETES

CHAPTER

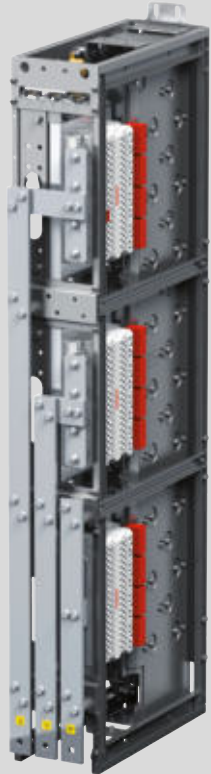


Diodes
Thyristors
Chips Page 196

4 STACKS

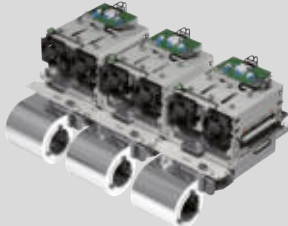
CHAPTER

Water-cooled IGBT



SEMISTACK RE Page 164

Air-cooled IGBT



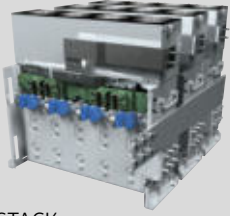
SEMIKUBE Page 166

Diode/Thyristor



SEMISTACK CLASSIC Page 168

Customized



SEMISTACK Application Page 170

FROM CHIP TO SYSTEM

What Sets Us Apart

SEMIKRON offers high-level vertical integration in power electronics – from chip to system. We push the boundaries of module technologies in series products with sinter technology and a wide range of packaging technologies. Besides our unrivalled portfolio of industry standard modules, we also develop custom-built solutions for extended requirements.



Helping Your Business Use Our Products

» Application expertise is our strength

Being able to access service, technical support and experts that our customers can always rely on is instrumental to our customers' success.

Today, increased product diversity in power semiconductors calls for customer support far beyond the information contained in data sheets. Only comparison under application-specific conditions – such as voltage, switching frequency or cooling conditions – can demonstrate the differences in performance of available devices. That's why we continue to invest in our professional application engineering support, including lab space and reference designs.

In recent years, we have built a network comprising 25 sites across the globe to provide fast, comprehensive application support. Our application engineering teams work both locally and globally with our customers throughout the entire project life cycle. We strive to understand and help our customers overcome both big and small challenges throughout their projects. For example, we conduct topology studies to fully understand the advantages in the end user application and carry out benchmark investigations when needed. It is this application-centred approach that sets us apart from others.

How can SEMIKRON's application team help you with inverter design?

- Heatsink selection and TIM application
- DC link design and capacitor selection
- Isolation coordination
- Lifetime calculations
- Measurement support
- Application samples and reference designs



www.semikron.com/service-support/application-support

Stay Cool – Heat Dissipation is Our Job

» Thermal Interface Materials

SEMIKRON was the first power module manufacturer on the market to offer power modules with pre-applied thermal interface material. With more than two decades of field experience and more than fifteen million pre-printed modules in the field, benchmarks are being set. The modules with pre-applied TIM are printed in a clean environment on an automated and SPC controlled silk screen and stencil printing line.

For each requirement SEMIKRON offers the right choice of material. In addition to the standard silicone thermal grease, a phase change material and high performance thermal paste with improved thermal performance are also available.

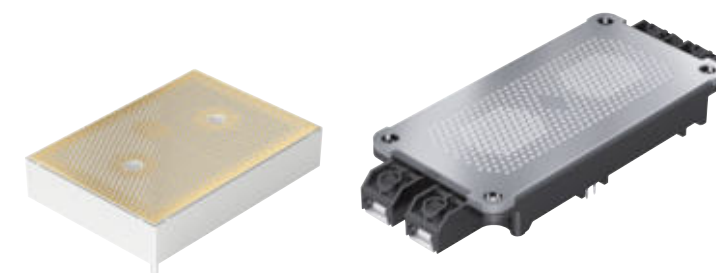
A thermal grease or a phase change material is recommended for the given customer needs for handling and module performance as well as for module type (with baseplate, baseplate-less). Phase change materials with a solid consistency at room temperatures can fully exploit the advantages that a non-smearing TIM layer offers on modules without any other drawbacks. Modules with no baseplate, on the other hand, usually require a lower-viscosity material to help improve robustness during assembly. Here, thermal grease is the preferred solution.

Key features

Increased productivity thanks to reduced handling costs and improved logistics
Low thermal resistance with optimised TIM layer thickness
Improved lifetime and reliability
Improved assembly robustness
Modules can be shipped directly to the assembly line without any additional treatment processes
Lower overall costs

Portfolio

Phase Change Material: TPC-Z-PC-P8; TPC-4000PE; PSX-PE = P8
Phase Change Material: TPC-V-PC-P-HT; TPC-7000 = HT
High Performance Thermal Paste = HPTP
Standard Thermal Paste: Wacker P12 = P12



mal-interface-materials



Four Key Factors for Your Success

» Power Electronic Stacks

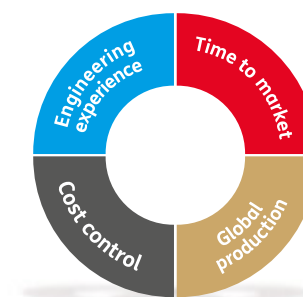
SEMIKRON's power electronic stacks enable our customers to prosper in dynamic markets and meet any global challenge. With more than 200,000 stacks in the field, SEMIKRON is the global market leader for power electronic stacks.

Our services are as multifaceted as our customers, highlighted by these four distinctive attributes: **time to market, cost savings, global production and engineering experience.** Our passion for power electronics and our commitment to high-performance design are the factors that make us your ultimate partner for value creation in the dynamic power electronics market.

The experience we have gained in over 40 years of high-performance stack design has reinforced the four essential ingredients needed for your success. In emerging markets, where new product innovation is essential, companies need to be nimble and have a fast time to market. In global markets, multiple production locations play a vital role in ensuring rapid deployment to more than one country, while also meeting local demand and building customer relationships. Quality and cost control are crucial factors in the long-term success of any project. Finally, success in highly competitive markets is underpinned by superior technical capability. All four of these prerequisites are addressed by SEMIKRON's power electronic stacks.



Contact us: power-stack@semikron.com
www.semikron.com/video/power-electronic-stacks



IGBT Generation 7: The New Benchmark for Motor Drives



IGBT Generation 7: The new benchmark for Motor Drives

The generation 7 IGBTs represent the latest IGBT chip technology. This new generation is specifically designed to match the requirements of motor drive applications. The IGBTs come with a significantly lower forward voltage drop and deliver optimised switching performance. Thanks to roughly 25% smaller chips, higher nominal currents can fit into existing power module packages.

In application, the IGBT 7 provides reduced power losses or increased maximum output power and power density. This translates into lower system costs. As to motor drives, the generation 7 IGBT will initially be introduced into conventional drive topologies: CIB (Converter-Inverter-Brake), sixpack and half-bridge configurations. For low and medium power drives, MiniSKiiP and SEMiX E1/E2 are the first available choice. For higher power classes IGBT 7 is available in SEMiX 3 press-fit and SEMiX 6 press-fit. More power modules are to follow.

Product specifications/features

Optimized IGBTs for motor drive applications

Reduced saturation voltage and chip size

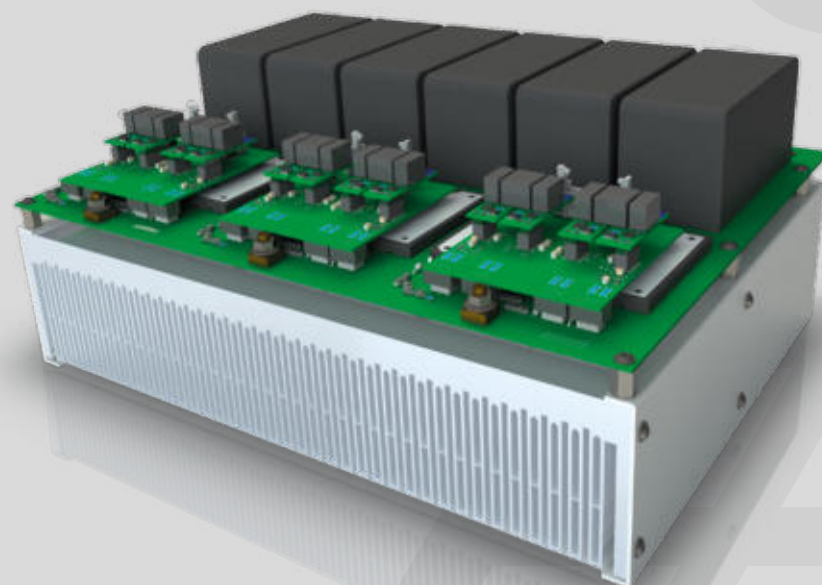
Higher nominal currents

Up to 45% more module output power

Lower overall system costs

IGBT 7

Up to 180kW for Solar String Inverters



MiniSKiiP Dual Split MLI

SEMIKRON offers a broad portfolio of 3-level modules, the latest addition being the MiniSKiiP Dual Split MLI. The new module increases the nominal current to 400A in 1200V and 950V devices and comes with the option of SiC Schottky diodes in the neutral path for maximum efficiency. This new module allows for baseplate-less, PCB-mounted inverter designs with benchmarking power density of up to 180kW for 1500VDC photovoltaic systems. The benefits of the MiniSKiiP Dual's SPRiNG contact layout are low-inductance DC-link designs, easy driver integration and parallel AC power connections.

Product specifications/features

Up to 180kW baseplate-less design for direct PCB mounting

950V IGBT 7 chips and SiC Schottky diodes in neutral path for maximum efficiency

Low-inductance DC-link connection

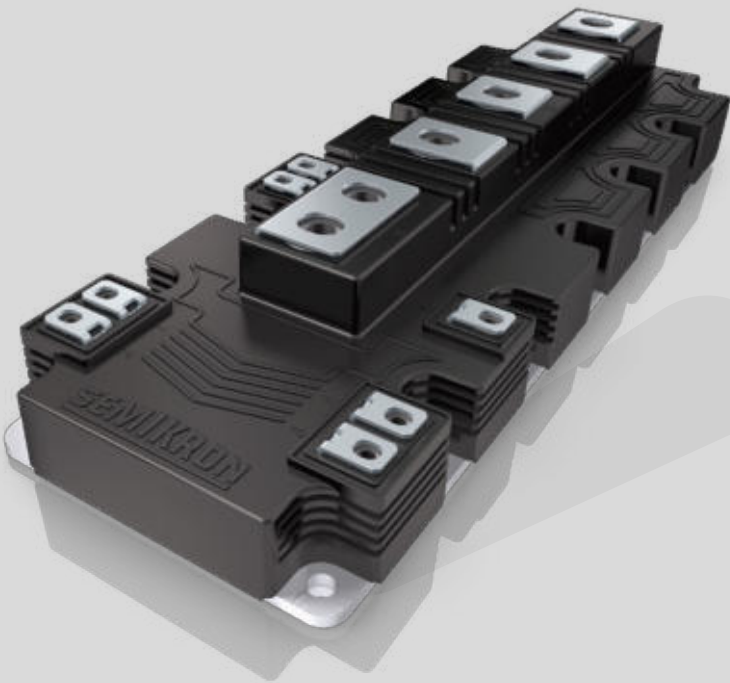
Spring contacts for easy PCB routing

Well established, highly reliable MiniSKiiP package

Optimised production costs thanks to quick and easy assembly

IGBT 7

3-Level Topologies for Wind Turbines



SEMIGRAN 10

In any new wind turbine developments, the primary objective is to reduce the cost of energy as well as to increase the output power. But this can't happen without new technologies. One solution is to increase the voltage up to the 1000VAC (1500VDC) Low-Voltage Directive limit. SEMIGRAN's SEMITRANS 10 MLI is a 3-level NPC module that meets the needs of wind energy converters perfectly. Using 3-level topologies helps cut converter losses by 50 percent, lowering filter costs by some 30 percent. Besides lower converter losses, cable losses or diameters can also be reduced by around 30 percent.

Product specifications/features

Reduced System Costs	Higher Efficiency
Neutral power module cost compared to 2-Level	Lower semiconductor losses
Lower filter costs	Lower filter losses
Lower cabling costs	Lower cable losses
Reduced cooling needs	
Smaller EMI filter	

High Power and Outstanding Reliability for EV Charger



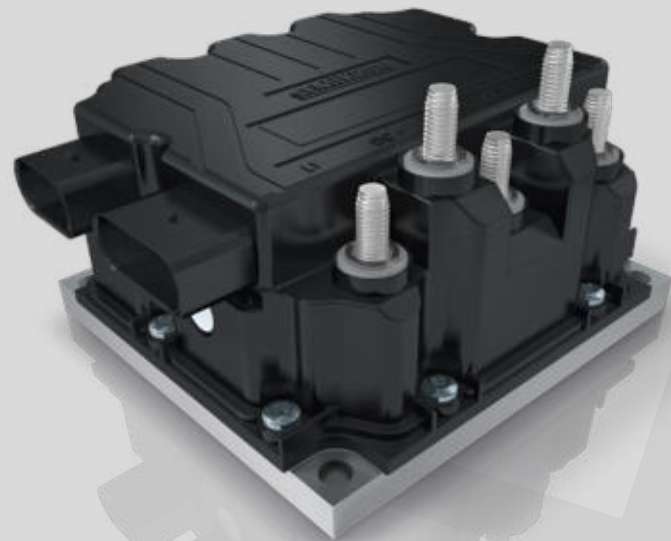
PowerCell

One of the main requirements for the widespread use of electric vehicles is having an accessible EV charging infrastructure. Governments and industries worldwide are preparing to invest in the charging infrastructure. The critical points in the product decision are costs, power and reliability. SEMIGRAN offers a comprehensive portfolio of products that meet the needs of fast charge equipment from as little as 22kW right up to 450kW. Our new 50kW PowerCell enables companies to market DC fast chargers using an existing power electronics platform. Availability, efficiency and reliability guarantees fast time to market and low upfront investment costs. In combination with a secure supply chain and a modular design, the PowerCell plays a vital role in the successful deployment of your DC fast chargers.

Product specifications/features

50kW rated power	3L PFC topology with 6 rather than 12 driver channels
AC Input: 400V ± 10 %	Efficient 650V IGBT technology thanks to split DC link
500VDC or 1000VDC output voltage	HF transformer for safe galvanic isolation
f _{sw} : 40kHz	40kHz switching frequency for optimum performance
PF > 0.98	Integrated pre-charge topology
Efficiency > 94%	Standard technology for high availability
Scalable up to 350kW	

Most Compact MOSFET Inverter Platform for Battery Vehicles



SKAI 3 LV

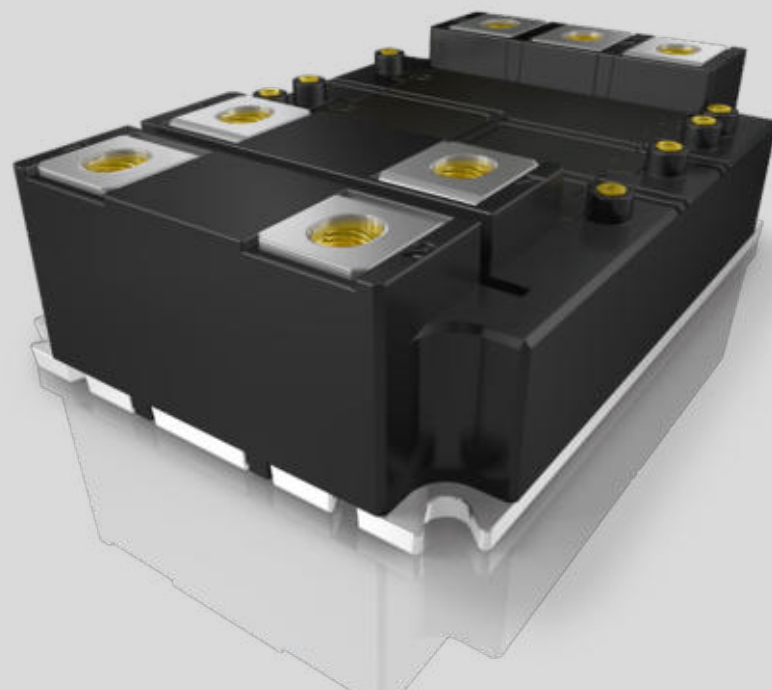
SKAI 3 LV is the 3rd generation of industrial MOSFET inverters for material handling and battery powered vehicles with more than 1.5 million MOSFET inverters in the field.

The 3rd generation is a platform concept for standard inverter designs or customized designs tailored to the customer's needs. The inverter connects easily to the customer control board, facilitating quick and easy design while leaving control to the customer.

Product specifications/features

Easy-to-use gate driver interface
Voltage, current and temperature sensors
Gate driver with protection
Low-inductance, low-loss power section
DC-link capacitors
Air and plate cooling
Platform for customised designs
Customer control board to be integrated in IP66 enclosure
Design-in kit available

The High-Power Standard in Traction, Renewables and Drives



SEMITRANS 20

The SEMITRANS 20 overcomes the limits of conventional module concepts and provides a new design approach for inverters used in applications such as traction, industrial drives and grid infrastructure. Optimised for the traction and medium-voltage market, the SEMITRANS 20 is designed as a half-bridge configuration featuring a built-in temperature sensor and opposite DC and AC power terminals. Compared to conventional modules, the stray inductance is as much as 75% lower, providing greater operational safety and facilitating paralleling. The service life of the new SEMITRANS 20 traction module is up to 3 times longer than that of conventional traction modules. This is achieved through the use of state-of-the-art technologies such as sintered chips and AlCu Bond wires. The standardised package meets the increasing demands for lower costs, greater efficiency and durability for power electronics in industry, transportation and infrastructure.

Product specifications/features

Available in 1.7kV and 3.3kV
Standard Package
Innovative technologies with sintered chip interconnects and AlCu wire bonds
Next level lifetime and power density
Lower mounting and material cost in inverter assemblies
Ideal for paralleling and scaling
Support Package for testing and qualification

Power Modules

	PAGE
IGBT Modules	38
Full Silicon Carbide Modules	78
Hybrid Silicon Carbide Modules	88
MOSFET Modules	98
Thyristor / Diode Modules	104
Bridge Rectifier Modules	120

MiniSKiiP®



Fast, Cost-Efficient and Reliable Single-Screw Mounting

MiniSKiiP®

Short facts

Low-cost assembly, high production run rate, high yield
Small and compact inverter design
Excellent reliability and long product life time

Key features

Solder-free SPRiNG technology for fast and easy assembly
Without copper baseplate for cost efficient designs
Easy and flexible PCB routing without pin holes
Current range 4A to 400A for inverter range up to 90kW with one product platform
Comprehensive setup of topologies:
CIB, Sixpack, Twelvepack, H-Bridge, Half-Bridge,
3-level, bridge rectifiers with brake chopper

required, no dedicated tools are needed for MiniSKiiP assembly. Instead, a single or two screw connection is used. The printed circuit board (PCB), the power module and the heat sink are assembled in one mounting step. This connection technology features a number of additional advantages: the PCB can be more flexible in design, as the printed circuit board does not need to include holes for solder pins or press-fit connections. The springs provide a flexible connection between the PCB and the power circuitry which is far superior to a soldered joint, particularly under thermal or mechanical stress conditions which can affect lifetime. Thanks to the high mechanical pressure provided by the springs, an air-tight, reliable electrical connection is achieved.

Applications

With two decades of field experience and more than 45 million modules in the field, this module platform has proven successful in all standard applications. Key applications include all kinds of inverters, such as standard drives, stand-alone drives, servo drives, system drives, solar inverters, UPS systems and welding machines. Thanks to the excellent reliability of spring contacts, applications such as agricultural vehicles or pitch drives in wind turbines benefit from MiniSKiiP technology as well.

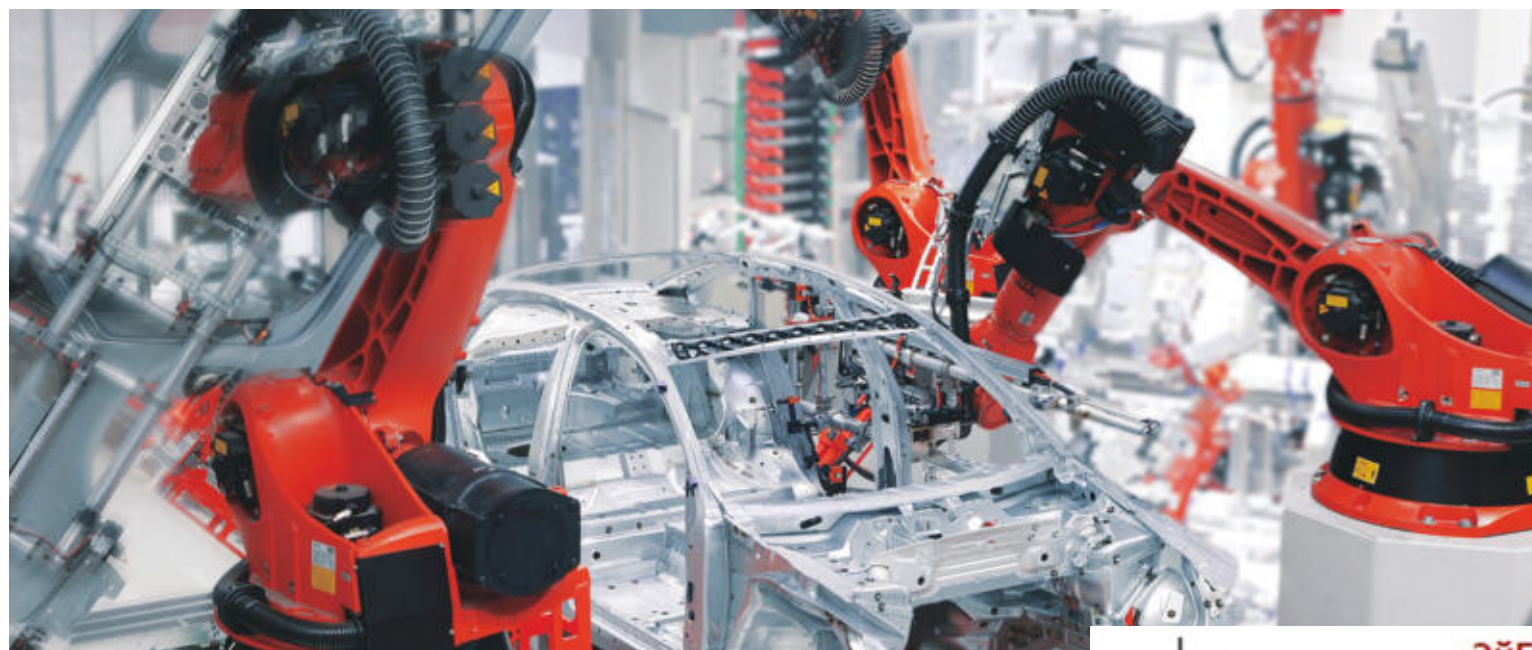
Benefits

An important mechanical feature of MiniSKiiP modules is the outstandingly easy assembly and service friendly spring contact for load and gate terminals. Compared to conventional solder or press-fit modules, where expensive equipment is

Product range

MiniSKiiP modules are designed for 600V/650V, 1200V and 1700V with 4A - 400A nominal chip currents, and feature Trench IGBT technology in combination with the SEMIKRON CAL diodes. 1200V Trench IGBT 4/IGBT 7 and CAL 4 diodes are designed for maximum junction temperatures of 175°C. In addition to CIB, sixpack, twelvepack, H-bridge, half-bridge, 3-level and uncontrolled/half-controlled rectifiers as well as brake chopper, customer-specific modules are also available. What's more, the latest chip technology such as full and hybrid silicon carbide power modules meet the highest of power density and efficiency demands. For fast evaluation, lab test boards can be ordered for each module type.

Further information: www.semikron.com/miniskiiP



ЭйБиЭн

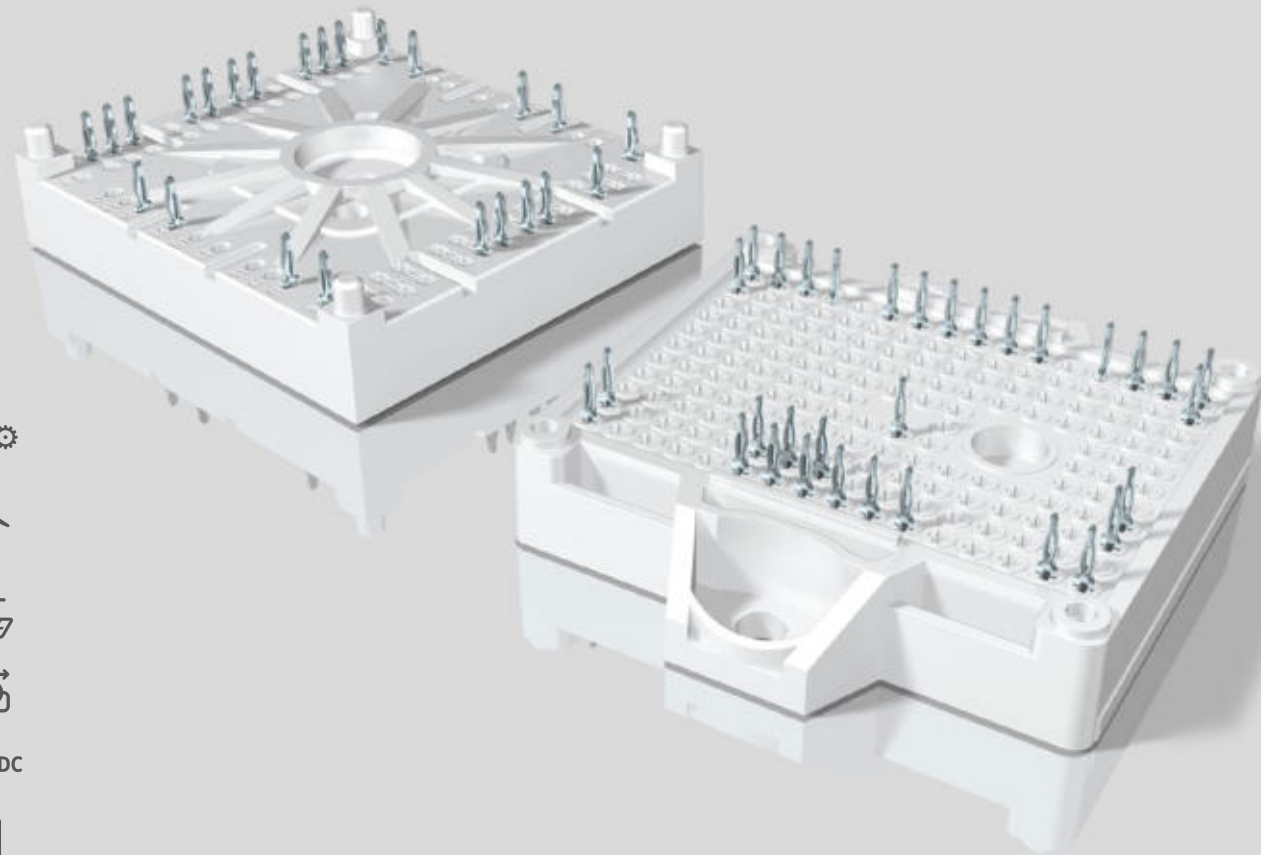
Tel.: +375 17 310 44 44

Tel. +375 44 592 00 86

Tel. +375 33 366 51 85

<https://www.abn.by>info@abn.by

SEMITOP® 1-4 SEMITOP® E1/E2



AC|DC



Flexible and High Performance Product for a Comprehensive Portfolio

SEMITOP®

Portfolio

SEMITOP 1, 2, 3, 4	up to 55kW
SEMITOP E1/E2	up to 70kW

Short facts

12mm module height
Reliable solder or press-fit connection
Low stray inductance case

Key features

No baseplate
Complex configurations possible
Different chip technologies and manufacturers available
Optimised system costs

Applications

The SEMITOP family features a cost effective design. This product generation is designed for the low and medium-power range of up to 70kW following the latest introduction of the SEMITOP E family. The scope this gives for compact and low inductance designs, coupled with the latest chip technologies and different topologies, makes the two platforms suitable for different markets such as UPS, solar, motor drives, power supplies and the new, emerging EV battery charger market.

Benefits

The SEMITOP platform centers around 12-mm-high modules, covering the low and medium-power range, with one or two mounting screws and no baseplate, featuring PCB interface via solder or press-fit pins. The low commutation inductance design and the choice of the latest Si and SiC chip technologies make this product suitable for UPS and solar applications, motor drives, power supplies, welding and the new EV battery charger market. A large variety of configurations is possible within the SEMITOP family, including 3-level (NPC/TNPC) and CIB (converter-inverter-brake) topologies.

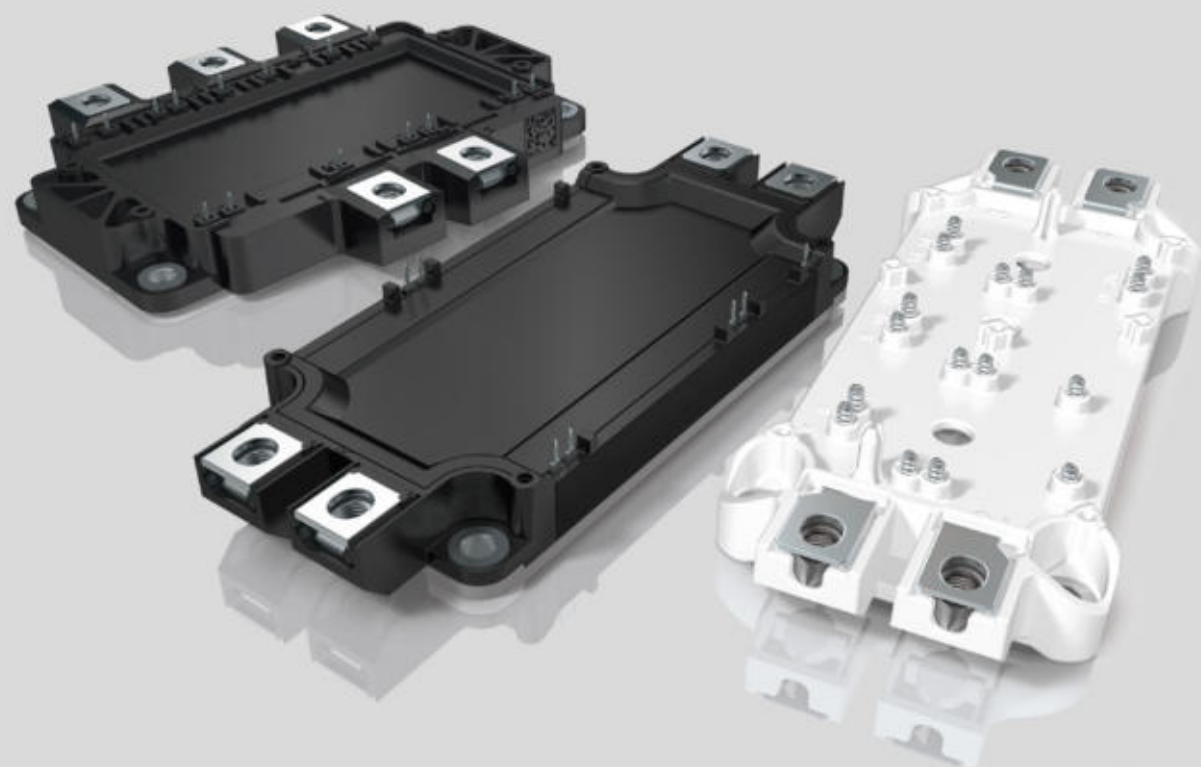
Product range

SEMITOP can include fast Si diodes, fast IGBTs in 650V/1200V class and MOSFETs even for high voltage. Even the latest SiC chip technologies for diodes and MOSFETs can be integrated in the platform, making a lot of different configurations with different chip combinations possible:

- Neutral point clamp 3-level configuration (NPC)
- T-type NPC 3-level configuration (TNPC)
- 3-phase inverter (Sixpack)
- CIB configurations (converter-inverter-brake)
- 3-phase bridge rectifier
- Full SiC and hybrid configurations
- Customised configurations possible

Further information: www.semikron.com/semitop

SEMiX® Spring
SEMiX® 3 Press-Fit
SEMiX® 5
SEMiX® 6 Press-Fit



IGBT and Rectifier Module Family for Solder-Free Mounting

SEMiX®

Portfolio

SEMiX Spring	75A up to 600A
SEMiX 3 Press-Fit	225A up to 600A
SEMiX 5	up to 350kVA
SEMiX 6 Press-Fit	up to 200A

Short facts

Low stray inductance case
Reliable spring or press-fit connection
Flat and compact inverter design

Key features

Half-Bridge, Chopper, Sixpack and 3-level topologies
Isolated copper baseplate using DBC technology
Also available with integrated shunt resistor (SEMiX 3 press-fit)
Multiple IGBT sources

Applications

SEMiX is a flexible and application-oriented module. On the basis of a scalable platform concept, modern chip technology is integrated into IGBT and rectifier modules which are used in a wide variety of applications, such as AC motor drives, switching power supplies and current source inverters. Other typical applications include uninterruptible power supplies, photovoltaic systems, wind energy and automotive applications.

Benefits

The family concept behind SEMiX includes uniform IGBT and rectifier housings. All have the same height (17mm) and can be connected by one principle DC-link design. This saves develop-

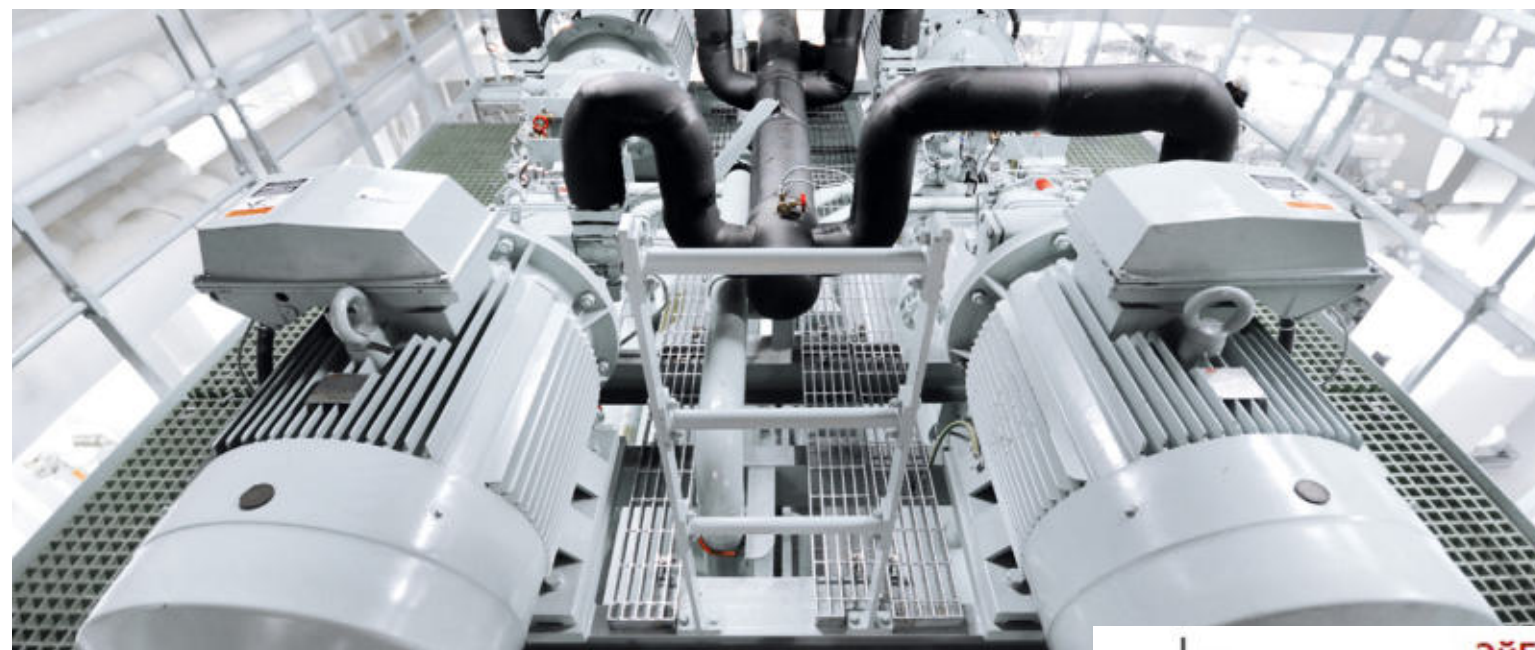
ment time and makes a simple and low-inductance DC-link profile possible. Spring or press-fit contacts allow for a gate driver to be mounted directly on top of the module, eliminating the risk of noise on wires or loose connectors. Thanks to the flat package and separate AC and DC terminals, highly compact, state-of-the-art inverter designs are possible. The auxiliary contacts avoid solder joints and offer highly reliable pressure contacts. This leads to increased product reliability and lifetime.

The solder-free contacts make for quick and easy assembly. Production at the customer site can be optimised by using a uniform direction of assembly (everything top down). This simplifies logistics and reduces manufacturing costs. The half-bridge topologies come with a selection of choices for connection technologies such as press-fit and spring contact as well as for the integration level: current measurement shunts can be included in the power module, plug & play driver solutions and pre-printed phase change material can be supplied to shorten the time-to-market and development times.

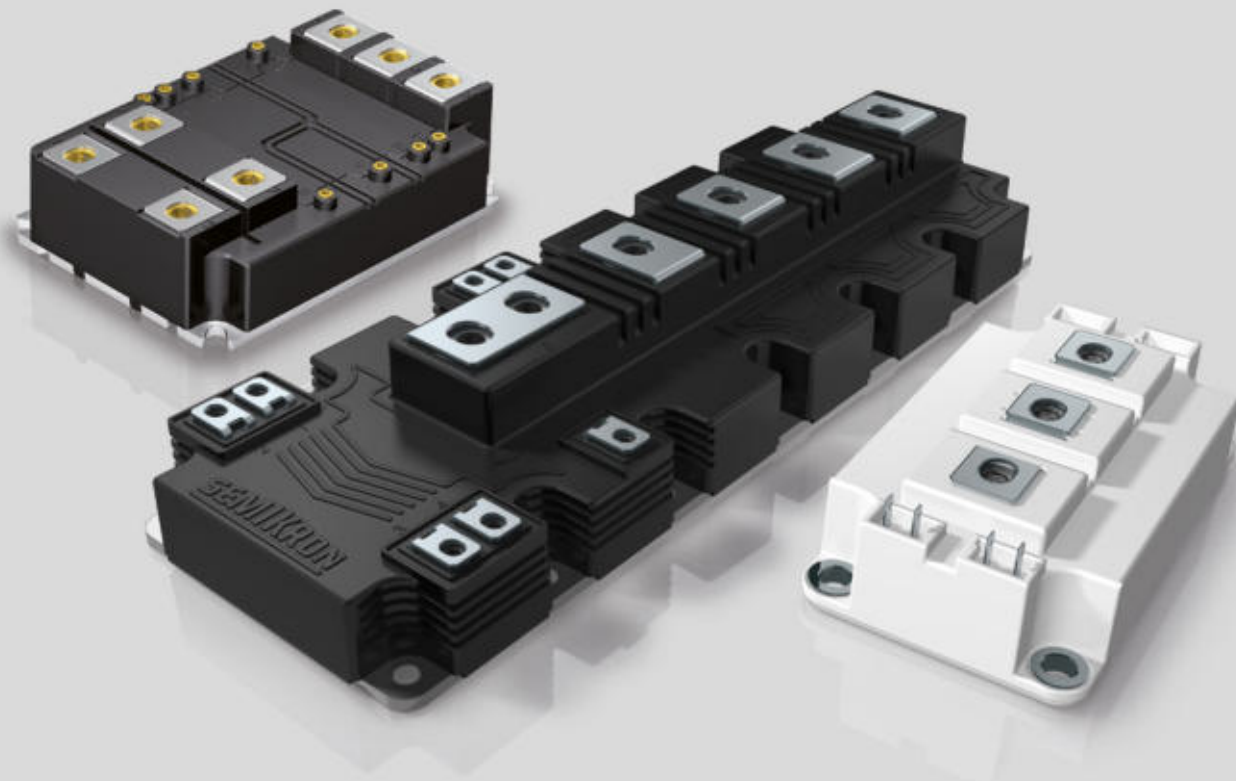
Product range

For the IGBT modules, different housing sizes are available in 600V, 1200V and 1700V. Half-bridge, sixpack and chopper topologies are available with a current range from 75A to 600A. Besides IGBT3 and IGBT4 chips, the 1200V range also includes a series with V-IGBT devices. Controlled, half-controlled and uncontrolled rectifier modules with identical footprint and 17mm height are also available. For the latest housing versions, we also offer optional integrated shunt resistors and 3-level topologies (NPC, TNPC or Buck-Boost-Converters).

Further information: www.semikron.com/semix



SEMITRANS® 2-9
SEMITRANS® 10
SEMITRANS® 20



AC | DC

Low Inductance Package Design Down to 10nH

SEMITRANS®

Portfolio

SEMITRANS 2-9	45kW up to 500kW
SEMITRANS 10	500kW up to 2MW
SEMITRANS 20	3,3 kV, 450A / 1,7kV, 1200A

Short facts

Safe operation with high DC-link voltages
Maximum power output
Multiple IGBT sources

Key features

Half-Bridge, Chopper, Single Switch, 3-level, common emitter
Isolated copper baseplate using DBC technology
With integrated gate resistor
High isolation voltage

Applications

SEMITRANS power modules are designed for a broad range of applications such as motor drives, regenerative inverters, power supplies or traction applications. The long service life is perfectly suited to ambitious applications such as AC drives, switched reluctance and DC motors.

Benefits

SEMITRANS 2-9 feature well-proven designs that come from over 25 years of market experience, but are still suitable for the latest chips generations, including silicon carbide, thanks to its low-inductance design. SEMITRANS 10 takes the power range into the realm of megawatt applications, utilizing the latest SEMIKRON packaging technologies including Direct Pressed Die technology for maximum reliability and minimum thermal resistance. SEMITRANS 20 serves low and medium-voltage applications with a low-inductance and easy-to-parallel power module design. With its advanced technologies such as sintered chips and AlCu bond wires, it boasts up to 5 time more lifetime than standard modules.

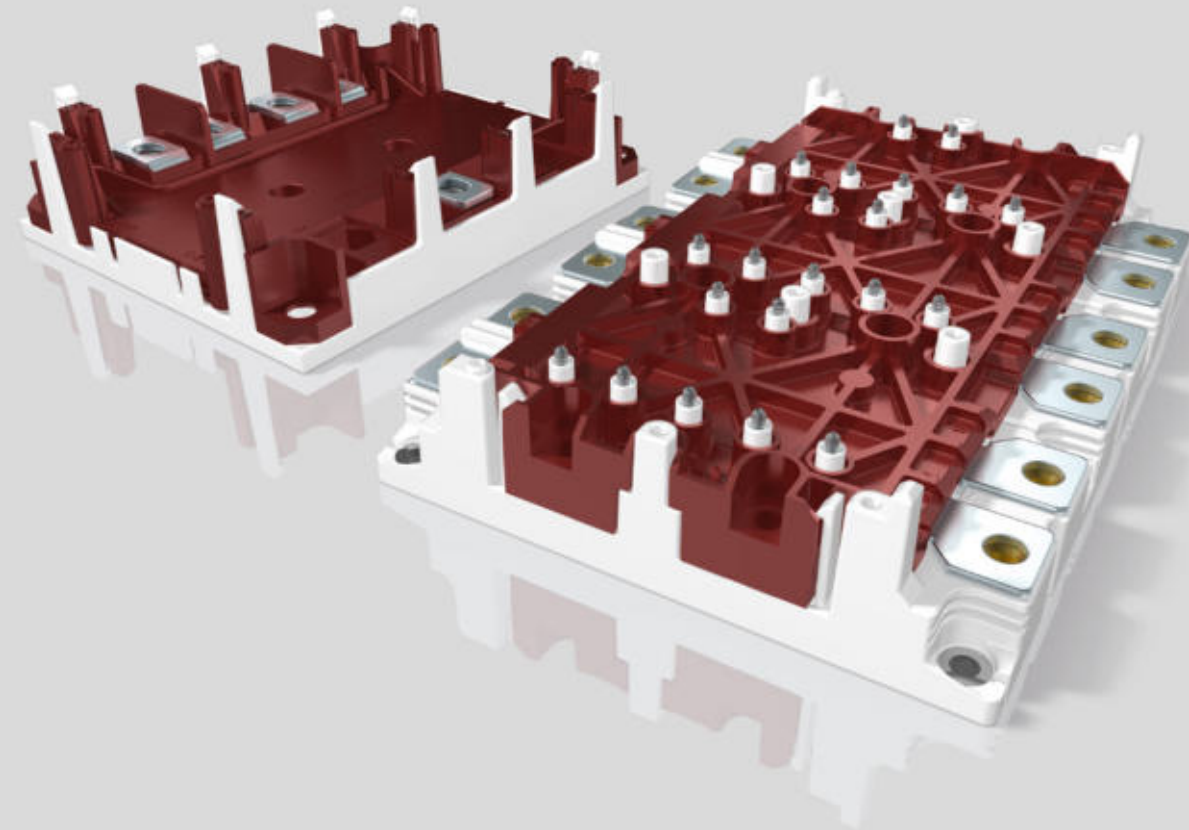
Product range

The SEMITRANS family offers a broad range of topologies and power ranges. All the standard voltage classes from 600V to 3300V are available. The current rating ranges from 25A to 1800A. The SEMITRANS package is available as half-bridge, chopper, single switch, 3-level and common emitter.

Further information: www.semikron.com/semitrans



SKiM® 4/5
SKiM® 63/93



AC | DC

100% Solder-Free for Maximum Durability

SKiM®

Portfolio

SKiM 4/5	200A up to 600A
SKiM 63/93	300A up to 900A

Short facts

No solder delamination thanks to sintered chips - SKiM 63/93

1500 temperature cycles without failure - SKiM 63/93

Up to 23% more performance with AlCu-bonded diodes and high performance thermal grease

Key features

IGBT power module in Sixpack configuration with 3 separate half-bridges - SKiM 63/93

Available in 600V, 1200V and 1700V and from 200A to 900A

NPC and TNPC configuration - SKiM4/5

In 1200V, 600A also available in buck/boost configuration - SKiM 63/93

Solder-free design for maximum durability - SKiM 63/93

Design without baseplate

Solder-free module and driver PCB mounting

Also available as solder version for less demanding cost-sensitive applications

Low inductance design thanks to symmetrical layout

Hybrid SiC version for maximum efficiency - SKiM 63/93

Applications

The SKiM 63/93 is designed for applications that require excellent inverter reliability. This applies first and foremost to automotive applications such as electric powertrains in electric utility vehicles, heavy-duty construction machinery

and tractors. It can also provide leading-edge performance in supersports and race cars. The SKiM 4/5 features proven 3-level topologies and can be found in ambitious applications such as solar and UPS.

Benefits

The SKiM module can improve the reliability of inverters several times over, even under substantial active and passive temperature swings. In addition to sintered chips, pressure contacts and spring technology, the SKiM63/93 featuring AlCu-bonded diodes and high performance thermal grease delivers as much as 23.3% better performance with the same chip set and same lifetime or twice the power cycling capability of standard sinter modules. The SKiM 93 is also available with hybrid SiC technology to extend efficiency and switching frequency.

Product range

The SKiM 4/5 modules are available as sixpack, 3-level (NPC and TNPC) configurations with nominal currents from 200A to 600A. The SKiM 63/93 offers 3-phase inverter topologies at 600V, 1200V and 1700V. The power ranges from 20kW to 180kW with nominal currents of 300A to 900A. Modules in buck and boost configurations for 1200V/600A round off the portfolio. Driver solutions are available as is an optimised water cooler for fast and customer-friendly evaluation. In addition, paralleling boards for a simple and powerful half-bridge configuration are also available.

Further information: www.semikron.com/skim



AbN

ЭйБиЭн

Tel.: +375 17 310 44 44

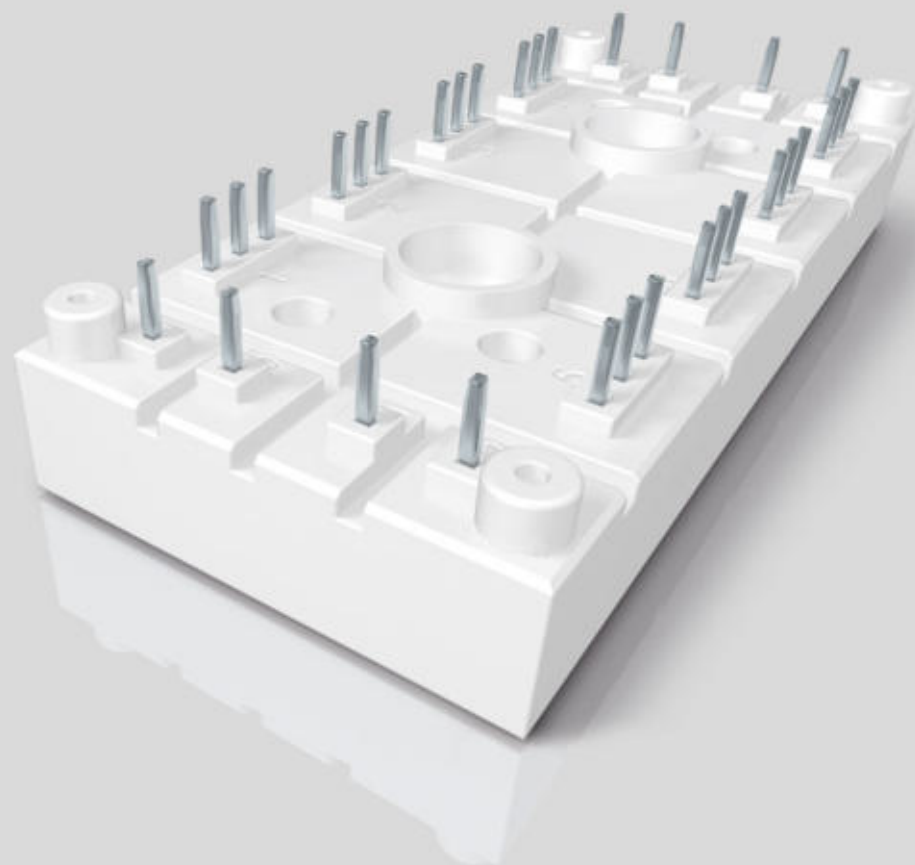
Tel. +375 44 592 00 86

Tel. +375 33 366 51 85

<https://www.abn.by>

info@abn.by

SEMIPONT®



Compact Package in Various Configurations

SEMIPONT®

Short facts

Compact packages with screw, fast-on or lead terminals
 High insulation voltages
 Diode, thyristor rectifier, rectifier/brake Chopper and AC controller

Key features

Diode, thyristor rectifier, rectifier/brake Chopper and AC controller
 From 400V up to 1.8kV blocking voltages
 From 28A up to 207A
 Compact packages with screw, fast-on or lead terminals

Applications

Typical application areas for the broad field of SEMIPONT power bridge rectifiers include AC and DC drives, servo drives, (controlled) field rectifiers for DC motors, (controllable) rectifiers for power supplies, input rectifiers for variable frequency drives, soft motor starters, temperature control, (controlled) battery charger rectifiers, DC motor field controllers, DC motor controllers and DC power supplies.

Benefits

With blocking voltages up to 1.8kV the SEMIPONT family offers high ruggedness for harsh industrial applications. The different housings with soldered PCB connection allow for compact inverter designs.

Product range

The SEMIPONT bridge rectifier family is available in various configurations with diode and thyristor rectifiers, rectifier/brake chopper or AC controller. The compact screw-mounted packages ensure quick and easy PCB assembly. High blocking voltages of up to 1800V, high ruggedness for harsh industrial applications and high insulation voltages are also realized in this package.

Further information: www.semikron.com/semipont



SEMIPACK®



AC | DC

Bipolar Modules from the Market Leader

SEMIPACK®

Short facts

Well established thyristor diode package

Over 40 years of market experience

Wide power and topology range

Key features

Industrial standard thyristor/diode modules

Over 40 years of market experience

Wide power and topology range

800V up to 2200V

15A up to 1360A

Uncontrolled, half-controlled and full-controlled rectifiers

Single thyristors and diodes

Applications

The target applications for the thyristor, thyristor/diode or diode modules include input rectifiers (single-phase, three-phase, uncontrolled, half-controlled or full-controlled) for inverters or UPS systems, soft start applications and control systems.

Benefits

SEMIPACK delivers a well-established industrial standard with regard to footprint and module outline. Thanks to the comprehensive product range, the ideal solution can be found for any application. With SemiSel, the free online calculation and simulation tool for losses and temperature, the power electronic system developer can make the right power module choice.

Product range

The SEMIPACK product line is a comprehensive product range with seven module lines covering voltage classes from 800V to 2200V, insulation voltages of 3.6kV, 4.8kV@1s and rated currents from 15A to 1360A. The SEMIPACK product line includes uncontrolled, half-controlled and full-controlled rectifier modules. Also available are custom topologies, single thyristor or diode modules and SEMIPACK modules featuring fast switching diodes for dedicated applications. The SEMIPACK FAST product line covers a current range from 40A to 600A with voltage classes from 600V to 1700V. The portfolio of the SEMIPACK product line is extended continuously to meet market requirements.

Further information: www.semikron.com/semipack


AbN

ЭйБиЭн

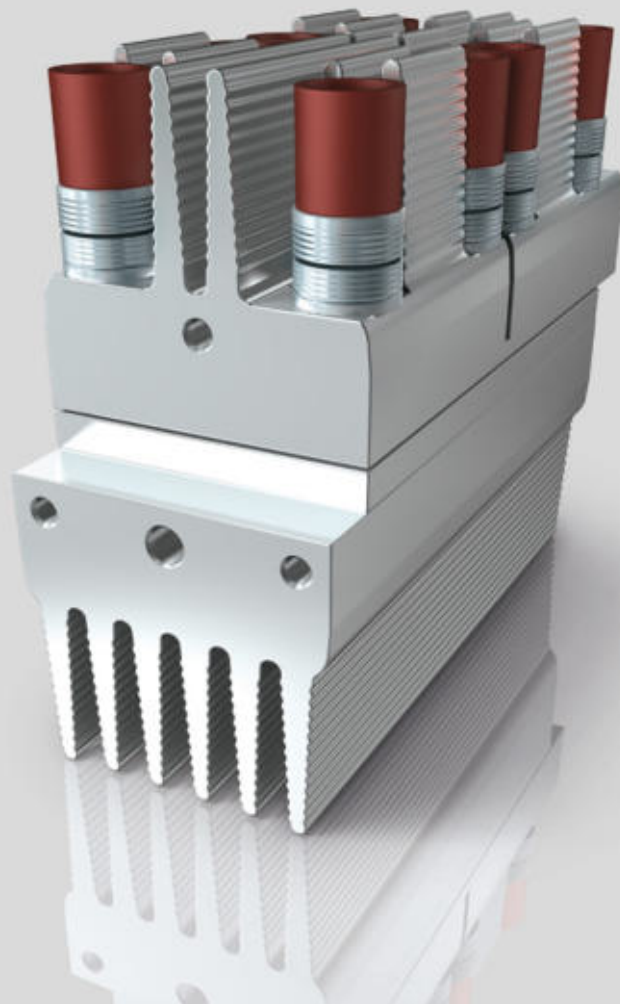
Tel.: +375 17 310 44 44

Tel. +375 44 592 00 86

Tel. +375 33 366 51 85

<https://www.abn.by>info@abn.by

SEMiSTART®



Compact Soft-Starter Module

SEMiSTART®

Short facts

Double-sided cooling for high load cycle capability

Robust pressure contact technology

Low thermal resistance

Key features

Up to 3080A

Qualified plug & play subsystem

Excellent thermal performance

From 560A to 3080A overload current

Applications

SEMiSTART, the anti-parallel thyristor module, is designed for soft-start applications.

Benefits

SEMiSTART – a power module with integrated heatsink – for ultra-compact designs in soft-start applications. Double-sided cooling along with pressure contact technology allows for a high current capability with overload currents of up to 3080A for 20s overload duration. SEMiSTART is a robust plug & play subsystem that helps cut development time and system costs.

Product range

SEMiSTART power modules are available in three housing sizes for overload currents ranging from 560A to 3080A. All overload current classes are available for voltages of 1400V and 1800V.

Further information www.semikron.com/semistart



IGBT Modules

For Maximum Performance

SEMIKRON offers IGBT (Insulated-Gate Bipolar Transistor) modules in SEMITRANS, SEMiX, SKiM, MiniSKiIP and SEMITOP packages in different topologies, current and voltage ratings. Starting from 4A to 1400A in voltage classes from 600V to 1700V, the IGBT modules are used in a variety of applications and feature key technologies such as sintering, spring or press-fit contacts for quick and easy assembly.

Different topologies are available - CIB (converter inverter brake), half-bridge, H-bridge, sixpack, 3-level and many more, covering almost every application field. Featuring the latest IGBT chips in combination with SEMIKRON's CAL diode technology.

The latest IGBT generation 7 is now also available in SEMIKRON power modules. It provides higher power densities and delivers the new benchmark, especially in motor drive and solar applications.

IGBT Generation 7

Optimized IGBTs for motor drive applications

Reduced saturation voltage and chip size

Higher nominal currents

Up to 45% more module output power

Lower overall system costs

IGBT
7

IGBT Generation 7 – MiniSKiIP, SEMITOP, SEMiX	40
MiniSKiIP	42
SEMITOP	48
SEMiX	58
SEMITRANS	65
SKiM 4/5	73
SKiM 63/93	75

For detailed information please refer to data sheets.

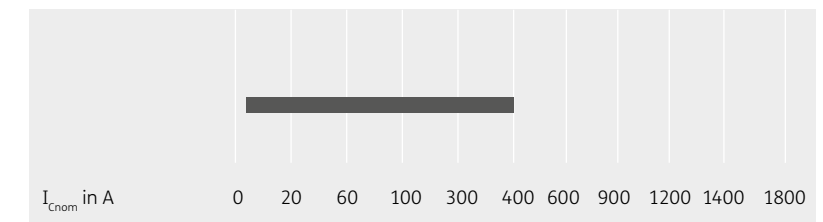
Further information: www.semikron.com/igbt-modules

MiniSKiIP®

Sixpack
3-level
H-Bridge
CIB
Half-Bridge
Twelvepack



600V up to 1700V

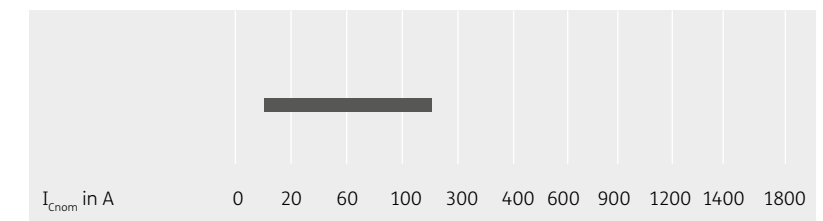


SEMITOP®

Half-Bridge
Sixpack
3-level
Chopper
H-Bridge
CIB



600V up to 1200V

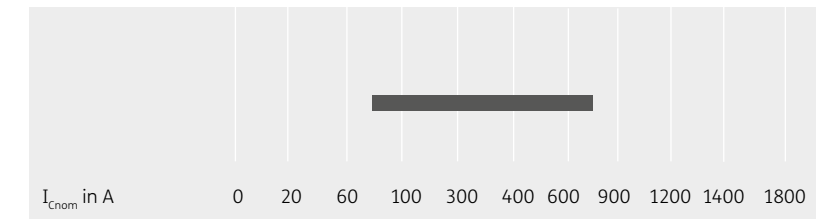


SEMiX®

Half-Bridge
Sixpack
3-level
Chopper
Buck-Boost converter

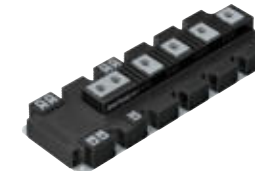


600V up to 1700V

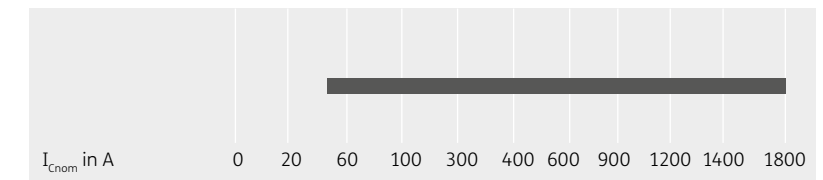


SEMITRANS®

Half-Bridge
Sixpack
Chopper
Single Switch
3-level

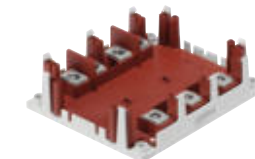


600V up to 3300V

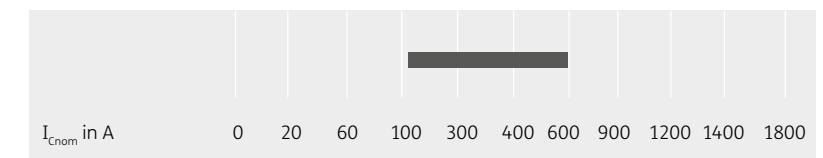


SKiM® 4/5

Sixpack
3-level

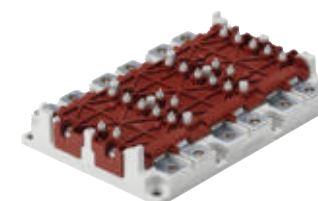


600V up to 1700V

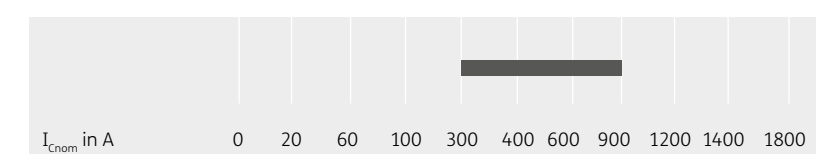


SKiM® 63/93

Sixpack
Chopper



600V up to 1700V



IGBT 7 Modules / MiniSKiiP

Type	IGBT 7			
	I_{Tnom}	Topology	Package	Topology
	A			
1200V - IGBT (T7)				
SKiiP11NAB12T7V1	10	CIB	MiniSKiiP 1	
SKiiP12NAB12T7V1	15	CIB	MiniSKiiP 1	
SKiiP23NAB12T7V1	25	CIB	MiniSKiiP 2	
SKiiP24NAB12T7V1	35	CIB	MiniSKiiP 2	
SKiiP25NAB12T7V2	50	CIB	MiniSKiiP 2	
SKiiP34NAB12T7V1	35	CIB	MiniSKiiP 3	
SKiiP35NAB12T7V1	50	CIB	MiniSKiiP 3	
SKiiP37NAB12T7V1	75	CIB	MiniSKiiP 3	
SKiiP38NAB12T7V2	100	CIB	MiniSKiiP 3	
SKiiP11AC12T7V1	10	Sixpack	MiniSKiiP 1	
SKiiP12AC12T7V1	15	Sixpack	MiniSKiiP 1	
SKiiP13AC2T7V1	25	Sixpack	MiniSKiiP 1	
SKiiP14AC12T7V1	35	Sixpack	MiniSKiiP 1	
SKiiP23AC12T7V1	25	Sixpack	MiniSKiiP 2	
SKiiP24AC12T7V1	35	Sixpack	MiniSKiiP 2	
SKiiP25AC12T7V1	50	Sixpack	MiniSKiiP 2	
SKiiP26AC12T7V1	70	Sixpack	MiniSKiiP 2	
SKiiP27AC12T7V1	75	Sixpack	MiniSKiiP 2	
SKiiP28AC12T7V1	100	Sixpack	MiniSKiiP 2	
SKiiP37AC12T7V1	75	Sixpack	MiniSKiiP 3	
SKiiP38AC12T7V1	100	Sixpack	MiniSKiiP 3	
SKiiP39AC12T7V1	150	Sixpack	MiniSKiiP 3	
SKiiP39AC12T7V10	200	Sixpack	MiniSKiiP 3	
SKiiP12ACC12T7V1	15	Twelvepack	MiniSKiiP 1	
SKiiP23ACC12T7V1	25	Twelvepack	MiniSKiiP 2	
SKiiP24ACC12T7V1	35	Twelvepack	MiniSKiiP 2	
SKiiP35ACC12T7V1	50	Twelvepack	MiniSKiiP 3	
SKiiP24GB12T7V1	150	Half-Bridge	MiniSKiiP 2 Dual	
SKiiP26GB12T7V1	200	Half-Bridge	MiniSKiiP 2 Dual	
SKiiP27GB12T7V1	300	Half-Bridge	MiniSKiiP 2 Dual	
SKiiP38GB12T7V1	300	Half-Bridge	MiniSKiiP 3 Dual	

IGBT 7 Modules / SEMITOP / SEMiX

Type	IGBT 7			
	I_{Tnom} A	Topology	Package	Topology
1200V - IGBT (T7)				
SK10DGD12T7ETE1	10	CIB	SEMITOP E1	
SK15DGD12T7ETE1	15	CIB	SEMITOP E1	
SK35DGD12T7ETE2	35	CIB	SEMITOP E2	
SK25GD12T7ETE1	25	Sixpack	SEMITOP E1	
SK35GD12T7ETE1	35	Sixpack	SEMITOP E1	
SK50GD12T7ETE2	50	Sixpack	SEMITOP E2	
SK75GD12T7ETE2	75	Sixpack	SEMITOP E2	
SK100GD12T7ETE2	100	Sixpack	SEMITOP E2	
1200V - IGBT (M7)				
SEMiX076DGD12M7p	75	CIB	SEMiX 6p	
SEMiX106DGD12M7p	100	CIB	SEMiX 6p	
SEMiX156DGD12M7p	150	CIB	SEMiX 6p	
SEMiX106GD12M7p	100	Sixpack	SEMiX 6p	
SEMiX156GD12M7p	150	Sixpack	SEMiX 6p	
SEMiX206GD12M7p	200	Sixpack	SEMiX 6p	
SEMiX223GB12M7p	220	Half-Bridge	SEMiX 3p	
SEMiX303GB12M7p	300	Half-Bridge	SEMiX 3p	
SEMiX453GB12M7p	450	Half-Bridge	SEMiX 3p	
SEMiX603GB12M7p	500	Half-Bridge	SEMiX 3p	
SEMiX703GB12M7p	700	Half-Bridge	SEMiX 3p	

IGBT Modules / MiniSKiiP

Type	IGBT					Diode		Rectifier		Module		
	$I_C @ T_J = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_J = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ	A			Topology
600V - IGBT3 (Trench)												
SKiiP 16GH066V1	65	50	1.45	1.7	1.7	56	1.50	1.3	-	II 1	P12, HPTP	
SKiiP 27GH066V1	88	75	1.45	2.7	3	77	1.50	1.8	-	II 2	P12, HPTP	
SKiiP 28GH066V1	112	100	1.45	3.4	3.5	112	1.30	3.3	-	II 2	P12, HPTP	
SKiiP 02AC066V1	20	10	1.45	0.45	0.3	20	1.30	0.3	-	II 0	P12, HPTP	
SKiiP 04AC066V1	33	20	1.45	0.8	0.7	31	1.60	0.55	-	II 0	P12, HPTP	
SKiiP 15AC066V1	40	30	1.45	1	1.1	39	1.50	1.1	-	II 1	P12, HPTP	
SKiiP 27AC066V1	88	75	1.45	2.7	3	77	1.50	1.8	-	II 2	P12, HPTP	
SKiiP 28AC066V1	112	100	1.45	3.4	3.5	112	1.30	3.3	-	II 2	P12, HPTP	
SKiiP 39AC066V4	146	150	1.45	7.9	5.6	164	1.30	3.5	-	II 3	P12, HPTP	
SKiiP 01NEC066V3	12	6	1.45	0.3	0.2	12	1.30	0.2	220	II 0	P12, HPTP	
SKiiP 02NEC066V3	20	10	1.45	0.5	0.3	20	1.30	0.5	220	II 0	P12, HPTP	
SKiiP 03NEC066V3	27	15	1.45	0.6	0.5	28	1.40	0.5	220	II 0	P12, HPTP	
SKiiP 01NAC066V3	12	6	1.45	0.3	0.2	12	1.30	0.2	220	II 0	P12, HPTP	
SKiiP 02NAC066V3	20	10	1.45	0.5	0.3	20	1.30	0.5	220	II 0	P12, HPTP	
SKiiP 02NEB066V3	20	10	1.45	0.5	0.3	20	1.30	0.5	220	II 0	P12, HPTP	
SKiiP 03NEB066V3	27	15	1.45	0.6	0.5	28	1.40	0.5	220	II 0	P12, HPTP	
SKiiP 25NEB066V1	43	30	1.45	0.9	1.2	39	1.50	1.1	370	II 2	P12, HPTP	
SKiiP 11NAB066V1	12	6	1.45	0.3	0.2	12	1.30	0.2	220	II 1	P12, HPTP	
SKiiP 12NAB066V1	20	10	1.45	0.5	0.3	20	1.30	0.5	220	II 1	P12, HPTP	
SKiiP 13NAB066V1	27	15	1.45	0.6	0.5	28	1.40	0.5	220	II 1	P12, HPTP	
SKiiP 14NAB066V1	33	20	1.45	0.75	0.7	31	1.60	0.55	220	II 1	P12, HPTP	
SKiiP 25NAB066V1	43	30	1.45	0.9	1.2	39	1.50	1.1	370	II 2	P12, HPTP	
SKiiP 26NAB066V1	65	50	1.45	1.6	1.6	56	1.50	1.3	370	II 2	P12, HPTP	
SKiiP 37NAB066V1	88	75	1.45	2.7	3	77	1.50	1.8	700	II 3	P12, HPTP	
SKiiP 38NAB066V1	112	100	1.45	3.4	3.5	112	1.30	3.3	700	II 3	P12, HPTP	
SKiiP 11HEB066V1	27	15	1.50	0.6	0.5	28	1.40	0.5	370	II 1	P12, HPTP	
SKiiP 12HEB066V1	33	15	1.50	0.8	0.7	29	1.40	0.6	370	II 1	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs

IGBT Modules / MiniSKiiP

Type	IGBT					Diode		Rectifier		Module		
	$I_C @ T_J = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_J = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ	A			Topology
650V - IGBT3 (Trench)												
SKiiP 24GB07E3V1 ²⁾	185	150	1.45	2.2	5.1	161	1.54	3.7	-	II 2	P12, HPTP	
SKiiP 26GB07E3V1 ²⁾	229	200	1.45	4.4	7.4	235	1.40	4.5	-	II 2	P12, HPTP	
SKiiP 38GB07E3V1 ²⁾	287	300	1.45	5.5	10.6	310	1.40	5.1	-	II 3	P12, HPTP	
SKiiP 26MLI07E3V1 ²⁾	98	75	1.45	2.8	2.8	75	1.54	1.4	-	II 2	P12, HPTP	
SKiiP 27MLI07E3V1 ²⁾	110	100	1.45	4.2	4.2	107	1.40	3.5	-	II 2	P12, HPTP	
SKiiP 28MLI07E3V1 ²⁾	135	150	1.45	5.5	5.6	126	1.40	5.5	-	II 2	P12, HPTP	
SKiiP 39MLI07E3V1 ²⁾	159	200	1.45	3.6	8.9	163	1.39	8.3	-	II 3	P12, HPTP	
1200V - IGBT3 (Trench)												
SKiiP 03AC126V1 ³⁾	16	8	1.70	0.9	0.9	8	1.90	0.7	-	II 0	P12, HPTP	
SKiiP 11AC126V1 ³⁾	16	8	1.70	0.9	1	14	1.90	0.9	-	II 1	P12, HPTP	
SKiiP 11AC126V10 ³⁾	16	6	1.65	18	1	48	1.10	16.4	-	II 1	P12, HPTP	
SKiiP 12AC126V1 ³⁾	28	15	1.70	1.7	1.9	26	1.60	1.2	-	II 1	P12, HPTP	
SKiiP 13AC126V1 ³⁾	41	25	1.70	4.1	3.1	30	1.80	2.2	-	II 1	P12, HPTP	
SKiiP 13AC126V20 ³⁾	41	25	1.65	2.9	3	27	2.00	1.2	-	II 1	P12, HPTP	
SKiiP 23AC126V1 ³⁾	41	25	1.70	3.7	3.1	30	1.80	2.6	-	II 2	P12, HPTP	
SKiiP 24AC126V1 ³⁾	52	35	1.70	4.2	4.4	38	1.80	3.5	-	II 2	P12, HPTP	
SKiiP 25AC126V1 ³⁾	73	50	1.70	5.8	6.5	62	1.60	5.1	-	II 2	P12, HPTP	
SKiiP 26AC126V1 ³⁾	88	70	1.70	9	7.7	91	1.50	7.5	-	II 2	P12, HPTP	
SKiiP 37AC126V2 ³⁾	97	75	1.70	9.6	8.7	90	1.60	9.6	-	II 3	P12, HPTP	
SKiiP 38AC126V2 ³⁾	118	105	1.70	13.1	13	118	1.60	11.2	-	II 3	P12, HPTP	
SKiiP 39AC126V2 ³⁾	157	140	1.70	19.9	17.2	167	1.50	16.2	-	II 3	P12, HPTP	
SKiiP 39AC126V20 ³⁾	157	140	1.65	13	17	-	2.00	8.1	-	II 3	P12, HPTP	
SKiiP 03NAC126V1 ³⁾	16	8	1.70	0.9	0.9	14	1.60	0.7	220	II 0	P12, HPTP	
SKiiP 11NAB126V1 ³⁾	16	8	1.70	0.8	1	14	1.90	0.9	220	II 1	P12, HPTP	
SKiiP 12NAB126V1 ³⁾	28	15	1.70	2	1.9	26	1.60	1.3	220	II 1	P12, HPTP	
SKiiP 12NAB126V20 ³⁾	28	15	1.65	1.5	1.8	28	2.45	0.9	220	II 1	P12, HPTP	
SKiiP 22NAB126V10 ³⁾	28	15	1.65	2	1.9	28	1.60	1.1	700	II 2	P12, HPTP	
SKiiP 23NAB126V1 ³⁾	41	25	1.70	3.5	3	30	1.80	2.5	370	II 2	P12, HPTP	
SKiiP 23NAB126V10 ³⁾	41	25	1.70	3.5	3	30	1.80	2.5	635	II 2	P12, HPTP	
SKiiP 23NAB126V20 ³⁾	-	25	1.65	2.7	2.9	41	2.00	1.2	370	II 2	P12, HPTP	
SKiiP 24NAB126V1 ³⁾	52	35	1.70	4.6	4	38	1.80	3.3	370	II 2	P12, HPTP	
SKiiP 24NAB126V10 ³⁾	52	35	1.70	4.6	4	38	1.80	3.3	635	II 2	P12, HPTP	
SKiiP 35NAB126V1 ³⁾	73	50	1.70	6.5	6.1	62	1.60	4.7	700	II 3	P12, HPTP	
SKiiP 35NAB126V10 ³⁾	72	50	1.70	6.5	6.1	60	1.67	4.7	850	II 3	P12, HPTP	
SKiiP 36NAB126V1 ³⁾	88	70	1.70	9	7.7	91	1.50	7.5	700	II 3	P12, HPTP	
SKiiP 36NAB126V10 ³⁾	91	80	1.70	9	7.7	87	1.64	7.5	850	II 3	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs

IGBT Modules / MiniSKiiP

Type	IGBT					Diode		Rectifier		Module		
	$I_C @ T_J = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_J = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	Topology
	A	A	V	mJ	mJ	A	V	mJ	A			
1200V - IGBT4 (Trench)												
SKiiP 24GB12T4V1 ²⁾	170	150	1.85	10.8	15.6	157	2.17	10.3	-	II 2	P12, HPTP	
SKiiP 26GB12T4V1 ²⁾	224	200	1.80	13.6	22.1	194	2.20	13.4	-	II 2	P12, HPTP	
SKiiP 38GB12E4V1 ²⁾	329	300	1.85	19.1	34.6	267	2.20	21.5	-	II 3	P12, HPTP	
SKiiP 39GB12E4V1 ²⁾	388	400	1.80	20.8	49.7	363	2.20	30.2	-	II 3	P12, HPTP	
SKiiP 39GA12T4V1 ²⁾	167	150	1.85	22.5	14	136	2.14	11.4	-	II 3	P12, HPTP	
SKiiP 26GH12T4V11	90	70	1.85	9.5	7.1	83	2.17	5.6	-	II 2	P12, HPTP	
SKiiP 39MLI12T4V1 ¹⁾	167	150	1.85	11.1	16.9	134	2.14	10.9	-	II 3	P12, HPTP	
SKiiP 39TMLI12T4V2 ²⁾	235	200	1.80	7.5	12.8	194	2.20	9.7	-	II 3	P12, HPTP	
SKiiP 11AC12T4V1	12	8	1.85	0.87	0.75	15	2.33	0.53	-	II 1	P12, HPTP	
SKiiP 12AC12T4V1	18	15	1.85	1.65	1.5	23	2.38	0.79	-	II 1	P12, HPTP	
SKiiP 13AC12T4V1	41	25	1.85	3.7	2.4	32	2.41	1.64	-	II 1	P12, HPTP	
SKiiP 23AC12T4V1	41	25	1.85	3.7	2.4	32	2.41	1.64	-	II 2	P12, HPTP	
SKiiP 24AC12T4V1	52	35	1.85	3.7	3	44	2.30	2.3	-	II 2	P12, HPTP	
SKiiP 25AC12T4V1	69	50	1.85	6	4.5	60	2.22	3.2	-	II 2	P12, HPTP	
SKiiP 26AC12T4V1	90	70	1.85	9.5	7.1	83	2.17	5.6	-	II 2	P12, HPTP	
SKiiP 37AC12T4V1	90	75	1.85	11.5	6.8	83	2.17	5.5	-	II 3	P12, HPTP	
SKiiP 38AC12T4V1	115	100	1.80	13.7	9.7	100	2.20	6.5	-	II 3	P12, HPTP	
SKiiP 39AC12T4V1	167	150	1.85	22.5	14	136	2.14	11.4	-	II 3	P12, HPTP	
SKiiP 39AC12T4V21 ²⁾	192	150	1.85	22.5	14	149	2.14	11.4	-	II 3	P12, HPTP	
SKiiP 02NAC12T4V1	6	4	1.85	0.66	0.37	7.5	1.82	0.34	220	II 0	P12, HPTP	
SKiiP 03NAC12T4V1	7.5	8	1.85	0.9	0.7	9	2.33	0.5	220	II 0	P12, HPTP	
SKiiP 10NAB12T4V1	6	4	1.85	0.66	0.37	7.5	1.82	0.34	220	II 1	P12, HPTP	
SKiiP 11NAB12T4V1	18	8	1.85	0.87	0.74	15	2.33	0.57	220	II 1	P12, HPTP	
SKiiP 12NAB12T4V1	28	15	1.85	1.4	1.3	23	2.38	1.1	220	II 1	P12, HPTP	
SKiiP 23NAB12T4V1	37	25	1.85	2.65	2.3	32	2.41	1.6	370	II 2	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs

IGBT Modules / MiniSKiiP

Type	IGBT					Diode		Rectifier		Module		Topology
	$I_C @ T_S = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_S = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ	A			
1200V - IGBT4 (Trench)												
SKiiP 22NAB12T4V2 ¹⁾	28	15	1.85	t.b.d.	t.b.d.	22	2.38	t.b.d.	220	II 2	P12, HPTP	
SKiiP 23NAB12T4V2 ²⁾	37	25	1.85	3.1	2.56	32	2.41	1.4	370	II 2	P12, HPTP	
SKiiP 24NAB12T4V4 ²⁾	48	35	1.85	4.3	3.25	40	2.30	2.4	370	II 2	P12, HPTP	
SKiiP 23NAB12T4V10	37	25	1.85	2.65	2.3	30	2.41	1.6	700	II 2	P12, HPTP	
SKiiP 24NAB12T4V1	48	35	1.85	4.3	3.25	44	2.30	2.4	370	II 2	P12, HPTP	
SKiiP 24NAB12T4V10	48	35	1.85	4.3	3.25	44	2.30	2.4	700	II 2	P12, HPTP	
SKiiP 34NAB12T4V1	52	35	1.85	4.3	3.3	44	2.30	2.4	370	II 3	P12, HPTP	
SKiiP 35NAB12T4V1	69	50	1.85	6	4.7	60	2.22	3.4	700	II 3	P12, HPTP	
SKiiP 37NAB12T4V1	90	75	1.85	9.7	6.8	83	2.17	4.9	700	II 3	P12, HPTP	
SKiiP 37NAB12T4V10	90	75	1.85	9.7	6.8	83	2.17	4.9	850	II 3	P12, HPTP	
SKiiP 38NAB12T4V1	115	100	1.80	11.2	10	99	2.20	6.5	1000	II 3	P12, HPTP	
SKiiP 12ACC12T4V10 ²⁾	28	15	1.85	2.1	1.6	23	2.38	0.8	60	II 1	P12, HPTP	
SKiiP 23ACC12T4V10 ²⁾	41	25	1.85	3.5	2.7	32	2.41	1.15	65	II 2	P12, HPTP	
SKiiP 24ACC12T4V10 ²⁾	52	35	1.85	3.9	3.5	44	2.30	2.3	100	II 2	P12, HPTP	
SKiiP 24ACC12T4V1 ²⁾	38	25	1.85	3.2	3	31	2.41	1.4	-	II 2	P12, HPTP	
1200V - IGBT4 (Fast Trench)												
SKiiP 26GB12F4V1 ²⁾	197	200	2.05	16.8	16.3	194	2.20	11.7	-	II 2	P12, HPTP	
SKiiP 28TMLI12F4V1 ²⁾	93	80	2.05	3.4	2.2	76	2.17	1.7	-	II 2	P12, HPTP	
SKiiP 29TMLI12F4V1 ²⁾	144	150	2.05	5.2	6.1	148	2.17	6.5	-	II 2	P12, HPTP	
SKiiP 35ACC12F4V1 ²⁾	54	50	2.05	4.8	3.4	58	2.22	3	270	II 3	P12, HPTP	
SKiiP39MLIT12F4V1 ¹⁾	409	400	2.05	t.b.d.	t.b.d.	193	2.20	t.b.d.	-	II 3	P12, HPTP	
SKiiP39MLIT12F4V22 ¹⁾	409	400	2.05	t.b.d.	t.b.d.	193	2.20	t.b.d.	-	II 3	P12, HPTP	
SKiiP39MLIT12F4V22 ¹⁾	409	400	2.05	t.b.d.	t.b.d.	193	2.20	t.b.d.	-	II 3	P12, HPTP	
SKiiP39MLIT12F4V22 ¹⁾	409	400	2.05	t.b.d.	t.b.d.	193	2.20	t.b.d.	-	II 3	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs

IGBT Modules / MiniSKiiP

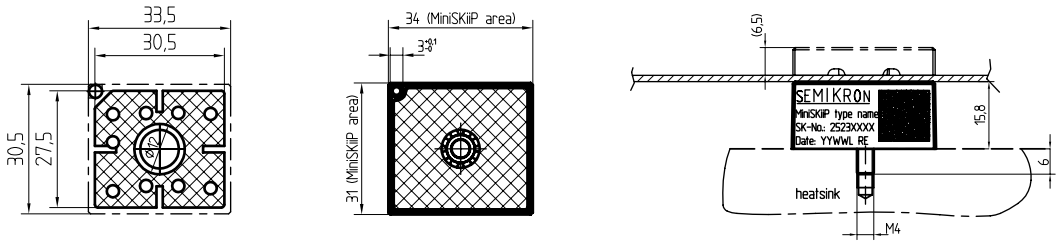
Type	IGBT					Diode		Rectifier	Module			
	$I_c @ T_s = 25^{\circ}C$ A	I_{cnom} A	$V_{CE(sat)} @ T_j = 25^{\circ}C$ typ. V	E_{on} mJ	E_{off} mJ	$I_F @ T_s = 25^{\circ}C$ A	$V_F @ T_j = 25^{\circ}C$ typ. V	E_{rr} mJ	$I_{FSM} @ T_j = 25^{\circ}C$ A	Package	Thermal Interface Material	Topology
1200V - IGBT4 (Fast Trench)												
SKiiP39MLIB12F4V1 ¹⁾	409	400	2.05	t.b.d.	t.b.d.	193	2.20	t.b.d.	-	II 3	P12, HPTP	
SKiiP39MLIB12F4V22 ¹⁾	409	400	2.05	t.b.d.	t.b.d.	193	2.20	t.b.d.	-	II 3	P12, HPTP	
SKiiP 37AC12F4V1 ¹⁾	81	75	2.05	t.b.d.	t.b.d.	83	2.17	t.b.d.	-	II 3	P12, HPTP	
1700V - IGBT3 (Trench)												
SKiiP 38AC176V2 ²⁾	118	100	2.00	23.8	32.2	115	1.76	26.2	-	II 3	P12, HPTP	
SKiiP 24NAB176V1 ²⁾	38	29	2.00	5.1	6.3	48	2.00	4.9	370	II 2	P12, HPTP	
SKiiP 34NAB176V3 ²⁾	67	58	2.00	11.2	12.8	66	2.06	6.6	635	II 3	P12, HPTP	
1700V - IGBT4 (Trench)												
SKiiP 22GB17E4V1 ²⁾	117	100	1.90	22.2	30.7	91	2.00	20.9	-	II 2	P12, HPTP	
SKiiP 24GB17E4V1 ²⁾	177	150	1.90	26	46	149	2.00	32.4	-	II 2	P12, HPTP	
SKiiP 36GB17E4V1 ²⁾	224	200	1.90	37	66	193	2.00	47	-	II 3	P12, HPTP	
SKiiP 38GB17E4V1 ²⁾	341	300	1.90	47	102	267	2.00	69	-	II 3	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs

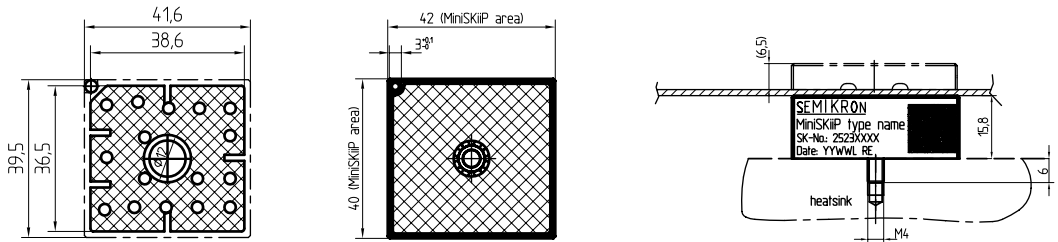
IGBT Modules / MiniSKiiP

Packages

MiniSKiiP II 0

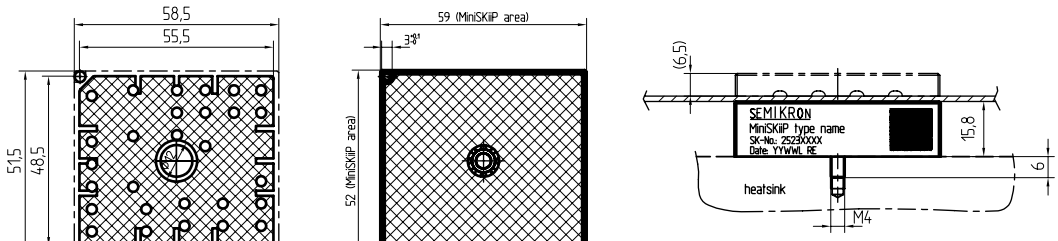


MiniSKiiP II 1



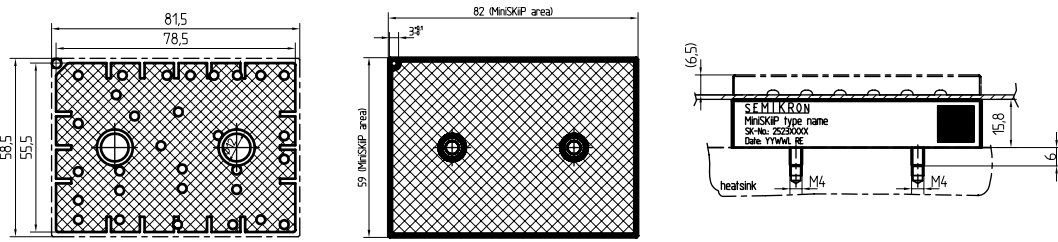
pin configuration depends on circuit
(details in data sheet)

MiniSKiiP II 2



pin configuration depends on circuit
(details in data sheet)

MiniSKiiP II 3



pin configuration depends on circuit
(details in data sheet)

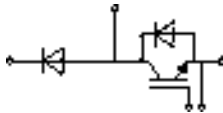
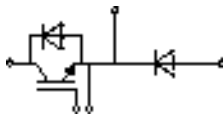
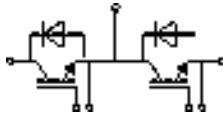
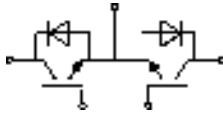
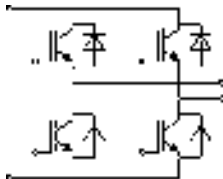
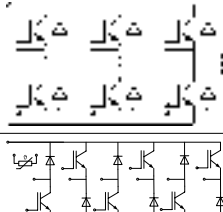
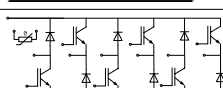
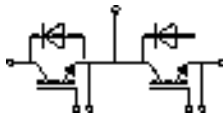
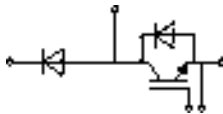
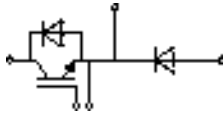
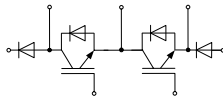
Dimensions in mm

IGBT Modules / SEMITOP

Type	IGBT					Diode		Rectifier		Module		
	I_C @ $T_S = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	I_F @ $T_S = 25^{\circ}\text{C}$	V_F @ $T_J = 25^{\circ}\text{C typ.}$	E_{rr}	I_{FSM} @ $T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	Topology
	A	A	V	mJ	mJ	A	V	mJ	A			
600V - IGBT3 (Trench)												
SK 75 GB 066 T	77	75	1.45	3.1	2.8	62	1.35	0.85	-	3	P12, HPTP	
SK 100 GB 066 T	96	100	1.45	7	6	108	1.35	1.7	-	3	P12, HPTP	
SK 150 GB 066 T	124	150	1.45	6.25	5.7	135	1.35	1.7	-	3	P12, HPTP	
SK 30 GBB 066 T	40	30	1.45	0.97	1.77	36	1.45	0.26	-	3	P12, HPTP	
SK 50 GBB 066 T	60	50	1.45	2.2	1.73	56	1.50	0.72	-	3	P12, HPTP	
SK 75 GBB 066 T	77	75	1.45	3.1	2.8	77	1.35	0.85	-	3	P12, HPTP	
SK 20 MLI 066	30	20	1.45	0.4	1.07	30	1.60	0.2	-	3	P12, HPTP	
SK 30 MLI 066	40	30	1.45	0.97	1.77	37	1.50	0.26	-	3	P12, HPTP	
SK 30 MLI 066p ¹⁾	37	30	1.45	0.97	1.77	34	1.50	0.26	-	3p	P12, HPTP	
SK 50 MLI 066	60	50	1.45	1.46	2.02	56	1.50	1.07	-	3	P12, HPTP	
SK 75 MLI 066 T	83	75	1.45	1.7	2.8	92	1.50	1.1	-	4	P12, HPTP	
SK 100 MLI 066 T	105	100	1.45	2.5	4.2	110	1.35	1.9	-	4	P12, HPTP	
SK 150 MLI 066 T	151	150	1.45	2.7	5.9	115	1.50	2.6	-	4	P12, HPTP	
SK 20 GD 066 ET	30	20	1.45	0.34	0.63	31	1.45	0.2	-	3	P12, HPTP	
SK 30 GD 066 ET	40	30	1.45	0.97	1.77	36	1.45	0.26	-	3	P12, HPTP	
SK 50 GD 066 ET	60	50	1.45	2.2	1.73	56	1.50	0.72	-	3	P12, HPTP	
SK 50 GD 066 ETp ¹⁾	59	50	1.45	2.2	1.73	51	1.47	0.72	-	3p	P12, HPTP	
SK 30 GD 066 ETp ¹⁾	40	30	1.45	0.97	1.77	36	1.45	0.26	-	3p	P12, HPTP	
SK 75 GD 066 T	83	75	1.45	3.1	2.8	92	1.35	0.85	-	4	P12, HPTP	
SK 100 GD 066 T	105	100	1.45	7	6	99	1.30	1.7	-	4	P12, HPTP	
SK 150 GD 066 T	151	150	1.45	6.25	5.7	198	1.30	1.7	-	4	P12, HPTP	
SK 200 GD 066 T ⁴⁾	174	200	1.45	13.9	12	99	1.30	3.4	-	4	P12, HPTP	
SK 20 DGD L 066 ET	30	20	1.45	0.3	0.6	27	1.40	0.2	220	3	P12, HPTP	
SK 30 DGD L 066 ET	40	30	1.45	0.55	1.15	36	1.50	0.53	370	3	P12, HPTP	
SK 50 DGD L 066 T	69	50	1.45	2.2	1.74	54	1.35	0.73	370	4	P12, HPTP	
SK 75 DGD L 066 T ³⁾	81	75	1.45	3.1	2.8	64	1.35	0.9	700	4	P12, HPTP	
SK 100 DGD L 066 T ⁴⁾	106	100	1.45	4.4	3.5	99	1.10	1.45	700	4	P12, HPTP	
SK 50 DGD L 066 ETE2 ¹⁾	53	50	1.45	0.85	1.6	51	1.00	0.9	520	E2	HPTP, HT	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 4) Discontinued

IGBT Modules / SEMITOP

Type	IGBT					Diode			Rectifier	Module		Topology
	$I_C @ T_S = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_S = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ	A			
600V - NPT IGBT (Standard)												
SK 45 GAL 063 ³⁾	45	50	2.10	1.4	1.2	57	1.45	0.25	-	2	P12	
SK 45 GAR 063 ³⁾	45	50	2.10	1.4	1.2	57	1.45	0.25	-	2	P12	
SK 45 GB 063 ⁴⁾	45	50	2.10	1.4	1.2	57	1.45	0.25	-	2	P12	
SK 80 GB 063 ⁴⁾	81	100	2.10	4	3	79	1.40	1.2	-	3	P12, HPTP	
SK 80 GM 063 ³⁾	81	100	2.00	3	2.3	105	1.30	0.2	-	2	P12	
SK 15 GH 063 ³⁾	20	15	2.00	0.71	0.4	20	1.45	0.45	-	2	P12	
SK 25 GH 063 ³⁾	30	30	2.10	1.1	0.8	36	1.45	0.25	-	2	P12	
SK 45 GH 063 ³⁾	45	50	2.10	1.4	1.2	57	1.30	0.9	-	3	P12, HPTP	
SK 13 GD 063 ³⁾	18	10	2.10	0.6	0.4	22	1.45	0.1	-	3	P12, HPTP	
SK 25 GD 063 ³⁾	30	30	2.10	1.3	0.9	36	1.45	0.25	-	3	P12, HPTP	
SK 45 GD 063 ³⁾	45	50	2.10	1.4	1.2	36	1.45	0.25	-	3	P12, HPTP	
SK 25 GAD 063 T ⁴⁾	30	30	2.10	1.3	0.9	36	1.45	0.25	-	3	P12, HPTP	
600V - NPT IGBT (Ultrafast)												
SK 50 GB 065 ⁴⁾	54	60	2.00	1.1	0.7	64	1.45	0.55	-	2	P12	
SK 50 GAL 065 ³⁾	54	60	2.00	1.1	0.7	57	1.30	0.2	-	2	P12	
SK 50 GAR 065 ³⁾	54	60	2.00	1.1	0.7	57	1.30	0.2	-	2	P12	
SK 50 GAR L 065 F ⁴⁾	54	60	1.70	1.03	0.8	82	1.70	0.45	-	2	P12	
SK 50 GAR L 065 USA ⁴⁾	54	60	1.70	1.07	0.76	64	1.40	0.55	-	2	P12	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 4) Discontinued

IGBT Modules / SEMITOP

Type	IGBT					Diode			Rectifier	Module		
	$I_c @ T_s = 25^{\circ}C$	I_{Cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}C \text{ typ.}$	E_{on}	E_{off}	$I_f @ T_s = 25^{\circ}C$	$V_f @ T_j = 25^{\circ}C \text{ typ.}$	E_{rr}	$I_{FSM} @ T_j = 25^{\circ}C$	Package	Thermal Interface Material	Topology
	A	A	V	mJ	mJ	A	V	mJ	A			
600V - NPT IGBT (Ultrafast)												
SK 55 GARL 065 E ³⁾	54	60	1.70	1.1	0.76	36	1.45	0.9	-	3	P12, HPTP	
SK 75 GARL 065 E ³⁾	80	90	1.70	2.71	2.75	57	1.30	0.2	-	3	P12, HPTP	
SK 50 GH 065 F ³⁾	54	60	2.00	1.07	1.76	82	1.10	0.42	-	3	P12, HPTP	
SK 35 GD 065 ET ³⁾	45	50	2.00	1.3	0.6	36	1.90	0.9	-	3	P12, HPTP	
SK 10 BGD 065 ET ⁴⁾	17	6	2.00	0.18	0.13	22	1.30	0.18	220	3	P12, HPTP	
SK 9 BGD 065 ET ³⁾	12	6	2.00	0.22	0.12	20	1.35	0.31	220	3	P12, HPTP	
SK 9 DGD 065 ET ³⁾	12	6	2.00	0.22	0.12	20	1.35	0.31	220	3	P12, HPTP	
SK 20 DGD 065 ET ³⁾	26	20	2.00	0.66	0.4	25	1.60	t.b.d.	370	3	P12, HPTP	
SK 10 DGD L 065 ET ⁴⁾	17	6	2.00	0.18	0.13	22	1.30	0.18	220	3	P12, HPTP	
SK 20 DGD L 065 ET ³⁾	24	20	2.00	0.69	0.39	25	1.60	t.b.d.	220	3	P12, HPTP	
650V - IGBT3 (Trench)												
SK 75 GD 07E3 ETE2 ¹⁾	66	75	1.45	1.1	2.55	70	1.43	1.85	-	E2	HPTP, HT	
SK50GD07E3ETE1 ²⁾	60	50	1.45	1.4	1.3	67	1.37	0.8	-	E1	-	
SK30GD07E3ETE1V1 ¹⁾	38	30	1.45	0.8	1.45	37	1.55	0.65	-	E1	-	
650V - IGBT3 (Fast Trench)												
SK 151 GALE 07F3 TUF ²⁾	-	150	1.85	8.8	4	116	1.59	0.26	635	3	P12, HPTP	
SK 50 MLI 07F3 D1p ¹⁾	51	50	1.85	1	1.18	56	1.37	0.95	-	3p	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 4) Discontinued

IGBT Modules / SEMITOP

Type	IGBT					Diode			Rectifier	Module			
	$I_c @ T_s = 25^{\circ}C$	I_{Cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}C \text{ typ.}$	E_{on}	E_{off}	$I_f @ T_s = 25^{\circ}C$	$V_f @ T_j = 25^{\circ}C \text{ typ.}$	E_{rr}	$I_{FSM} @ T_j = 25^{\circ}C$	Package	Thermal Interface Material	Topology	
	A	A	V	mJ	mJ	A	V	mJ	A				
650V - IGBT3 (Fast Trench)													
SK100MLI07F3TD1p ²⁾	109	100	1.85	4.6	1	137	1.37	1.76	-	4p	P12, HPTP		
SK 150 MLI 07F3 TD1p ²⁾	151	150	1.85	9.07	1.3	137	1.37	1.76	-	4p	P12, HPTP		
SK 100 GD 07F3 TD1 ²⁾	104	100	1.85	3.92	2.1	95	1.35	0.92	-	4	P12, HPTP		
SK150DBB07F3TD1p ²⁾	74	150	1.85	1.52	0.65	108	1.35	0.9	-	4p	P12, HPTP		
SK100DBB07F3TD1p ²⁾	54	100	1.85	1	0.5	115	1.35	0.7	-	4p	P12, HPTP		
650V - IGBT H5 (High speed Trench5 technology)													
SK225GH07H5TD1E2 ¹⁾	162	225	1.65	2.3	0.9	66	1.35	0.7	-	E2	HPTP, HT		
650V - IGBT L5 (Low saturation voltage Trench5 technology)													
SK150MLI07L5TD1E2 ¹⁾	96	150	1.65	5.3	1.97	107	1.35	1.13	-	E2	HPTP, HT		
650V-IGBT S5 (High Speed Soft Switching)													
SK75GARL07S5TD1E1 ¹⁾	68	75	1.42	2.3	1	66	1.35	0.7	-	E1	-		
SK75MLI07S5TD1E1 ¹⁾	64	75	1.42	0.5	1.2	49	1.35	1.5	-	E1	-		
SK100MLI07S5TD1E2 ¹⁾	142	100	1.06	0.7	1.6	106	1.55	1.6	-	E2	HPTP, HT		
SK150MLI07S5TD1E2 ¹⁾	128	150	1.42	0.9	2.4	106	1.55	3	-	E2	HPTP, HT		
1200V - IGBT3 (Trench)													
SK 10 GD 126 ET ³⁾	15	8	1.70	1	1	25	1.90	1.4	-	3	P12, HPTP		
SK 15 GD 126 ET ³⁾	22	15	1.70	2	1.8	25	1.60	1.4	-	3	P12, HPTP		
SK 25 GD 126 ET	32	25	1.70	3.3	3.1	28	1.80	2.1	-	3	P12, HPTP		
SK 35 GD 126 ET	40	35	1.70	4.6	4.3	34	1.80	2.9	-	3	P12, HPTP		

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 4) Discontinued

IGBT Modules / SEMITOP

Type	IGBT					Diode			Rectifier	Module		Topology
	$I_C @ T_S = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_S = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ	A			
1200V - IGBT3 (Trench)												
SK 50 GD 126 T ⁴⁾	68	50	1.70	4.6	6.3	62	1.35	3.6	-	4	P12, HPTP	
SK 75 GD 126 T ⁴⁾	88	75	1.70	11.3	10	91	1.46	6	-	4	P12, HPTP	
SK 100 GD 126 T ⁴⁾	114	100	1.70	9.8	11.7	118	1.50	7.3	-	4	P12, HPTP	
SK 10 DGD L 126 ET ³⁾	15	8	1.70	1	1	25	1.90	1.4	220	3	P12, HPTP	
SK 15 DGD L 126 ET	22	15	1.70	2	1.8	25	1.60	1.1	220	3	P12, HPTP	
SK 25 DGD L 126 T ⁴⁾	41	25	1.70	2.8	3.1	30	1.50	2	370	4	P12, HPTP	
SK 35 DGD L 126 T ⁴⁾	52	35	1.70	3.7	4.8	38	1.50	3	370	4	P12, HPTP	
SK 50 DGD L 126 T ³⁾	68	50	1.70	4.6	6.3	62	1.35	3.6	700	4	P12, HPTP	
1200V - IGBT4 (Trench)												
SK 35 GAL 12T4	44	35	1.85	3.27	3.3	38	2.30	1.46	-	2	P12	
SK 75 GAL 12T4	80	75	1.85	13	7	70	2.10	3	-	2	P12	
SK 35 GAR 12T4 ¹⁾	44	35	1.85	3.27	3.3	38	2.30	1.46	-	2	P12	
SK 75 GAR 12T4	80	75	1.85	13	7	70	2.10	3	-	2	P12	
SK 25 GB 12T4 ²⁾	37	25	1.85	2.27	2.7	30	2.40	1.28	-	2	P12	
SK 35 GB 12T4	44	35	1.85	3.27	3.3	38	2.30	1.46	-	2	P12	
SK 50 GB 12T4 T ²⁾	71	50	1.85	8.3	5	50	2.20	2.15	-	3	P12, HPTP	
SK 75 GB 12T4 T	80	75	1.85	13.6	8.2	70	2.10	3.39	-	3	P12, HPTP	
SK 100 GB 12T4 T ²⁾	100	100	1.85	16.6	10	85	2.25	5.2	-	3	P12, HPTP	
SK 200 GB 12T4 Tp ¹⁾	210	200	1.80	13.6	22.1	190	2.20	13.4	-	4p	P12, HPTP	
SK 150 GAH 12T4 Tp ¹⁾	167	150	1.85	10.8	15.6	33	2.33	0.82	-	4p	P12, HPTP	
SK 25 GH 12T4 ²⁾	35	25	1.85	2.27	2.7	28	2.41	1.28	-	3	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 4) Discontinued

IGBT Modules / SEMITOP

Type	IGBT					Diode			Rectifier	Module		Topology
	$I_C @ T_J = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_J = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ	A			
1200V - IGBT4 (Trench)												
SK 50 GH 12T4 T ²⁾	75	50	1.80	8.3	5	56	2.20	2.15	-	4	P12, HPTP	
SK 100 GH 12T4 T	126	100	1.80	16.6	10	102	2.20	5.2	-	4	P12, HPTP	
SK 35 MLI 12T4 p ¹⁾	43	35	1.85	1.6	3.27	38	2.30	1.73	-	3p	P12, HPTP	
SK 70 MLI 12T4 Tp ¹⁾	90	70	1.85	13.5	8.5	78	2.30	2.73	-	4p	P12, HPTP	
SK 10 GD 12T4 ET ²⁾	17	8	1.85	0.41	0.76	15	2.38	0.41	-	3	P12, HPTP	
SK 15 GD 12T4 ET	27	15	1.85	0.83	1.52	21	2.38	0.82	-	3	P12, HPTP	
SK 25 GD 12T4 ET	37	25	1.85	2.27	2.7	30	2.40	1.28	-	3	P12, HPTP	
SK 25 GD 12T4 ETp ¹⁾	35	25	1.85	2.27	2.7	28	2.41	1.28	-	3p	P12, HPTP	
SK 35 GD 12T4 ET ²⁾	44	35	1.85	3.27	3.3	40	2.30	1.46	-	3	P12, HPTP	
SK 50 GD 12T4 T	75	50	1.85	8.3	5	60	2.20	2.15	-	4	P12, HPTP	
SK 50 GD 12T4 Tp ²⁾	72	50	1.85	8.3	5	60	2.22	2.15	-	4p	P12, HPTP	
SK 75 GD 12T4 T	102	75	1.85	13.6	8.2	83	2.20	3.38	-	4	P12, HPTP	
SK 75 GD 12T4 Tp ¹⁾	97	75	1.85	13.6	8.2	83	2.17	3.38	-	4p	P12, HPTP	
SK 100 GD 12T4 T	126	100	1.85	16.6	10	102	2.25	5.2	-	4	P12, HPTP	
SK 10 DGD L 12T4 ET	17	8	1.85	0.41	0.75	15	2.38	0.41	220	3	P12, HPTP	
SK 15 DGD L 12T4 ET	27	15	1.85	0.82	1.52	21	2.38	0.82	220	3	P12, HPTP	
SK 25 DGD L 12T4 T	45	25	1.85	2.27	2.7	30	2.40	t.b.d.	370	4	P12, HPTP	
SK 25 DGD L 12T4 ETE2 ¹⁾	33	25	1.85	2.6	2.35	53	1.00	2.05	520	E2	HPTP, HT	
SK 35 DGD L 12T4 T	58	35	1.85	3.27	3.3	46	2.30	1.46	370	4	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 4) Discontinued

IGBT Modules / SEMITOP

Type	IGBT					Diode			Rectifier	Module		Topology
	$I_C @ T_J = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_J = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ	A			
1200V - IGBT4 (Trench)												
SK 35 DGD1 12T4 ETE2 ¹⁾	43	35	1.85	3.15	3.2	53	1.00	2.6	520	E2	HPTP, HT	
SK 50 DGD1 12T4 T	75	50	1.85	8.3	5	60	2.22	2.15	700	4	P12, HPTP	
SK25GD12T4ETE1 ¹⁾	33	25	1.85	2.6	2.35	29	2.41	2.05	-	E1	-	
SK35GD12T4ETE1 ¹⁾	43	35	1.85	3.15	3.2	38	2.30	2.6	-	E1	-	
SK50GD12T4ETE2 ¹⁾	66	50	1.85	5.8	4.5	59	2.22	3.6	-	E2	HPTP, HT	
SK75GD12T4ETE2 ¹⁾	84	75	1.85	8	6.4	82	2.17	5.5	-	E2	HPTP, HT	
1200V - IGBT4 (Fast Trench)												
SK 120 GB 12F4 T ¹⁾	174	120	2.05	8.8	7.47	29	2.38	2.04	-	3	P12, HPTP	
SK80TMLI12F4Tp ¹⁾	88	80	2.05	1.9	2.04	83	2.17	1.6	-	3p	P12, HPTP	
SK 150 TMLI 12F4 Tp ²⁾	180	150	2.05	3.13	5.29	100	2.20	4.8	-	4p	P12, HPTP	
SK200TMLI12F4TE2 ²⁾	166	200	2.05	4.44	5.4	65	2.17	3.2	-	E2	HPTP, HT	
SK 150 MLIT 12F4 TE2 ¹⁾	149	150	2.05	12.6	11	80	2.20	8.3	-	E2	HPTP, HT	
SK 150 MLIB 12F4 TE2 ¹⁾	149	150	2.05	12.6	11	80	2.20	8.3	-	E2	HPTP, HT	
1200V - NPT IGBT (Ultrafast)												
SK 60 GAL 125 ³⁾	51	50	3.20	8.36	3.32	43	2.00	2	-	2	P12	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 4) Discontinued

IGBT Modules / SEMITOP

Type	IGBT					Diode			Rectifier	Module		
	$I_C @ T_J = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_J = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	$I_{FSM} @ T_J = 25^{\circ}\text{C}$	Package	Thermal Interface Material	Topology
1200V - NPT IGBT (Ultrafast)												
SK 60 GAR 125 ⁴⁾	51	50	3.20	8.36	3.32	43	2.00	2	-	2	P12	
SK 60 GB 125	51	50	3.20	8.36	3.32	57	2.00	2	-	3	P12, HPTP	
SK 80 GB 125 T	85	75	3.20	9.9	5	90	2.00	1	-	3	P12, HPTP	

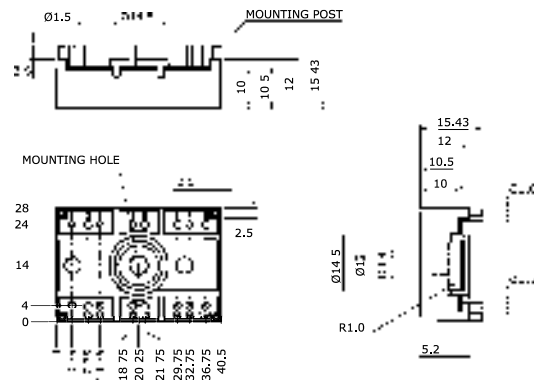
Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 4) Discontinued

IGBT Modules / SEMITOP

Packages

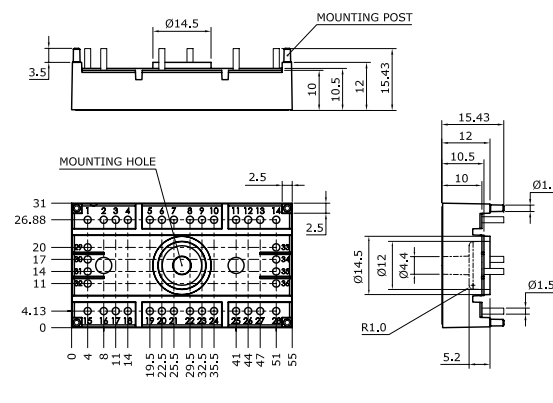
SEMITOP 2

Dimensions: mm
Tolerance system: ISO 2768-m



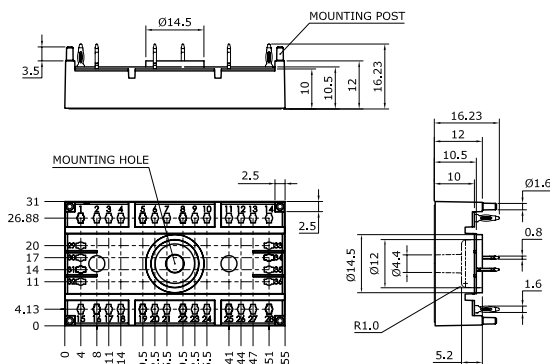
SEMITOP 3

Dimensions: mm
Tolerance system: ISO 2768-m



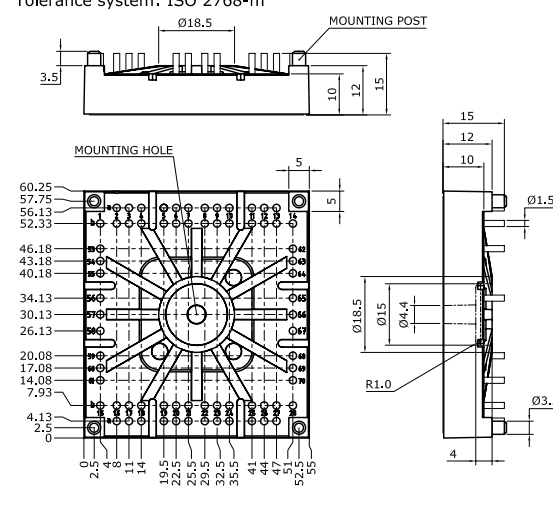
SEMITOP 3 Press-Fit

Dimensions: mm
Tolerance system: ISO 2768-m



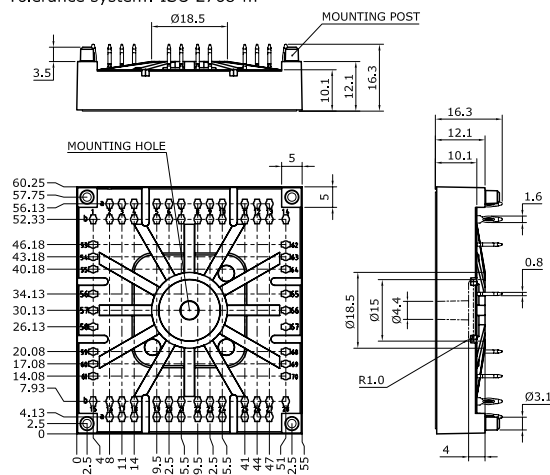
SEMITOP 4

Dimensions: mm
Tolerance system: ISO 2768-m



SEMITOP 4 Press-Fit

Dimensions: mm
Tolerance system: ISO 2768-m

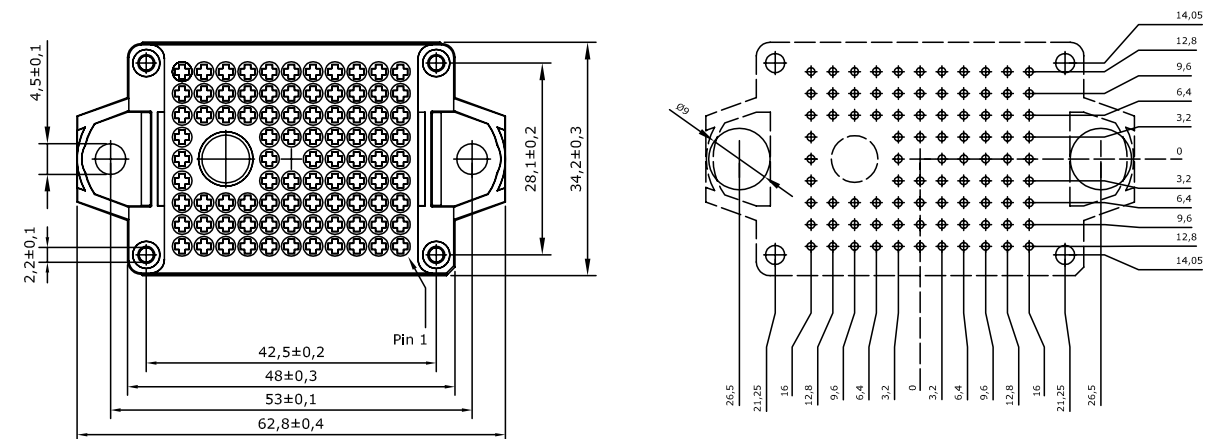


Dimensions in mm

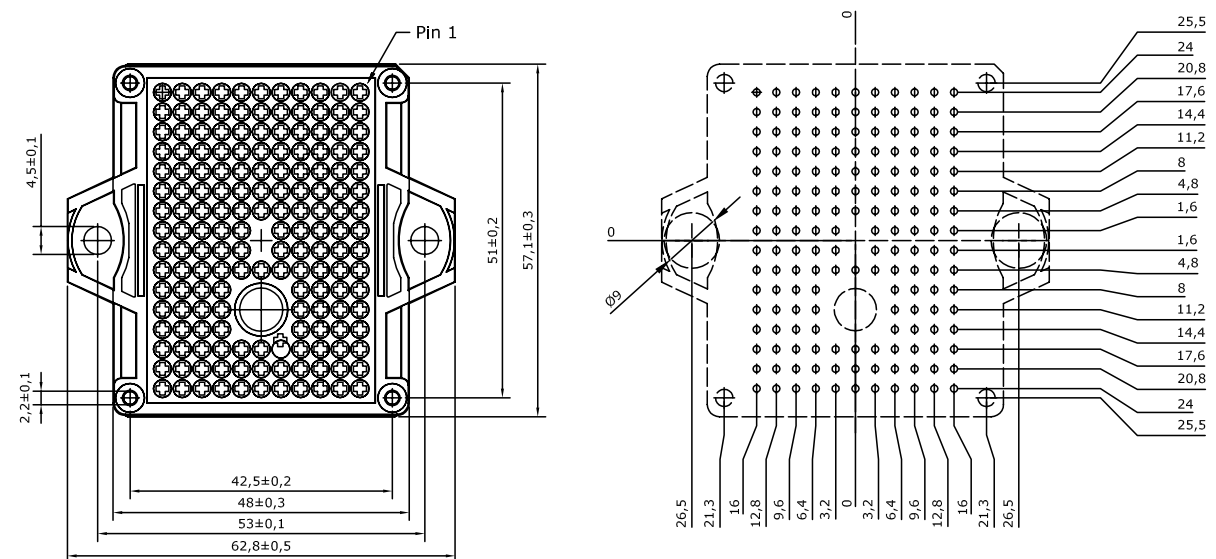
IGBT Modules / SEMITOP

Packages

SEMITOP E1



SEMITOP E2



Dimensions in mm

IGBT Modules / SEMiX

Type	IGBT					Diode			Module			
	$I_C @ T_C = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_C = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	Package	Thermal Interface Material		
	A	A	V	mJ	mJ	A	V	mJ			Topology	
600V - IGBT3 (Trench)												
SEMiX402GAL066HDs	502	400	1.45	22	24	543	1.40	10	2s	P8		
SEMiX603GAL066HDs	720	600	1.45	12	43	771	1.40	13	3s	P8, HT		
SEMiX402GAR066HDs	502	400	1.45	22	24	543	1.40	10	2s	P8		
SEMiX603GAR066HDs	720	600	1.45	12	43	771	1.40	13	3s	P8, HT		
SEMiX202GB066HDs	272	200	1.45	6	8	291	1.40	6.5	2s	P8		
SEMiX302GB066HDs	379	300	1.45	12	15	419	1.40	7.5	2s	P8		
SEMiX402GB066HDs	502	400	1.45	22	24	543	1.40	10	2s	P8		
SEMiX603GB066HDs	720	600	1.45	12	43	771	1.40	13	3s	P8, HT		
SEMiX101GD066HDs	139	100	1.45	3	4	151	1.40	4.5	13	P8		
SEMiX151GD066HDs	200	150	1.45	3.8	6.1	219	1.40	5.8	13	P8		
SEMiX201GD066HDs	258	200	1.45	5	8	284	1.40	7.5	13	P8		
650V - IGBT4 (Trench)												
SEMiX405GARL07E3 ¹⁾	457	400	1.45	28	28	86	1.37	-	5p	P8, HT		
SEMiX453GB07E3p ²⁾	558	450	1.45	8	20	591	1.40	9	3p	P8, HT		
SEMiX155MLI07E4 ²⁾	187	150	1.55	1.5	8.6	145	1.40	2.3	5p	P8, HT		
SEMiX205MLI07E4 ²⁾	262	200	1.55	2	10	294	1.40	4.5	5p	P8, HT		
SEMiX305MLI07E4 ²⁾	388	300	1.55	2.5	16	294	1.40	7.7	5p	P8, HT		
SEMiX405MLI07E4 ²⁾	474	400	1.55	5.3	20	377	1.40	11	5p	P8, HT		
SEMiX305GD07E4 ¹⁾	372	300	1.55	5.5	16	335	1.40	5.2	5p	P8, HT		
1200V - V-IGBT												
SEMiX151GAL12Vs	231	150	1.75	19	17	189	2.14	12	1s	HT		
SEMiX151GB12Vs	231	150	1.75	19	17	189	2.14	12	1s	HT		
SEMiX202GB12Vs	310	200	1.75	25	24	229	2.20	15	2s	P8		
SEMiX223GB12Vs	323	225	1.85	20	27	263	2.17	16	3s	P8, HT		
SEMiX302GB12Vs	448	300	1.75	37	36	356	2.14	22	2s	P8		
SEMiX303GB12Vs	448	300	1.75	27	36	327	2.20	21	3s	P8, HT		
SEMiX404GB12Vs	596	400	1.75	39	52	440	2.20	34	4s	HT		
SEMiX453GB12Vs	673	450	1.75	40	54	516	2.14	33	3s	P8, HT		
SEMiX603GB12Vs	800	600	1.85	50	83	516	2.42	40	3s	P8, HT		
SEMiX604GB12Vs	880	600	1.75	59	79	707	2.14	50	4s	HT		

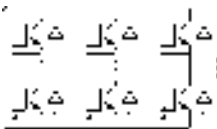
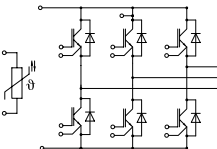
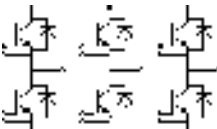
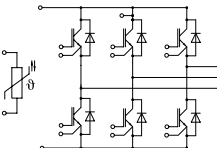
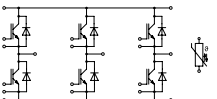
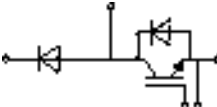
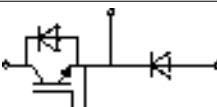
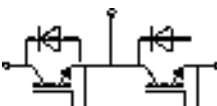
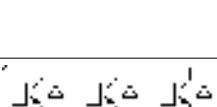
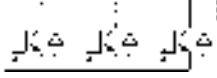
Footnotes: 1) Sample status / 2) In production new

IGBT Modules / SEMiX

Type	IGBT					Diode			Module			
	I _C @ T _C = 25°C	I _{Cnom}	V _{CE(sat)} @ T _J = 25°C typ.	E _{on}	E _{off}	I _F @ T _C = 25°C	V _F @ T _J = 25°C typ.	E _{rr}	Package	Thermal Interface Material		
	A	A	V	mJ	mJ	A	V	mJ			Topology	
1200V - V-IGBT												
SEMiX101GD12Vs	159	100	1.75	13	11	121	2.20	7.7	13	P8		
SEMiX151GD12Vs	231	150	1.75	19	17	189	2.14	12	13	P8		
SEMiX223GD12Vc	323	225	1.85	20	27	263	2.17	16	33c	P8		
SEMiX303GD12Vc	448	300	1.75	27	36	327	2.20	21	33c	P8		
SEMiX453GD12Vc	673	450	1.75	40	54	516	2.14	33	33c	P8		
1200V - IGBT4 (Trench)												
SEMiX151GAL12E4s	232	150	1.80	17	18	189	2.14	8.9	1s	HT		
SEMiX302GAL12E4s	463	300	1.80	30	44	356	2.14	19	2s	P8		
SEMiX453GAL12E4s	683	450	1.80	45	67	544	2.14	28	3s	P8, HT		
SEMiX603GAL12E4p ²⁾	1110	600	1.80	59	76	856	2.08	33	3p	P8, HT		
SEMiX604GAL12E4s	916	600	1.80	35	110	707	2.14	44	4s	HT		
SEMiX151GAR12E4s	232	150	1.80	17	18	189	2.14	8.9	1s	HT		
SEMiX302GAR12E4s	463	300	1.80	30	44	356	2.14	19	2s	P8		
SEMiX453GAR12E4s	683	450	1.80	45	67	544	2.14	28	3s	P8, HT		
SEMiX603GAR12E4p ²⁾	1110	600	1.80	64	76	856	2.08	32	3p	P8, HT		
SEMiX604GAR12E4s	916	600	1.80	35	110	707	2.14	44	4s	HT		
SEMiX151GB12E4s	232	150	1.80	17	18	189	2.14	8.9	1s	HT		
SEMiX202GB12E4s	312	200	1.80	22	28	229	2.20	12	2s	P8		
SEMiX223GB12E4p	326	225	1.85	14	26	287	2.17	17	3p	P8, HT		
SEMiX302GB12E4s	463	300	1.80	30	44	356	2.14	19	2s	P8		
SEMiX303GB12E4p	469	300	1.80	23	38	378	2.20	23	3p	P8, HT		
SEMiX303GB12E4s	466	300	1.80	30	41	338	2.20	18	3s	P8, HT		
SEMiX404GB12E4s	618	400	1.80	27	60	440	2.20	26	4s	HT		
SEMiX453GB12E4p	678	450	1.80	25	57	578	2.14	37	3p	P8, HT		
SEMiX453GB12E4s	683	450	1.80	45	67	544	2.14	28	3s	P8, HT		
SEMiX603GB12E4p	1110	600	1.80	69	80	856	2.08	40	3p	P8, HT		
SEMiX604GB12E4s	916	600	1.80	35	110	707	2.14	44	4s	HT		
SEMiX303GB12E4I50p ¹⁾	469	300	1.80	23	38	378	2.20	23	3Ip	P8, HT		
SEMiX453GB12E4Ip	678	450	1.80	33	57	578	2.14	39	3Ip	P8, HT		
SEMiX603GB12E4Ip	1110	600	1.80	63	80	856	2.08	40	3Ip	P8, HT		
SEMiX453GM12E4p ¹⁾	678	450	1.80	11	66	544	2.14	32	3Ip	P8, HT		
SEMiX205MLI12E4 ¹⁾	313	200	1.80	13	25	229	2.20	5.8	5p	P8, HT		
SEMiX305MLI12E4 ²⁾	451	300	1.80	17	39	344	2.14	22	5p	P8, HT		
SEMiX205TMLI12E4B ²⁾	318	200	1.80	5	4	229	2.20	5.9	5p	P8, HT		
SEMiX305TMLI12E4B ²⁾	479	300	1.80	4.5	21	363	2.20	8.8	5p	P8, HT		
SEMiX405TMLI12E4B ²⁾	636	400	1.80	6	28	461	2.20	12	5p	P8, HT		

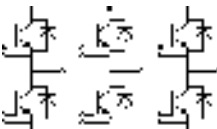
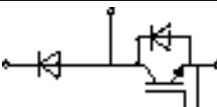
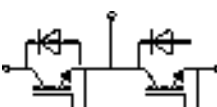
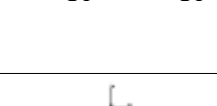
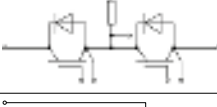
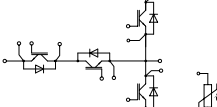
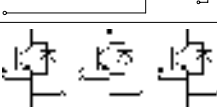
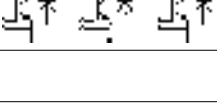
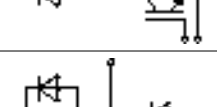
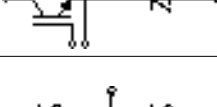
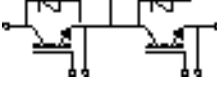
Footnotes: 1) Sample status / 2) In production new

IGBT Modules / SEMiX

Type	IGBT					Diode			Module			
	I_C @ $T_C = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^{\circ}\text{C}$ typ.	E_{on}	E_{off}	I_F @ $T_C = 25^{\circ}\text{C}$	V_F @ $T_J = 25^{\circ}\text{C}$ typ.	E_{rr}	Package	Thermal Interface Material	Topology	
	A	A	V	mJ	mJ	A	V	mJ				
1200V - IGBT4 (Trench)												
SEMiX71GD12E4s	115	75	1.85	7.5	9	97	2.17	5.3	13	P8		
SEMiX101GD12E4s	160	100	1.80	11	13	121	2.20	6.5	13	P8		
SEMiX151GD12E4s	232	150	1.80	14	19	189	2.14	8.9	13	P8		
SEMiX205GD12E4 ²⁾	313	200	1.80	14	23	224	2.20	16	5p	P8, HT		
SEMiX223GD12E4c	333	225	1.85	22	31	270	2.17	17	33c	P8		
SEMiX303GD12E4c	466	300	1.80	29	42	338	2.20	23	33c	P8		
SEMiX453GD12E4c	683	450	1.80	52	68	544	2.14	28	33c	P8		
1200V - IGBT4 (Fast Trench)												
SEMiX155GD12T4 ¹⁾	219	150	1.80	13	21	175	2.14	14	5p	P8, HT		
SEMiX106GD12T4p ¹⁾	161	100	1.80	7.5	9.5	118	2.20	8	6p	HT		
SEMiX156GD12T4p ¹⁾	236	150	1.80	10	16	182	2.14	13.5	6p	HT		
SEMiX206GD12T4p ¹⁾	302	200	1.80	19	20	209	2.21	14.5	6p	HT		
1200V - IGBT3 (Trench)												
SEMiX452GAL126HDs	455	300	1.70	35	45	394	1.60	33	2s	P8		
SEMiX703GAL126HDs	642	450	1.70	32	68	561	1.60	60	3s	P8, HT		
SEMiX703GAR126HDs	642	450	1.70	32	68	561	1.60	60	3s	P8, HT		
SEMiX252GB126HDs	242	150	1.70	20	21	228	1.60	18	2s	P8		
SEMiX302GB126HDs	311	200	1.70	30	26	292	1.60	23	2s	P8		
SEMiX353GB126HDs	364	225	1.70	27	33	329	1.60	29	3s	P8, HT		
SEMiX452GB126HDs	455	300	1.70	35	45	394	1.60	33	2s	P8		
SEMiX503GB126HDs	466	300	1.70	28	44	431	1.60	33	3s	P8, HT		
SEMiX604GB126HDs	590	400	1.70	36	60	533	1.60	46	4s	HT		
SEMiX703GB126HDs	642	450	1.70	32	68	561	1.60	60	3s	P8, HT		
SEMiX904GB126HDs	821	600	1.70	60	88	752	1.60	75	4s	HT		
SEMiX101GD126HDs	129	75	1.70	10	11	117	1.60	9	13	P8		
SEMiX151GD126HDs	168	100	1.70	12	14	152	1.60	12	13	P8		
SEMiX251GD126HDs	242	150	1.70	19	22	207	1.60	15	13	P8		

Footnotes: 1) Sample status / 2) In production new

IGBT Modules / SEMiX

Type	IGBT					Diode			Module			
	I_C @ $T_C = 25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^\circ\text{C}$ typ.	E_{on}	E_{off}	I_F @ $T_C = 25^\circ\text{C}$	V_F @ $T_J = 25^\circ\text{C}$ typ.	E_{rr}	Package	Thermal Interface Material		
	A	A	V	mJ	mJ	A	V	mJ			Topology	
1200V - IGBT3 (Trench)												
SEMiX353GD126HDc	364	225	1.70	27	33	329	1.60	29	33c	P8		
SEMiX503GD126HDc	466	300	1.70	28	44	412	1.60	33	33c	P8		
SEMiX703GD126HDc	642	450	1.70	32	68	561	1.59	60	33c	P8		
1700V - IGBT4 (Trench)												
SEMiX302GAL17E4s	516	300	1.90	140	122	324	1.98	70	2s	P8		
SEMiX453GAL17E4s	762	450	1.90	250	190	482	1.98	100	3s	P8, HT		
SEMiX151GB17E4s	260	150	1.90	52	60	169	1.98	41	1s	HT		
SEMiX202GB17E4s	321	200	1.90	75	82	213	2.00	55	2s	P8		
SEMiX302GB17E4s	516	300	1.90	140	122	324	1.98	70	2s	P8		
SEMiX303GB17E4s	477	300	1.90	140	125	311	2.00	85	3s	P8, HT		
SEMiX404GB17E4s	633	400	1.90	190	165	412	2.00	97	4s	HT		
SEMiX453GB17E4p	731	450	1.90	131	146	557	1.98	72	3p	P8, HT		
SEMiX453GB17E4s	762	450	1.90	250	190	482	1.98	100	3s	P8, HT		
SEMiX603GB17E4p ²⁾	981	600	1.95	125	200	794	1.88	120	3p	P8, HT		
SEMiX604GB17E4s	1015	600	1.90	255	255	629	1.98	150	4s	HT		
SEMiX453GB17E4Ip	731	450	1.90	153	150	557	1.98	73	3Ip	P8, HT		
SEMiX305TMLI17E4C ¹⁾	486	300	1.90	38	60	338	2.00	38	5p	P8, HT		
SEMiX453GD17E4c	762	450	1.90	186	183	482	1.98	122	33c	P8		
1700V - IGBT3 (Trench)												
SEMiX653GAL176HDs	619	450	2.00	300	180	545	1.70	73	3s	P8, HT		
SEMiX653GAR176HDs	619	450	2.00	300	180	545	1.70	73	3s	P8, HT		
SEMiX252GB176HDs	246	150	2.00	90	55	288	1.55	32	2s	P8		
SEMiX302GB176HDs	308	200	2.00	130	77	389	1.50	43	2s	P8		
SEMiX353GB176HDs	353	225	2.00	155	85	428	1.55	45	3s	P8, HT		
SEMiX452GB176HDs	437	300	2.00	180	110	389	1.70	46	2s	P8		
SEMiX453GB176HDs	444	300	2.00	215	125	545	1.50	65	3s	P8, HT		
SEMiX604GB176HDs	567	400	2.00	215	165	740	1.50	95	4s	HT		

Footnotes: 1) Sample status / 2) In production new

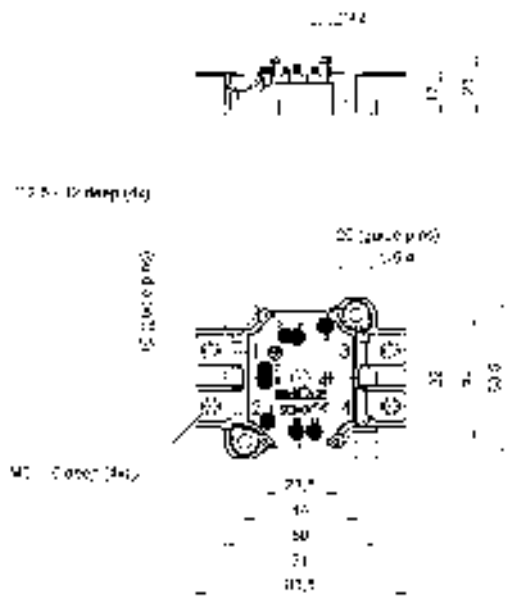
IGBT Modules / SEMiX

Type	IGBT					Diode			Module		
	I_C @ $T_C = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	I_F @ $T_C = 25^{\circ}\text{C}$	V_F @ $T_J = 25^{\circ}\text{C typ.}$	E_{rr}	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ			Topology
1700V - IGBT3 (Trench)											
SEMiX653GB176HDs	619	450	2.00	300	180	545	1.70	73	3s	P8, HT	
SEMiX854GB176HDs	779	600	2.00	300	250	740	1.70	170	4s	HT	
SEMiX353GD176HDc	353	225	2.00	155	85	428	1.55	45	33c	P8	
SEMiX453GD176HDc	444	300	2.00	215	125	545	1.50	65	33c	P8	
SEMiX653GD176HDc	619	450	2.00	300	180	545	1.70	73	33c	P8	

Footnotes: 1) Sample status / 2) In production new

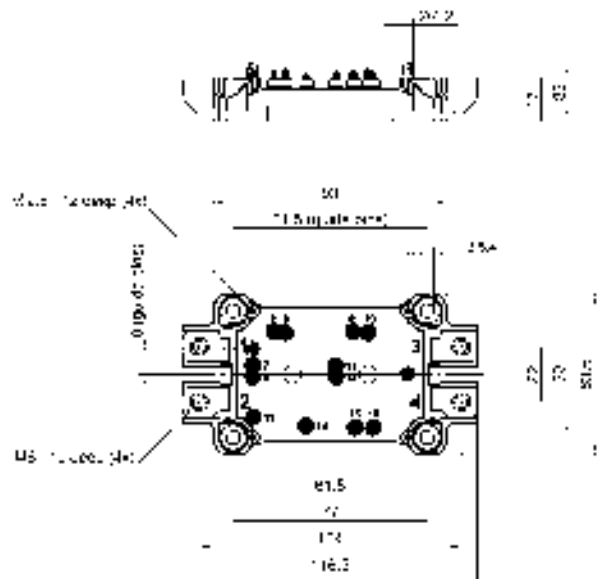
Packages

SEMiX 1s



Dimensions in mm

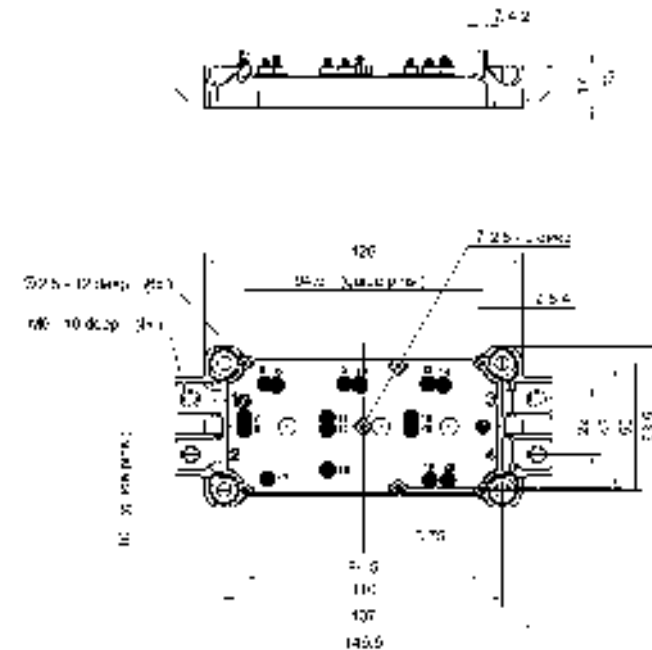
SEMiX 2s



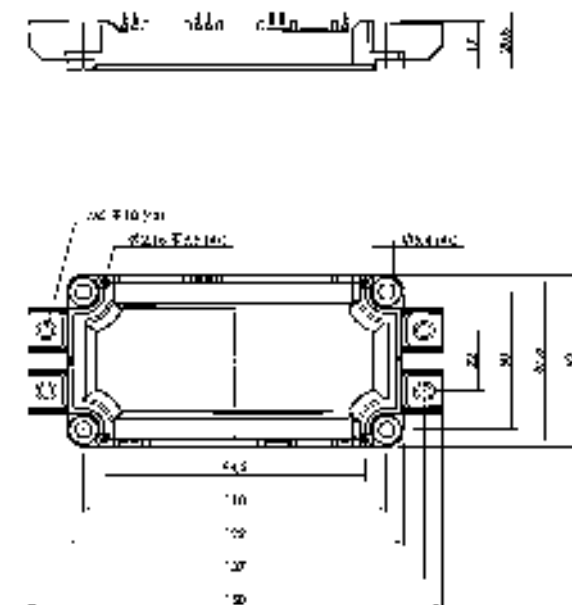
IGBT Modules / SEMiX

Packages

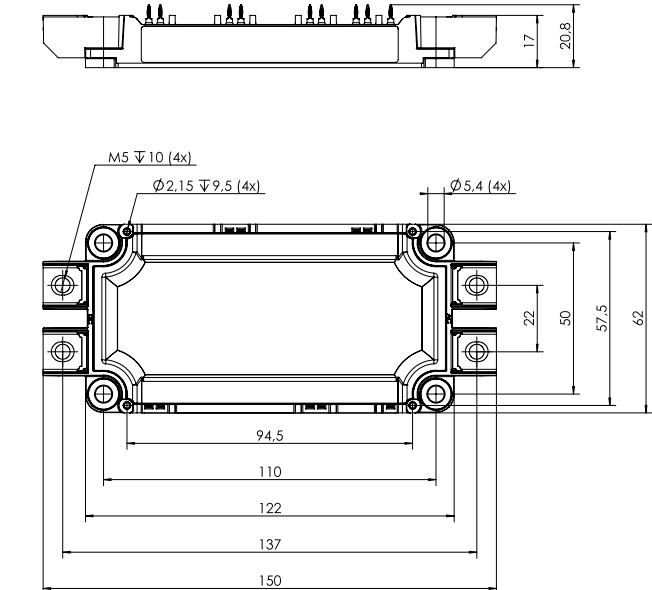
SEMiX 3s



SEMiX 3p

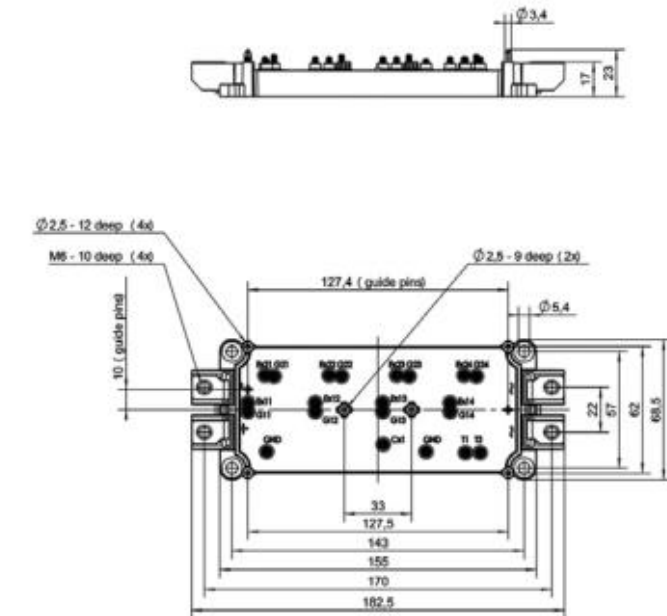


SEMiX 3Ip



Dimensions in mm

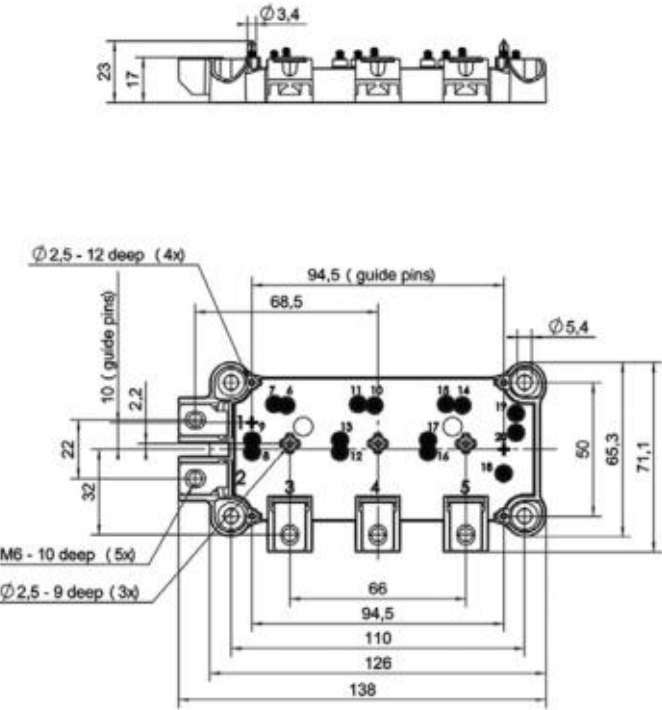
SEMiX 4s



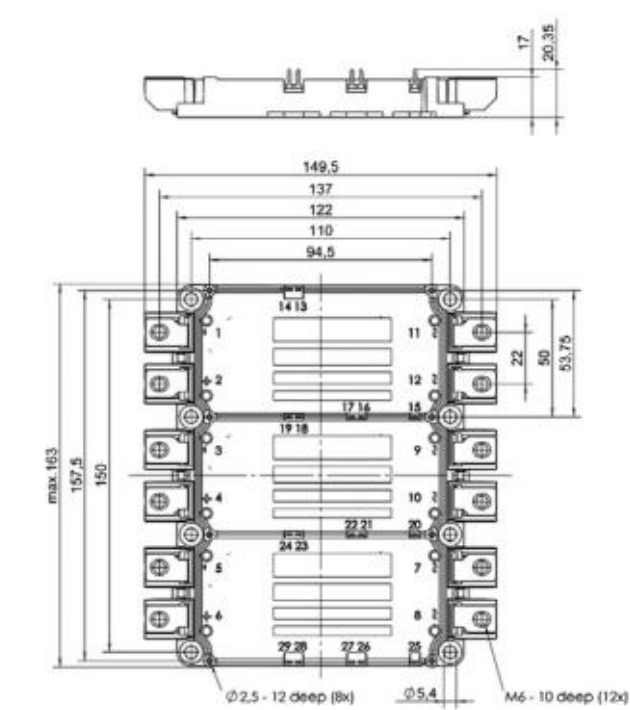
IGBT Modules / SEMiX

Packages

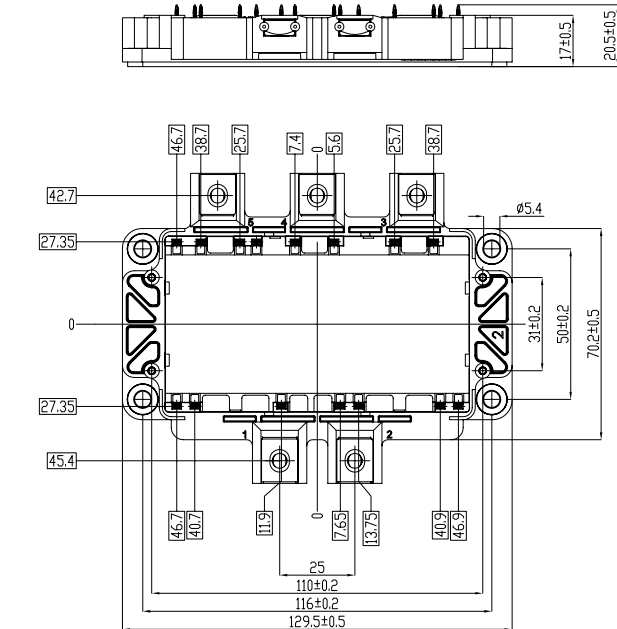
SEMIX 13



SEMIX 33c

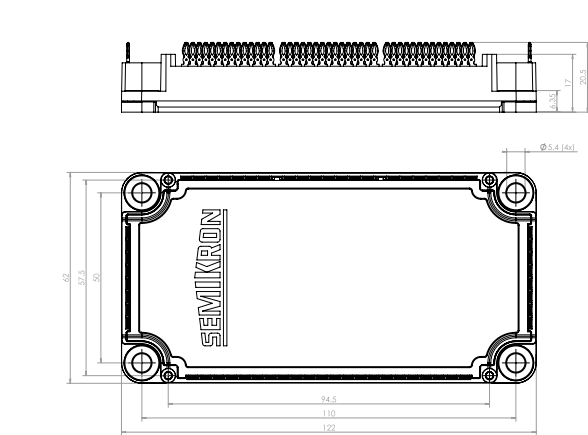


SEMIX 5p

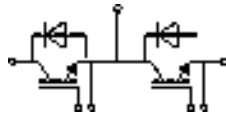
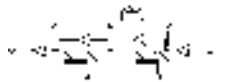
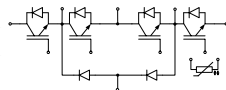
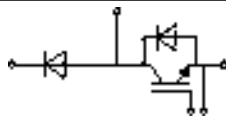
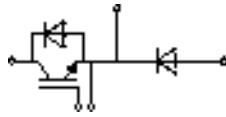
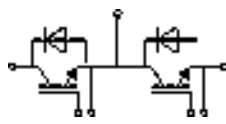
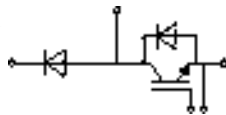
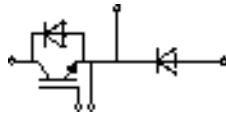
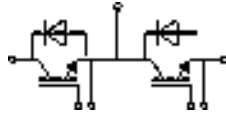
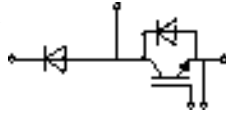


Dimensions in mm

SEMIX 6p

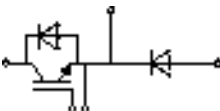
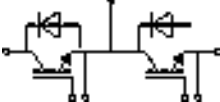
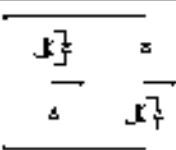
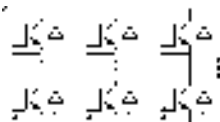
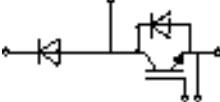
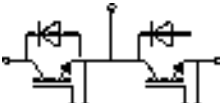
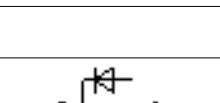
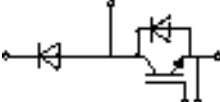
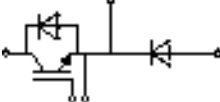


IGBT Modules / SEMITRANS

Type	IGBT					Diode		Module			
	I _C @ T _C = 25°C	I _{Cnom}	V _{CE(sat)} @ T _J = 25°C typ.	E _{on}	E _{off}	I _F @ T _C = 25°C	V _F @ T _J = 25°C typ.	E _{rr}	Package	Thermal Interface Material	
	A	A	V	mJ	mJ	A	V	mJ			Topology
600V - IGBT3 (Trench)											
SKM145GB066D	195	150	1.46	8.5	5.5	150	1.40	3.5	2	HT	
SKM195GB066D	265	200	1.46	14	8	200	1.40	5.6	2	HT	
SKM300GB066D	390	300	1.45	7.5	11.5	350	1.38	10.5	3	P8	
SKM400GB066D	500	400	1.45	8	16	450	1.40	14	3	P8	
SKM600GB066D	760	600	1.45	7.5	29.5	700	1.40	25	3	P8	
SKM200GARL066T ²⁾	280	200	1.45	2.24	7.89	270	1.45	4	5	-	
SKM300GARL066T ²⁾	393	300	1.45	3.5	10.1	421	1.54	4	5	-	
SKM400GARL066T ¹⁾	504	400	1.45	4.48	15.78	421	1.54	8	5	-	
SKM150MLI066TAT ¹⁾	200	150	1.45	1.7	5.1	200	1.35	2	5	-	
SKM200MLI066TAT ²⁾	280	200	1.45	2.53	6.82	270	1.4	4	5	-	
SKM300MLI066TAT ²⁾	400	300	1.45	3.5	10.1	324	1.35	4	5	-	
600V - NPT IGBT (Standard)											
SKM75GAL063D ³⁾	100	75	2.1	3	2.5	75	1.55	0.53	2	HT	
SKM300GAL063D ³⁾	400	300	2.1	14	13	250	1.65	4	3	P8	
SKM75GAR063D ³⁾	100	75	2.1	3	2.5	75	1.55	0.53	2	HT	
SKM300GAR063D ³⁾	400	300	2.1	14	13	250	1.65	4	3	P8	
SKM50GB063D ³⁾	70	50	2.10	2.5	1.8	75	1.35	0.48	2	HT	
SKM75GB063D ³⁾	100	75	2.1	3	2.5	75	1.55	0.53	2	HT	
SKM100GB063D ³⁾	130	100	2.1	4	3	100	1.55	1.5	2	HT	
SKM200GB063D ³⁾	260	200	2.1	11	7.5	200	1.55	2.1	3	P8	
SKM300GB063D ³⁾	400	300	2.1	14	13	250	1.65	4	3	P8	
650V - IGBT3 (Trench)											
SKM195GAL07E3 ²⁾	266	200	1.46	6.3	8.3	217	1.39	4.5	2	HT	
SKM300GAL07E3 ²⁾	382	300	1.45	3	14	335	1.40	6.4	3	P8	
SKM195GAR07E3 ²⁾	266	200	1.46	6.3	8.3	217	1.39	4.5	2	HT	
SKM300GAR07E3 ²⁾	382	300	1.45	3	14	335	1.40	6.4	3	P8	
SKM195GB07E3 ²⁾	266	200	1.46	6.3	8.3	217	1.39	4.5	2	HT	
SKM300GB07E3 ²⁾	382	300	1.45	3	14	335	1.40	6.4	3	P8	
SKM400GB07E3 ²⁾	506	400	1.45	4	17	449	1.39	12	3	P8	
SKM600GB07E3 ²⁾	758	600	1.45	4.7	37	770	1.40	9.3	3	P8	
1200V - NPT IGBT (Ultrafast)											
SKM600GA125D	580	400	3.3	30	22	500	2.00	24	4	P8	
SKM800GA125D	760	600	3.20	88	48	720	2.3	28	4	P8	
SKM200GAL125D	200	150	3.3	14	8	200	2.06	8	3	P8	
SKM400GAL125D	400	300	3.3	17	18	390	2.06	16	3	P8	

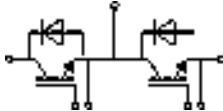
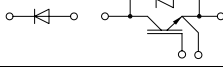
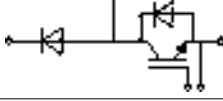
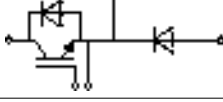
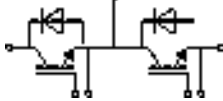
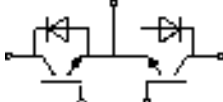
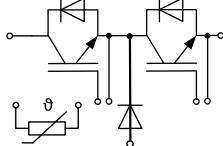
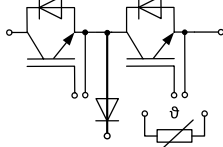
Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 11) Values at T_j=150°C

IGBT Modules / SEMITRANS

Type	IGBT					Diode			Module			
	$I_C @ T_C = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_C = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_r	Package	Thermal Interface Material	Topology	
	A	A	V	mJ	mJ	A	V	mJ				
1200V - NPT IGBT (Ultrafast)												
SKM200GAR125D	200	150	3.3	14	8	200	2.06	8	3	P8		
SKM400GAR125D	400	300	3.3	17	18	390	2.06	16	3	P8		
SKM100GB125DN	100	75	3.3	9	3.5	95	2.06	4	2N	-		
SKM200GB125D	200	150	3.3	14	8	200	2.06	8	3	P8		
SKM300GB125D	300	200	3.3	16	11	260	2.00	13	3	P8		
SKM400GB125D	400	300	3.3	17	18	390	2.06	16	3	P8		
SKM25GAH125D ³⁾	39	25	3.20	3.9	1.6	47	2.13	1.1	6	-		
SKM25GD125D ³⁾	39	25	3.20	3.9	1.6	47	2.13	1.1	6	-		
SKM50GD125D ³⁾	73	50	3.20	8	3.2	77	2.00	2.1	6	-		
1200V - IGBT3 (Trench)												
SKM600GA126D	660	400	1.70	39	64	490	1.60	41	4	P8		
SKM800GA126D	910	600	1.70	65	95	703	1.60	59	4	P8		
SKM195GAL126D	220	150	1.71	16	24.5	143	2.00	5.8	2	HT		
SKM200GAL126D	260	150	1.71	18	24	200	1.60	18	3	P8		
SKM400GAL126D	470	300	1.69	29	48	352	1.60	27	3	P8		
SKM600GAL126D	660	400	1.70	39	64	490	1.60	41	3	P8		
SKM195GB126D	220	150	1.71	16	24.5	143	2.00	5.8	2	HT		
SKM200GB126D	260	150	1.71	18	24	200	1.60	18	3	P8		
SKM300GB126D	310	200	1.70	21	33	250	1.60	18	3	P8		
SKM400GB126D	470	300	1.69	29	48	352	1.60	27	3	P8		
SKM600GB126D	660	400	1.70	39	64	490	1.60	41	3	P8		
1200V - V-IGBT												
SKM300GA12V	420	300	1.84	23	33	353	2.17	21	4	P8		
SKM400GA12V	612	400	1.74	39	42	440	2.20	26	4	P8		
SKM600GA12V	908	600	1.75	76	76	707	2.14	43	4	P8		
SKM150GAL12V	231	150	1.75	13.5	14.2	189	2.14	8.5	2	HT		
SKM200GAL12VL2 ²⁾	299	200	1.86	24	22	189	2.14	8.5	2	HT		
SKM400GAL12V	612	400	1.74	39	42	440	2.20	26	3	P8		
SKM150GAR12V ²⁾	231	150	1.75	13.5	14.2	189	2.14	8.5	2	HT		
SKM400GAR12V	612	400	1.74	39	42	440	2.20	26	3	P8		

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 11) Values at T_J=150°C

IGBT Modules / SEMITRANS

Type	IGBT					Diode			Module		
	I_C @ $T_C = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	I_F @ $T_C = 25^{\circ}\text{C}$	V_F @ $T_J = 25^{\circ}\text{C typ.}$	E_r	Package	Thermal Interface Material	Topology
	A	A	V	mJ	mJ	A	V	mJ			
1200V - V-IGBT											
SKM50GB12V	77	50	1.84	4.9	4.5	65	2.22	2.8	2	HT	
SKM75GB12V	114	75	1.84	6.7	7.1	97	2.17	4.2	2	HT	
SKM100GB12V	159	100	1.75	10.7	8.7	121	2.20	5.7	2	HT	
SKM150GB12V	231	150	1.75	13.5	14.2	189	2.14	8.5	2	HT	
SKM150GB12VG	222	150	1.86	10	16.5	187	2.17	11	3	P8	
SKM200GB12V	311	200	1.76	14	22	229	2.20	13	3	P8	
SKM300GB12V	420	300	1.84	23	33	353	2.17	21	3	P8	
SKM400GB12V	612	400	1.74	39	42	440	2.20	26	3	P8	
1200V - IGBT4 (Trench)											
SKM300GA12E4	422	300	1.85	23.4	35	353	2.17	22.2	4	P8	
SKM400GA12E4	616	400	1.80	28	59	461	2.20	37	4	P8	
SKM600GA12E4	913	600	1.80	30	77	707	2.14	39	4	P8	
SKM900GA12E4	1305	900	1.83	130	121	871	2.31	53	4	P8	
SKM600GAE12E4 ²⁾	860	600	1.80	81	83	54	14.62	35.5	5	-	
SKM200GAL12E4	313	200	1.80	21	27	229	2.20	13	3	P8	
SKM300GAL12E4	422	300	1.85	27	39	353	2.17	23	3	P8	
SKM400GAL12E4	616	400	1.80	33	56	461	2.20	30.5	3	P8	
SKM200GAR12E4	313	200	1.80	21	27	229	2.20	13	3	P8	
SKM300GAR12E4	422	300	1.85	27	39	353	2.17	23	3	P8	
SKM400GAR12E4	616	400	1.80	33	56	461	2.20	30.5	3	P8	
SKM200GB12E4	313	200	1.80	21	27	229	2.20	13	3	P8	
SKM300GB12E4	422	300	1.85	27	39	353	2.17	23	3	P8	
SKM400GB12E4	616	400	1.80	33	56	461	2.20	30.5	3	P8	
SKM450GB12E4	700	450	1.84	32	60	461	2.31	28	3	P8	
SKM600GB12E4 ²⁾	860	600	1.80	30	77	623	2.28	39	3	P8	
SKM450GM12E4 ¹⁾	700	450	1.84	32	60	461	2.31	28	3	P8	
SKM1200MLI12TE4 ²⁾	2082	1200	1.80	108	189	1065	2.46	76	10	HT	
SKM1200MLI12BE4 ²⁾	2082	1200	1.80	108	189	1065	2.46	76	10	HT	
1200V - IGBT4 Fast (Trench)											
SKM300GA12T4	422	300	1.85	23.4	26	353	2.17	22.2	4	P8	
SKM400GA12T4	616	400	1.80	28	44	461	2.20	37	4	P8	
SKM600GA12T4	913	600	1.80	74	63	707	2.14	38	4	P8	

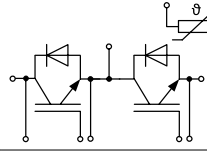
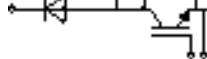
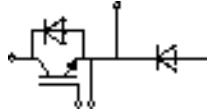
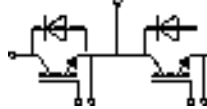
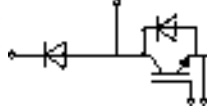
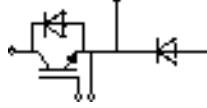
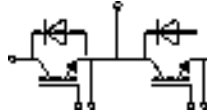
Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 11) Values at T_J=150°C

IGBT Modules / SEMITRANS

Type	IGBT					Diode			Module			
	I_C @ $T_C = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^{\circ}\text{C}$ typ.	E_{on}	E_{off}	I_F @ $T_C = 25^{\circ}\text{C}$	V_F @ $T_J = 25^{\circ}\text{C}$ typ.	E_r	Package	Thermal Interface Material		
	A	A	V	mJ	mJ	A	V	mJ			Topology	
1200V - IGBT4 Fast (Trench)												
SKM50GAL12T4	81	50	1.85	5.5	4.5	65	2.22	3.6	2	HT		
SKM100GAL12T4	160	100	1.80	15	10.2	121	2.20	5.9	2	HT		
SKM150GAL12T4	232	150	1.81	19.2	15.8	189	2.14	13	2	HT		
SKM200GAL12T4	313	200	1.80	21	20	229	2.20	13	3	P8		
SKM300GAL12T4	422	300	1.85	27	29	353	2.17	23	3	P8		
SKM400GAL12T4	616	400	1.80	33	42	461	2.20	30.5	3	P8		
SKM600GAL12T4 ²⁾	860	600	1.80	33	70	623	2.28	40	3	P8		
SKM150GAR12T4	232	150	1.81	19.2	15.8	189	2.14	13	2	HT		
SKM400GAR12T4	616	400	1.80	33	42	461	2.20	30.5	3	P8		
SKM600GAR12T4 ²⁾	860	600	1.80	33	70	623	2.28	40	3	P8		
SKM50GB12T4	81	50	1.85	5.5	4.5	65	2.22	3.8	2	HT		
SKM75GB12T4	115	75	1.85	11	6.9	97	2.17	4.7	2	HT		
SKM100GB12T4	160	100	1.80	15	10.2	121	2.20	5.9	2	HT		
SKM100GB12T4G	154	100	1.90	16.1	8.6	118	2.22	6	3	P8		
SKM150GB12T4	232	150	1.81	19.2	15.8	189	2.14	13	2	HT		
SKM150GB12T4G	223	150	1.85	18.7	14.1	183	2.17	9	3	P8		
SKM200GB12T4	313	200	1.80	21	20	229	2.20	13	3	P8		
SKM300GB12T4	422	300	1.85	27	29	353	2.17	23	3	P8		
SKM400GB12T4	616	400	1.80	33	42	461	2.20	30.5	3	P8		
SKM450GB12T4 ²⁾	699	450	1.84	32	49	461	2.31	28	3	P8		
SKM600GB12T4 ²⁾	860	600	1.80	33	70	623	2.28	40	3	P8		
SKM150GM12T4G	229	150	1.85	19.2	15.8	187	2.17	13	3	P8		
SKM200GM12T4	313	200	1.80	21	20	229	2.20	13	3	P8		
SKM300GM12T4	422	300	1.85	27	29	353	2.17	23	3	P8		
SKM400GM12T4	616	400	1.80	33	42	461	2.20	30.5	3	P8		
SKM300GBD12T4	422	300	1.85	27	29	56	2.41	30.5	3	P8		
1200V - IGBT4 High Speed (Trench) (new product series, target data)												
SKM100GAL12F4 ²⁾	142	100	2.05	6.2	7.9	111	2.55	6.4	2	HT		
SKM400GAL12F4 ¹⁾	548	400	2.06	26	28	402	2.55	20	3	P8		
SKM100GAR12F4 ²⁾	142	100	2.05	6.2	7.9	111	2.55	6.4	2	HT		
SKM400GAR12F4 ¹⁾	548	400	2.06	26	28	402	2.55	20	3	P8		
SKM75GB12F4 ²⁾	103	75	2.08	7	5	93	2.43	3	2	HT		
SKM100GB12F4 ²⁾	142	100	2.05	6.2	7.9	111	2.55	6.4	2	HT		
SKM150GB12F4 ¹⁾	201	150	2.05	14	10	174	2.43	5.8	2	HT		
SKM150GB12F4G ¹⁾	201	150	2.05	8	12	174	2.43	8.4	3	P8		
SKM200GB12F4 ¹⁾	279	200	2.06	15	14	211	2.55	8.5	3	P8		
SKM300GB12F4 ¹⁾	380	300	2.06	27	23	334	2.43	12	3	P8		
SKM400GB12F4 ¹⁾	548	400	2.06	26	28	402	2.55	20	3	P8		

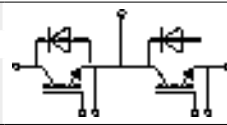
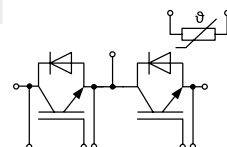
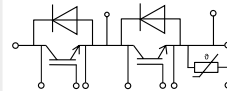
Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 11) Values at T_J=150°C

IGBT Modules / SEMITRANS

Type	IGBT					Diode			Module			
	I_C @ $T_C = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^{\circ}\text{C}$ typ.	E_{on}	E_{off}	I_F @ $T_C = 25^{\circ}\text{C}$	V_F @ $T_J = 25^{\circ}\text{C}$ typ.	E_{rr}	Package	Thermal Interface Material		
	A	A	V	mJ	mJ	A	V	mJ			Topology	
1200V - IGBT4 High Power (Trench)												
SKM1400GB12P4 ²⁾	2165	1400	1.75	150	277	1768	2.06	85	10	HT		
1700V - IGBT3 (Trench)												
SKM600GA176D	660	400	2.00	255	155	600	1.6	102	4	P8		
SKM800GA176D	830	600	2.00	335	245	630	1.6	155	4	P8		
SKM145GAL176D	160	100	2.00	60	38	140	1.6	27.5	2	HT		
SKM200GAL176D	260	150	2.01	93	58	210	1.70	31	3	P8		
SKM400GAL176D	432	300	1.99	170	118	440	1.70	78	3	P8		
SKM400GAR176D	432	300	1.99	170	118	440	1.70	78	3	P8		
SKM75GB176D	80	50	2.00	25	18	80	1.70	14.5	2	HT		
SKM100GB176D	125	75	1.98	44	28.5	100	1.6	21.4	2	HT		
SKM145GB176D	160	100	2.00	60	38	140	1.6	27.5	2	HT		
SKM200GB176D	260	150	2.01	93	58	210	1.70	31	3	P8		
SKM400GB176D	432	300	1.99	170	118	440	1.70	78	3	P8		
1700V - IGBT4 (Trench)												
SKM600GA17E4	1021	600	1.90	258	246	629	1.98	132	4	P8		
SKM100GAL17E4	164	100	1.90	43	39	113	2.00	26	2	HT		
SKM200GAL17E4	321	200	1.90	69	79	213	2.00	45	3	P8		
SKM400GAL17E4	614	400	1.92	156.5	180	443	2.00	130	3	P8		
SKM100GAR17E4	164	100	1.90	43	39	113	2.00	26	2	HT		
SKM200GAR17E4	321	200	1.90	69	79	213	2.00	45	3	P8		
SKM400GAR17E4	614	400	1.92	156.5	180	443	2.00	130	3	P8		
SKM75GB17E4	125	75	1.93	30	29	88	2.00	21	2	HT		
SKM100GB17E4	164	100	1.90	43	39	113	2.00	26	2	HT		
SKM150GB17E4	261	150	1.90	67	59	169	1.98	32	2	HT		
SKM150GB17E4G	242	150	1.90	39	59	163	2.00	33	3	P8		
SKM200GB17E4	321	200	1.90	69	79	213	2.00	45	3	P8		
SKM300GB17E4	476	300	1.91	88	121	314	2.00	77	3	P8		
SKM400GB17E4	614	400	1.92	156.5	180	443	2.00	130	3	P8		
SKM500GB17E4 ¹⁾	737	500	1.90	195	220	546	1.96	140	3	P8		
SKM400GM17E4	614	400	1.92	156.5	180	443	2.00	130	3	P8		

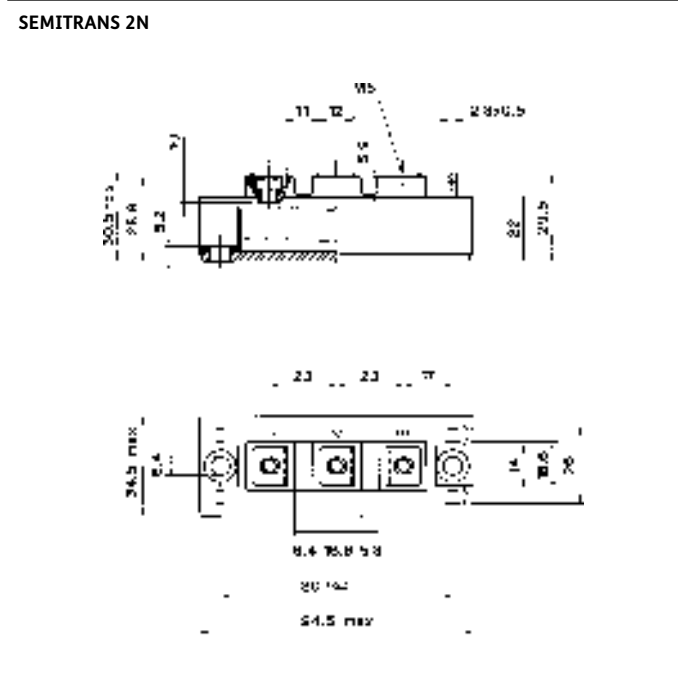
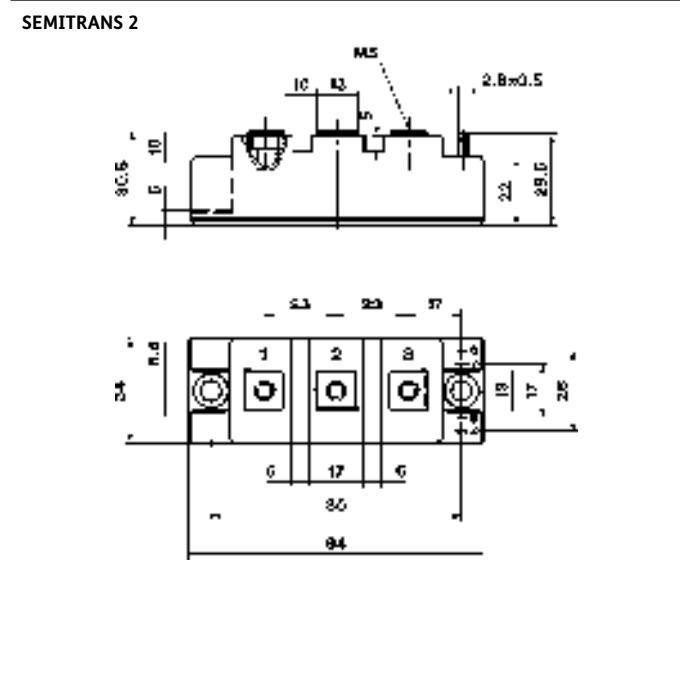
Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 11) Values at T_J=150°C

IGBT Modules / SEMITRANS

Type	IGBT					Diode			Module			Topology
	$I_c @ T_c = 25^{\circ}\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_c = 25^{\circ}\text{C}$	$V_F @ T_j = 25^{\circ}\text{C typ.}$	E_{rr}	Package	Thermal Interface Material		
	A	A	V	mJ	mJ	A	V	mJ				
1700V - IGBT4 (Trench) chip - dedicated for humid environment (target data)												
SKM75GB17E4H16 ²⁾	132	75	1.93	37	29	88	2.00	18	2	HT		
SKM150GB17E4GH16 ²⁾	255	150	1.96	69	59	163	2.00	36	3	P8		
SKM300GB17E4H16 ²⁾	500	300	1.97	106	122	314	2.00	71	3	P8		
1700V - Renesas Gen 8												
SKM1000GB17R8 ²⁾	1574	1000	1.66	465	332	1449	1.78	159	10	HT		
SKM1400GB17R8 ²⁾	2337	1400	1.63	866	495	1874	1.84	253	10	HT		
3300V - N-Channel F-IGBT (new product series, target data)												
SKM450GB33F ²⁾ ¹¹⁾	760	450	2.07	601	601	674	2.05	542	20	-		

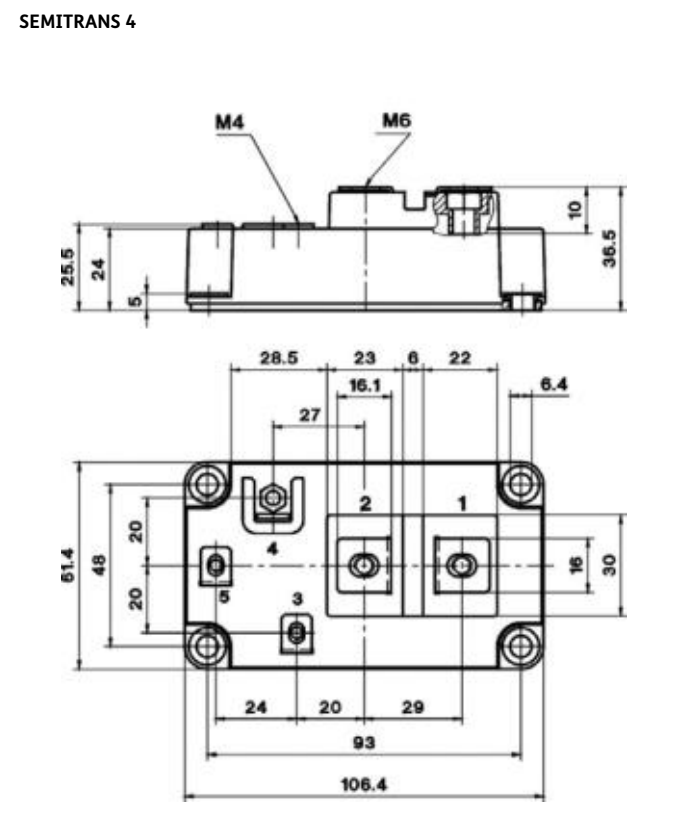
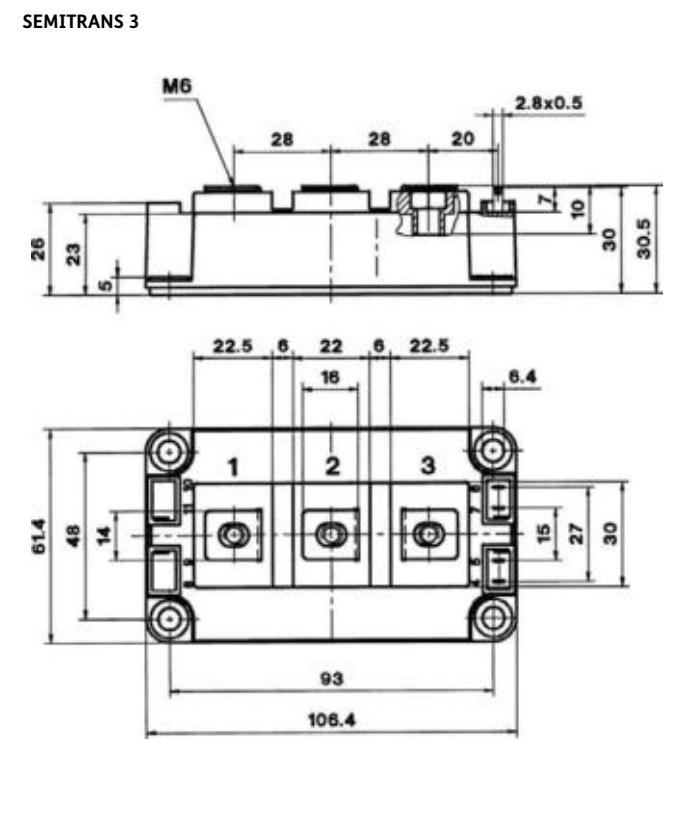
Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs / 11) Values at T_J=150°C

Packages

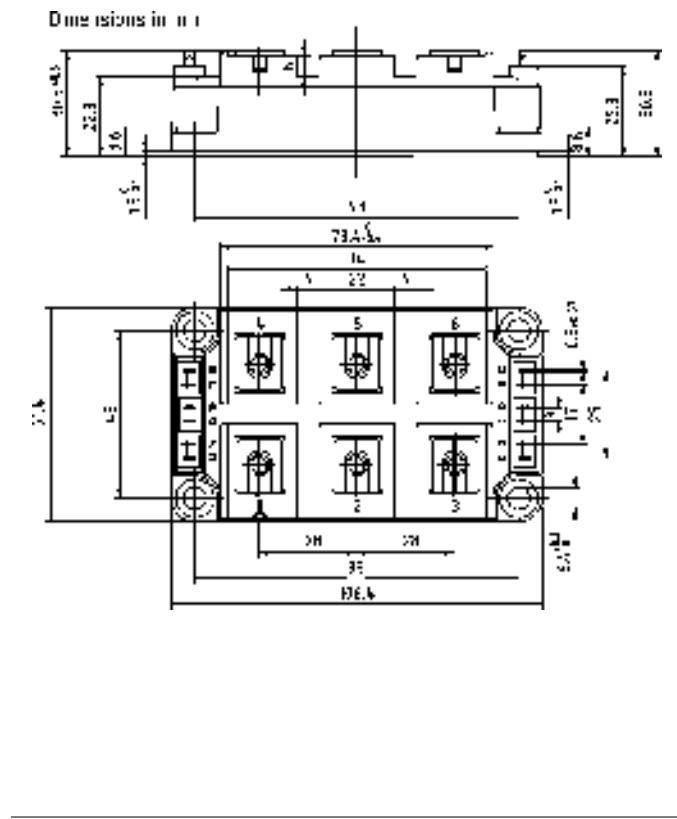


IGBT Modules / SEMITRANS

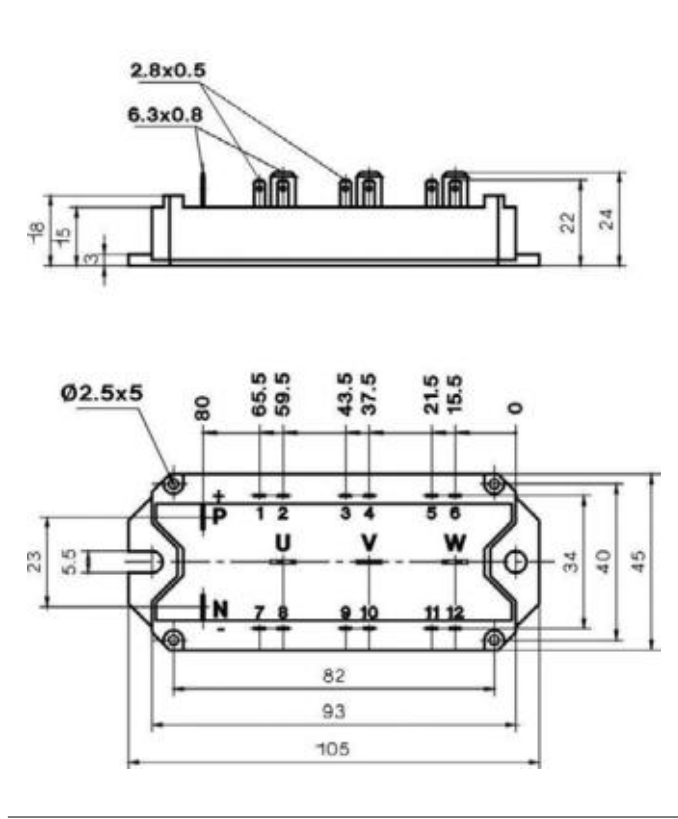
Packages



SEMISTRANS 5



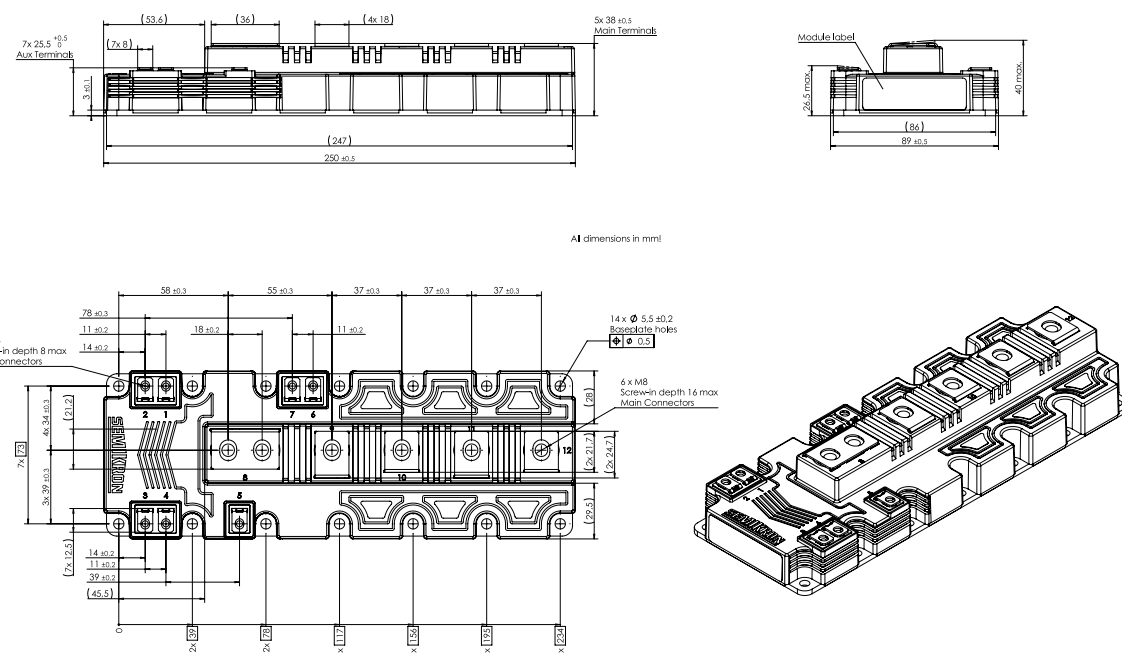
SEMISTRANS 6



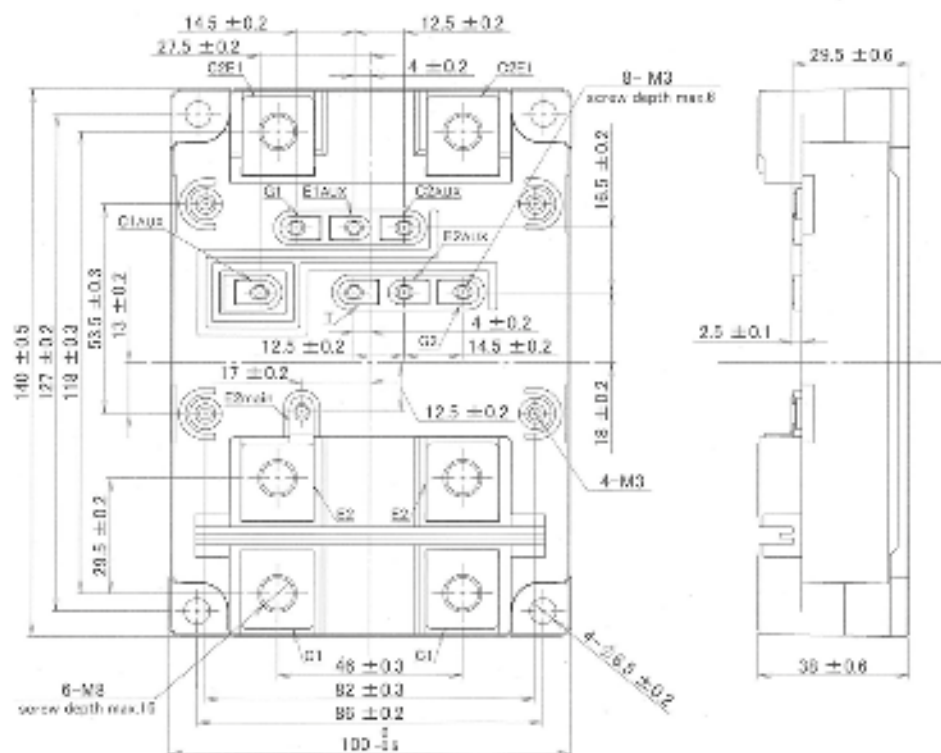
IGBT Modules / SEMITRANS

Packages

SEMITRANS 10



SEMITRANS 20



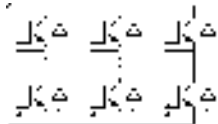
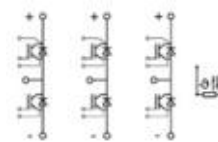
Dimensions in mm

IGBT Modules / SKiM 4/5

Type	IGBT					Diode		Module			
	I_C @ $T_S = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	I_F @ $T_S = 25^{\circ}\text{C}$	V_F @ $T_J = 25^{\circ}\text{C typ.}$	E_{rr}	Package	Thermal Interface Material	Topology
	A	A	V	mJ	mJ	A	V	mJ			
600V - IGBT3 (Trench)											
SKiM301MLI07E4	252	300	1.55	2.8	17	177	1.40	-	4	P12 + HPTP	
SKiM401MLI07E4	314	400	1.55	3.3	21	289	1.40	1.8	4	P12 + HPTP	
SKiM601MLI07E4	433	600	1.55	6.1	44	318	1.39	2.4	4	P12 + HPTP	
1200V - IGBT3 (Trench)											
SKiM200GD126D ³⁾	-	200	1.65	15	25	152	2.39	-	4	P12 + HPTP	
SKiM300GD126D	265	300	1.70	28	47	260	1.92	-	4	P12 + HPTP	
SKiM300GD126DL	265	300	1.65	28	47	260	1.92	-	4	P12 + HPTP	
SKiM400GD126DM	330	300	1.70	25	36	300	1.92	22	4	P12 + HPTP	
SKiM400GD126DLM	330	300	1.65	29	46	300	1.92	-	4	P12 + HPTP	
SKiM450GD126D	390	450	1.70	42	70	345	1.92	-	5	HPTP	
SKiM450GD126DL ³⁾	390	450	1.65	42	70	345	1.92	-	5	HPTP	
SKiM600GD126DLM	480	450	1.65	42	70	450	1.92	-	5	HPTP	
SKiM601GD126DM	480	450	1.70	42	70	450	1.92	-	5	HPTP	
1200V - IGBT4 (Trench)											
SKiM301TMLI12E4B	311	300	1.80	6.6	19	249	2.20	1.8	4	P12 + HPTP	
SKiM401TMLI12E4B	388	400	1.80	8.8	26	311	2.20	2.4	4	P12 + HPTP	
SKiM601TMLI12E4B	529	600	1.80	11	45	495	2.14	4.4	4	P12 + HPTP	
SKiM201MLI12E4	206	200	1.80	15	23	187	2.20	15	4	P12 + HPTP	
SKiM301MLI12E4	311	300	1.80	22	34	282	2.20	22	4	P12 + HPTP	
SKiM455GD12T4D1 ³⁾	400	450	1.80	34	40	295	2.33	28	5	HPTP	
SKiM304GD12T4D ³⁾	312	300	1.80	-	-	221	2.33	-	4	P12 + HPTP	

Footnotes: 3) Not for new designs

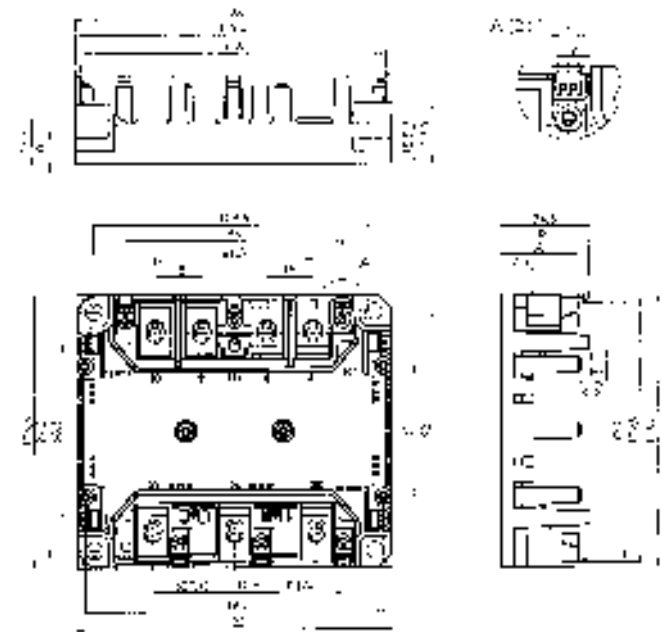
IGBT Modules / SKiM 4/5

Type	IGBT					Diode			Module			
	I_c @ $T_s = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j = 25^{\circ}\text{C}$ typ.	E_{on}	E_{off}	I_F @ $T_s = 25^{\circ}\text{C}$	V_F @ $T_j = 25^{\circ}\text{C}$ typ.	E_{rr}	Package	Thermal Interface Material		
	A	A	V	mJ	mJ	A	V	mJ			Topology	
1700V - IGBT3 (Trench)												
SKiM120GD176D	110	125	2.00	72	46	105	1.6	22	4	P12 + HPTP		
SKiM220GD176DH4	220	250	2.00	145	100	220	1.7	65	4	P12 + HPTP		
SKiM270GD176D	260	300	2.00	170	120	215	1.7	-	5	HPTP		

Footnotes: 3) Not for new designs

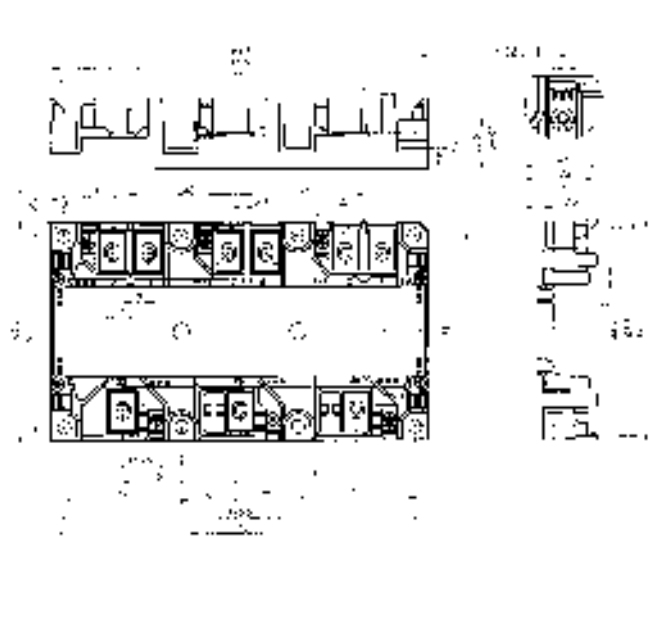
Packages

SKiM 4



Dimensions in mm

SKiM 5



IGBT Modules / SKiM 63/93

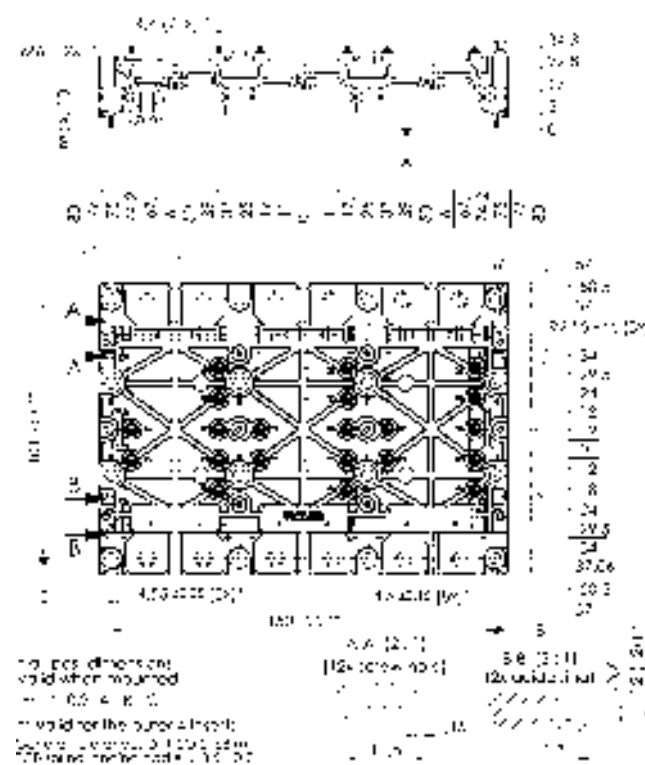
Type	IGBT					Diode			Module					
	I_c @ $T_s = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j = 25^{\circ}\text{C}$ typ.	E_{on}	E_{off}	I_F @ $T_s = 25^{\circ}\text{C}$	V_F @ $T_j = 25^{\circ}\text{C}$ typ.	E_{rr}	Package	Thermal Interface Material				
	A	A	V	mJ	mJ	A	V	mJ			Topology			
600V - IGBT3 (Trench)														
SKiM406GD066HD ¹⁰⁾	468	400	1.45	8	25	360	1.53	12	63	P12, HPTP				
SKiM606GD066HD ¹⁰⁾	640	600	1.45	16	53	462	1.52	21	63	P12, HPTP				
SKiM909GD066HD ¹⁰⁾	897	900	1.45	36	88	690	1.52	29	93	P12, HPTP				
650V - IGBT3 (Trench)														
SKiM606GD07V1 ¹⁰⁾	-	600	1.45	14	39	-	1.57	15	63	P12, HPTP				
SKiM909GD07V1 ¹⁰⁾	-	900	1.45	30	57	573	1.57	19	93	P12, HPTP				
1200V - IGBT4 (Trench)														
SKiM459GD12E4 V2 ¹⁰⁾	554	450	1.85	22	57	438	2.14	40	93	P12, HPTP				
SKiM306GD12E4 V2 ¹⁰⁾	410	300	1.85	19	39	305	2.14	21	63	P12, HPTP				
SKiM609GAL12E4 ¹⁰⁾	748	600	1.85	136	83	1397	1.7	39	93	P12, HPTP				
SKiM609GAR12E4 ¹⁰⁾	748	600	1.85	136	83	1397	1.7	39	93	P12, HPTP				
1700V - IGBT4 (Trench)														
SKiM429GD17E44F ¹⁰⁾	608	420	1.90	178	189	394	1.93	119	93	P12, HPTP				

Footnotes: 10) Also available with new HpTp, see Accessories/Thermal Interface Materials

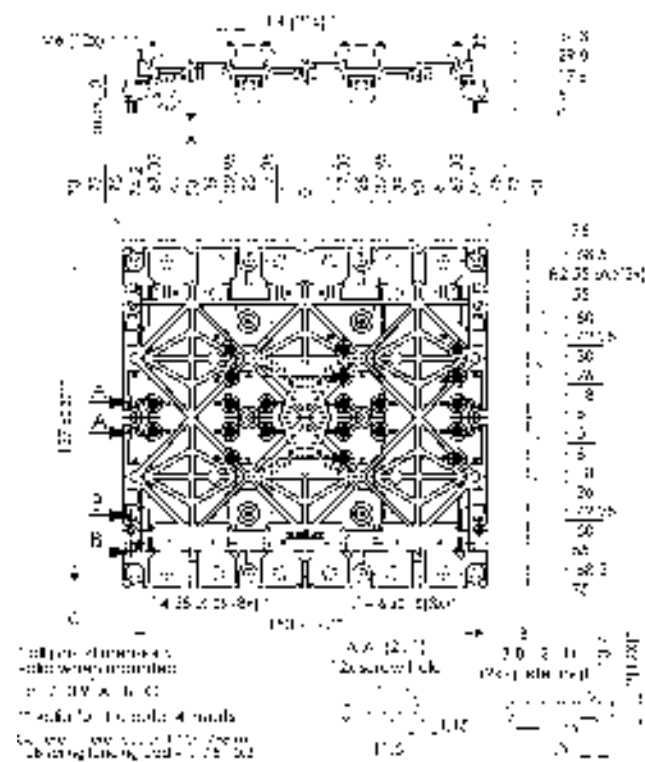
IGBT Modules / SKiM 63/93

Packages

SKiM 63



SKiM 93



Full Silicon Carbide Modules

Highest Power Output and Efficiency

SEMIKRON offers full silicon carbide power modules in MiniSKiiP, SEMITOP and SEMITRANS housings. Using SiC MOSFETs from leading suppliers, excellent output power and power densities are reached in combination with high switching frequencies, minimal losses and maximum efficiency.

The increase in switching frequency means passive filter components can be drastically reduced. Power losses are reduced at the same time, resulting in smaller heat sinks and reducing cooling needs in general. Both benefits result in a major decrease in overall system costs.

The full silicon carbide power modules are available from 20A to 540A in 1200V, with and without anti-parallel free-wheeling Schottky diode. The standard topology sixpacks in classic configuration but split output is also an option that allows for flexible adaption to your application.

Other half-bridges and boost converters including a bypass diode are also available. Beside its SiC MOSFET module portfolio, SEMIKRON offers also single SiC Schottky diodes in SEMIPACK 2 housing.

Full SiC

MiniSKiiP	80
SEMITOP	82
SEMITRANS	86
SEMIPACK	87

For detailed information please refer to data sheets.

Further information

<http://www.semikron.com/full-sic>

Full SiC

MiniSKiiP®

Sixpack



1200V

I in A 0 40 60 80 100 200 300 400 500 600

SEMITOP®

Sixpack
Chopper
H-Bridge
Half-Bridge
Rectifier



1200V

I in A 0 40 60 80 100 200 300 400 500 600

SEMITRANS®

Half-Bridge



1200V

I in A 0 40 60 80 100 200 300 400 500 600

SEMIPACK® 2

Rectifier



1200V

I in A 0 40 60 80 100 200 300 400 500 600

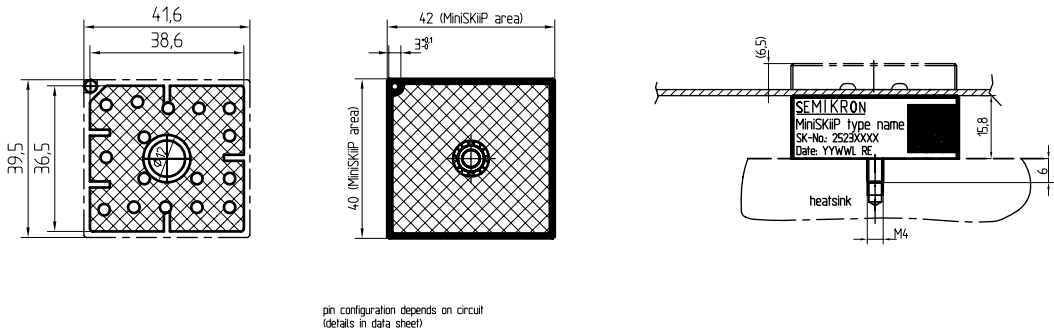
SiC Modules / Full SiC / MiniSKiiP

Type						
	V_{DS} V	$I_D @ T_c = 25^{\circ}C$ A	$R_{DS(on)} @ T_j = 25^{\circ}C$ typ. mΩ	Package	Thermal Interface Material	Topology
1200V - SiC MOSFET						
SKiiP 13ACM12V17 ¹⁾	1200	25	80	II 1	P12, HPTP	
SKiiP 13ACM12V18 ¹⁾	1200	25	80	II 1	P12, HPTP	
SKiiP 26ACM12V17 ¹⁾	1200	72	23	II 2	P12, HPTP	

Footnotes: 1) Sample status

Packages

MiniSKiiP II 1

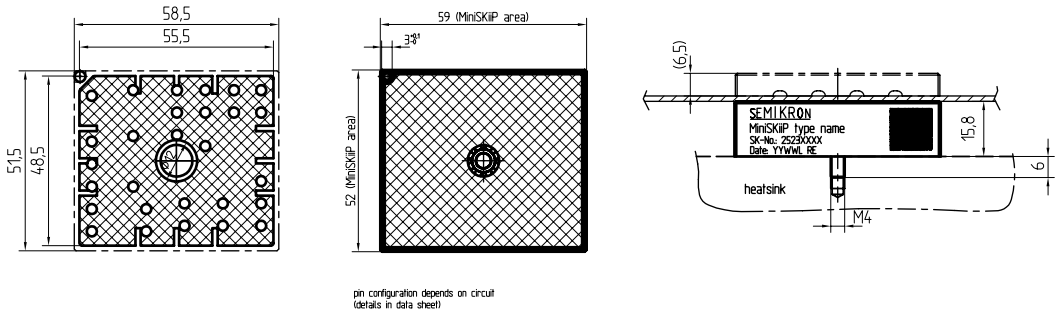


Dimensions in mm

SiC Modules / Full SiC / MiniSKiiP

Packages

MiniSKiiP II 2



Dimensions in mm

SiC Modules / Full SiC / SEMITOP

Type	V_{DS} V	$I_D @ T_C = 25^{\circ}C$ A	$R_{DS(on)} @ T_J = 25^{\circ}C \text{ typ.}$ mΩ	Package	Thermal Interface Material	Topology
1200V - SiC MOSFET						
SK45MH120TSCp ¹⁾	1200	40	45	2p	P12	
SK25MH120SCTp ¹⁾	1200	26	80	2p	P12	
SK45MAHT12SCp ²⁾	1200	39	45	3p	P12, HPTP	
SK45MLET12SCp ¹⁾	1200	39	45	3p	P12, HPTP	
SK35MLLE120SCp ¹⁾	1200	36	40	2p	P12	
SK250MB120SCTE2 ¹⁾	1200	251	3.7	E2	HPTP, HT	
SK508MB120SCTE2 ¹⁾	1200	52	80	E2	HPTP, HT	
SEMITOP rectifier module						
SK20KDD12SCp ¹⁾	1200	18	-	2p	P12	

Footnotes: 1) Sample status / 2) In production new

SiC Modules / Full SiC / SEMITOP

Type	V_{DS} V	$I_D @ T_C = 25^{\circ}C$ A	$R_{DS(on)} @ T_J = 25^{\circ}C \text{ typ.}$ mΩ	Package	Thermal Interface Material	Topology
SEMITOP rectifier module						
SK70B12SCTE1 ¹⁾	1200	54	-	E1	-	

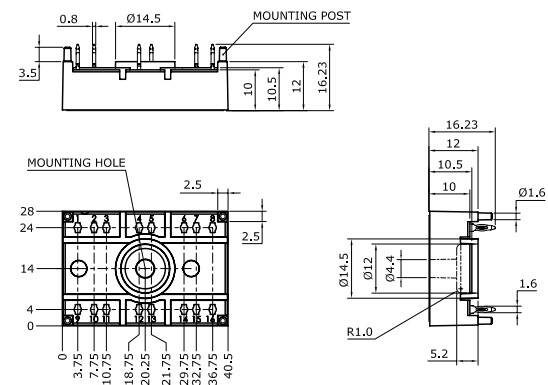
Footnotes: 1) Sample status / 2) In production new

SiC Modules / Full SiC / SEMITOP

Packages

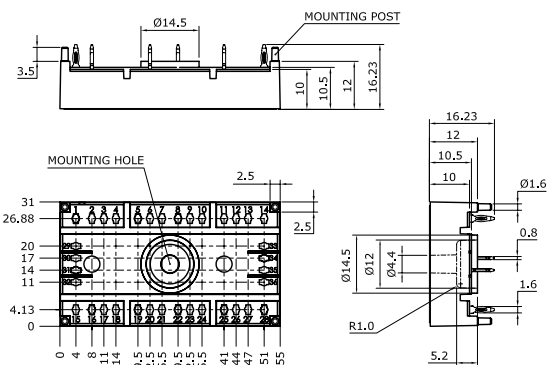
SEMITOP 2 Press-Fit

Dimensions: mm
Tolerance system: ISO 2768-m

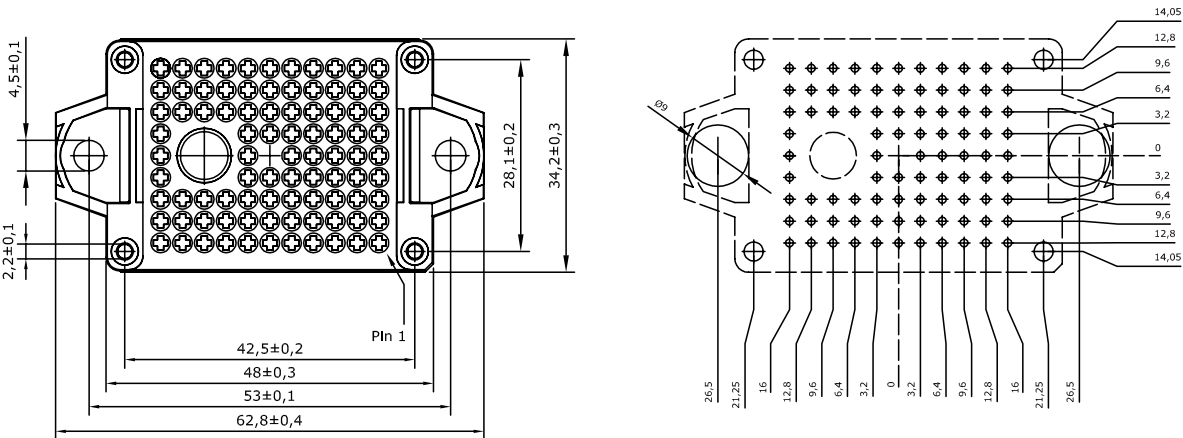


SEMITOP 3 Press-Fit

Dimensions: mm
Tolerance system: ISO 2768-m



SEMITOP E1

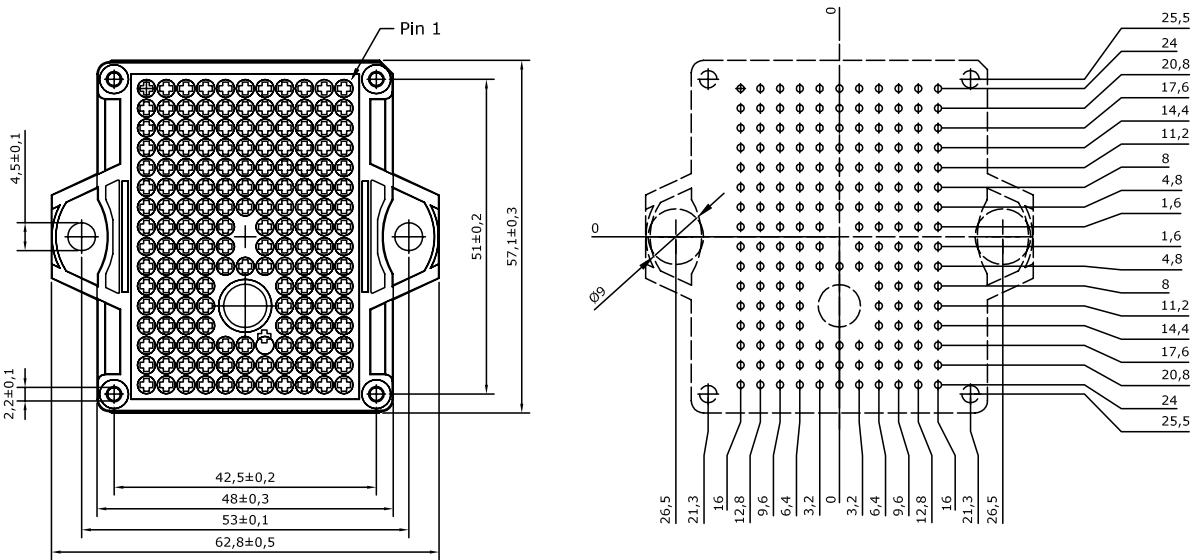


Dimensions in mm

SiC Modules / Full SiC / SEMITOP

Packages

SEMITOP E2



Dimensions in mm

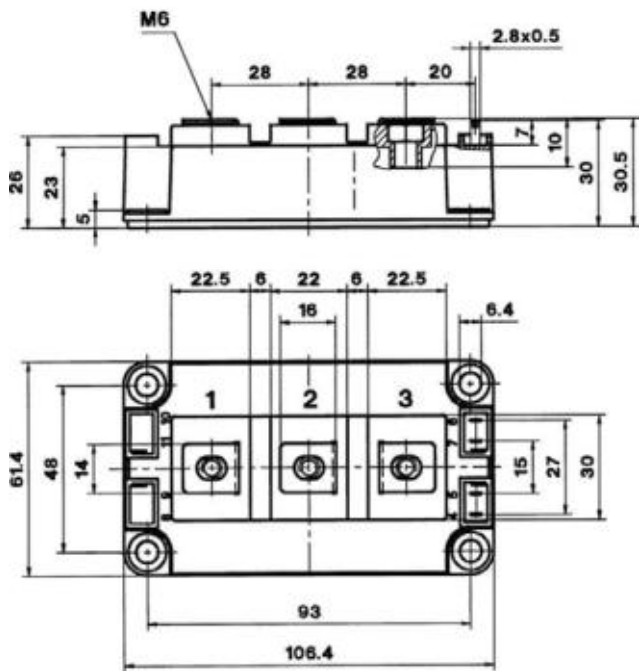
SiC Modules / Full SiC / SEMITRANS

Type	V_{DS} V	I_D @ $T_c = 25^{\circ}\text{C}$ A	$R_{DS(on)}$ @ $T_j = 25^{\circ}\text{C typ.}$ mΩ	Package	Thermal Interface Material	Topology
1200V - SiC MOSFET						
SKM350MB120SCH15 ¹⁾	1200	523	5.6	3	P8	
SKM500MB120SC ¹⁾	1200	541	3.8	3	P8	
SKM350MB120SCH17 ¹⁾	1200	523	5.6	3	P8	
1200V - SiC Rectifier						
SKM125KD12SC ¹⁾	1200	236	-	3	P8	

Footnotes: 1) Sample status

Packages

SEMISTRANS 3



Dimensions in mm

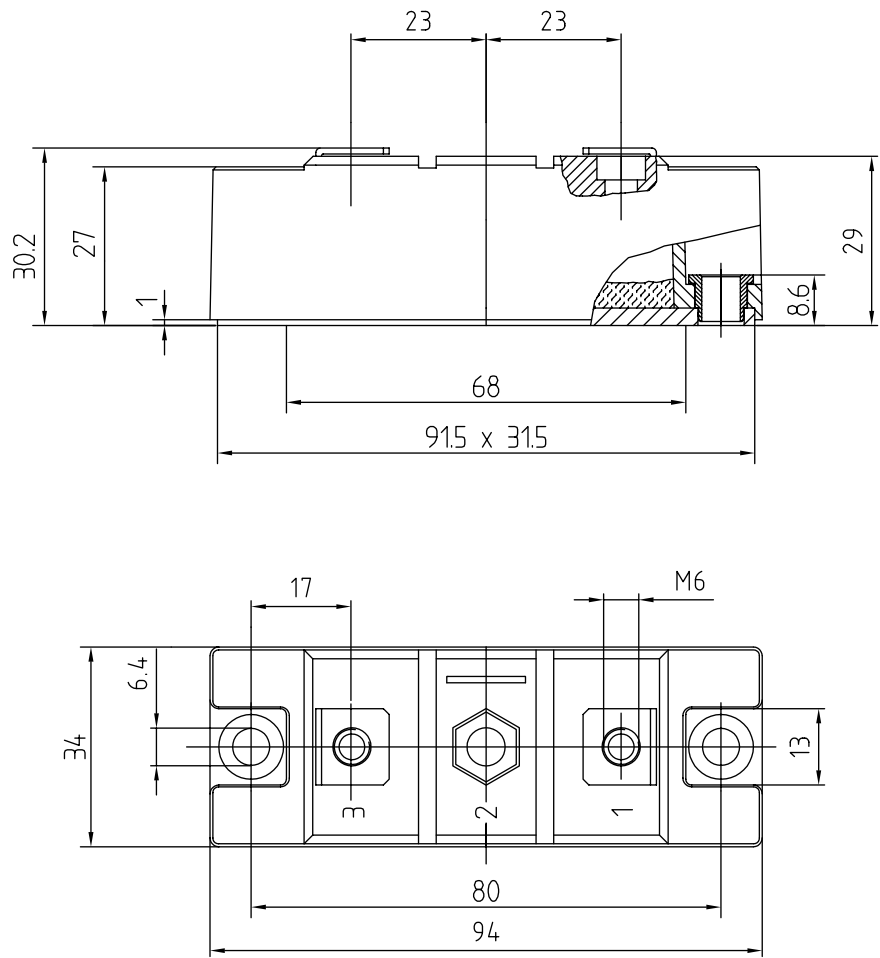
SiC Modules / Full SiC / SEMIPACK

Type	V_{RRM} V	I_{FAV} @ T_c A	T_c °C	V_{FO} @ $T_j = 150^{\circ}\text{C max.}$ V	r_F @ $T_j = 150^{\circ}\text{C max.}$ mΩ	T_j °C	Package	Thermal Interface Material	Topology
SKKE60S12 ¹⁾	1200	64	85	0.90	15	-40 ... +175	2	-	
SKKE300S12 ¹⁾	1200	400	85	0.90	3.0	-40 ... +175	2	-	

Footnotes: 1) Sample status

Packages

SEMIPACK 2



Dimensions in mm

Hybrid Silicon Carbide Modules

For Maximum Energy Efficiency

SEMIKRON offers hybrid silicon carbide power modules in MiniSKiiP, SEMITOP, SEMITRANS, SEMiX 3 Press-Fit and SKiM63/93. The latest IGBT technology is combined with SiC Schottky diodes from leading suppliers to increase the switching frequency and reduce power losses at the same time.

The hybrid silicon carbide power modules are available from 50A to 600A in 1200V in sixpack, half-bridge and chopper topologies.

SiC Schottky free-wheeling diodes have virtually no switching losses and reduce the turn-on losses of the IGBT drastically. With these effects, higher switching frequencies can be achieved in the same module package, which efficiently lowers the filter needs on the output side, for example, of solar inverters, UPS systems or high frequency power supplies. Higher output powers than with standard silicon power modules can also be achieved.

Hybrid SiC	
MiniSKiiP	90
SEMITOP	92
SEMiX Press-Fit	95
SEMITRANS	96
SKiM 63/93	97

For detailed information please refer to data sheets.

Further information
<http://www.semikron.com/hybrid-sic>

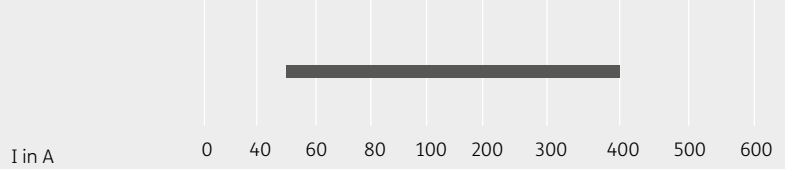
Hybrid SiC

MiniSKiiP®

Half-Bridge
Sixpack
3-level



1200V



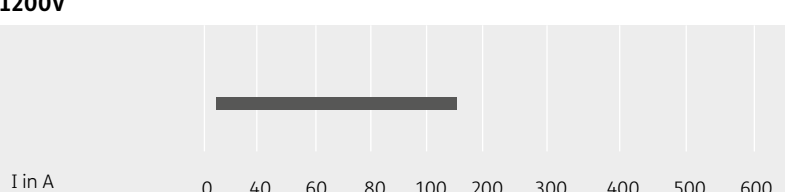
I in A

SEMITOP®

Chopper
3-level



1200V



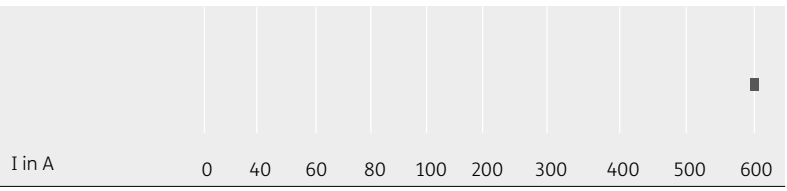
I in A

SEMiX Press-Fit®

Half-Bridge



1200V



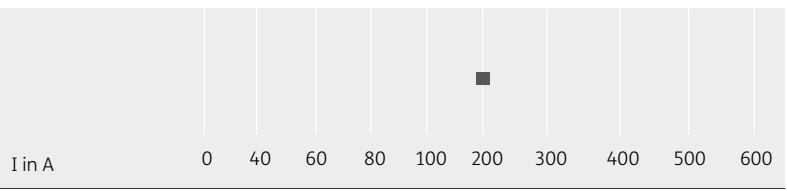
I in A

SEMITRANS®

Half-Bridge



1200V



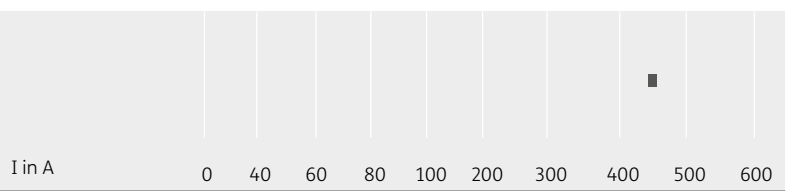
I in A

SKiM® 63/93

Sixpack



1200V



I in A

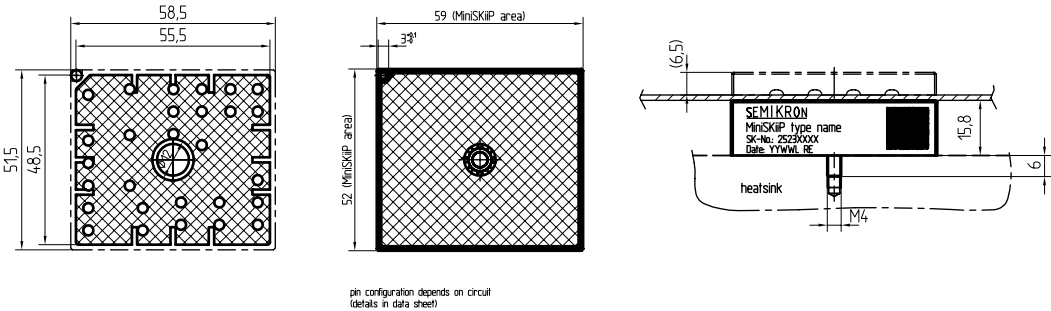
SiC Modules / Hybrid SiC / MiniSKiiP

Type	IGBT					Diode		Module		Thermal Interface Material	Topology
	$I_c @ T_s = 25^{\circ}C$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}C$ typ.	E_{on}	E_{off}	$I_f @ T_s = 25^{\circ}C$	V_f	Package			
	A	A	V	mJ	mJ	A	V				
1200V - IGBT4 (Fast Trench)											
SKiiP 38GB12F4V19 ¹⁾	303	300	2.05	10	22	133	1.40	II 3	P12, HPTP		
SKiiP25AC12F4V19 ¹⁾	61	50	2.05	0.6	3.1	45	1.40	II 2	P12, HPTP		
SKiiP38AC12F4V19 ¹⁾	102	100	2.05	6.4	6.3	64	1.36	II 3	P12, HPTP		
SKiiP39AC12F4V19 ¹⁾	144	150	2.05	9.6	9.4	118	1.40	II 3	P12, HPTP		
SKiiP39MLIB12F4V22 ¹⁾	409	400	2.05	t.b.d.	t.b.d.	193	2.20	II 3	P12, HPTP		
SKiiP39MLIT12F4V22 ¹⁾	409	400	2.05	t.b.d.	t.b.d.	193	2.20	II 3	P12, HPTP		

Footnotes: 1) Sample status

Packages

MiniSKiiP II 2

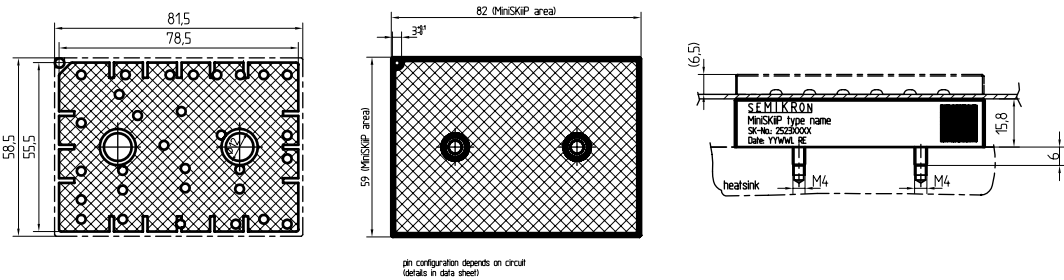


Dimensions in mm

SiC Modules / Hybrid SiC / MiniSKiiP

Packages

MiniSKiiP II 3



Dimensions in mm

SiC Modules / Hybrid SiC / SEMITOP

Type	IGBT					Diode		Module		
	I_c @ $T_s = 25^{\circ}\text{C}$ A	I_{cnom} A	$V_{CE(sat)}$ @ $T_j = 25^{\circ}\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	I_F @ $T_s = 25^{\circ}\text{C}$ A	V_F V	Package	Thermal Interface Material	Topology
1200V - IGBT4 Fast (Trench)										
SK 25 GAR 12F4 TSC ¹⁾	33	25	2.05	2.27	2.7	21	1.40	2	P12	
SK 50 GLLE 12F4 TSC ¹⁾	56	50	2.05	4.5	5.4	67	1.00	2	P12	
SK150MLIT12F4TSCE2 ¹⁾	149	150	2.05	8.9	11	80	2.20	E2	HPTP, HT	
SK150MLIB12F4TSCE2 ¹⁾	149	150	2.05	8.9	11	80	2.20	E2	HPTP, HT	
600V - CoolMOS										
SK35MLT60SCKE1 ¹⁾	-	45	-	t.b.d.	t.b.d.	-	1.35	E1	-	

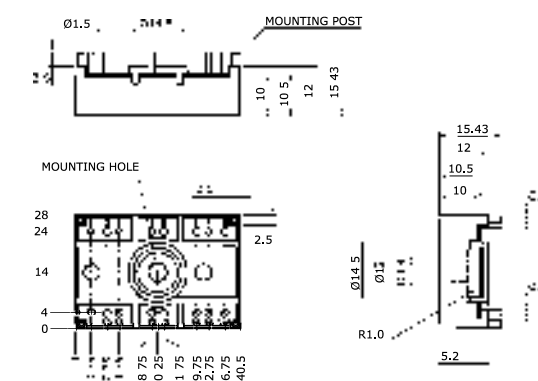
Footnotes: 1) Sample status

SiC Modules / Hybrid SiC / SEMITOP

Packages

SEMITOP 2

Dimensions: mm
Tolerance system: ISO 2768-m

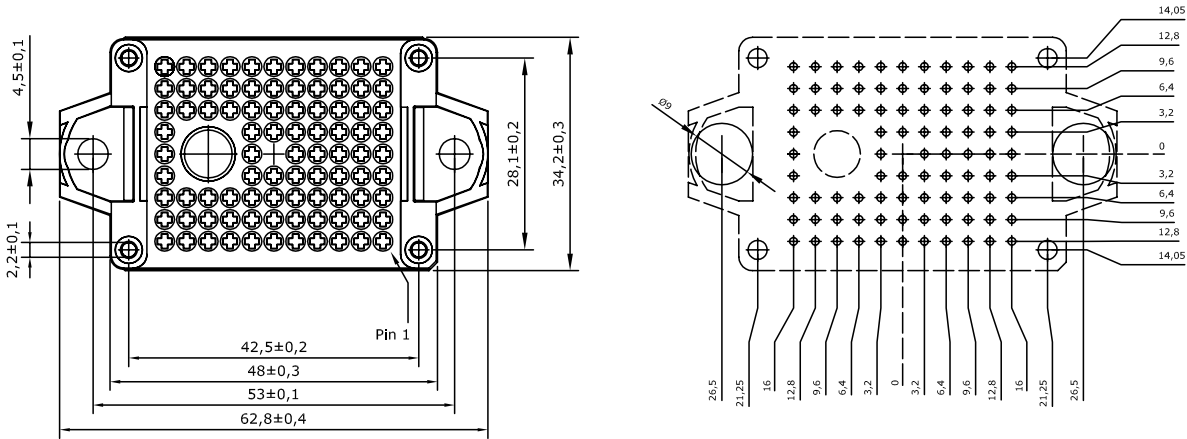


Dimensions in mm

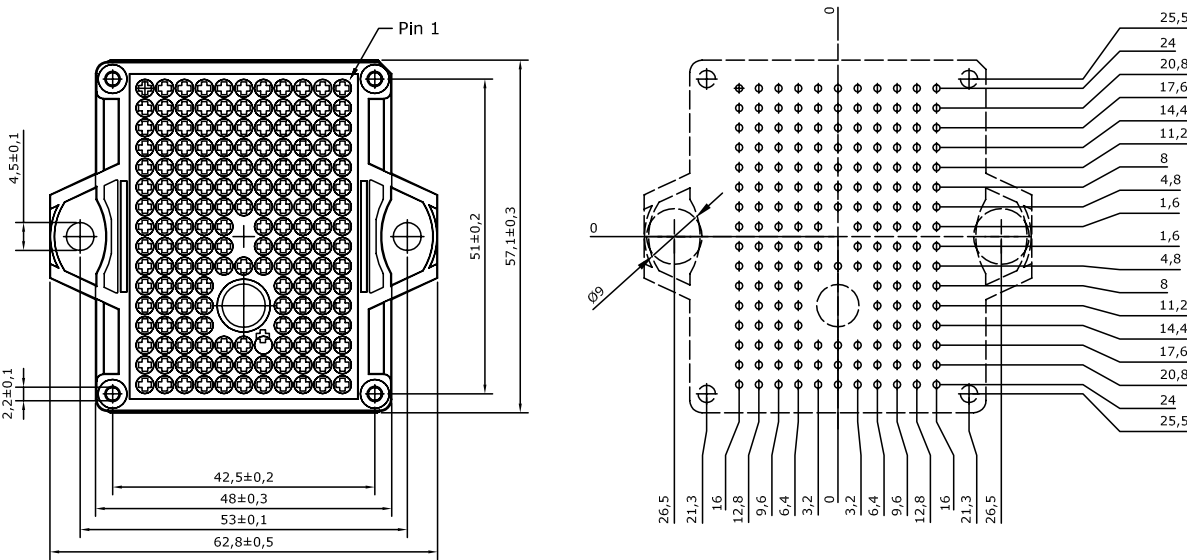
SiC Modules / Hybrid SiC / SEMITOP

Packages

SEMISTOP E1



SEMISTOP E2



Dimensions in mm

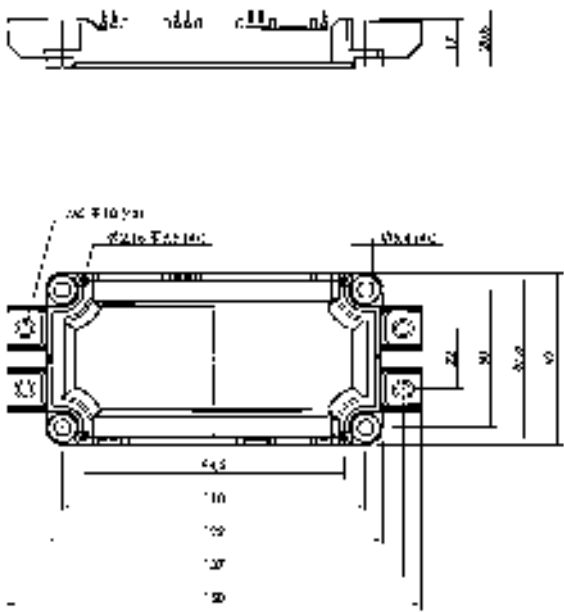
SiC Modules / Hybrid SiC / SEMIX

Type	IGBT		Diode		Module	
	$I_c @ T_c = 25^\circ\text{C}$ A	I_{cnom} A	$V_{CE(sat)} @ T_j = 25^\circ\text{C typ.}$ V	E_{on} mJ	E_{off} mJ	$I_f @ T_c = 25^\circ\text{C}$ A
						V_f V
						Package
						Thermal Interface Material
						Topology
1200V - IGBT4 (Trench)						
SEMIx603GB12E4SiCp ¹⁾	1110	600	1.80	17	72	404
						1.40
						3p
						P8, HT

Footnotes: 1) Sample status

Packages

SEMIx 3p



Dimensions in mm

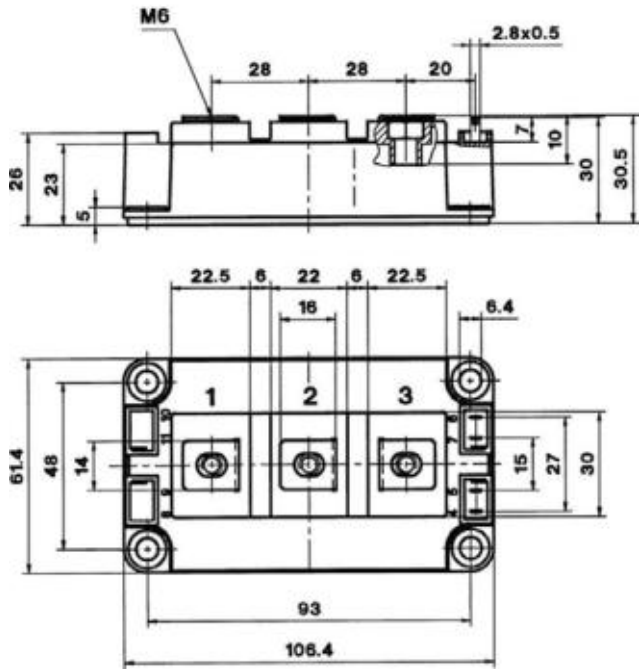
SiC Modules / Hybrid SiC / SEMITRANS

Type	IGBT					Diode		Module		
	$I_c @ T_c = 25^{\circ}\text{C}$	I_{cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_F @ T_c = 25^{\circ}\text{C}$	V_F	Package	Thermal Interface Material	Topology
1200V - IGBT4 (Trench)										
SKM200GB12T4SiC2 ¹⁾	313	200	1.80	7	20	246	1.40	3	P8	
1200V - IGBT4 (Fast Trench)										
SKM200GB12F4SiC2 ¹⁾	279	200	2.06	7	17	246	1.40	3	P8	
SKM200GB12F4SiC3 ¹⁾	279	200	2.06	7	17	123	1.40	3	P8	
Footnotes: 1) Sample status										
Packages										

Footnotes: 1) Sample status

Packages

SEMITRANS 3



Dimensions in mm

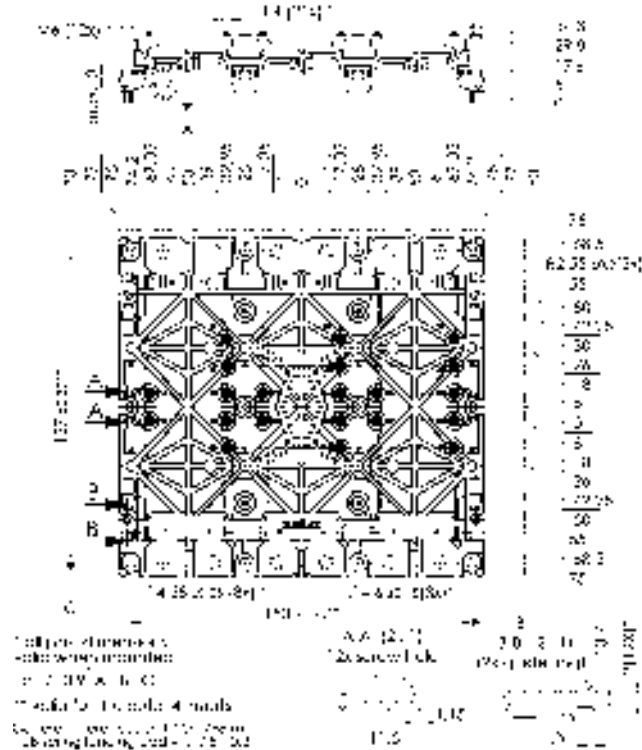
SiC Modules / Hybrid SiC / SKiM 63/93

Type	IGBT					Diode		Module		
	$I_c @ T_s = 25^{\circ}\text{C}$	I_{Cnom}	$V_{CE(sat)} @ T_j = 25^{\circ}\text{C typ.}$	E_{on}	E_{off}	$I_f @ T_s = 25^{\circ}\text{C}$	V_f	Package	Thermal Interface Material	Topology
	A	A	V	mJ	mJ	A	V			
1200V - IGBT4 (Fast Trench)										
SKiM459GD12F4V3 ¹⁾	476	450	2.05	2	11	214	1.33	93	P12, HPTP	
SKiM459GD12F4V4 ¹⁾	476	450	2.05	5	20	357	1.33	93	P12, HPTP	

Footnotes: 1) Sample status

Packages

SKiM 93



Dimensions in mm

MOSFET Modules

Best in Class Switching Performance

SEMIKRON produces MOSFET (Metal Oxide Semiconductor Field Effect Transistor) modules in single switch, half-bridge, H-bridge and sixpack configuration in SEMITOP and SEMITRANS packages.

The available MOSFET modules in the voltage range from 55V up to 600V and current ratings of 40A up to 290A are designed for high-speed switching applications, in particular, and boast low switching losses.

SEMITOP	100
SEMITRANS	102

For detailed information please refer to data sheets.

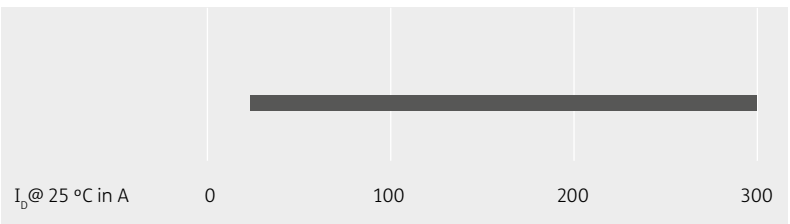
Further information: <http://www.semikron.com/mosfet-modules>

SEMITOP®

Sixpack
H-Bridge
Half-Bridge



60V up to 100V

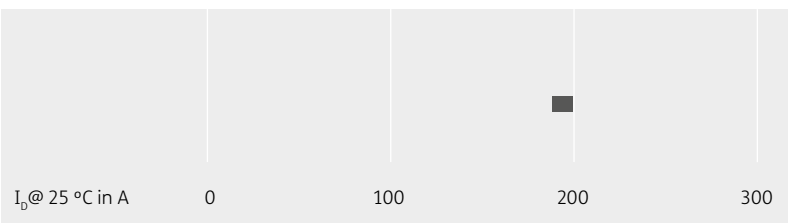


SEMITRANS®

Single Switch



100V up to 200V



MOSFET Modules / SEMITOP

Type						
	V_{DS} V	I_D @ $T_C = 25^{\circ}C$ A	$R_{DS(on)}$ @ $T_J = 25^{\circ}C$ typ. mΩ	Package	Thermal Interface Material	Topology
80V						
SK300MB080 ¹⁾	80	317	0.90	3	P12, HPTP	
100V						
SK 85 MH 10 T ³⁾	100	80	-	2	P12	
SK280MB10 ¹⁾	100	278	1.15	3	P12, HPTP	
600V						
SK35MLT60SCKE1 ¹⁾	600	45	37	E1	-	
SK50MH65TE1 ¹⁾	650	55	9.8	E1	-	

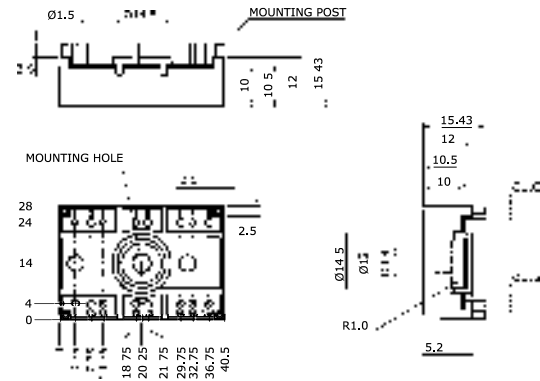
Footnotes: 1) Sample status / 3) Not for new designs

MOSFET Modules / SEMITOP

Packages

SEMITOP 2

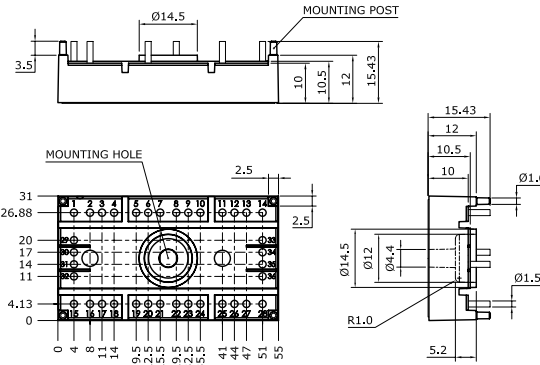
Dimensions: mm
Tolerance system: ISO 2768-m



Dimensions in mm

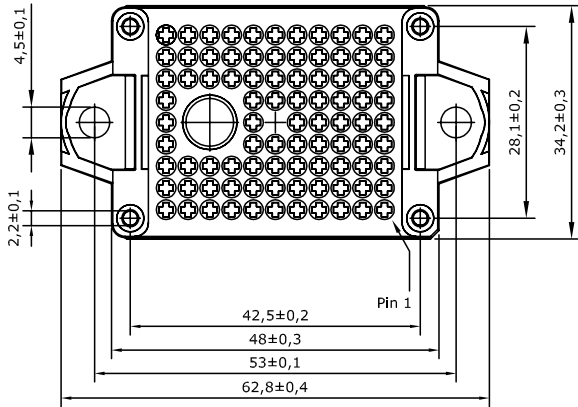
SEMITOP 3

Dimensions: mm
Tolerance system: ISO 2768-m

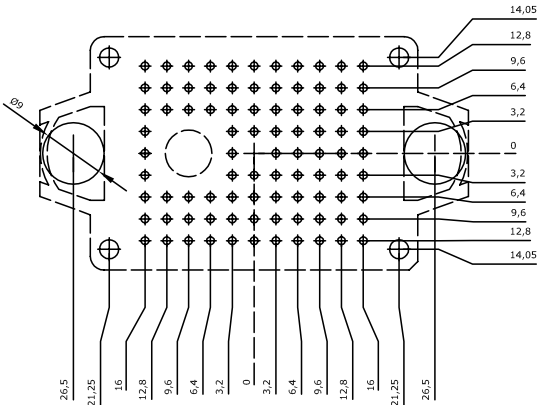


Packages

SEMITOP E1



Dimensions in mm

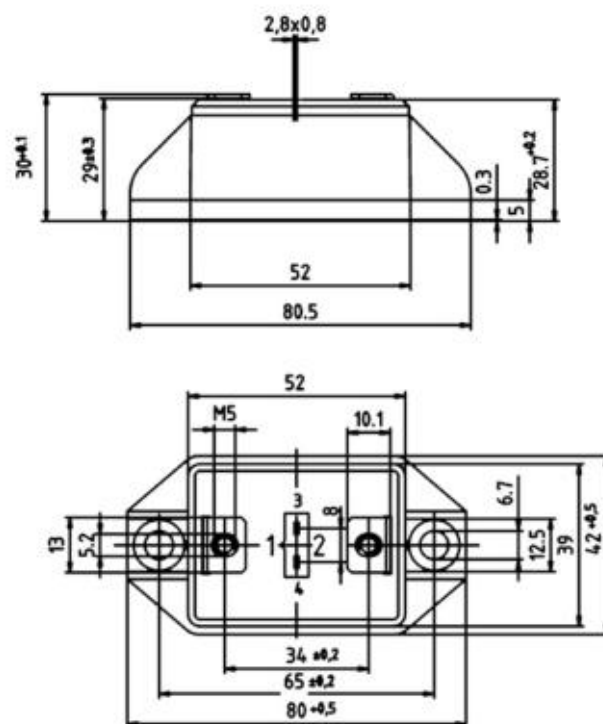


MOSFET Modules / SEMITRANS

Type							
	V_{DS} V	I_D @ $T_C = 25^{\circ}C$ A	$R_{DS(on)}$ @ $T_J = 25^{\circ}C$ typ. mΩ	Package	Thermal Interface Material	Topology	
100V							
SKM 111 AR	100	200	7	M1	-		
SKM 111 RZR	100	200	7	M1	-		
200V							
SKM 180 A020	200	180	9	M1	-		

Packages

SEMITRANS M1



Dimensions in mm

Thyristor / Diode Modules With Proven Packages

The SEMIKRON thyristor/diode modules are available in different packages such as SEMIPACK, SEMiSTART, SEMIPONT, SEMiX and SEMITOP. Different contact technologies – soldered contact, bonded contact or pressure contact modules – are available.

The thyristor/diode modules come in a variety of dual and single topologies for virtually any phase control or rectifier application.

The product class offers a product range with voltages of up to 2200V. Thanks to the comprehensive product range, the optimum solution can be found for each application.

SEMITOP	106
SEMIX	108
SEMIPONT	110
SEMIPACK	111
SEMIPACK Fast	115
SEMiSTART	117

For detailed information please refer to data sheets.

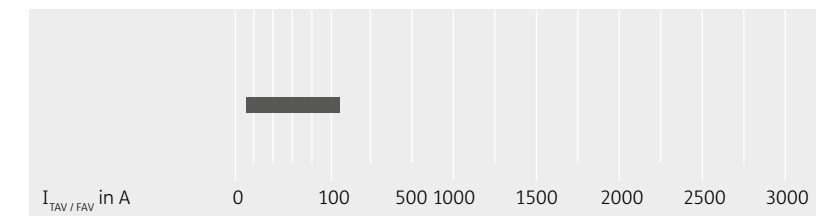
Further information: www.semikron.com/thyristor-diode-modules

SEMITOP®

Rectifier
Thyristor



800V up to 1600V

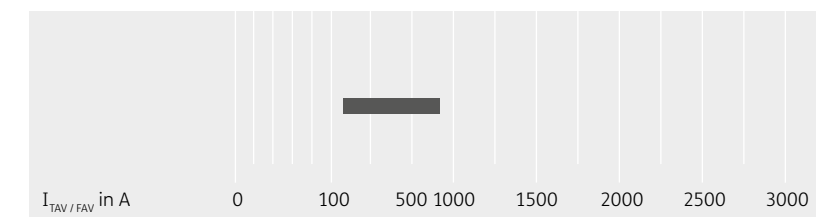


SEMIX®

Rectifier
Thyristor



1600V up to 2200V

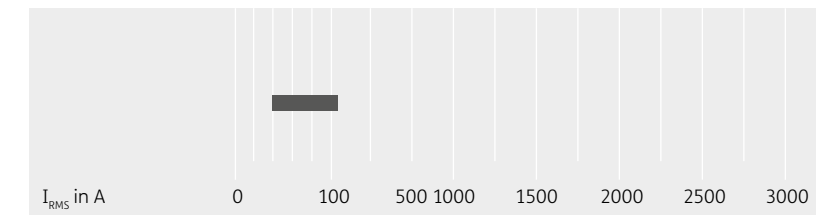


SEMIPONT®

Rectifier
Thyristor



800V up to 2200V

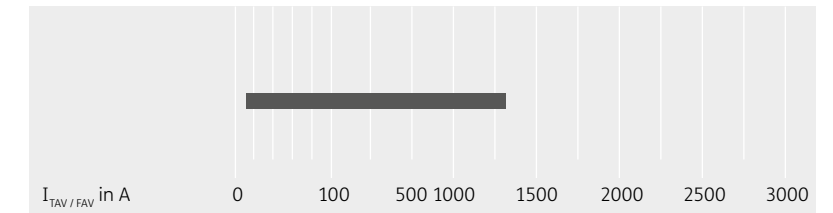


SEMIPACK®

Rectifier
Thyristor



400V up to 2200V

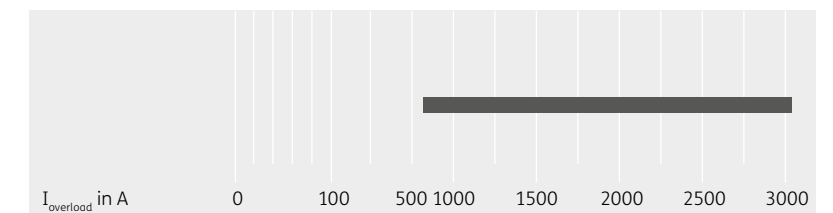


SEMiSTART®

Thyristor



1400V up to 1800V



Thyristor / Diode Modules / SEMITOP

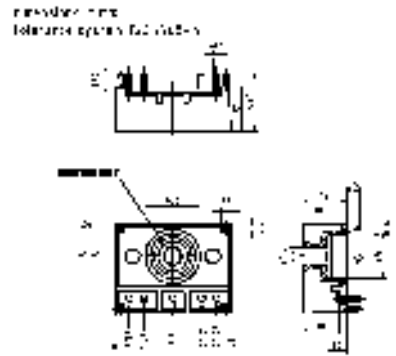
Type	V_{RRM} V_{DRM} V	I_{TAV} I_{FAV} @ T_S A	T_S °C	I_{TSM} I_{FSM} @ T_{jmax} A	$V_{T(TO)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	T_j °C	Package	Thermal Interface Material	Topology
SK 35 TAA ²⁾	800-1600	35	80	380	0.85	9.10	-40 ... +130	2	P12	
SK 55 TAA	800-1600	55	80	900	0.85	5.70	-40 ... +130	2	P12	
SK 75 TAA ²⁾	800-1600	75	80	1500	0.90	4.50	-40 ... +130	2	P12	
SK 100 TAA ²⁾	800-1600	100	80	2000	0.90	3.50	-40 ... +130	2	P12	
SK 75 TAE 12	1200	75	80	1250	0.85	4.40	-40 ... +130	2	P12	
SK 25 KQ	800-1600	29	85	280	1.10	20.00	-40 ... +125	1	-	
SK 45 KQ	800-1600	47	85	380	1.00	10.00	-40 ... +125	1	-	
SK 70 KQ	800-1600	72	85	900	1	6.00	-40 ... +125	1	-	
SK 100 KQ	800-1600	101	85	1350	0.90	4.50	-40 ... +125	2	P12	
SK 120 KQ	800-1600	134	85	1800	0.90	3.50	-40 ... +125	2	P12	
SK 25 WT	800-1600	29	85	280	1.10	20.00	-40 ... +125	2	P12	
SK 45 WT	800-1600	47	85	380	1.00	10.00	-40 ... +125	2	P12	
SK 70 WT	800-1600	72	85	900	1.00	6.00	-40 ... +125	3	P12, HPTP	
SK 100 WT	800-1600	101	85	1350	0.90	4.50	-40 ... +125	3	P12, HPTP	
SK 35 BZ ²⁾	800-1600	35	80	270	0.85	14.00	-40 ... +125	2	P12	
SK 45 STA	800-1600	47	75	380	1.00	10.00	-40 ... +125	3	P12, HPTP	
SK 25 UT	800-1600	29	85	280	1.10	20.00	-40 ... +125	3	P12, HPTP	
SK 45 UT	800-1600	47	85	380	1.00	10.00	-40 ... +125	3	P12, HPTP	
SK 30 DTA	800-1600	25	80	900	1.00	6.00	-40 ... +150	3	P12, HPTP	
SK 60 DTA	800-1600	61	80	1350	0.90	0.60	-40 ... +125	3	P12, HPTP	
SK 80 DTA	800-1600	65	80	1800	0.90	3.50	-40 ... +150	3	P12, HPTP	

Footnotes: 2) In production new

Thyristor / Diode Modules / SEMITOP

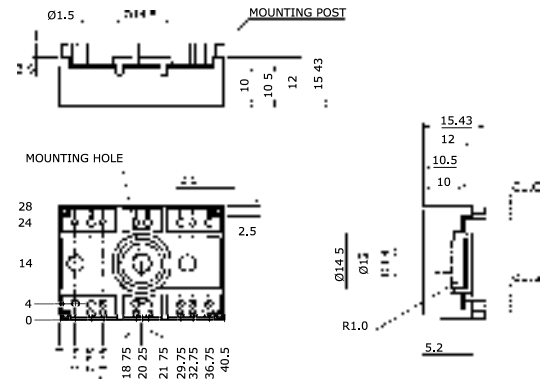
Packages

SEMISTOP 1



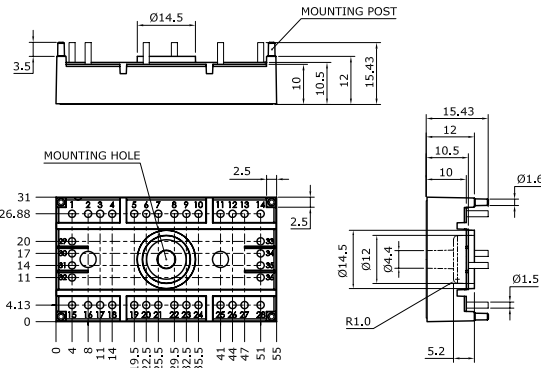
SEMISTOP 2

Dimensions: mm
Tolerance system: ISO 2768-m



SEMISTOP 3

Dimensions: mm
Tolerance system: ISO 2768-m



Dimensions in mm

Thyristor / Diode Modules / SEMiX

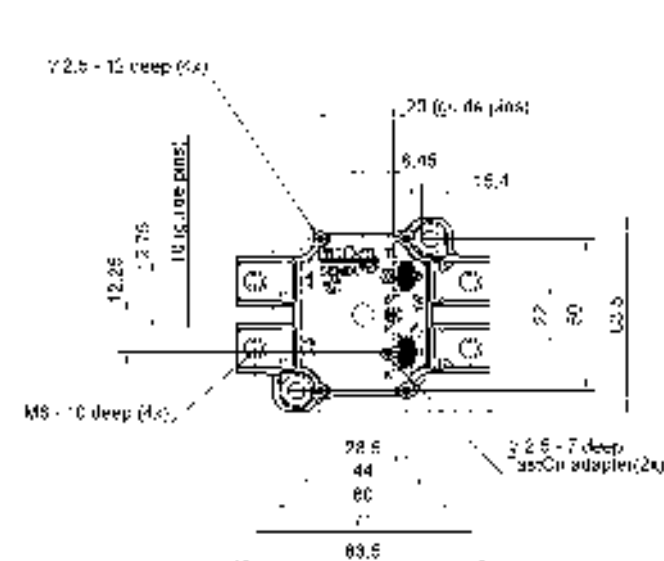
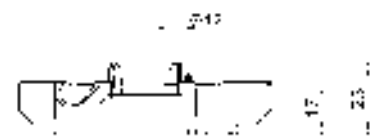
Type

	V_{RRM} V	V_{FWM} V	I_{TAV} A	I_{FAV} A	T_C °C	I_{FSM} A	I_{FSM} A	T_{jmax} °C	$V_{T(TO)}$ V	r_T mΩ	T_j °C	Package	Thermal Interface Material	Topology
SEMiX191KD16s	1600		190		85	5000		0.85	0.95		-40 ... +130	1s	HT	
SEMiX302KD16s	1600		300		85	7500		0.85	1.1		-40 ... +130	2s	P8	
SEMiX443KD16p ¹⁾	1600		585		85	8200		0.916	2.0		-40 ... +175	3Ip	P8, HT	
SEMiX603KD16p ²⁾	1600		732		85	9000		0.916	1.9		-40 ... +175	3Ip	P8, HT	
SEMiX443KD22p ²⁾	2200		580		85	8200		0.834	2.0		-40 ... +150	3Ip	P8, HT	
SEMiX171KH16s	1600		170		85	4800		0.85	1.5		-40 ... +130	1s	HT	
SEMiX302KH16s	1600		300		85	8000		0.85	1.1		-40 ... +130	2s	P8	
SEMiX141KT16s	1600		140		85	3000		0.85	2.1		-40 ... +130	1s	HT	
SEMiX302KT16s	1600		300		85	8000		0.85	1.7		-40 ... +130	2s	P8	

Footnotes: 1) Sample status / 2) In production new

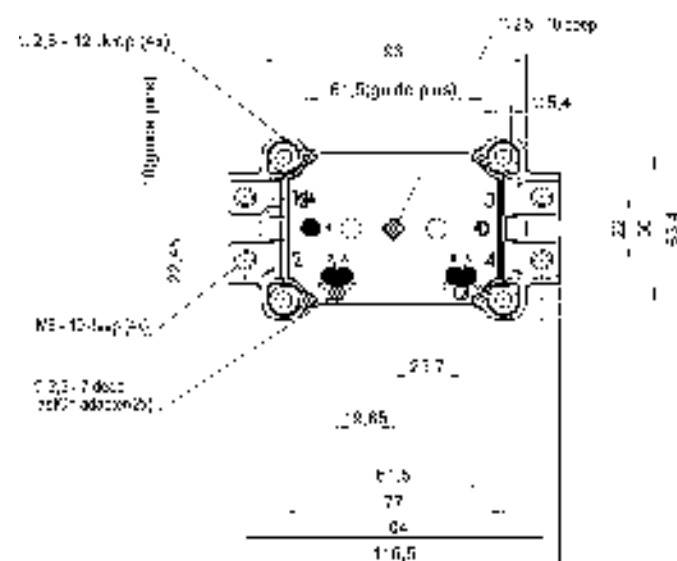
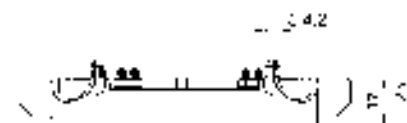
Packages

SEMIX 1s



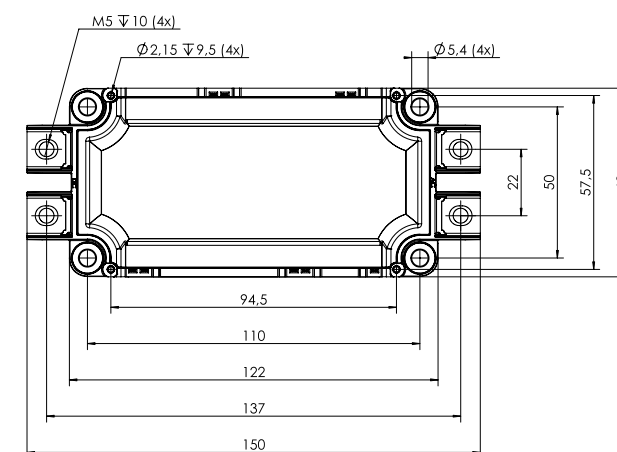
Dimensions in mm

SEMIX 2s



Packages

SEMIX 3Ip



Dimensions in mm

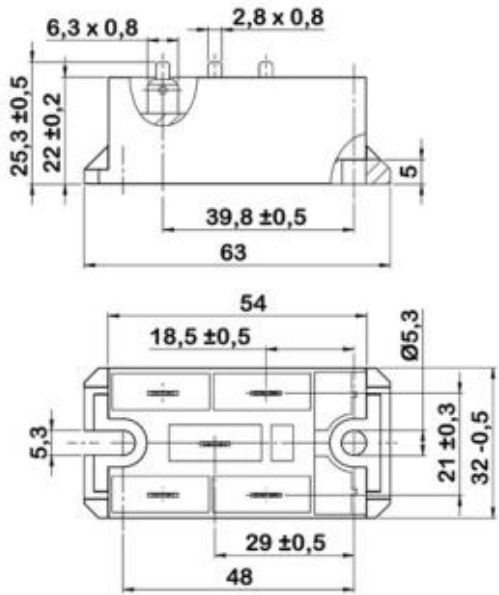
Thyristor / Diode Modules / SEMIPONT

Type	V_{RRM} V	I_{AV} I_{AV} @ T_S A	T_S °C	I_{FSM} I_{FSM} @ T_{jmax} A	$V_{T(TO)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	T_j °C	Package	Thermal Interface Material	Topology
SKUT 85/12 T V2 ²⁾	1200	94	85	1050	1.10	6.0	-40 ... +125	5	-	
SKWT 40 ¹⁾	800-2200	40	85	580	0.9	6.0	-40 ... +125	1	-	
SKUT 85/16 T V2 ²⁾	1600	94	85	1050	1.10	6.0	-40 ... +125	5	-	
SKUT 115/12T V2 ²⁾	1200	127	85	1250	0.90	5	-40 ... +125	5	-	
SKUT 115/16T V2 ²⁾	1600	127	85	1250	0.90	5	-40 ... +125	5	-	
SKUT 85/12 V2 ²⁾	1200	85	85	1050	1.1	6.0	-40 ... +125	5	-	
SKUT 85/16 V2 ²⁾	1600	85	85	1050	1.1	6.0	-40 ... +125	5	-	
SKUT 115/12 V2 ²⁾	1200	105	85	1250	0.9	5.0	-40 ... +125	5	-	
SKUT 115/16 V2 ²⁾	1600	105	85	1250	0.9	5.0	-40 ... +125	5	-	

Footnotes: 1) Sample status / 2) In production new

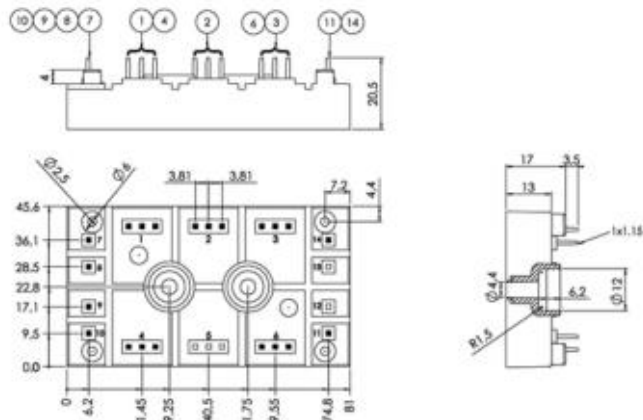
Packages

SEMIPONT 1



Dimensions in mm

SEMIPONT 5



Thyristor / Diode Modules / SEMIPACK

Type	V_{RRM} V	I_{AV} I_{AV} @ T_c A	T_c °C	I_{FSM} I_{FSM} @ T_{jmax} A	$V_{T(TO)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	T_j °C	Package	Thermal Interface Material	Topology
SKET 330	800-2200	295	85	8000	1.20	0.55	-40 ... +130	4	-	
SKET 400	800-1800	392	85	12000	0.92	0.3	-40 ... +130	4	-	
SKET 741/22 E	2200	819	85	26500	0.82	0.17	-40 ... +125	6	-	
SKET 801/18 E	1800	819	85	30000	0.82	0.17	-40 ... +125	6	-	
SKKE 15	600-1600	14	85	280	0.85	15	-40 ... +125	0	-	
SKKE 81	800-1600	82	85	1750	0.85	1.8	-40 ... +125	1	-	
SKKE 162	800-2200	195	85	5000	0.85	1.2	-40 ... +135	2	HT	
SKKE 212/16 H2	1600	213	85	5500	0.75	1.05	-40 ... +135	2	HT	
SKKE 380	1200-1600	380	100	10000	0.80	0.35	-40 ... +150	3	-	
SKKE 600	1200-2200	600	100	18000	0.75	0.25	-40 ... +150	4	-	
SKKE 1201/22	2200	1360	85	35000	0.75	0.073	-40 ... +125	6	-	
SKKL 92	800-1800	95	85	1750	0.90	2	-40 ... +125	1	-	
SKMT 92	800-1800	95	85	1750	0.90	2	-40 ... +125	1	-	
SKKD 15	600-1600	14	85	280	0.85	15	-40 ... +125	0	-	
SKKD 26	1200-1600	31	85	480	0.85	6	-40 ... +125	1	-	
SKKD 46	800-1800	47	85	600	0.85	5	-40 ... +125	1	-	
SKKD 81	800-1800	82	85	1750	0.85	1.8	-40 ... +125	1	-	
SKKD 81 H4	2000-2200	82	85	1750	0.85	1.8	-40 ... +125	1	-	
SKKD 100	400-1800	100	85	2000	0.85	1.3	-40 ... +125	1	-	
SKKD 101/16	1600	134	85	2000	0.87	2.45	-40 ... +130	1	-	
SKKD 152/16 H1	1600	171	85	4500	0.82	1.35	-40 ... +135	2	HT	
SKKD 162	800-2200	195	85	5000	0.85	1.2	-40 ... +135	2	HT	
SKKD 212	1200-1800	212	85	5500	0.75	1.05	-40 ... +135	2	HT	
SKKD 260	800-2200	260	85	10000	0.9	0.37	-40 ... +130	3	-	
SKKD 353	1200-1800	350	85	9500	0.84	0.75	-40 ... +130	3	-	
SKKD 380	800-2200	380	100	10000	0.80	0.35	-40 ... +150	3	-	
SKKD 701	1200-2200	701	100	22500	0.70	0.28	-40 ... +160	5	-	
SKKH 15	600-1600	13.5	85	280	1.10	20	-40 ... +125	0	-	
SKKH 27	800-1800	25	85	480	0.90	12	-40 ... +125	1	-	
SKKH 42	800-1800	40	85	850	1.00	4.5	-40 ... +125	1	-	
SKKH 57	800-1800	50	85	1250	0.90	3.5	-40 ... +125	1	-	
SKKH 57 H4	2000-2200	50	85	1250	0.90	3.5	-40 ... +125	1	-	
SKKH 58/16 E	1600	55	85	1200	1.00	4.8	-40 ... +130	1	-	
SKKH 72	800-1800	70	85	1450	0.90	3.5	-40 ... +125	1	-	
SKKH 72 H4	2000-2200	70	85	1450	0.90	3.5	-40 ... +125	1	-	
SKKH 92	800-1800	95	85	1750	0.90	2	-40 ... +125	1	-	
SKKH 106	800-1800	106	85	1900	0.90	2	-40 ... +130	1	-	
SKKH 107/16 E	1600	119	85	1900	0.90	3.35	-40 ... +130	1	-	
SKKH 122	800-1800	129	85	3200	0.85	2	-40 ... +125	2	HT	
SKKH 132	800-1800	137	85	4000	1.00	1.6	-40 ... +125	2	HT	
SKKH 132 H4	2000-2200	128	85	3800	1.10	2	-40 ... +125	2	HT	
SKKH 162	800-1800	156	85	5000	0.85	1.5	-40 ... +125	2	HT	
SKKH 162 H4	2000-2200	143	85	4800	0.95	2	-40 ... +125	2	HT	
SKKH 172/16 E	1600	175	85	5000	0.83	1.3	-40 ... +125	2	HT	

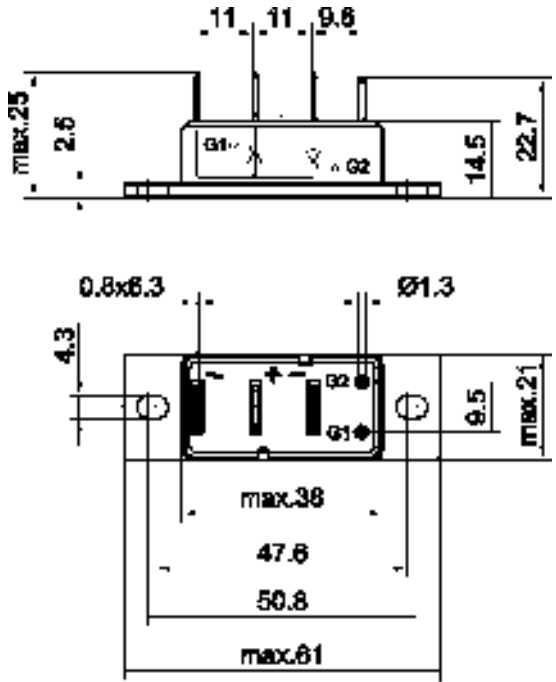
Thyristor / Diode Modules / SEMIPACK

Thyristor / Diode Modules / SEMIPACK

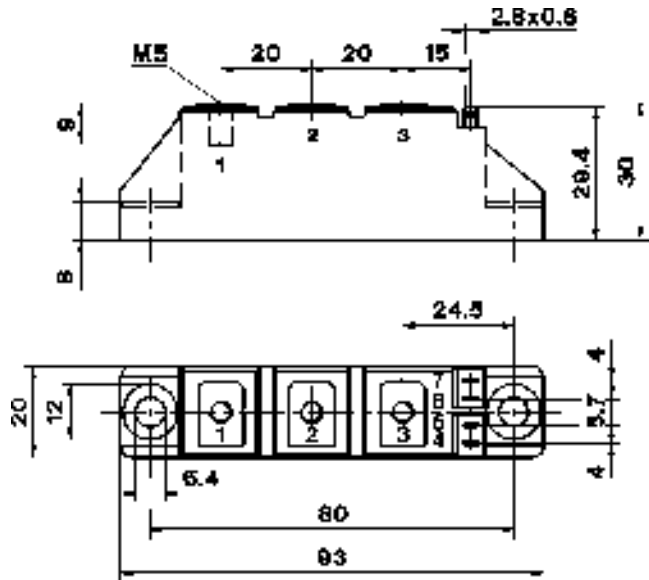
Type										
	V_{RRM} V_{DRM}	I_{FAV} $I_{FAV} @ T_c$	T_c	I_{FSM} $I_{FSM} @ T_{jmax}$	$V_{T(10)}$ $V_{T(10)} @ T_{jmax}$	r_T $r_T @ T_{jmax}$	T_j	Package	Thermal Interface Material	Topology
	V	A	°C	A	V	mΩ	°C			
SKKH 250	1200-1800	250	85	8000	0.93	0.45	-40 ... +130	3	-	
SKKH 273	1200-1800	273	85	8000	0.90	0.92	-40 ... +130	3	-	
SKKH 280 H4	2000-2200	252	85	7500	0.90	0.75	-40 ... +125	3	-	
SKKH 323	1200-1800	320	85	8200	0.81	0.85	-40 ... +130	3	-	
SKKH 330	800-1800	305	85	8000	0.80	0.6	-40 ... +130	3	-	
SKKH 460	1600-2200	460	85	15500	0.88	0.45	-40 ... +130	5	-	
SKKH 570	1600-1800	570	85	15500	0.78	0.32	-40 ... +135	5	-	
SKKT 15	600-1600	13.5	85	280	1.10	20	-40 ... +125	0	-	
SKKT 20	800-1600	18	85	280	1.00	16	-40 ... +125	1	-	
SKKT 20B	800-1600	18	85	280	1.00	16	-40 ... +125	1	-	
SKKT 27	800-1600	25	85	480	0.90	12	-40 ... +125	1	-	
SKKT 27B	800-1600	25	85	480	0.90	12	-40 ... +125	1	-	
SKKT 42	800-1800	40	85	850	1.00	4.5	-40 ... +125	1	-	
SKKT 42B	800-1800	40	85	850	1.00	4.5	-40 ... +125	1	-	
SKKT 57	800-1800	50	85	1250	0.90	3.5	-40 ... +125	1	-	
SKKT 57B	800-1800	50	85	1250	0.90	3.5	-40 ... +125	1	-	
SKKT 57 H4	2000-2200	50	85	1250	0.90	3.5	-40 ... +125	1	-	
SKKT 58/16 E	1600	55	85	1200	1.00	4.8	-40 ... +130	1	-	
SKKT 58B16 E	1600	55	85	1200	1.00	4.8	-40 ... +130	1	-	
SKKT 72	800-1800	70	85	1450	0.90	3.5	-40 ... +125	1	-	
SKKT 72B	800-1800	70	85	1450	0.90	3.5	-40 ... +125	1	-	
SKKT 72 H4	2000-2200	70	85	1450	0.90	3.5	-40 ... +125	1	-	
SKKT 92	800-1800	95	85	1750	0.90	2	-40 ... +125	1	-	
SKKT 92B	800-1800	95	85	1750	0.90	2	-40 ... +125	1	-	
SKKT 106	800-1800	106	85	1900	0.90	2	-40 ... +130	1	-	
SKKT 106B	800-1800	106	85	1900	0.90	2	-40 ... +130	1	-	
SKKT 107/16 E	1600	119	85	1900	0.90	3.35	-40 ... +130	1	-	
SKKT 107B16 E	1600	119	85	1900	0.90	3.35	-40 ... +130	1	-	
SKKT 122	800-1800	129	85	3200	0.85	2	-40 ... +125	2	HT	
SKKT 132	800-1800	137	85	4000	1.00	1.6	-40 ... +125	2	HT	
SKKT 132 H4	2000-2200	128	85	3800	1.10	2	-40 ... +125	2	HT	
SKKT 162	800-1800	156	85	5000	0.85	1.5	-40 ... +125	2	HT	
SKKT 162 H4	2000-2200	143	85	4800	0.95	2	-40 ... +125	2	HT	
SKKT 172	1400-1800	175	85	5000	0.83	1.3	-40 ... +125	2	HT	
SKKT 215/16 E	1600	215	85	5700	0.85	1.2	-40 ... +125	2	HT	
SKKT 215/18 E	1800	215	85	5700	0.85	1.2	-40 ... +125	2	HT	
SKKT 250	800-1800	250	85	8000	0.93	0.45	-40 ... +130	3	-	
SKKT 273	1200-1800	273	85	8000	0.90	0.92	-40 ... +130	3	-	
SKKT 280 H4	2000-2200	252	85	7500	0.90	0.75	-40 ... +125	3	-	
SKKT 323	1200-1800	320	85	8200	0.81	0.85	-40 ... +130	3	-	
SKKT 330	800-1800	305	85	8000	0.80	0.6	-40 ... +130	3	-	
SKKT 460/16 E	1600	460	85	15500	0.88	0.45	-40 ... +130	5	-	
SKKT 460/22 E H4	2200	460	85	15500	0.88	0.45	-40 ... +130	5	-	
SKKT 570	1200-1800	570	85	15500	0.78	0.32	-40 ... +135	5	-	

Packages

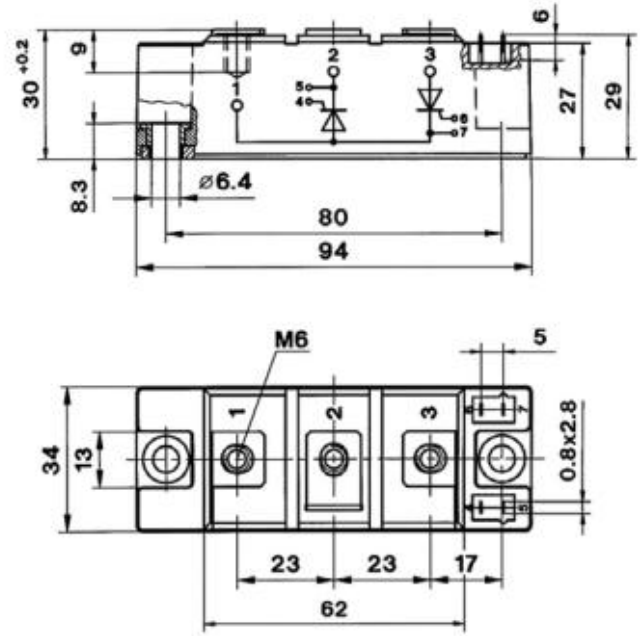
SEMIPACK 0



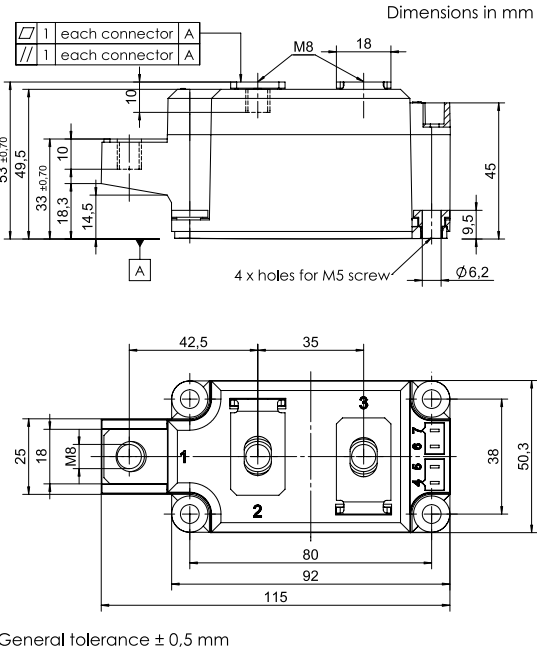
SEMIPACK 1



SEMIPACK 2



SEMIPACK 3



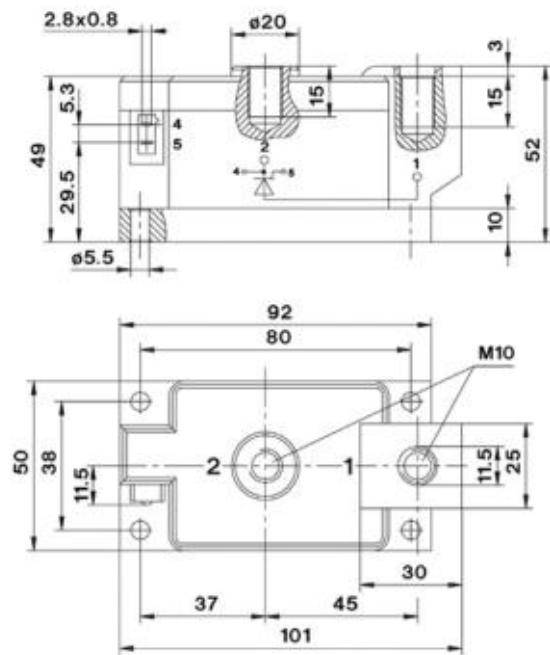
Dimensions in mm

General tolerance ± 0,5 mm

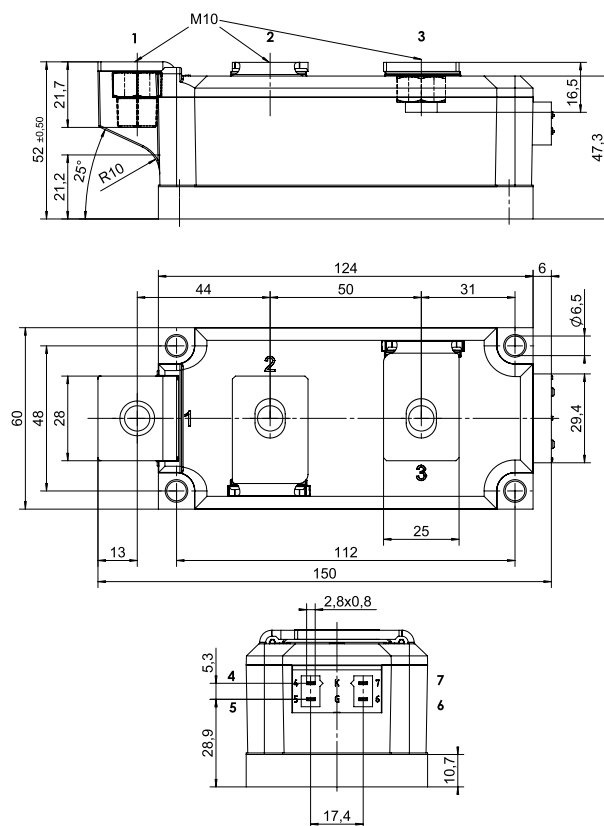
Thyristor / Diode Modules / SEMIPACK

Packages

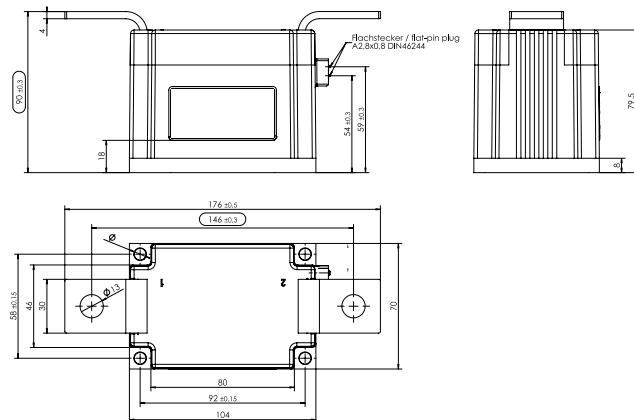
SEMIPACK 4



SEMIPACK 5



SEMIPACK 6



Dimensions in mm

Thyristor / Diode Modules / SEMIPACK FAST

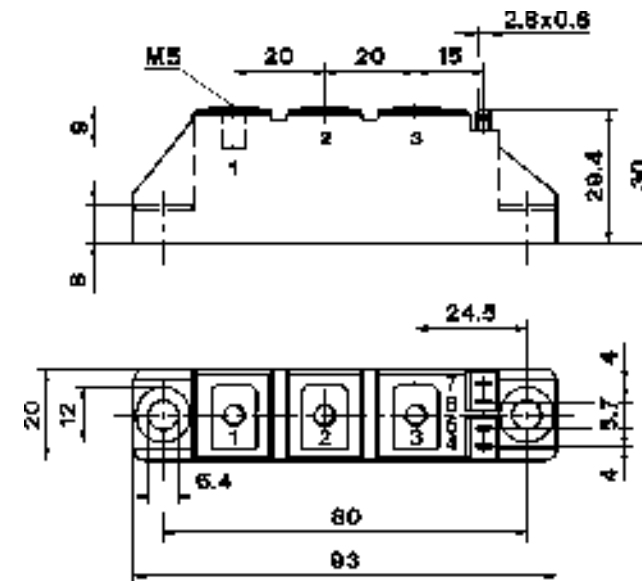
Type

	V_{RRM} V_{DRM}	I_{TAV} I_{FAV} @ T_c	T_c	I_{FSM} @ I_{Tmax}	$V_{T(TO)}$ @ T_{jmax}	r_f @ T_{jmax}	T_j	Package	Thermal Interface Material	Topology
SKKE 120F17	1700	120	82	1800	1.5	4.5	-40 ... +150	2	-	
SKKE 290F06	600	290	109	6000	0.9	1.2	-40 ... +150	2	-	
SKKE 301F12	1200	300	43	3600	1.2	2.75	-40 ... +150	2	-	
SKKE 310F12	1200	310	84	5500	1.2	1.9	-40 ... +150	2	-	
SKKE 330F17 ⁵⁾	1700	330	70	5200	1.5	1.9	-40 ... +150	4	-	
SKKE 600F12 ⁵⁾	1200	600	85	5800	1.2	1.9	-40 ... +150	4	-	
SKKD 40F	600-1000	40	80	940	1.2	4	-40 ... +125	1	-	
SKKD 42F	1200-1400	42	85	1100	1	5	-40 ... +130	1	-	
SKKD 60F	1700	60	83	900	1.5	9	-40 ... +150	2	-	
SKKD 75F12	1200	75	55	900	1.2	11	-40 ... +150	2	-	
SKKD 105F16	1600	105	83	2100	1.2	2.5	-40 ... +130	1	-	
SKKD 150F12	1200	150	54	1800	1.2	5.5	-40 ... +150	2	-	
SKKD 170F	1200	170	85	2300	1.2	3.5	-40 ... +150	2	-	
SKKD 205F06	600	205	87	3000	0.9	2	-40 ... +150	2	-	
SKMD 150F12	1200	150	54	1800	1.2	5.5	-40 ... +150	2	-	
SKND 150F12	1200	150	54	1800	1.2	5.5	-40 ... +150	2	-	
SKND 205F06	600	205	87	3000	0.9	2	-40 ... +150	2	-	

Footnotes: 5) SEMIPACK Fast in SEMITRANS 4 case

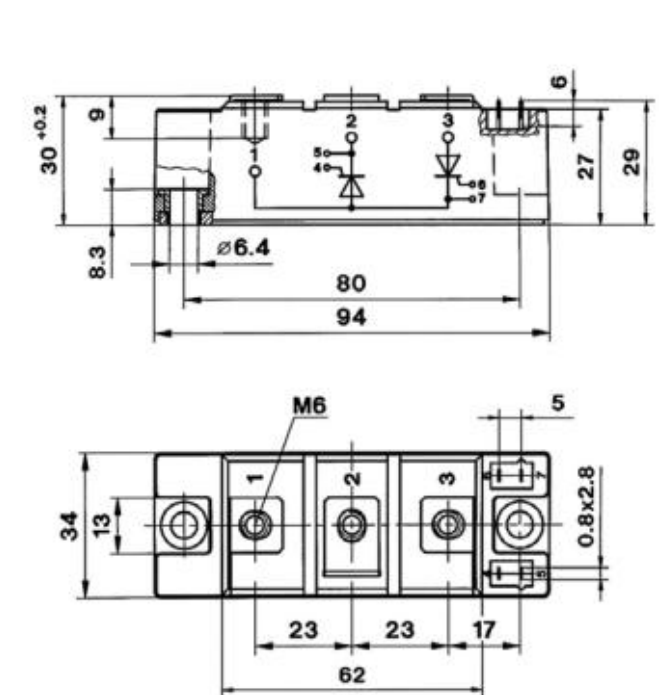
Packages

SEMIPACK 1



Dimensions in mm

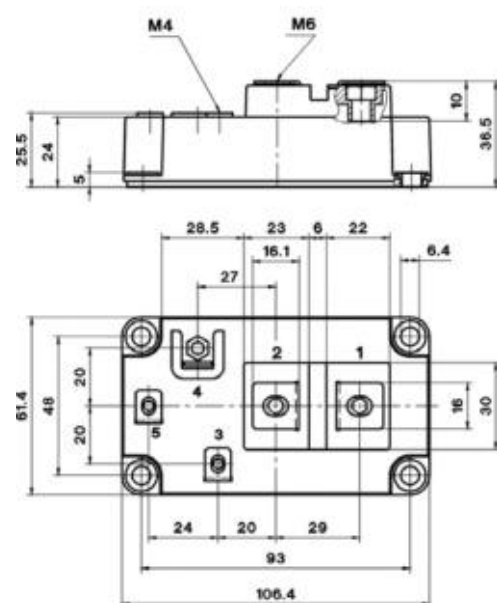
SEMIPACK 2



Thyristor / Diode Modules / SEMIPACK FAST

Packages

SEMIPACK Fast in SEMITRANS 4



Dimensions in mm

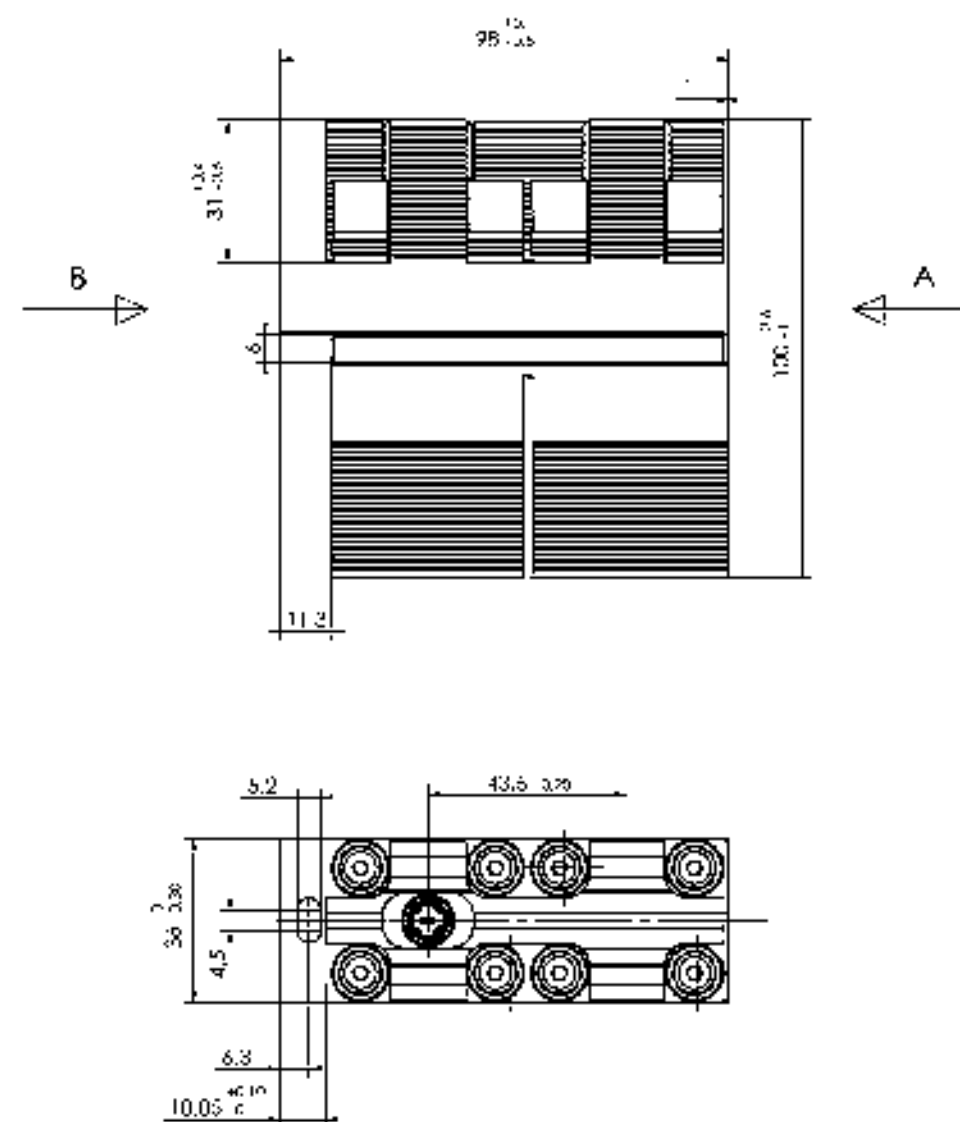
Thyristor Modules / SEMiSTART

Type

	V_{RRM} V_{DRM} V	$I_{overload}$ A	T_c °C	I_{SM} @ $T_j = 125^{\circ}C$ A	$V_{T(TO)}$ @ $T_{jmax}=125^{\circ}C$ V	r_l @ $T_{jmax}=125^{\circ}C$ mΩ	T_{jmax} (for 20s) °C	Package	Thermal Interface Material	Topology
SKKQ 560	1400-1800	560	150	5200	0.9	0.9	150	1	-	
SKKQ 800	1400-1800	800	150	5200	0.9	0.8	150	2	-	
SKKQ 1200	1400-1800	1225	150	8000	0.9	0.5	150	2	-	
SKKQ 1500	1400-1800	1500	150	15000	0.85	0.3	150	2	-	
SKKQ 3000	1400-1800	3080	150	25500	0.95	0.18	150	3	-	

Packages

SEMİSTART 1



Dimensions in mm

Bridge Rectifier Modules For Reliable Inverter Designs

Bridge rectifiers include every branch of a rectifier topology in a single, compact case. Bridge rectifiers exist from a few amps to several hundred amps in different package types.

SEMIKRON offers bridge rectifier modules in single phase or 3-phase topology with or without brake chopper. The bridge rectifier modules are available in different packages such as SEMiX, SEMITOP, SEMIPONT, Power Bridge and MiniSKiiP.

MiniSKiiP	122
SEMITOP	124
SEMIPONT	128
SEMiX	132
Power Bridge	134

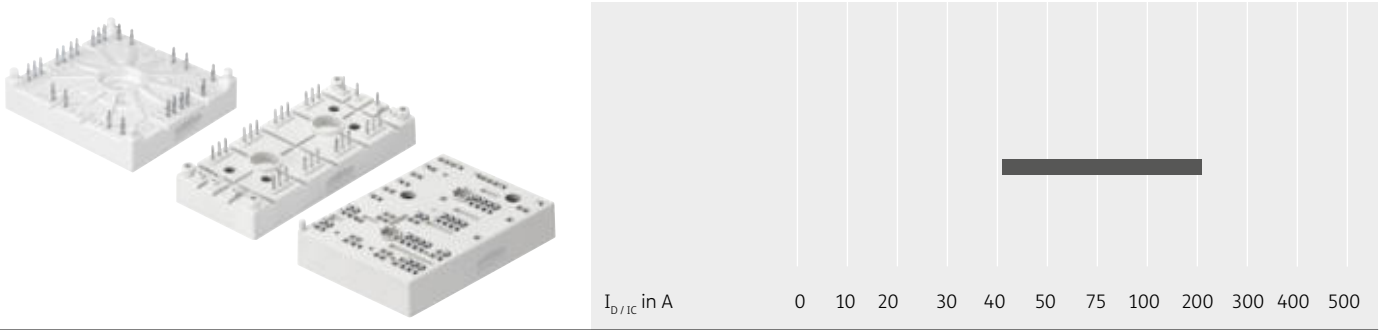
For detailed information please refer to data sheets.

Further information: www.semikron.com/bridge-rectifier-modules

SEMITOP®/SEMIPONT®/MiniSKiiP®

Rectifier with
Brake Chopper

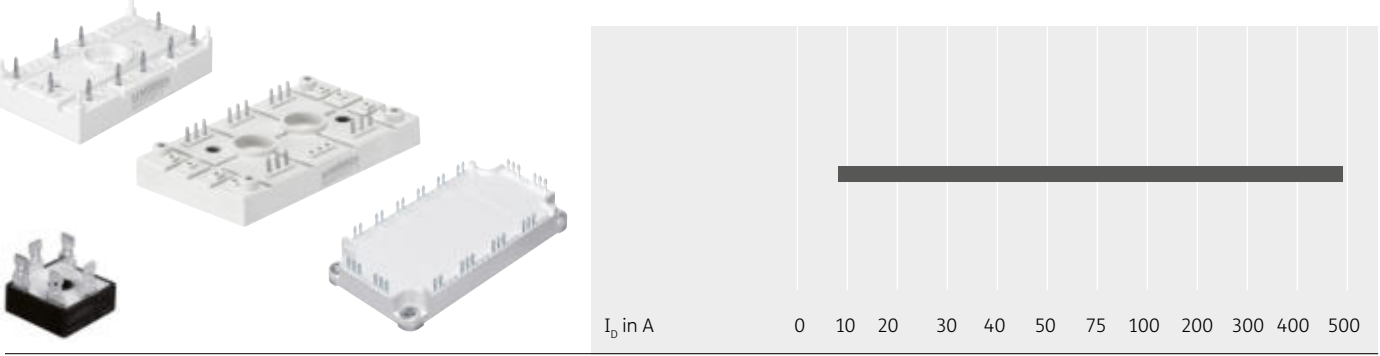
600V up to 1800V



SEMITOP®/SEMIPONT®/SEMiX®/ Power Bridge

Three Phase Rectifier

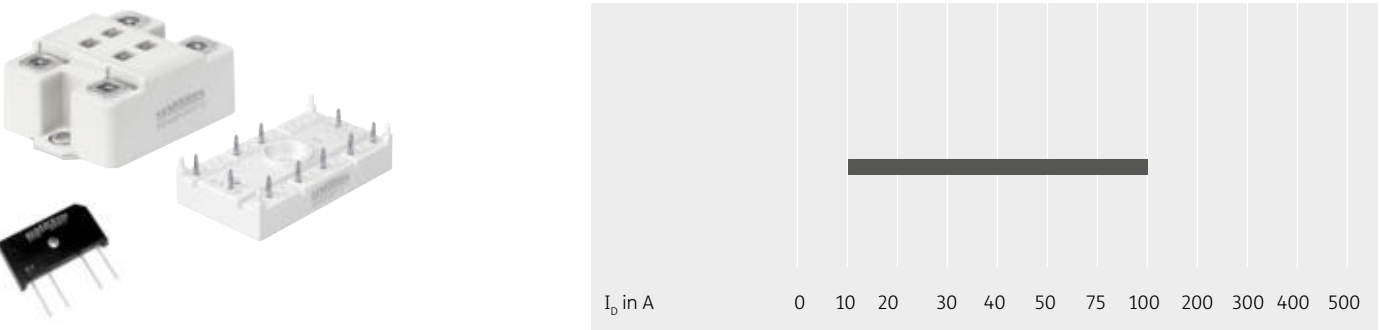
200V up to 2200V



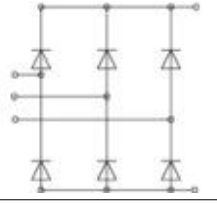
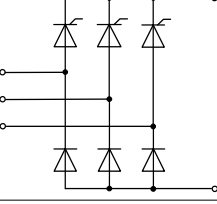
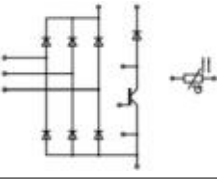
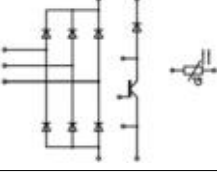
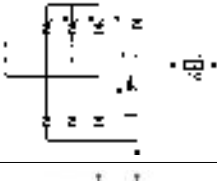
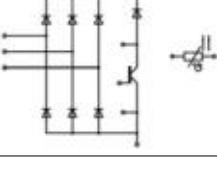
SEMIPONT®/SEMITOP®/ Power Bridge

Single Phase Rectifier

100V up to 2200V

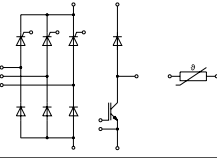


Bridge Rectifier Modules / MiniSKiiP

Type	V_{RRM} V	$I_F@T_s$ A	T_s °C	$I_{FSM(TSM)}@T_s=25^{\circ}C$ A	$V_{T(TO)}$ V	$r_F@T_{jmax}$ mΩ	T_j °C	Package	Thermal Interface Material	Topology
3-phase Rectifier										
SKiiP 28AN16V2 ²⁾	1200	86	70	890	0.83	6	-40 ... +150	II 2	P12, HPTP	
SKiiP 39AN16V1 ¹⁾	1600	179	70	3200	0.83	2.5	-40 ... +150	II 3	P12, HPTP	
SKiiP 39AH16V1 ¹⁾	1600	112	70	2900	0.85	2.4	-40 ... +130	II 3	P12, HPTP	
3-phase Rectifier + Chopper										
SKiiP 28ANB16V1	1600	83	70	1000	0.8	7	-40 ... +150	II 2	P12, HPTP	
SKiiP 28ANB16V2	1600	83	70	1000	0.8	7	-40 ... +150	II 2	P12, HPTP	
SKiiP 28ANB16V10	1600	83	70	1000	0.8	7	-40 ... +150	II 2	P12, HPTP	
SKiiP 28ANB18V3 ²⁾	1800	98	70	1000	0.965	3.4	-40 ... +150	II 2	P12, HPTP	
SKiiP 28AHB16V1	1600	82	70	1000	0.85	7	-40 ... +125	II 2	P12, HPTP	
SKiiP 39AHB16V1	1600	121	70	1250	0.85	4	-40 ... +125	II 3	P12, HPTP	
SKiiP 39ANB16V1	1600	124	70	1600	0.8	4	-40 ... +150	II 3	P12, HPTP	

Footnotes: 1) Sample status / 2) In production new

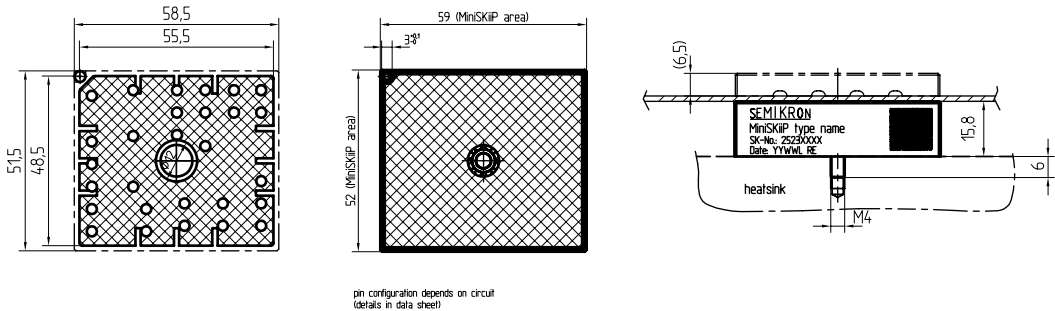
Bridge Rectifier Modules / MiniSKiiP

Type	V_{RRM} V	$I_F@T_s$ A	T_s °C	$I_{FSM(TSM)}@T_s=25^{\circ}C$ A	$V_{T(TO)}$ V	$r_F@T_{jmax}$ mΩ	T_j °C	Package	Thermal Interface Material	Topology
3-phase Rectifier + Chopper										
SKiiP 39AHB16V3 ¹⁾	1600	126	70	1250	0.85	2.8	-40 ... +130	II 3	P12, HPTP	

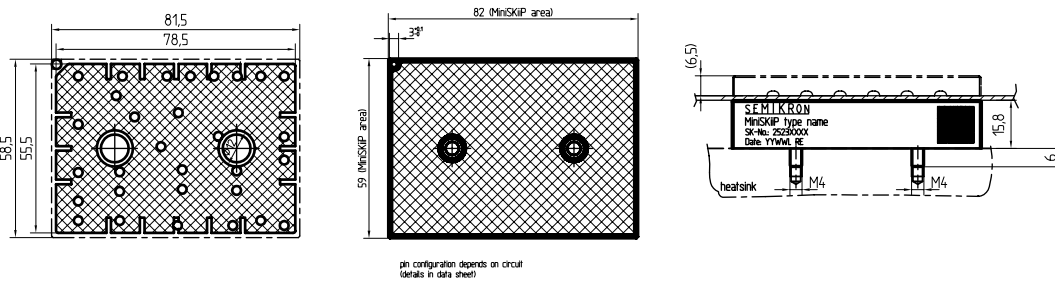
Footnotes: 1) Sample status / 2) In production new

Packages

MiniSKiiP II 2



MiniSKiiP II 3



Dimensions in mm

Bridge Rectifier Modules / SEMITOP

Type	V_{RRM} V_{DRM} V	I_P @ T_S A	T_S °C	I_{TSM} I_{FSM} @ T_{jmax} A	$V_{T(TO)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	T_j °C	Package	Thermal Interface Material	Topology
1 and 3 phase										
SK 50 B 06 UF	600	46	80	400	0.80	11.00	-40 ... +150	2	P12	
SK 50 B	800-1600	51	80	270	0.8	13.00	-40 ... +150	2	P12	
SK 55 B 06 F	600	54	80	440	0.9	16.00	-40 ... +150	2	P12	
SK 55 B 12 F	1200	57	80	550	1.20	22.00	-40 ... +150	2	P12	
SK 70 B	800-1600	68	80	560	0.8	11.00	-40 ... +150	2	P12	
SK 100 B	800-1600	100	80	890	0.83	3.90	-40 ... +150	2	P12	
SK 40 DT	800-1600	42	80	280	1.1	20.00	-40 ... +125	3	P12, HPTP	
SK 70 DT	800-1600	68	80	380	1	10.00	-40 ... +125	3	P12, HPTP	
SK 55 D	800-1600	55	80	200	0.8	13.00	-40 ... +150	2	P12	
SK 70 D	800-1600	70	80	270	0.8	13.00	-40 ... +150	2	P12	
SK 80 D 12F 4)	1200	80	80	550	1.2	22.00	-40 ... +150	3	P12, HPTP	
SK 95 D	800-1600	95	80	560	0.8	11.00	-40 ... +150	2	P12	
SK 95 D 16p 2)	1600	95	80	560	0.8	11.00	-40 ... +150	2p	P12	
SK 40 DH	800-1600	42	80	270	1.1	20.00	-40 ... +150	3	P12, HPTP	
SK 70 DH	800-1600	68	80	270	1	10.00	-40 ... +125	3	P12, HPTP	
SK 55 DGL 126	1200	55	80	370	0.80	13.00	-40 ... +150	3	P12, HPTP	
SK 95 DGL 126	1600	96	80	700	0.8	11.00	-40 ... +150	3	P12, HPTP	
SK 170 DHL 126 1)	1200	170	70	1000	0.8	7.00	-40 ... +150	4	P12, HPTP	
SK 200 DHL 066 1)	600	210	70	1250	0.8	4.00	-40 ... +150	4	P12, HPTP	
SK 40 BHL 066T 2)	1600	42	42	280	0.85	20.00	-40 ... +130	3	P12, HPTP	
SK150DGL12T4 1)	1200	49	-	-	0.83	-	-40 ... +150	3	P12, HPTP	
SK40BB07TD1E2 1)	650	42	42	-	1.1	20.00	-40 ... +125	E2	HPTP, HT	

Footnotes: 1) Sample status / 2) In production new / 4) Discontinued

Bridge Rectifier Modules / SEMITOP

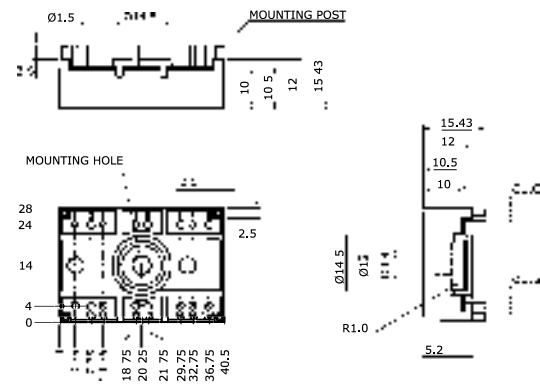
Type	V_{RRM} V_{DRM} V	I_P @ T_S A	T_S °C	I_{TSM} I_{FSM} @ T_{jmax} A	$V_{T(TO)}$ @ T_{jmax} V	r_T @ T_{jmax} mΩ	T_j °C	Package	Thermal Interface Material	Topology
1 and 3 phase										
SK60B12TUF1 1)	650	51	-	-	-	-	-40 ... +175	E1	-	
SK225BV07S5D1E2 1)	800	135	-	1250	0.83	3.09	-40 ... +130	E2	HPTP, HT	
SK70B07TD1E1 1)	650	68	68	560	0.8	11.00	-40 ... +150	E1	-	
SK90DZNT16TE2	1600	56	-	1000	0.83	4.38	-40 ... +130	E2	HPTP, HT	

Footnotes: 1) Sample status / 2) In production new / 4) Discontinued

Packages

SEMITOP 2

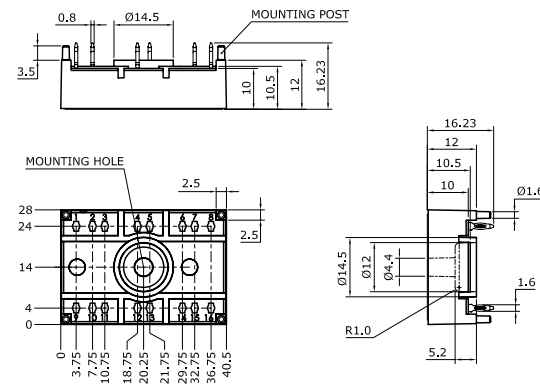
Dimensions: mm
Tolerance system: ISO 2768-m



Dimensions in mm

SEMITOP 2 Press-Fit

Dimensions: mm
Tolerance system: ISO 2768-m

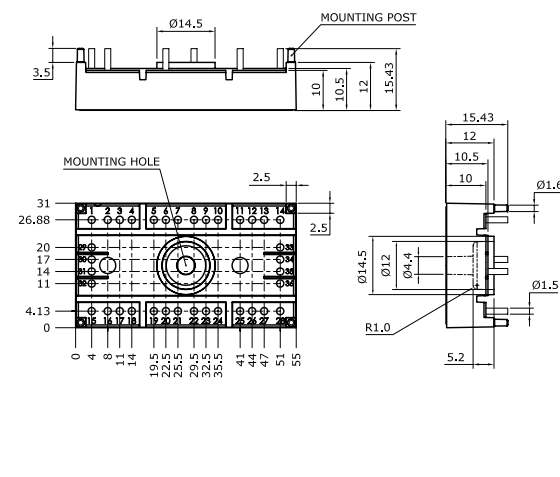


Bridge Rectifier Modules / SEMITOP

Packages

SEMITOP 3

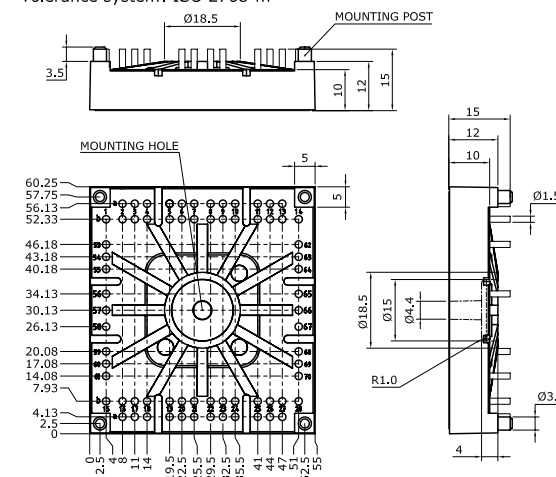
Dimensions: mm
Tolerance system: ISO 2768-m



Dimensions in mm

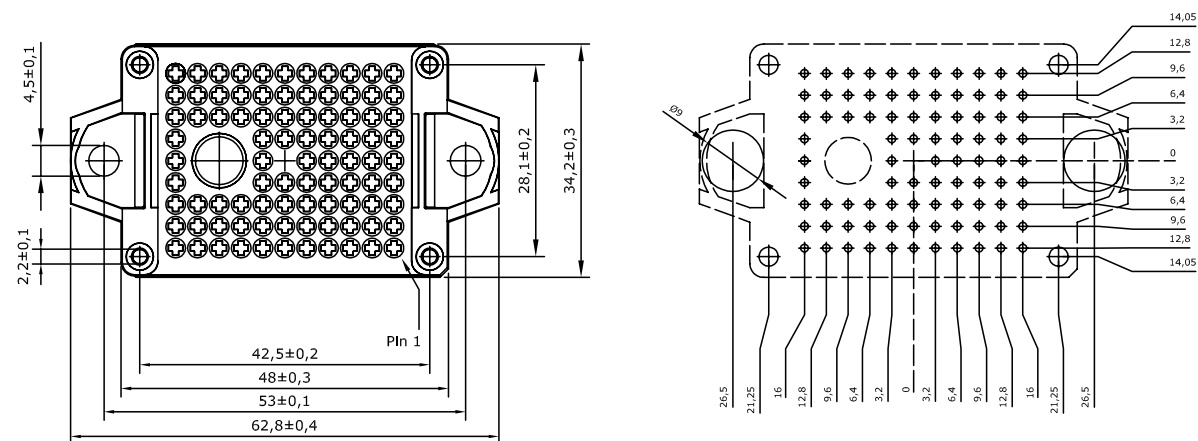
SEMITOP 4

Dimensions: mm
Tolerance system: ISO 2768-m



Packages

SEMITOP E1

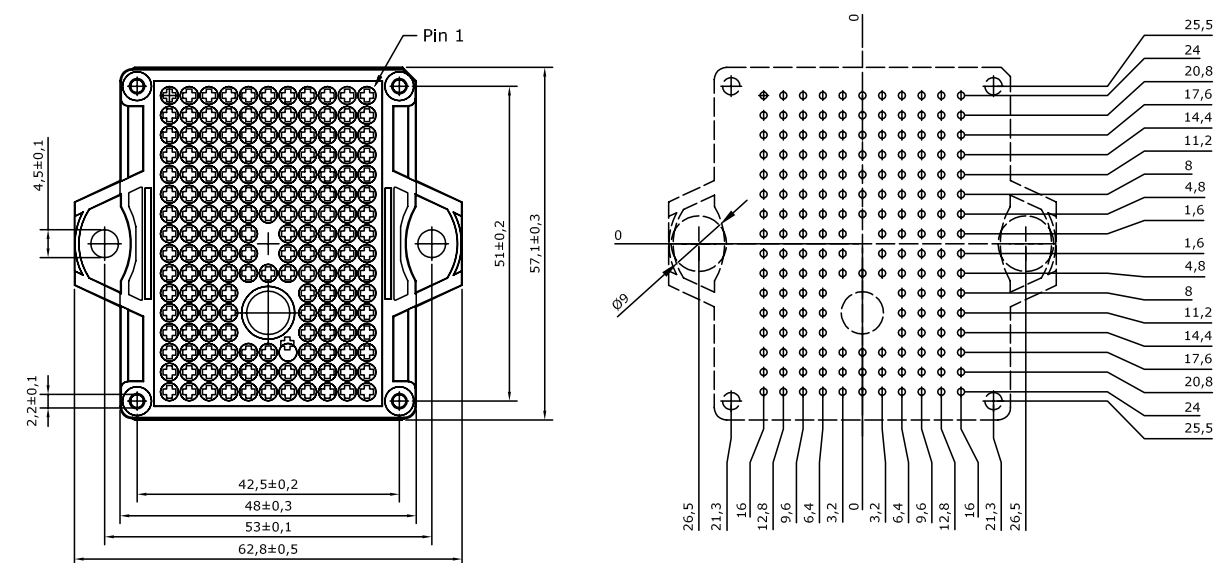


Dimensions in mm

Bridge Rectifier Modules / SEMITOP

Packages

SEMITOP E2



Dimensions in mm

Bridge Rectifier Modules / SEMIPONT

Type										
	V_{RRM} V_{DRM} V	$I_D @ T_c$ A	T_c °C	I_{FSM} $I_{FSM} @ T_{jmax}$ A	$V_{T(T0)} @ T_{jmax}$ V	$r_f @ T_{jmax}$ mΩ	T_j °C	Package	Thermal Interface Material	Topology
1 and 3 phase										
SKB 28	200-1600	28	87	320	0.85	12.0	-40 ... +125	1	-	
SKB 52	400-1800	50	99	425	0.85	8.0	-40 ... +150	3	-	
SKB 60	400-1600	60	88	850	0.85	5.0	-40 ... +125	2	-	
SKB 72	400-1800	70	101	640	0.85	5.0	-40 ... +150	3	-	
SKBH 28	600-1400	28	89	280	1	16.0	-40 ... +125	1	-	
SKBZ 28	400-1400	28	89	280	1	16.0	-40 ... +125	1	-	
SKBT 28	600-1400	28	89	280	1	16.0	-40 ... +125	1	-	
SKBT 40	800-1400	40	92	400	1	16.0	-40 ... +125	2	-	
SKCH 28	400-1400	28	89	280	1	16.0	-40 ... +125	1	-	
SKCH 40	400-1600	40	92	400	1	16.0	-40 ... +125	2	-	
SKDT 60	400-1400	60	86	400	1	16.0	-40 ... +125	2	-	
SKDT 115 ³⁾	1200-1600	110	80	950	1.1	6.0	-40 ... +125	5	-	
SKDT 145	1200-1600	145	80	1250	0.9	5.0	-40 ... +125	5	-	

Footnotes: 2) In production new / 3) Not for new designs

Bridge Rectifier Modules / SEMIPONT

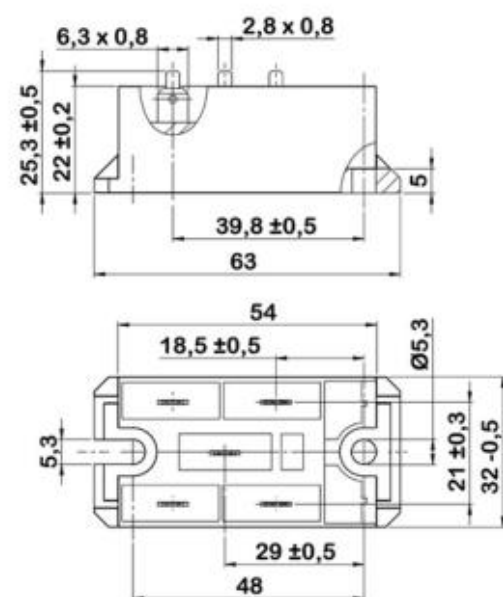
Type										
	V_{RRM} V_{DRM}	$I_D @ T_c$	T_c	I_{TSM} $I_{FSM} @ T_{jmax}$	$V_{T(TO)} @ T_{jmax}$	$r_T @ T_{jmax}$	T_j	Package	Thermal Interface Material	Topology
	V	A	°C	A	V	mΩ	°C			
1 and 3 phase										
SKD 31	200-1600	31	100	320	0.85	12.0	-40 ... +125	1	-	
SKD 60	400-1600	60	102	850	0.85	5.0	-40 ... +125	2	-	
SKD 62	400-1800	60	110	425	0.85	8.0	-40 ... +150	3	-	
SKD 82	400-1800	80	110	640	0.85	5.0	-40 ... +150	3	-	
SKD 100	400-1600	100	93	1000	0.85	5.0	-40 ... +125	2	-	
SKD 110	800-1800	110	100	1000	0.85	4.0	-40 ... +150	4	-	
SKD 115	1200-1800	110	85	1150	0.8	7.0	-40 ... +150	5	-	
SKD 145	1200-1800	145	85	1700	0.8	4.0	-40 ... +150	5	-	
SKD 160	800-1800	205	85	1500	0.85	3.0	-40 ... +150	4	-	
SKD 210	900-1800	207	99	1600	0.85	3.0	-40 ... +150	4	-	
SKDH 100	800-1400	100	84	850	1	4.5	-40 ... +125	2	-	
SKDH 115	1200-1600	110	80	950	1.1	6.0	-40 ... +125	5	-	
SKDH 145	1200-1600	145	80	1250	0.9	5.0	-40 ... +125	5	-	
3 phase with brake chopper										
SKD 116/..-L105 ²⁾	1200-1600	110	85	1050	0.8	7.0	-40 ... +125	6	-	
SKD 116/..-L140 ²⁾	1200-1600	110	85	1050	0.8	7.0	-40 ... +125	6	-	
SKD 146/..-L105 ²⁾	1200-1600	140	85	1250	0.8	4.0	-40 ... +125	6	-	
SKD 146/..-L140T4 ²⁾	1200-1600	140	85	1250	0.8	4.0	-40 ... +125	6	-	
SKDH 116/..L105 ²⁾	1200-1600	110	85	1000	0.8	7.0	-40 ... +125	6	-	
SKDH 116/..L140 ²⁾	1200-1600	110	85	1000	0.8	7.0	-40 ... +125	6	-	
SKDH 146/..-L105 ²⁾	1200-1600	140	85	1250	0.8	4.0	-40 ... +125	6	-	
SKDH 146/..-L140 ²⁾	1200-1600	140	85	1250	0.8	4.0	-40 ... +125	6	-	
SKD 146/16-L140	1600	140	-	1250	0.83	-	-40 ... +150	6	-	
SKD 146/12-L140 ²⁾	1200	140	-	1250	0.83	-	-40 ... +150	6	-	

Footnotes: 2) In production new / 3) Not for new designs

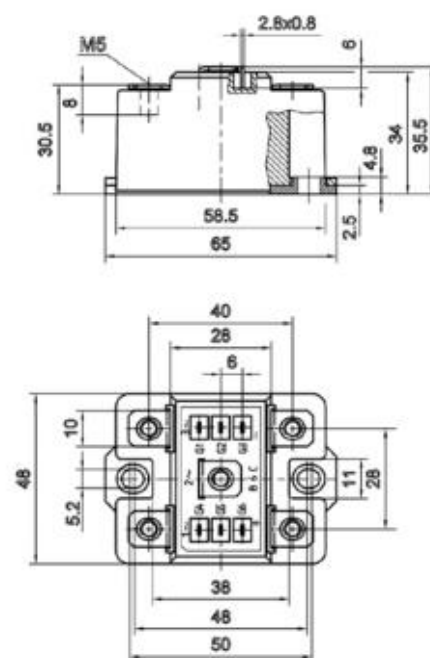
Bridge Rectifier Modules / SEMIPONT

Packages

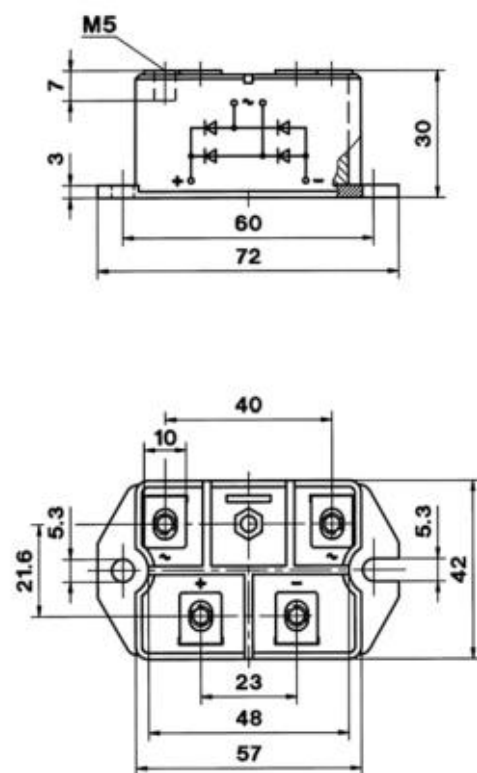
SEMIPONT 1



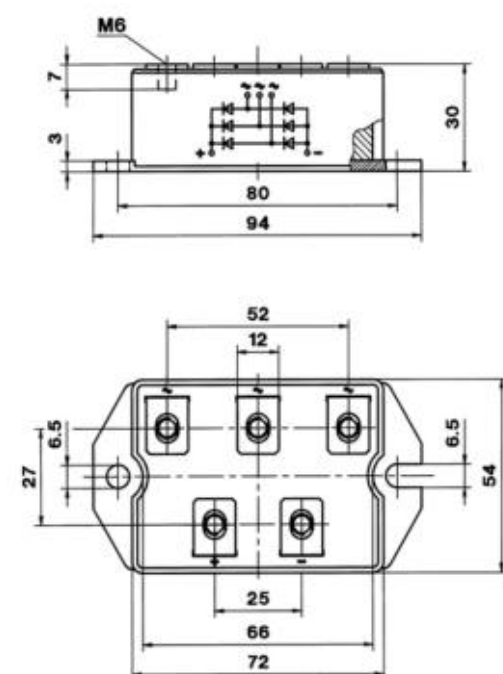
SEMIPONT 2



SEMIPONT 3



SEMIPONT 4

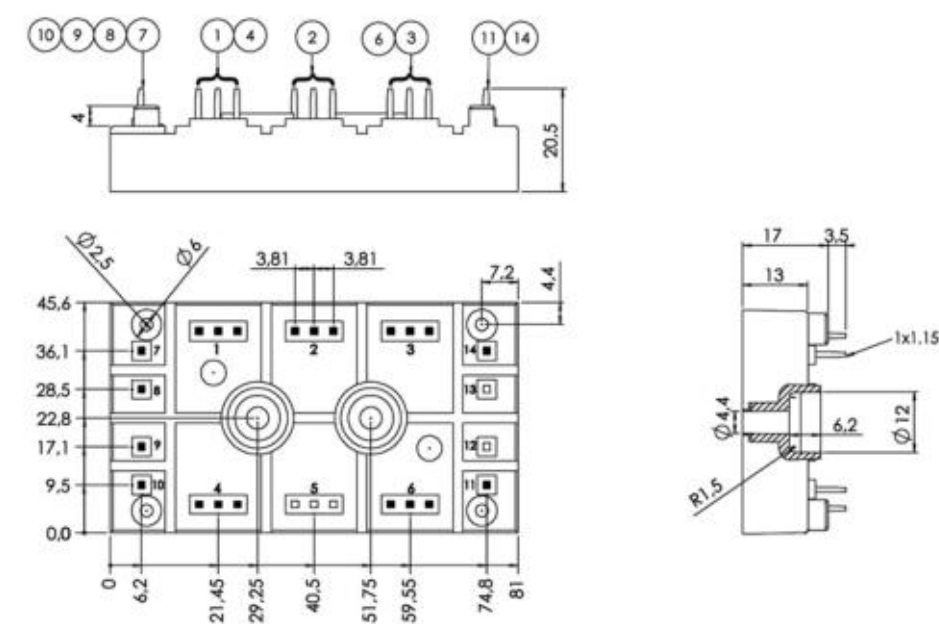


Dimensions in mm

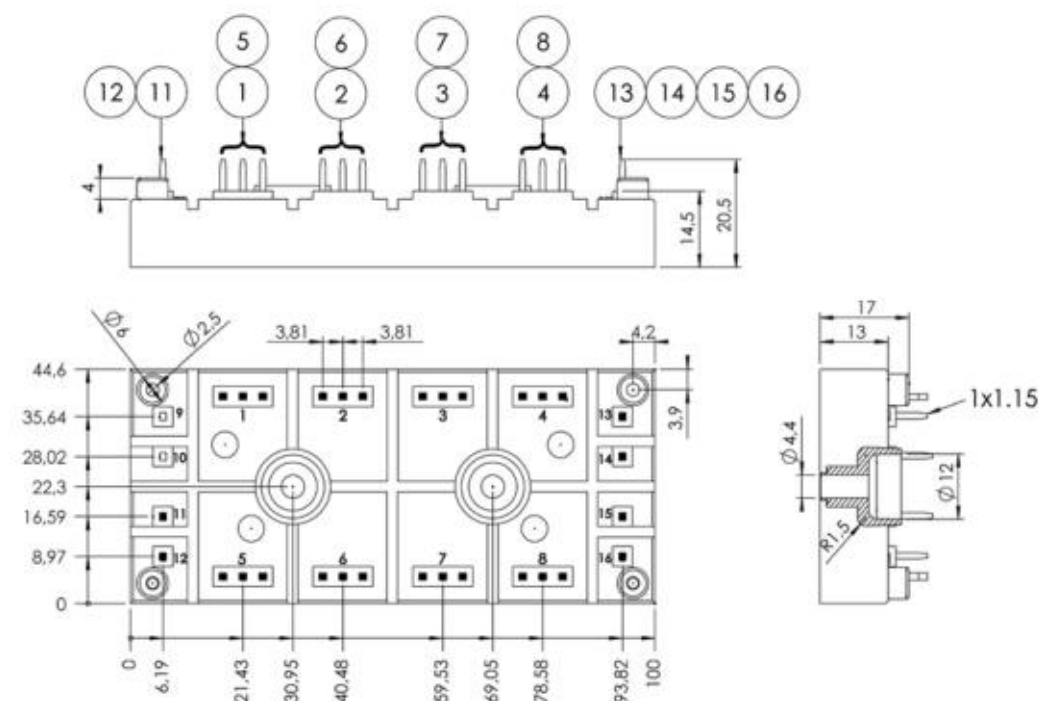
Bridge Rectifier Modules / SEMIPONT

Packages

SEMIPONT 5



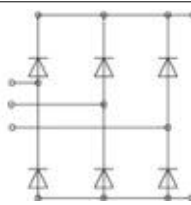
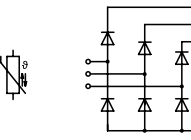
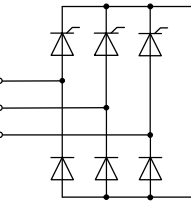
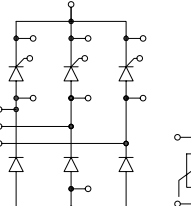
SEMIPONT 6



Dimensions in mm

Bridge Rectifier Modules / SEMiX

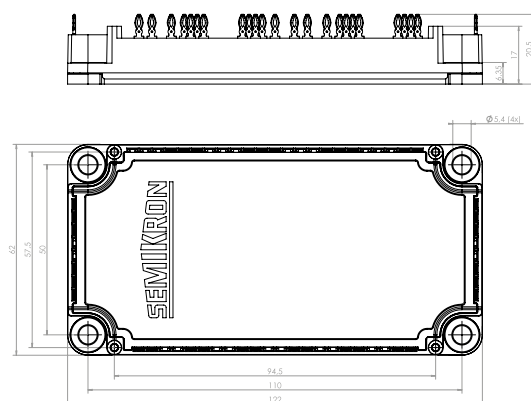
Type

	V_{RRM} V	$I_p @ T_c$ A	T_c °C	I_{FSM} $I_{FSM} @ T_{jmax}$ A	$V_{T(ro)} @ I_{jmax}$ V	$r_T @ T_{jmax}$ mΩ	T_j °C	Package	Thermal Interface Material	Topology
3 phase										
SEMiX251D12Fs ³⁾	1200	256	85	1330	1.20	7	-40 ... +150	13	P8	
SEMiX291D16s	1600	232	85	1380	0.83	4.6	-40 ... +150	13	P8	
SEMiX341D16s	1600	348	85	2000	0.9	2.7	-40 ... +130	13	P8	
SEMiX501D17Fs	1700	494	85	2140	1.10	2.7	-40 ... +150	13	P8	
SEMiX586D16p ¹⁾	1600	700	85	4200	0.916	1.4	-40 ... +175	6p	HT	
SEMiX636D16p ¹⁾	1600	700	85	5500	0.916	1.3	-40 ... +175	6p	HT	
SEMiX526D22p ¹⁾	2200	650	85	5300	0.834	1.4	-40 ... +150	6p	HT	
SEMiX241DH16s	1600	298	100	1800	0.85	3.4	-40 ... +130	13	P8	
SEMiX245DH16 ²⁾	1600	336	96	1800	0.91	3.0	-40 ... +130	5p	P8, HT	
SEMiX365DH16 ²⁾	1600	484	96	2750	0.85	2.5	-40 ... +130	5p	P8, HT	

Footnotes: 1) Sample status / 2) In production new / 3) Not for new designs

Packages

SEMIX 6p

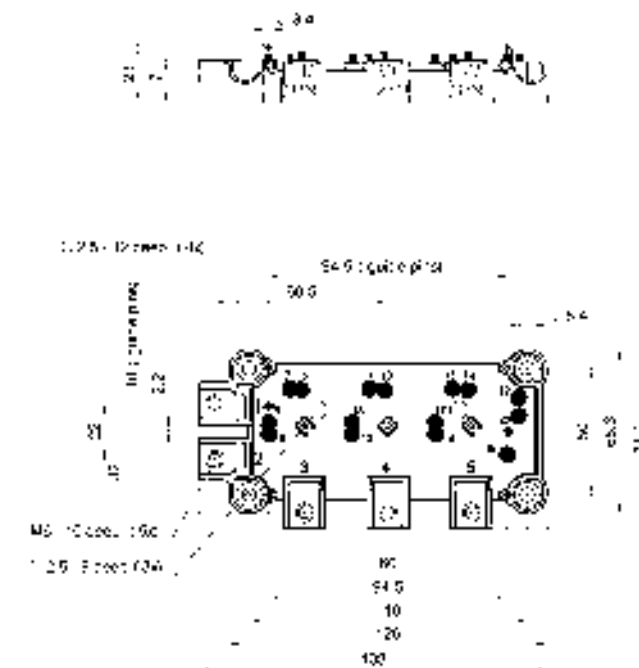


Dimensions in mm

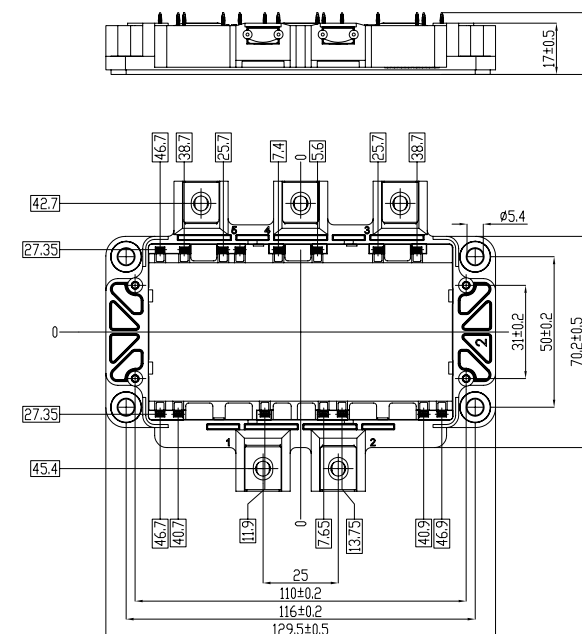
Bridge Rectifier Modules / SEMiX

Packages

SEMIX 13



SEMIX 5p



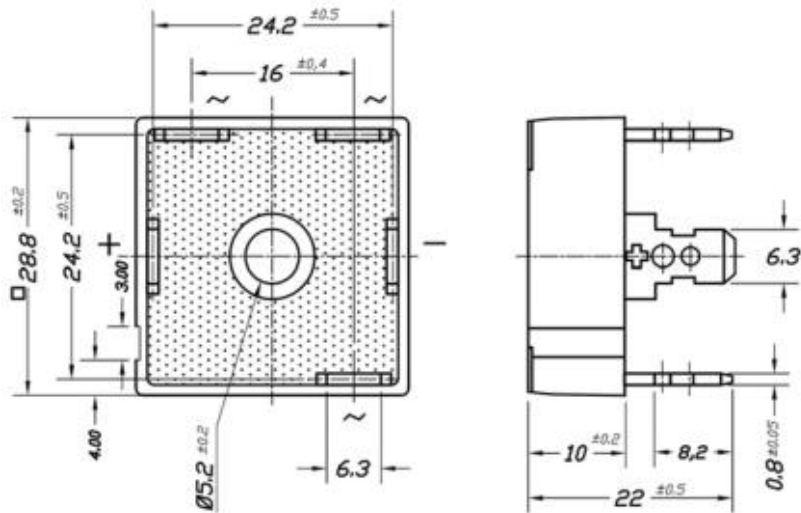
Dimensions in mm

Bridge Rectifier Modules / Power Bridge

Type										
	V_{RRM} V_{DRM}	$I_p @ T_c$	T_c	$I_{FSM} @ T_{jmax}$	$V_{T(TO)} @ T_{jmax}$	$r_T @ T_{jmax}$	T_j	Package	Thermal Interface Material	Topology
	V	A	°C	A	V	mΩ	°C			
1 phase										
SKB 25	100-1600	17	75	320	0.85	12.00	-40 ... +150	G 10b	-	
SKB 26	200-2000	18	75	320	0.85	12.00	-40 ... +150	G 50a	-	
SKB 30	200-1600	30	94	320	0.85	12.00	-40 ... +150	G 12, G 13	-	
SKB 35	400-1600	35	29	330	0.85	7.00	-40 ... +150	G 10b	-	
3 phase										
SKD 25	200-1600	20	73	320	0.85	12.00	-40 ... +150	G 11b	-	
SKD 26	400-1600	20	73	320	0.85	12.00	-40 ... +150	G 50b	-	
SKD 30	200-1600	30	98	320	0.85	12.00	-40 ... +150	G 12, G 13	-	
SKD 33	400-1800	33	110	240	0.8	18.00	-40 ... +150	G55	-	
SKD 35	400-1600	36	70	320	0.85	7.00	-40 ... +150	G 11b	-	
SKD 35 AV	1200-1600	39	70	345	0.9	6.00	-40 ... +150	G 11b	-	
SKD 51	400-1800	50	127	700	0.8	8.50	-40 ... +150	G51	-	
SKD 53	400-1800	53	100	270	0.8	13.00	-40 ... +150	G55	-	
SKD 83	400-1800	83	95	560	0.8	7.50	-40 ... +150	G55	-	
DBI 6 P	400-2200	9	113	165	0.8	24.00	-40 ... +150	DBI P	-	
DBI 25 P	400-2200	27	32	310	0.85	9.00	-40 ... +150	DBI P	-	

Packages

G 10b, G 11b

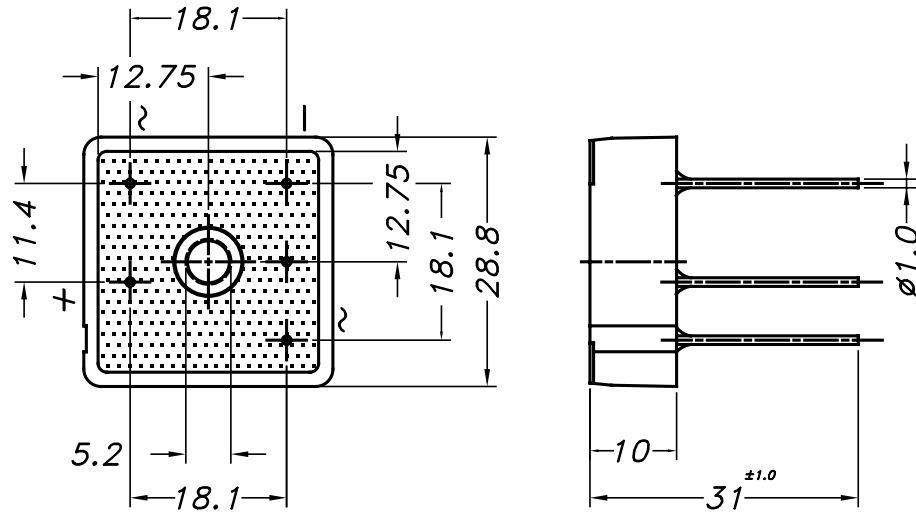


Dimensions in mm

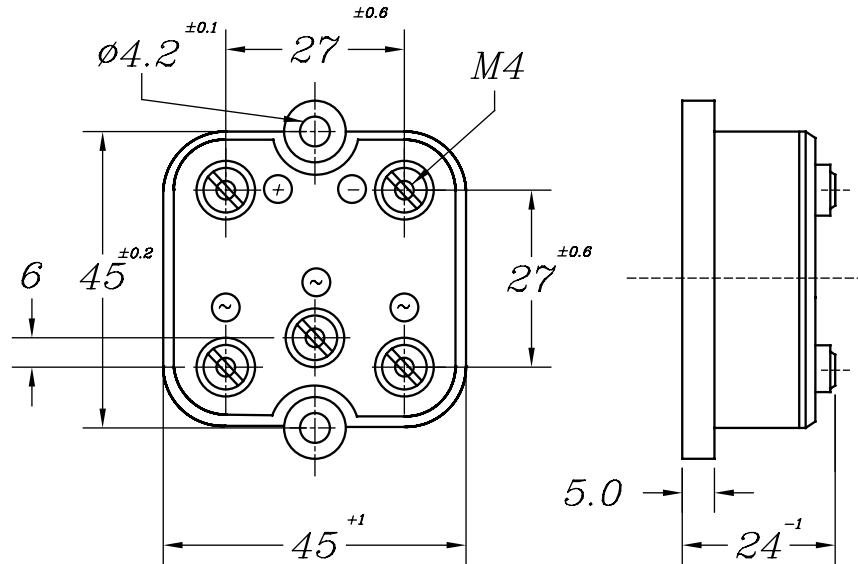
Bridge Rectifier Modules / Power Bridge

Packages

G 50a, G 50b



G 12, G 13

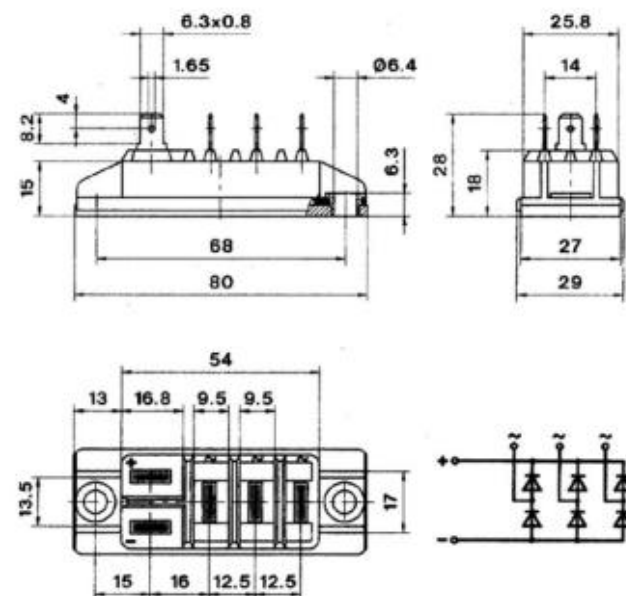


Dimensions in mm

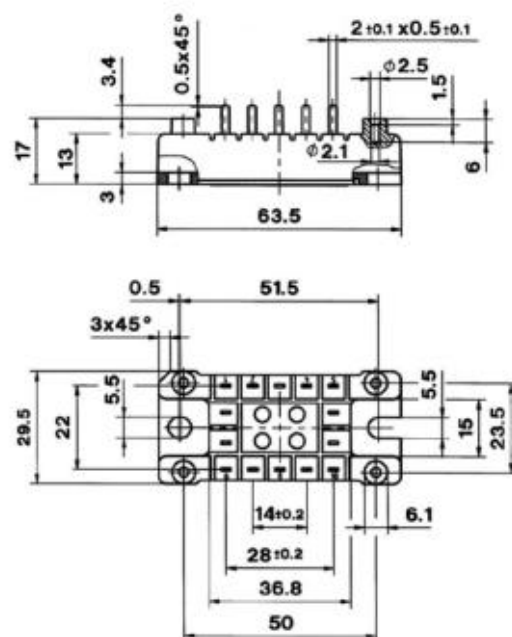
Bridge Rectifier Modules / Power Bridge

Packages

G 51



G 55

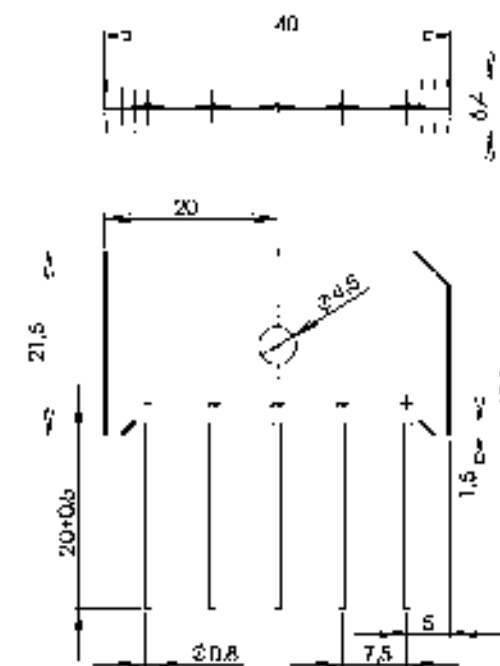


Dimensions in mm

Bridge Rectifier Modules / Power Bridge

Packages

DBI P



Dimensions in mm



Intelligent Power Modules

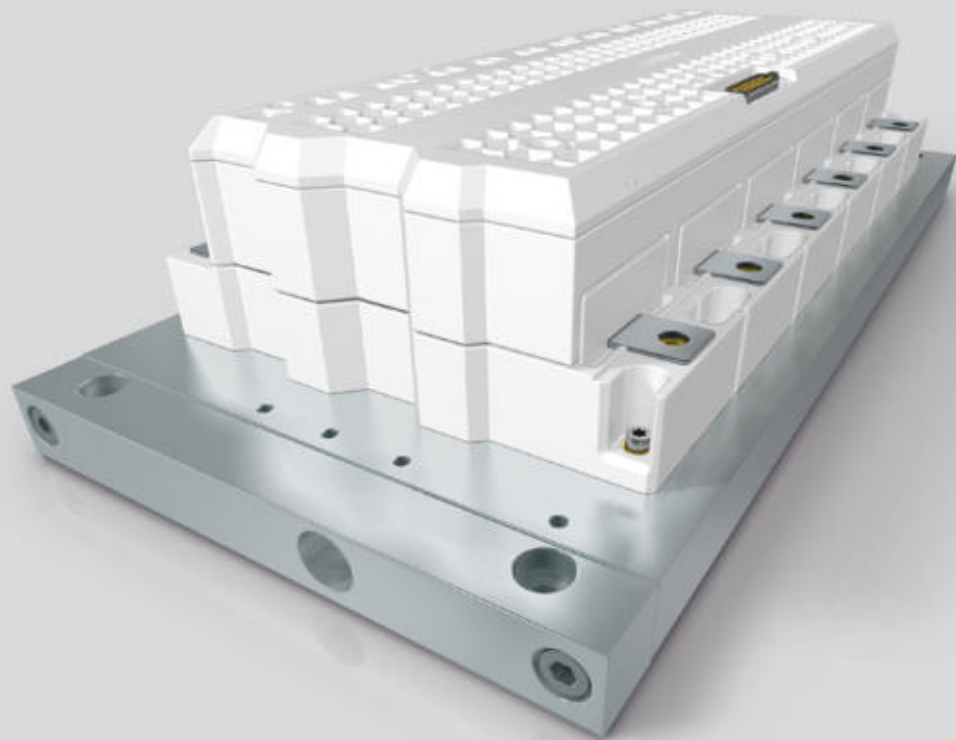
IPMs

PAGE

SKiiP 140

2

SKiiP® 3/4



Intelligent Power Module (IPM) for Maximum Reliability

SKiiP®

Portfolio

SKiiP 3, 4 500A up to 3600A

Short facts

3-in-1: Driver, semiconductor and cooling

2-3 times higher power cycling capability thanks to sinter technology (SKiiP 4)

Fully assembled and 100% tested

Key features

Integrated driver, semiconductor and cooling

Integrated temperature measurement

Integrated current sensors

Integrated DC-Link monitoring

100% solder-free (SKiiP 4)

Applications

SKiiP fully meets the specific requirements for wind turbines in the 0.5 to 6MW power range. Besides wind power applications, SKiiP modules can also be found in elevators, solar power and railway applications – in fact, in any area where powerful, safe and reliable IGBT IPMs are a must.

Benefits

SKiiP is the most powerful IPM on the market. The power semiconductors used in SKiiP 4 modules can be operated up to a junction temperature of 175°C. To make sure these components can be reliably used at these temperatures, the power circuitry is 100% solder-free. Sinter technology is used to create a sintered silver layer instead of the solder layer which could limit the service life of power modules. Reliability during active and passive thermal cycling is greatly improved.

The integrated gate driver in the SKiiP 4 sets new standards in terms of reliability and functionality. The digital driver guarantees safe isolation between the primary and secondary side for both switching signals and parameter measurement. This means the user no longer has to introduce complex and costly topology components to provide safe isolation.

Product range

SKiiP IPMs are available in half-bridge and sixpack topologies in power ratings of up to 2MW without paralleling. Cooling solutions range from water to air-cooled systems and customised cooling in SKiiP 3/4. A wide range of accessories is now also available for both SKiiP 3 and SKiiP 4. These include fiber optic boards, paralleling boards for SKiiP systems and adapter boards to connect SKiiP 4 to SKiiP 3 controller.

Further information: www.semikron.com/skiip



IPM

SEMIKRON For Highly Integrated IPMs

The SKiiP IPMs set a benchmark for high performance and robust converter designs. Especially the SKiiP 4 with its sintered chips is an enabler for maximum load cycle capability and lifetime for use in renewable energy converters such as wind turbines and solar inverters as well as for traction applications.

SKiiP 3/4	144
SKiiP Accessories	153

For detailed information please refer to data sheets.

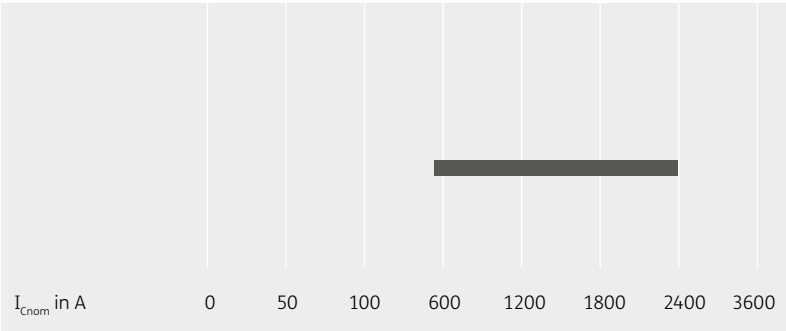
Further information: www.semikron.com/ipm

SKiiP®3

Sixpack
Half-Bridge



1200V up to 1700V

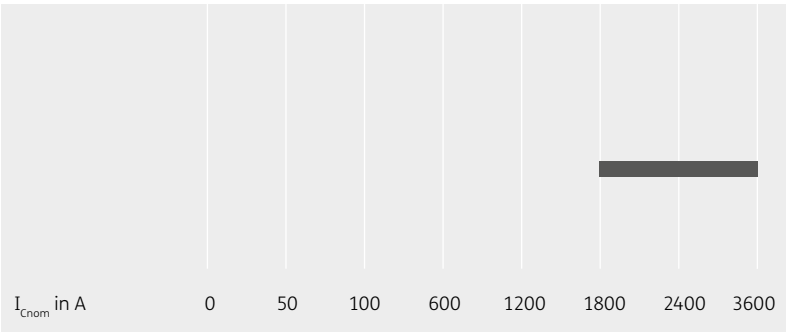


SKiiP®4

Half-Bridge



1200V up to 1700V



IPM / SKiiP

Type	IGBT				Diode			Module		
	$I_C @ T_S = 25^{\circ}\text{C}$	I_{nom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	$E_{on} + E_{off}$	$I_F @ T_S = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	Options F=F-Option U=U-Option S=SKiFace Adapter	Package	Topology
	A	A	V	mJ	A	V	mJ			
1200V - IGBT 3 (Trench) - SKiiP3										
SKiiP 603 GD123-3DUL V3	627	600	1.7	195	508	1.50	28	-	S33	
SKiiP 603 GD123-3DUW V3	627	600	1.7	195	508	1.50	28	-	S33	
SKiiP 613 GD123-3DUL V3	577	600	1.7	195	466	1.50	28	-	S33	
SKiiP 613 GD123-3DUW V3	577	600	1.7	195	466	1.50	28	-	S33	
SKiiP 1213 GB123-2DL V3	1145	1200	1.7	390	925	1.50	56	F	S23	
SKiiP 1213 GB123-2DW V3	1145	1200	1.7	390	925	1.50	56	F	S23	
SKiiP 1813 GB123-3DL V3	1695	1800	1.7	585	1411	1.50	84	F,U	S33	
SKiiP 1813 GB123-3DW V3	1695	1800	1.7	585	1411	1.50	84	F,U	S33	
SKiiP 1813 GB123-3DUL V3	1695	1800	1.7	585	1411	1.50	84	F,U	S33	
SKiiP 2413 GB123-4DUL V3	2280	2400	1.7	780	1807	1.50	112	F,U	S43	
SKiiP 2413 GB123-4DL V3	2280	2400	1.7	780	1807	1.50	112	F,U	S43	
SKiiP 2413 GB123-4DW V3	2280	2400	1.7	780	1807	1.50	112	F,U	S43	
1200V - IGBT 4 (Trench) - SKiiP4										
SKiiP 1814 GB12E4-3DUL	2345	1800	2.01	1260	1776	2.33	150	F,S	S34	
SKiiP 1814 GB12E4-3DUW	2345	1800	2.01	1260	1776	2.33	150	F,S	S34	
SKiiP 1814 GB12E4-3DUSL	2345	1800	2.01	1260	1776	2.33	150	F,S	S34	
SKiiP 2414 GB12E4-4DUL	3109	2400	2.01	1680	2369	2.33	200	F,S	S44	
SKiiP 2414 GB12E4-4DUW	3109	2400	2.01	1680	2369	2.33	200	F,S	S44	
SKiiP 2414 GB12E4-4DUSL	3109	2400	2.01	1680	2369	2.33	200	F,S	S44	
SKiiP 2414 GB12E4-4DULR	3109	2400	2.01	1680	2369	2.33	200	F,S	S44	
SKiiP 3614 GB12E4-6DUL	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
SKiiP 3614 GB12E4-6DUW	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
SKiiP 3614 GB12E4-6DULR	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
SKiiP 3614 GB12E4-6DUSL	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
SKiiP 3614 GB12E4-6DUL	4664	3600	2.01	2520	3558	2.33	300	F,S	S64	
1700V - IGBT 3 (Trench) - SKiiP3										
SKiiP 513 GD172-3DUL V3	540	500	1.9	288	438	2.00	43	-	S33	
SKiiP 513 GD172-3DUW V3	540	500	1.9	288	438	2.00	43	-	S33	
SKiiP 603 GD172-3DUL V3	587	570	1.9	288	476	2.00	43	-	S33	
SKiiP 603 GD172-3DUW V3	570	570	1.9	288	476	2.00	43	-	S33	

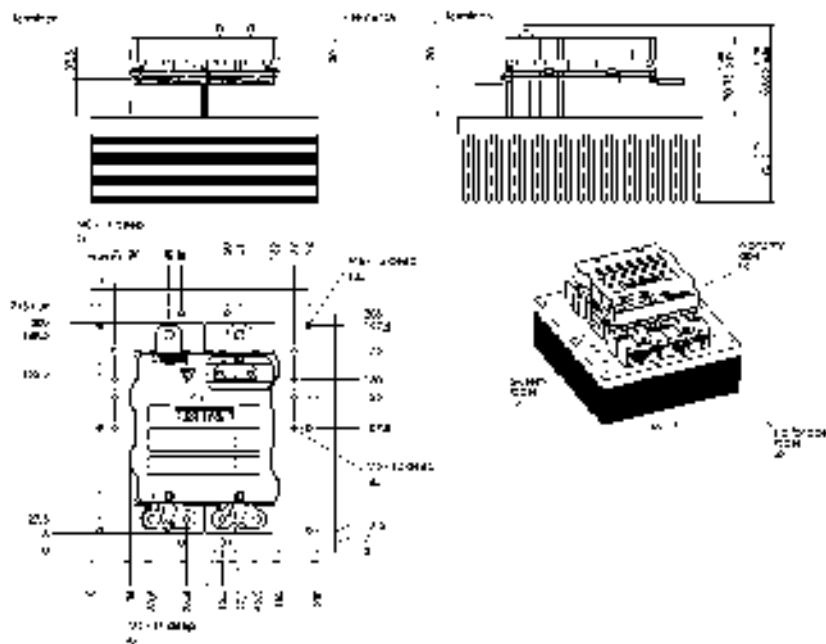
IPM / SKiiP

Type	IGBT			Diode			Module			
	$I_C @ T_S = 25^{\circ}\text{C}$	I_{nom}	$V_{CE(sat)} @ T_J = 25^{\circ}\text{C typ.}$	$E_{on} + E_{off}$	$I_F @ T_S = 25^{\circ}\text{C}$	$V_F @ T_J = 25^{\circ}\text{C typ.}$	E_{rr}	Options F=F-Option U=U-Option S=SKiFace Adapter	Package	Topology
	A	A	V	mJ	A	V	mJ			
1700V - IGBT 3 (Trench) - SKiiP3										
SKiiP 1013 GB172-2DL V3	1072	1000	1.9	575	879	2.00	86	F	S23	
SKiiP 1013 GB172-2DW V3	1072	1000	1.9	575	879	2.00	86	F	S23	
SKiiP 1203 GB172-2DL V3	1159	1200	1.9	575	961	2.00	86	F	S23	
SKiiP 1203 GB172-2DW V3	1159	1200	1.9	575	961	2.00	86	F	S23	
SKiiP 1513 GB172-3DL V3	1589	1500	1.9	863	1336	2.00	128	F,U	S33	
SKiiP 1513 GB172-3DW V3	1589	1500	1.9	863	1336	2.00	128	F,U	S33	
SKiiP 1513 GB172-3DFL V3	1589	1500	1.9	863	1336	2.00	128	F,U	S33	
SKiiP 1803 GB172-3DL V3	1744	1800	1.9	863	1454	2.00	128	F,U	S33	
SKiiP 1803 GB172-3DW V3	1744	1800	1.9	863	1454	2.00	128	F,U	S33	
SKiiP 2013 GB172-4DL V3	2102	2000	1.9	1150	1758	2.00	171	F,U	S43	
SKiiP 2013 GB172-4DW V3	2102	2000	1.9	1150	1758	2.00	171	F,U	S43	
SKiiP 2013 GB172-4DFL V3	2102	2000	1.9	1150	1758	2.00	171	F,U	S43	
SKiiP 2403 GB172-4DL V3	2282	2400	1.9	1150	1921	2.00	171	F,U	S43	
SKiiP 2403 GB172-4DW V3	2282	2400	1.9	1150	1921	2.00	171	F,U	S43	
1700V - IGBT 4 (Trench) - SKiiP4										
SKiiP 1814 GB17E4-3DUL V2	2547	1800	2.12	2130	1771	2.02	498	F,S	S34	
SKiiP 1814 GB17E4-3DUW V2	2547	1800	2.12	2130	1771	2.02	498	F,S	S34	
SKiiP 2414 GB17E4-4DUL V2	3385	2400	2.12	2840	2362	2.02	664	F,S	S44	
SKiiP 2414 GB17E4-4DUW V2	3385	2400	2.12	2840	2362	2.02	664	F,S	S44	
SKiiP 2414 GB17E4-4DPVL	3385	2400	2.12	2840	2362	2.02	664	F,S	S44	
SKiiP 2414 GB17E4-4DPVW	3385	2400	2.12	2840	2362	2.02	664	F,S	S44	
SKiiP 3614 GB17E4-6DUL V2	5078	3600	2.12	6840	3547	2.02	996	F,S	S64	
SKiiP 3614 GB17E4-6DUW V2	5078	3600	2.12	6840	3547	2.02	996	F,S	S64	
SKiiP 3614 GB17E4-6DULR V2	5078	3600	2.12	6840	3547	2.02	996	F,S	S64	
SKiiP 3614 GB17E4-6DPVLR	5078	3600	2.12	6840	3547	2.02	996	F,S	S64	
SKiiP 3614 GB17E4-6DPVL	5078	3600	2.12	6840	3547	2.02	996	F,S	S64	

IPM / SKiïP

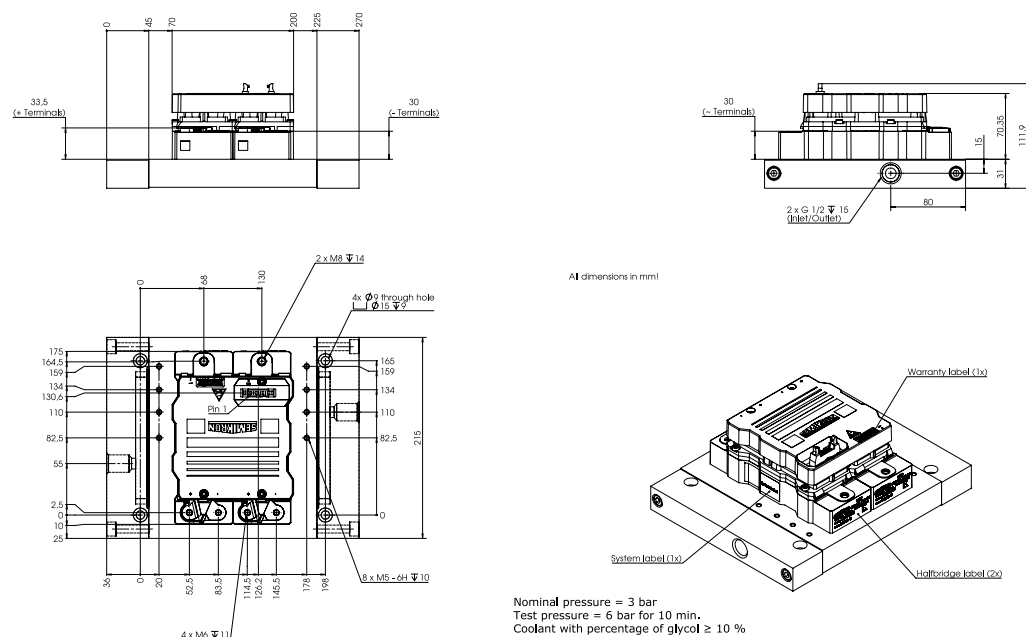
SKiIP 3

Package S 23 mounted on P3016 heat sink



Weight without heat sink:	1,7 kg
P3016:	4,4 kg

Package S 23 mounted on liquid cooled heat sink NWK 40



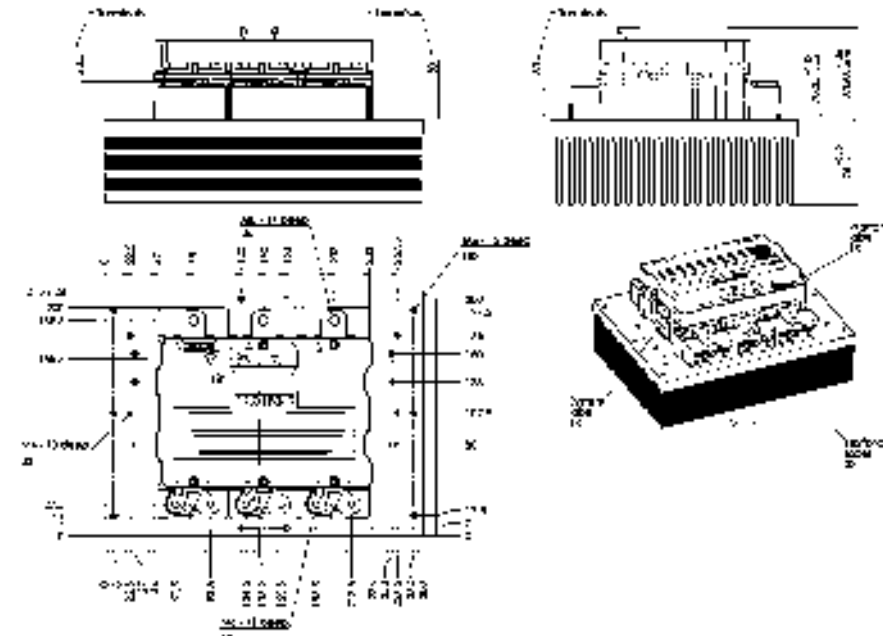
NWK 40: 2,8 kg

Dimensions in mm

IPM / SKiïP

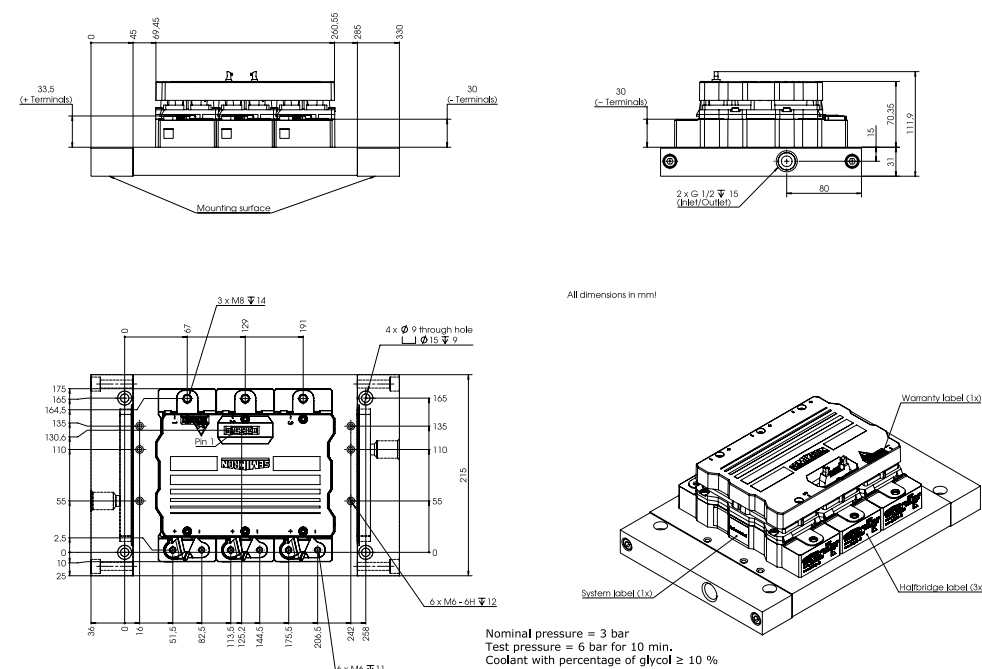
SKiIP 3

Package S 33 mounted on P3016 heat sink



Weight without heat sink:	2,4 kg
P3016:	6,2 kg

Package S 33 mounted on liquid cooled heat sink NWK 40



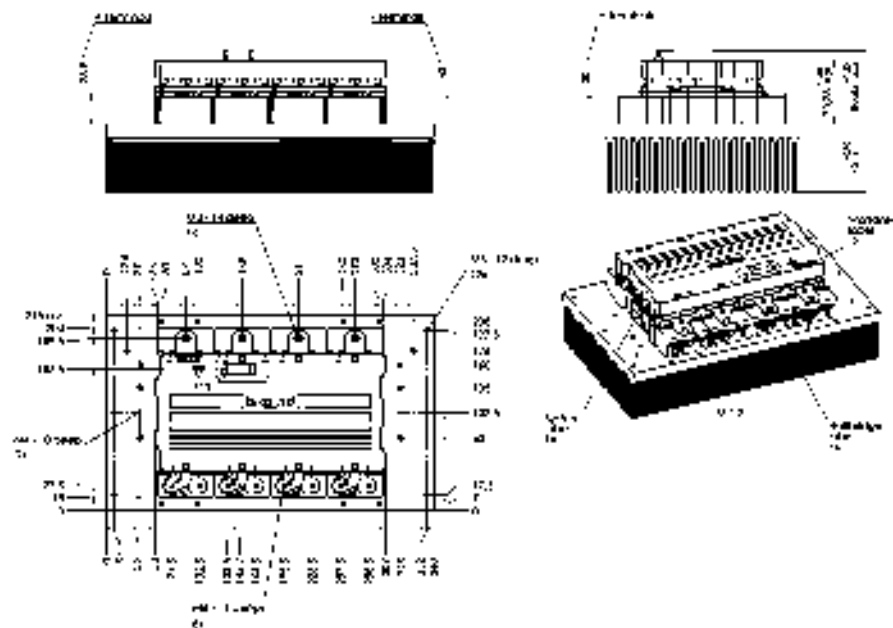
NWK 40: 5,2 kg

Dimensions in mm

IPM / SKiïP

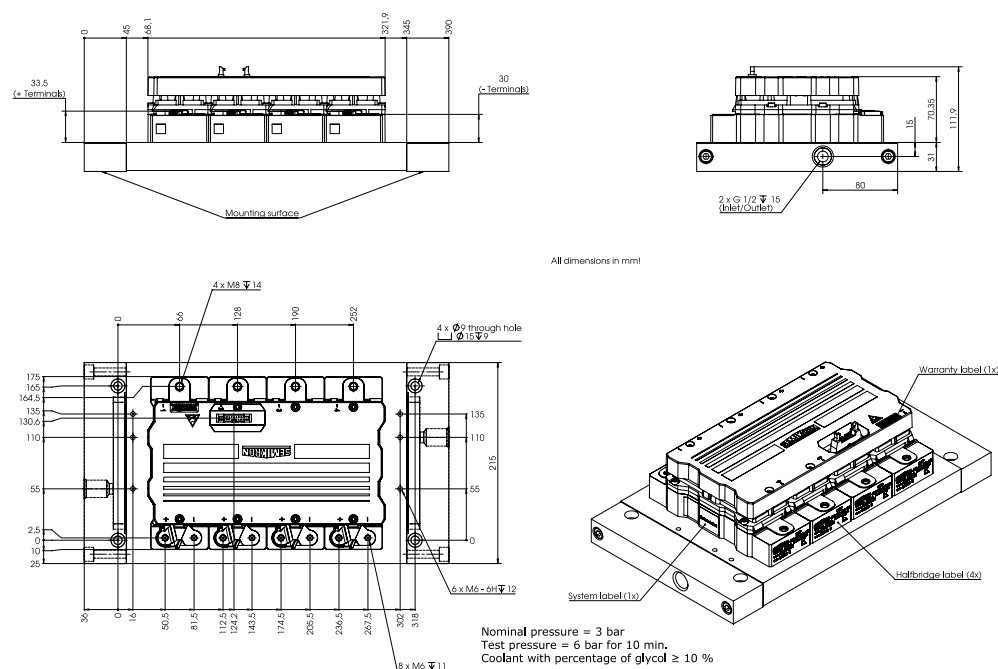
SKiIP 3

Package S 43 mounted on P3016 heat sink



Weight without heat sink:	3,1 kg
P3016:	8,0 kg

Package S 43 mounted on liquid cooled heat sink NWK 40



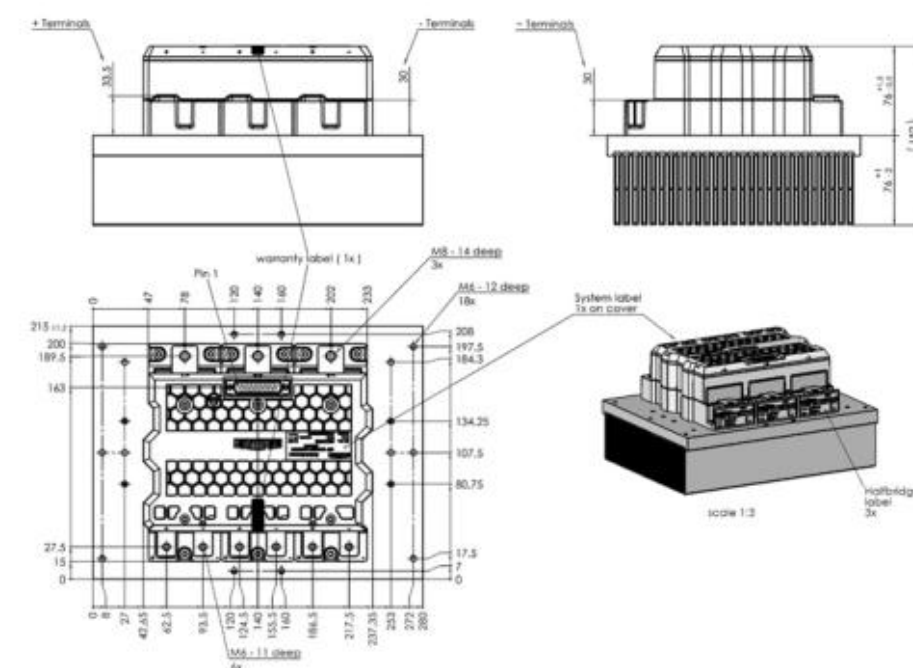
NWK 40: 6,2 kg

Dimensions in mm

IPM / SKiïP

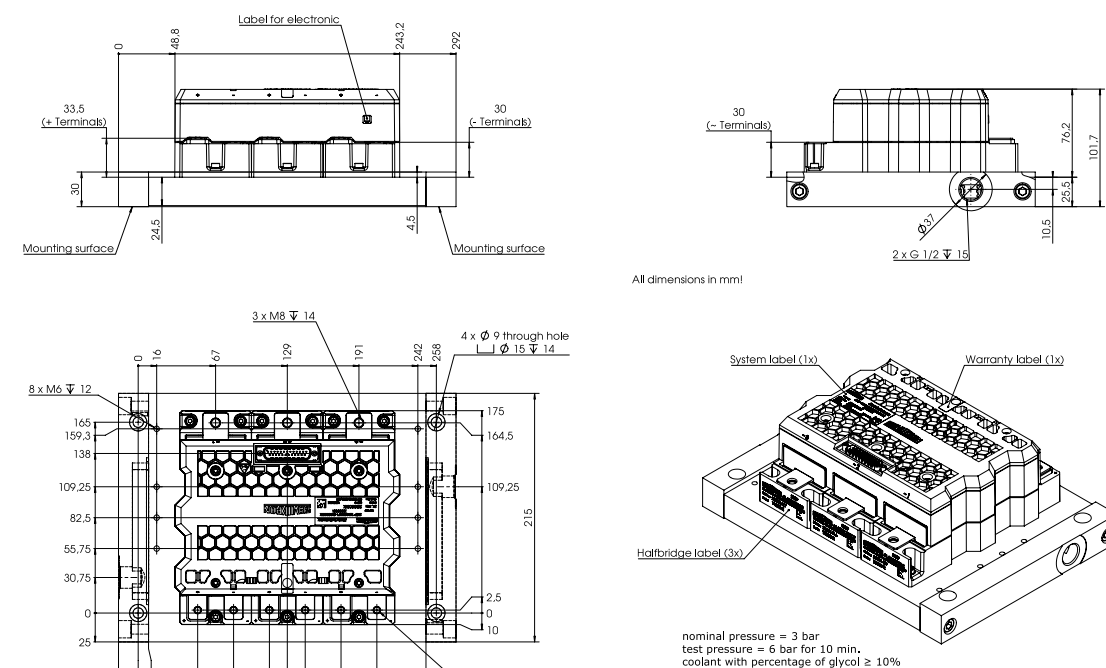
SKiIP 4

Package S 34 mounted on P4016 heat sink



Weight without heat sink:	2,48 kg
P4016:	5,9 kg

Package S 34 mounted on liquid cooled heat sink NHC



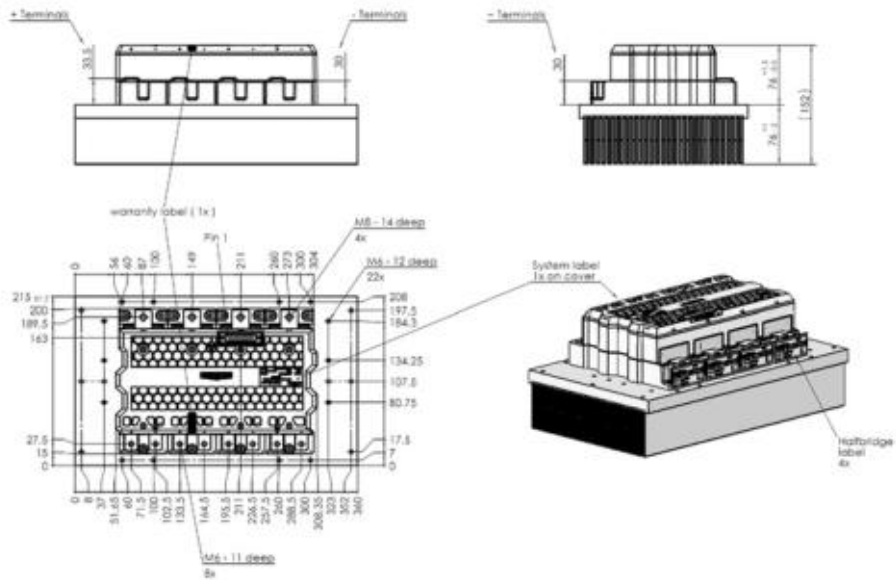
NHC: 3,49 kg

Dimensions in mm

IPM / SKiip

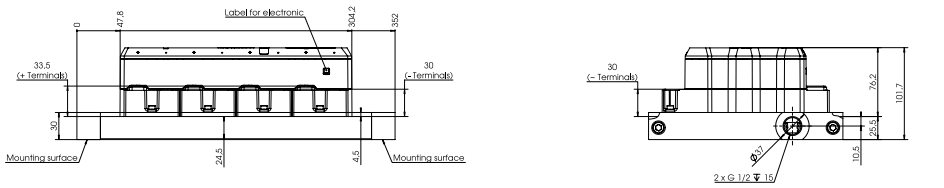
SKiip 4

Package S 44 mounted on P4016 heat sink

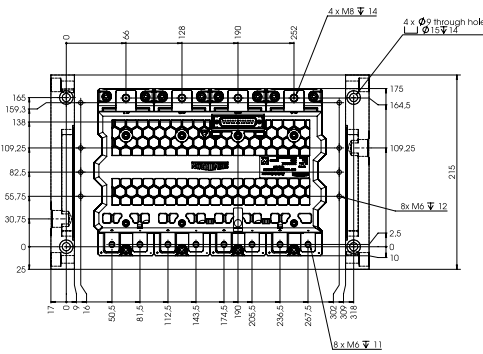


Weight without heat sink: 3,22 kg
P4016: 7,55 kg

Package S 44 mounted on liquid cooled heat sink NHC



All dimensions in mm!



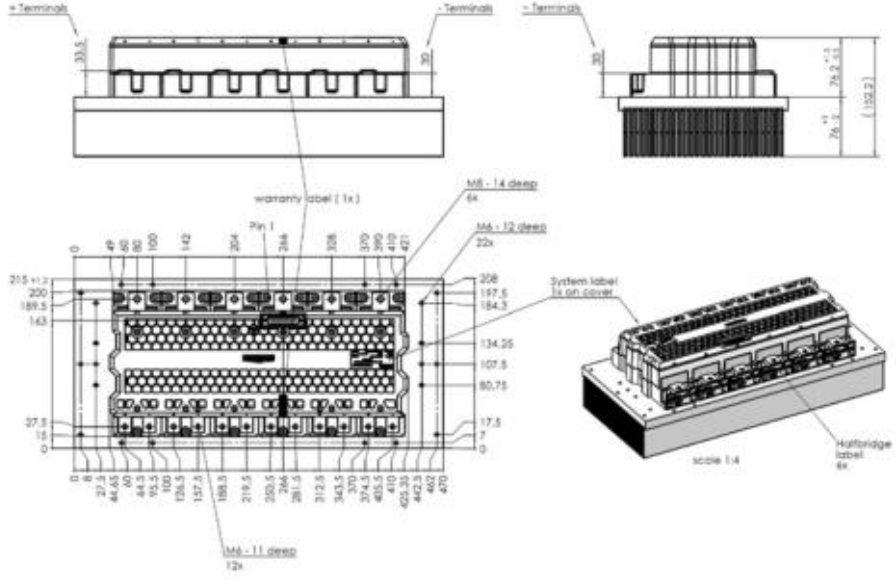
NHC: 4,25 kg

Dimensions in mm

IPM / SKiip

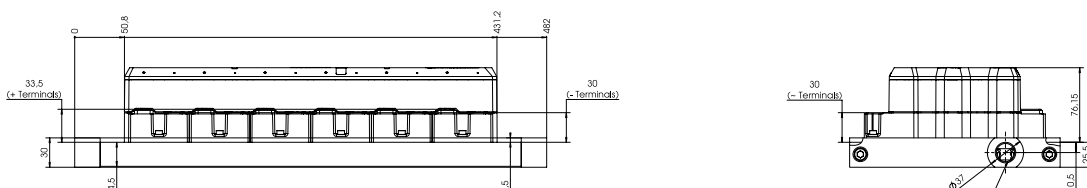
SKiip 4

Package S 64 mounted on P4016 heat sink

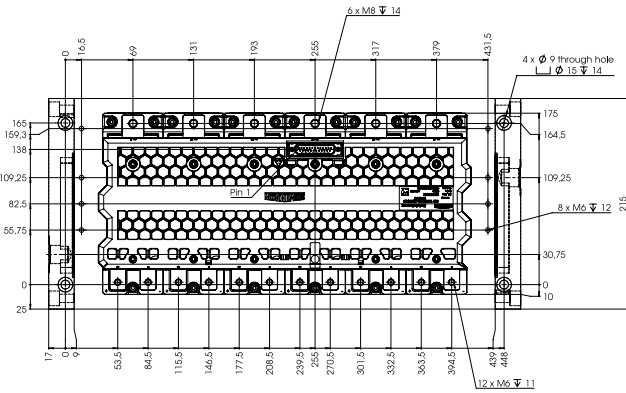


Weight without heat sink: 4,84 kg
P4016: 9,9 kg

Package S 64 mounted on liquid cooled heat sink NHC



All dimensions in mm!



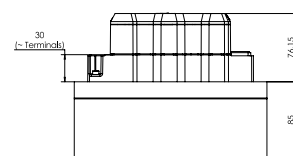
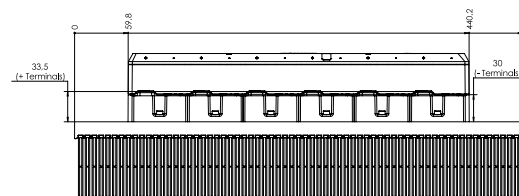
NHC: 5,77 kg

Dimensions in mm

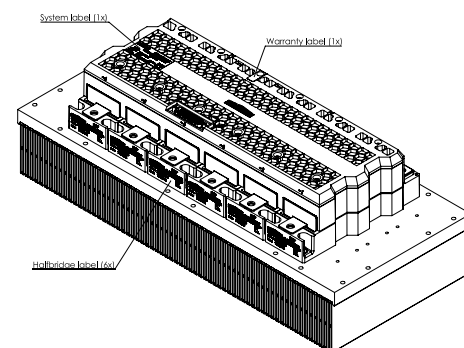
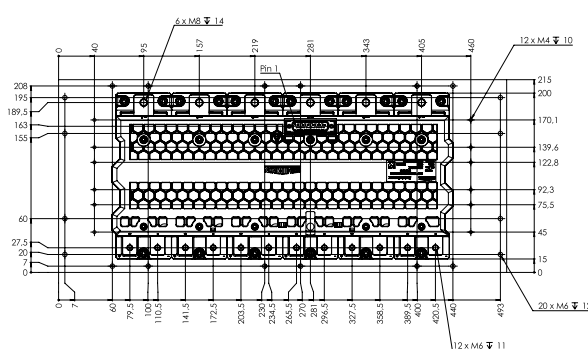
IPM / SKiïP

SKiIP 4

Package S 64 mounted on P4016 heat sink with 90° rotated fins

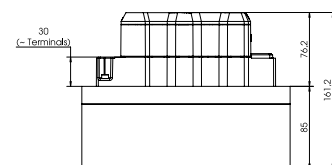
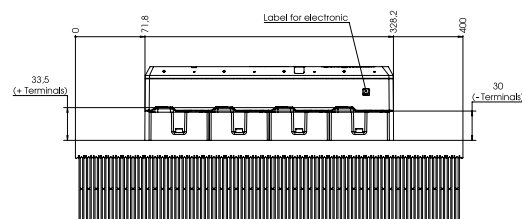


All dimensions in mm!

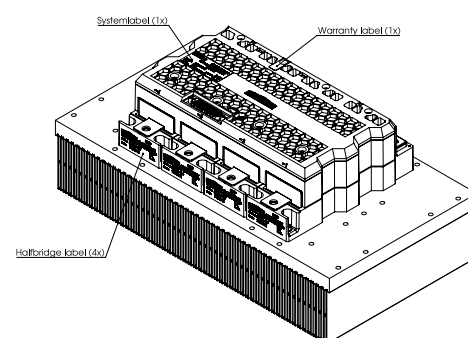
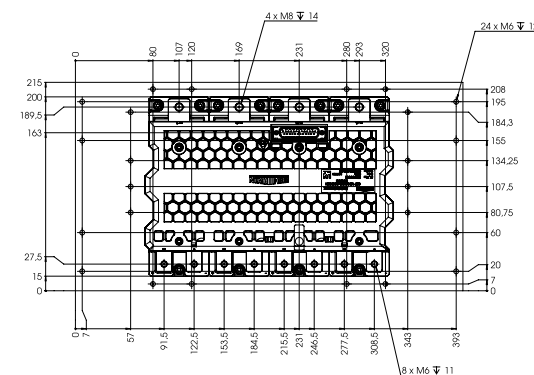


Weight without heat sink:	4,84 kg
P4016:	9,9 kg

Package S 44 mounted on P4016 heat sink with 90° rotated fins



All dimensions in mm



Weight without heat sink:	3,22 kg
P4016:	8,5 kg

Dimensions in mm

IPM / SKiïP Accessories

Type

F-Option SKiiP3

SKiiP3 F-Option	Fiber optic control board for SKiiP3
------------------------	--------------------------------------

F-Option SKiiP4

SKiiP4 F-Option	Fiber optic control board for SKiiP4
SKiiP4 F-Option with D-Sub connector	Fiber optic control board for SKiiP4

SKiiP3 Parallel Board

SKiiP3 Parallel Board 4-fold	Board for paralleling of 4 SKiiP3, F-Option usage possible
SKiiP3 Parallel Board 3-fold	Board for paralleling of 3 SKiiP3, F-Option usage possible
SKiiP3 Parallel Board 2-fold	Board for paralleling of 2 SKiiP3, F-Option usage possible

SKiiP4 Parallel Board

SKiiP4 Parallel Board 4-fold without F-Option	Board for paralleling of 4 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 4-fold F-Option	Board for paralleling of 4 SKiiP4, F-Option usage possible
SKiiP4 Parallel Board 3-fold without F-Option	Board for paralleling of 3 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 3-fold F-Option	Board for paralleling of 3 SKiiP4, F-Option usage possible
SKiiP4 Parallel Board 2-fold without F-Option	Board for paralleling of 2 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 2-fold F-Option	Board for paralleling of 2 SKiiP4, F-Option usage possible

SKiFace Adapter Board

SKiiP4 SKiFace Adapter UZK	Adapter board to connect SKiiP4 to SKiiP3 controller with DC-Link voltage measurement function
SKiiP4 SKiFace Adapter Temp	Adapter board to connect SKiiP4 to SKiiP3 controller with temperatur measurement function

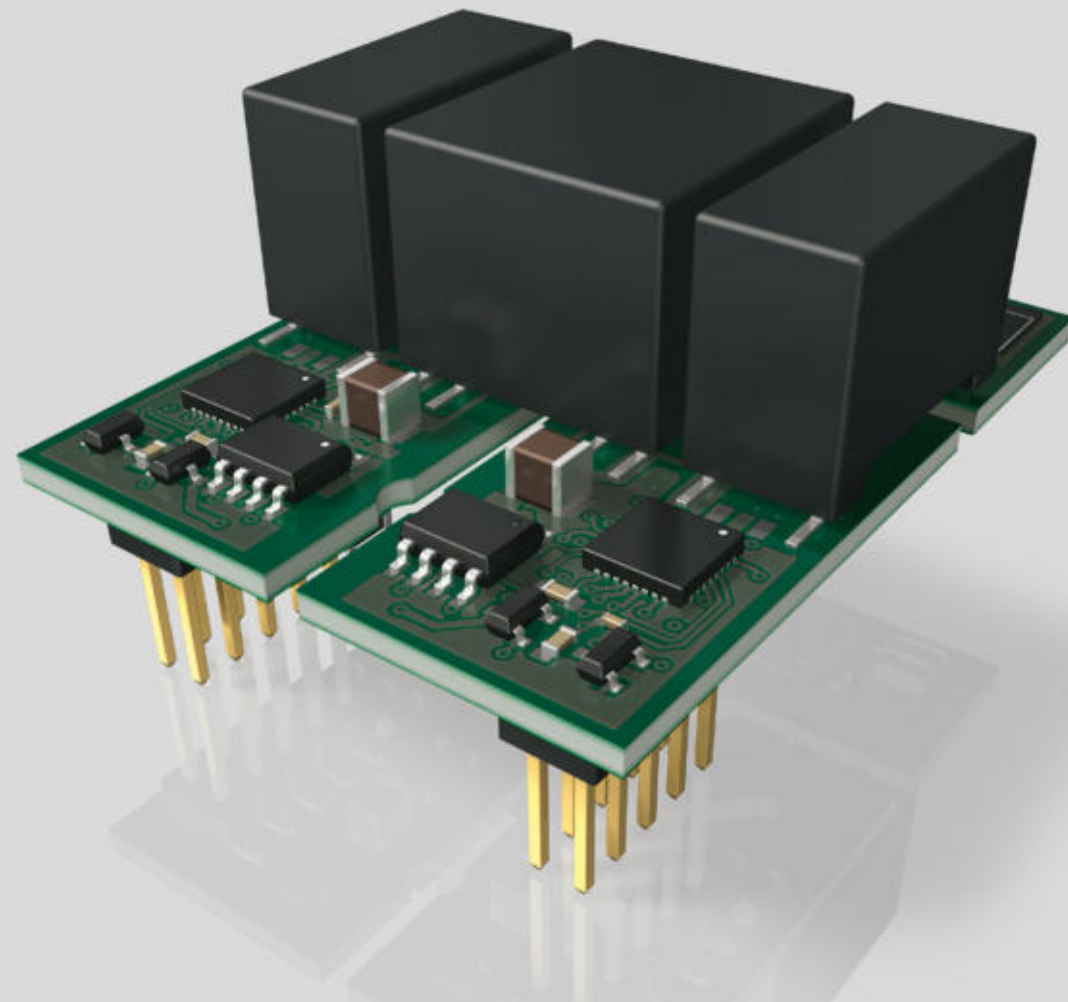
IGBT Drivers

PAGE

SKYPER 156

3

Driver Cores Plug & Play Drivers Adapter Boards



Drives 3 Times Longer

SKYPER[®]

Short facts

MTBF rate of 5×10^6 hours (29500) with new SEMIKRON ASIC chipset

Safe gate control with separate signal transmission

7kV burst durability thanks to interlayer connection and metal pad ASICs

Key features

Two driver channels for IGBT single and half-bridges

For 600V, 1200V and 1700V IGBT modules

Driving up to 2500A

Short pulse suppression and EMC cage

SoftOff and separate error channels

Adjustable filter and failure management

Customized adapter boards on request

Applications

SKYPER 12 PV R is the latest driver core which delivers 20A output peak current and allows for operation at 1500VDC in an unrivalled compact design. Its features and the robustness make it perfect for use in solar applications. The SKYPER 12 PF is a plug & play driver solution based on the same platform, allowing solutions without adapter board for 17mm modules and direct press-fit mounting. SKYPER 42 LJ offers the benefits of digital signal consistency while maintaining full performance. Ambitious applications such as medical technology or large drives of up to 500kW are powered reliably and safely. SKYPER 32 is the perfect solution for industrial drives and process control applications. SKYPER 42 meets the requirements of induction heating / welding applications that call for high currents, durable solar inverters and motor drives between 500kW and 1.5MW. The new plug & play driver SKYPER Prime and Prime O is the best match for high power with SEMITRANS 10 modules for up to 1700V and 1800A.

Benefits

The high integration level of SEMIKRON's new ASIC chipset provides safe IGBT gate control throughout the entire lifecycle. Short circuits are managed quickly by separate error channels. SoftOff and over voltage feedback help prevent dangerous overvoltages. The mixed signal ASICs guarantee minimum tolerances across the full temperature range. NPC or paralleled IGBT topologies are managed by adjustable error handling. With an optimised interface and the adjustable filter setting, the SKYPER IGBT driver family survives external interference over 100% of IEC standards.

Product range

The SKYPER drivers are available as IGBT driver cores and plug & play drivers. The SKYPER platform can drive 600V, 1200V and 1700V IGBT modules. SKYPER 32 uses a standard and a PRO version 1W per channel. The PRO version has additional protection features such as external failure inputs and SoftOff. The SKYPER 42 has 4W per channel and can drive up to 2500A IGBTs. The SKYPER 42LJ has 3W per channel, closing the gap between SKYPER 32 and 42. The driver core SKYPER 12 R and the two qualified plug & play drivers, SKYPER 12 press-fit and SKYPER Prime, offer maximum performance when using SEMiX press-fit or SEMITRANS 10 modules.

Further information: www.semikron.com/skyper

IGBT Driver

SEMIKRON IGBT Driver Family

SEMIKRON offers two different IGBT driver families for any application. Driver cores from the SKHI and SKYPER family can be optimised using adapter boards for each module type. Drivers such as the SKYPER Prime offer a fully qualified plug & play solution, saving time and costs in application. The SKYPER family with 1W to 4W output power per channel covers the entire range of inverters from 30kW to 2MW. The high integration level of SEMIKRON's new ASIC chipset ensures safe IGBT gate control throughout the entire lifecycle. Short topologies are managed very fast by separate error channels.

SoftOff and over voltage feedback prevent dangerous over voltages. The mixed signal ASICs guarantee minimum tolerances over the full temperature range. NPC or paralleled IGBT topologies are managed thanks to adjustable error management. With an optimised interface and adjustable filter settings, the SKYPER family operates safely in noisy environments. The SEMIKRON adapter boards enable a wide range of inverter platforms to be built using various types of IGBT modules.

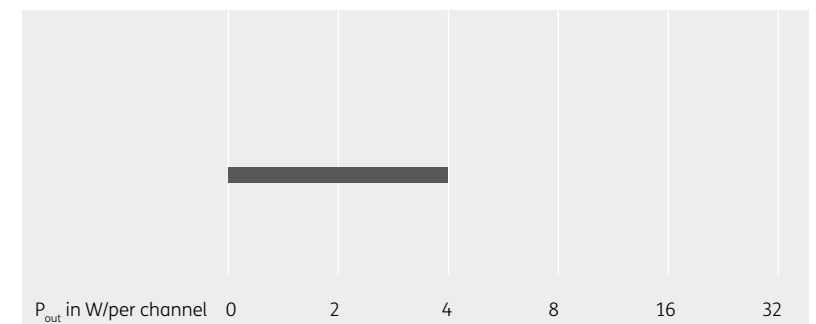
The latest highlights are the SKYPER 12 driver core and the plug & play driver SKYPER Prime that features electrical and optical interfaces. SKYPER 12 PV R is the latest driver core which delivers 20A output peak current and allows for operation at 1500VDC in an unrivalled compact design. Its features and the robustness makes it perfect for use in solar applications. The SKYPER Prime offers integrated insulated DC link and temperature measurement and can help customers reduce system costs significantly.

SKYPER® & SKHI

Driver Cores

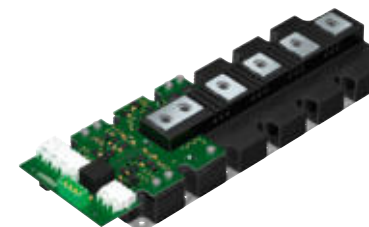


Up to 1700V

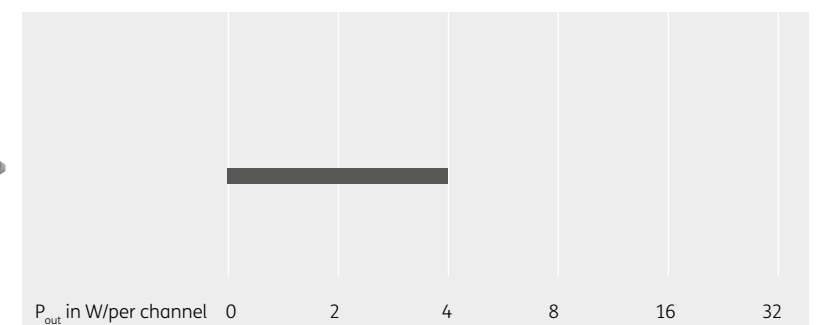


SKYPER®

Plug & Play Driver

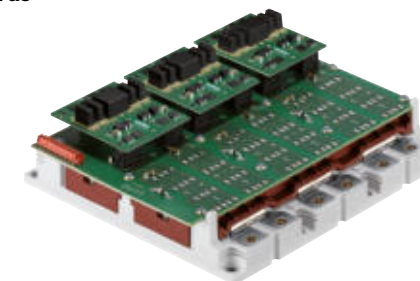


600V up to 1700V

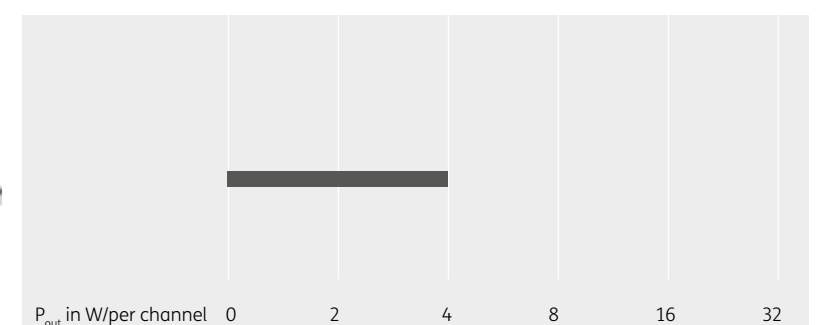


SKYPER® & SKHI

Adapter Boards



Up to 1700V



IGBT Driver

Type									
	Channels	V _{CE} V	V _{G(on)} V	V _{G(off)} V	I _{outPEAK} A	Q _{out/pulse} µC	f _{max} kHz	VisolIO kV	dv/dt kV/µs
Driver									
SKHI 10/12 R	1	1200	15	-8	8	9.6	100	2500	75
SKHI 10/17 R	1	1700	15	-8	8	9.6	100	4000	75
SKHI 23/12 R	2	1200	15	-8	8	4.8	100	2500	75
SKHI 23/17 R	2	1700	15	-8	8	4.8	100	4000	75
SKHIT 01 R ⁷⁾	3	528	-	-	-	-	10	2500	-
SKYPER 12 press-fit 300A	2	1200	15	-11.3	15	8	20	4000	50
SKYPER 12 press-fit 450A	2	1200	15	-11.3	15	8	13	4000	50
SKYPER 12 press-fit 600A	2	1200	15	-11.3	15	8	10	4000	50
SKYPER 12 press-fit C 300A	2	1200	15	-11.3	15	8	20	4000	50
SKYPER 12 press-fit C 450A	2	1200	15	-11.3	15	8	13	4000	50
SKYPER 12 press-fit C 600A	2	1200	15	-11.3	15	8	10	4000	50
SKYPER 12 press-fit 450A 1700V	2	1700	15	-11.3	15	8	9	4000	50
SKYPER 12 press-fit 600A 1700V	2	1700	15	-11.3	15	8	7	4000	50
SKYPER 12 press-fit C 450A 1700V	2	1700	15	-11.3	15	8	9	4000	50
SKYPER 12 press-fit C 600A 1700V	2	1700	15	-11.3	15	8	7	4000	50
SKYPER PRIME 1000A / 1700V PP ²⁾	2	1700	15	-8	15	10	10	5000	50
SKYPER PRIME 1000A / 1700V ST10 ²⁾	2	1700	15	-8	15	7	10	5000	50
SKYPER PRIME 1400A / 1700V PP ²⁾	2	1700	15	-8	15	13.5	7	5000	50
SKYPER PRIME 1400A / 1700V ST10 ²⁾	2	1700	15	-8	15	10	10	5000	50
SKYPER PRIME 1400A / 1200V PP ²⁾	2	1200	15	-8	15	10	10	5000	50
SKYPER PRIME 1400A / 1200V ST10 ²⁾	2	1200	15	-8	15	7.5	10	5000	50
SKYPER PRIME O 1400A / 1200V PP ²⁾	2	1200	15	-8	15	10	10	5000	50
SKYPER PRIME O 1400A / 1200V ST10 ²⁾	2	1200	15	-8	15	7.5	10	5000	50
SKYPER PRIME O 1400A / 1700V PP ²⁾	2	1700	15	-8	15	13.5	7.4	5000	50
SKYPER PRIME O 1400A / 1700V ST10 ²⁾	2	1700	15	-8	15	10	10	5000	50
Driver Core									
SKHI 21A R ⁸⁾	2	1200	15	0	8	4	50	2500	50
SKHI 22 A/B H4 R	2	1700	15	-7	8	4	50	4000	50
SKHI 24 R	2	1700	15	-8	15	5	50	4000	50
SKHI 61 R ⁴⁾	6	900	15	-7	2	1	50	2500	15
SKHI 71 R ⁴⁾	7	900	15	-7	2	1	50	2500	15
SKYPER 12 R ²⁾	2	1700	15	-9	20	20	100	5000	50
SKYPER 12 PV R ²⁾	2	1700	15.4	-9.5	20	20	100	5000	50
SKYPER 32 R	2	1700	15	-7	15	2.5	50	4000	50
SKYPER 32 PRO R	2	1700	15	-7	15	6.3	50	4000	50
SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
SKYPER 42 R/O2 (coated) ²⁾	2	1700	15	-8	30	50	100	4000	100
SKYPER 42 LJ R	2	1700	14.8	-8	24	20	100	4000	100
SKYPER 42 LJ R (coated) ²⁾	2	1700	14.8	-8	24	20	100	4000	100
Adapter Board									
Board 1 SKYPER 32 R	2	1700	15	-7	15	2.5	50	4000	50
Board 1 SKYPER 32PRO R	2	1700	15	-7	15	6.3	50	4000	50
Board 2 // 4S SKYPER 42 R	2	1200	15	-8	30	50	100	4000	100
Board 2 generic SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 2//3S SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 2S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 2S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 3S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 3S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 4S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 4S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 63 GB SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 93 GB SKYPER 42 R ²⁾	2	1700	15	-8	30	50	100	4000	100

Footnotes: 2) In production new / 4) Discontinued / 7) Thyristor Driver / 8) MOSFET Driver

Stacks

	PAGE
Water-Cooled IGBT	164
Air-Cooled IGBT	166
Diode/Thyristor	168
Customized	170

4

SEMISTACK® RE
SKiiPRACK®



AC | DC



IGBT Platforms up to 6MVA Standards for Water-Cooled Inverter

Water-Cooled IGBT STACKS

Short facts

Off-the-shelf product range

2 and 4-quadrant 3-phase converter

IGBT inverter power density of up to 10.4kVA/L

Long life expectancy

Key features

Maximum continuous output current from 600A to 1400A_{RMS}

DC bus voltage of up to 1250V_{DC}

Inverter output voltage of up to 690V_{AC}

DC bus polypropylene capacitor bank lifetime rates at 100,000 hours at 40°C

Analogue measurements for T_{heatsink} , V_{bus} , I_{out}

CAN interface (configuration & monitoring)

Applications

The SEMISTACK platforms comply with wind turbine requirements, making it possible to build 4-quadrant converters that are suitable for use with synchronous generators and double fed induction generators, with an optional brake chopper design. The platform flexibility allows for the requirements of solar central inverters to be met with a continuous DC bus voltage of up to 900V_{DC}. Alternatively, SEMISTACK platforms can be used in low-voltage applications requiring high power and a high degree of reliability, such as 3-phase inverters in a shipyard or in a battery energy storage unit installed close to renewable energy power plants.

Benefits

The SEMISTACK water-cooled platforms offer a pre-qualified power assembly ready for integration following rigorous

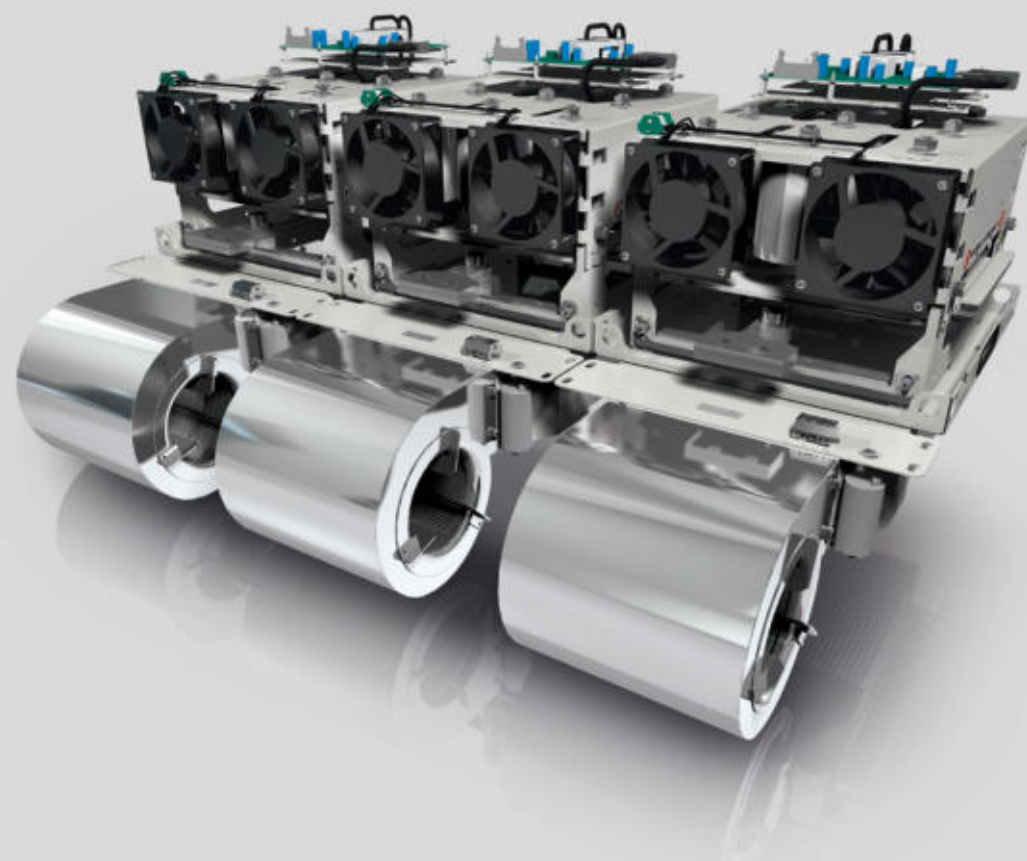
SEMIKRON qualification tests and the latest environmental standards (IEC 60721-3). The platform design has been optimised to achieve the ideal balance between costs and performance for a water-cooled power inverter in the megawatt power range. They are designed for applications requiring a high degree of reliability and a long service life of up to 20 years. The design and footprint enables compact integration into standard industrial cabinets, making high power of up to 6MVA low-voltage possible. Specified for wind turbine applications, the SEMISTACK family boasts excellent IGBT cycling capability and a high capacitor bank lifetime, reducing maintenance requirements.

Product range

The SEMISTACK water-cooled platform offers various inverter sizes to fit two power sub-assemblies into a 600 x 600 x 2000mm cabinet. The standard size has a current range between 1000A and 1400A_{RMS}. For applications with lower current ratings or with tighter cabinet size constraints, a smaller inverter size is available with a continuous output current rated for up to 900A_{RMS}. The SEMISTACKs embed the SKiiP IPM product family, which in turn integrates IGBT gate driver and monitors analogue outputs (temperature, output current and DC bus voltage). As an option, a CAN interface is also available to monitor the SKiiP. To increase power capacity up to 6MVA, SEMISTACKs can be put in parallel, connected together through the DC bus and controlled all-in-one using a SEMIKRON paralleling board. Optionally, SEMISTACK platforms are also available integrated into an industrial cabinet with suitable AC and/or DC power filters, electrical and hydraulic distribution systems.

Further information: www.semikron.com/water-cooled-igbt-stacks

SEMIKUBE® SEMIKUBE® SlimLine SEMIKUBE® 1500V



AC | DC

IGBT Converter Family up to 1MVA Standards for Air-Cooled Inverter

Air-Cooled IGBT

STACKS

Short facts

Off-the shelf product range
Air-cooled power assemblies
Maximum output current from 150A to 1500A
Customizable

Key features

Frame sizes ranging from 75kVA up to 1500kVA
AC output voltage of up to 690V_{AC}
Current measurement accuracy <1%
Analogue measurements or CAN monitoring for T_{heatsink} , V_{bus} , I_{out}
Forced-air cooled platform
For 300mm cabinet
UL1741 1500V ready

Applications

The SEMIKUBE platform is optimised for general-purpose inverters and central solar inverters. Designed for the most commonly used PV central inverter ratings on the market, i.e. 500kW, 670kW up to as much as 1200kW, the SEMIKUBE 3-phase inverter operates at up to 1500V_{DC} bus voltage. Designed in accordance with IEC 62109, the platform is set to obtain UL recognition. The SEMIKUBE family complies with most AC drives application requirements. The current measurement precision of 1% (at 25°C) allows for premium motor control as required in highly dynamic applications and motion control systems.

Benefits

The SEMIKUBE platform is a family of pre-qualified power assemblies which are in line with the rigorous SEMIKRON qualification tests and certifications. The platform integrates advanced technologies which maximize performance and power density. SEMIKUBE, thanks to its modular design and patented DC connections, allows for designs in various converter power ranges.

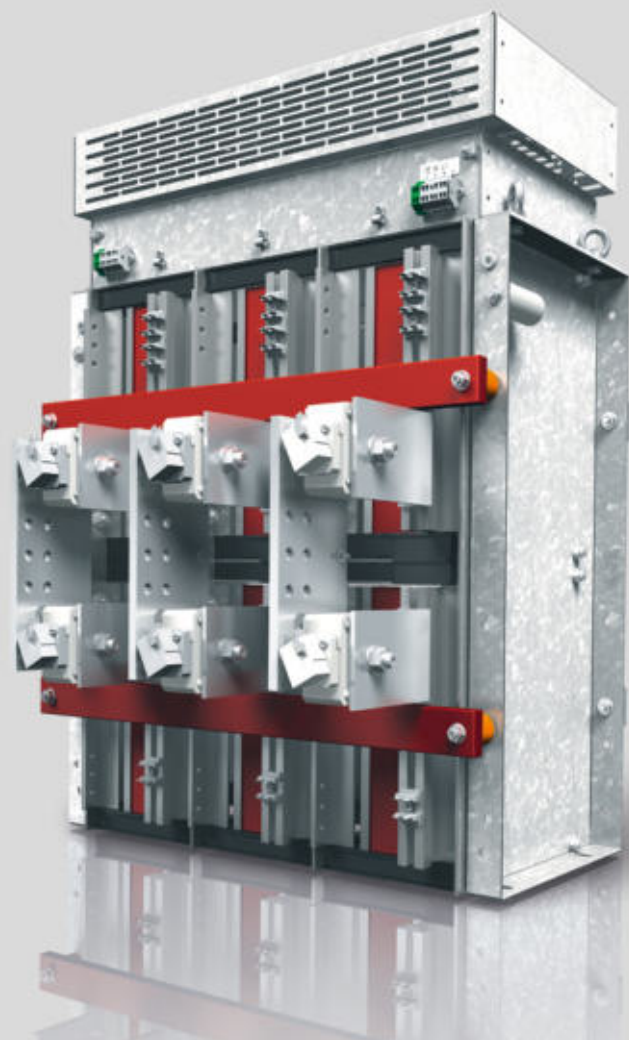
Product range

The SEMIKUBE platform comes in four frame sizes for continuous rated currents ranging from 150A to 1500A and features SEMITRANS 1200V and 1700V IGBT Trench E4 modules. The SEMIKUBE design is optimised for 3-phase inverter topologies. A dedicated rectifier with 3-phase inverter and optional brake chopper can be added. The IGBTs are controlled by a SEMIKRON embedded driver for error management, and analogue outputs for current, DC voltage and heatsink temperature. For the SEMIKUBE SlimLine a CAN interface is available for parameter configuration and diagnostics monitoring. Air cooling is provided by highly efficient long-life axial and radial fans, achieving maximum power within a compact package. SEMIKUBE is a versatile product, allowing for converter designs around a common DC link, including four quadrant converters, multiphase converters and a 1500V inverter for central solar power systems. Thanks to its optimised layout, the platform integrates state-of-the-art hybrid SiC and full SiC modules, extending the SEMIKUBE Slimline portfolio.

Further information: www.semikron.com/air-cooled-igbt-stacks



SEMISTACK® CLASSIC B6U
SEMISTACK® CLASSIC B6C
SEMISTACK® CLASSIC W3C



Rectifier Stacks Standards for LV Diode/Thyristor Rectifiers

Diode/Thyristor STACKS

Short facts

Off-the shelf product range
Air-cooled power assemblies
Ready for integration
Customizable

Key features

Various topologies (B6U, B6C, B2C, B2U, W3C, W1C)
Maximum continuous DC Current from 60A to 4015A
Rectifier AC voltage of up to 500V_{AC}
DC bus voltage of up to 670V_{DC}
RC, fuses, cooling fans and thermal switches

Applications

The SEMISTACK CLASSIC product range is designed for fast integration of industrial rectifiers. Each power bridge has been sized to embed semiconductors with a suitable RC commutation topology, proper AC fuses and cooling devices. The high rectifier power range has been improved using a new heatsink profile, resulting in modularity, various fan options, low maintenance and weight reductions.

Benefits

The SEMISTACK CLASSIC family offers a pre-qualified power assembly ready for integration in line with rigorous SEMIKRON qualification tests and current environmental standards. The platform design has been optimised to achieve the best balance between costs and performance for power inverters and rectifiers right up to the megawatt range.

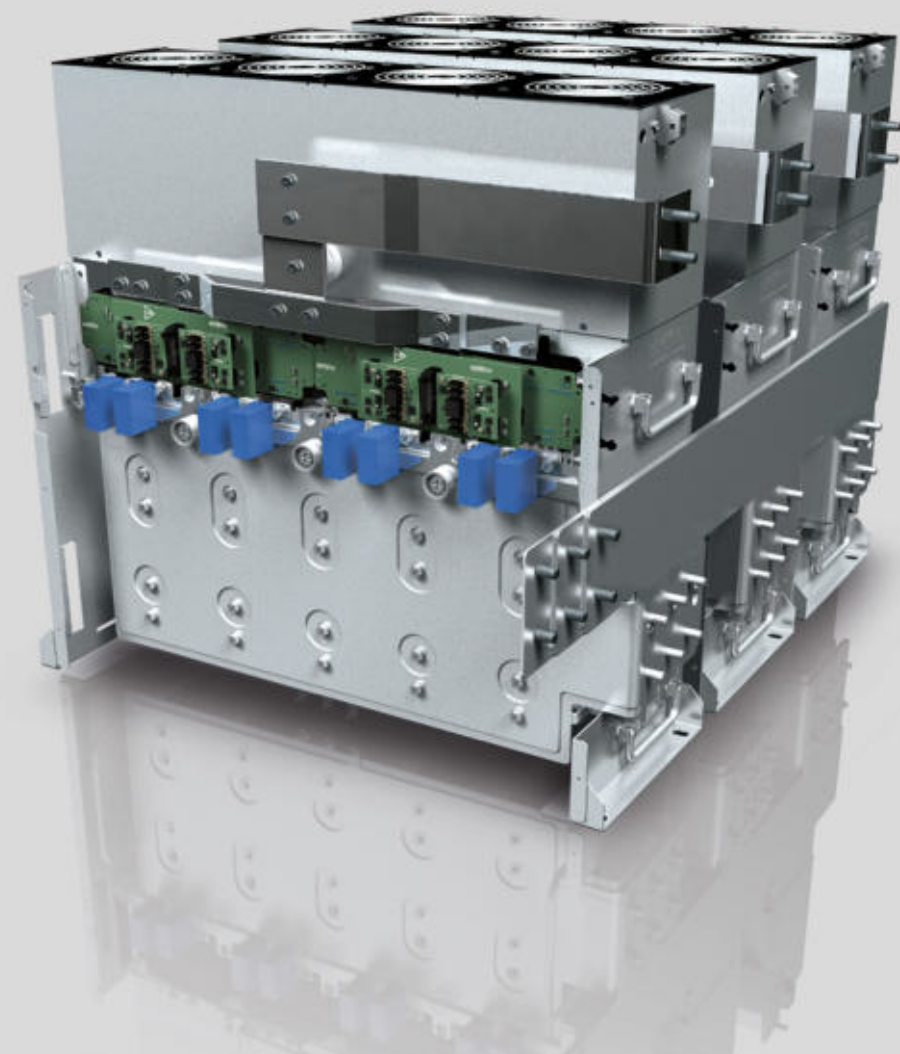
Product range

The SEMISTACK family consists of a broad portfolio of over 200 stacks with different topologies of uncontrolled, half-controlled and fully controlled rectifiers. These products are available with natural or forced cooling, with or without fuses. All SEMISTACK Classics include RC protection circuitry and are optimised for fast cabinet integration.

Further information: www.semikron.com/diode-thyristor-stacks



SEMISTACK® Application



Customized Power Electronic Stacks Create the Standard for Your Inverter

Customized STACKS

Short facts

45 years of experience in stack design, manufacture and service
Global market leader in power electronic stacks
7 local engineering & production locations for direct and fast communication
More than 200,000 stacks already in the field
1,500 different assemblies available
Air and water-cooled power assemblies

Outsource design and manufacturing to:

Focus on your core competencies
Reduce production fluctuations
Benefit from economy of scale
Cut design, assembly and production costs
Reduce your risks

Applications

SEMIKRON provides custom stacks to the world's leading electric industries, ranging from simple press-fit diode plates for battery chargers or welding equipment, to thyristor and IGBT industrial drives, complex high-power four-quadrant inverters for wind energy generation, and IGBT converters for main traction drives in railway applications. SEMIKRON has experience in many different applications each with their specific constraints. This extensive knowledge ensures a robust and reliable design.

Benefits

If our platforms and/or standard stacks do not suit the customer requirements, our stack center can always offer a 100% customized turn-key solution. Our unparalleled experience in the stack business coupled with direct access to our core semiconductor and driver technology enables us to provide highly efficient, cost effective designs to meet every customer need. We encourage exchange and transfers between the stack centers and transform local success into global competence. Thanks to this internal information exchange, you get an optimised, pre-qualified and field-tested stack in the shortest possible time.

Product range

SEMIKRON designs, builds and tests customized stacks based on your needs. With our long-term experience and successful track record, we are the global market leader in stack design and production. With our vast portfolio of standard stacks we deliver short lead times while adapting the stacks to your requirements. SEMIKRON continuously develops new stack assemblies with the latest materials, topologies and technologies in order to guarantee our customers up-to-date products for a short time-to-market. Semikron offers full cycle cooperation from the product concept stage to mass delivery and beyond for repairs & aftermarket services. Costs and delivery times are kept to the minimum. Our R&D departments continuously focus on designing re-useable standard sub-assemblies in our SEMISTACKS. As an example, the SEMIKUBE platform is the result of 45 years of experience in the stacks business and with more than 75,000 SEMIKUBEs in the field, the most successful stack to date.

Stack Platforms – Fully Qualified Inverter Assemblies Tailored to Your Specific Needs

In addition to standard semiconductor components, SEMIKRON has developed a full range of power converter assemblies. Stack center application engineers are available to offer specific power solutions by adapting existing platforms or designing customized converters.

SEMISTACK RE	174
SKiiPRACK	176
SEMIKUBE	177
SEMIKUBE SlimLine	178
SEMISTACK CLASSICS	179

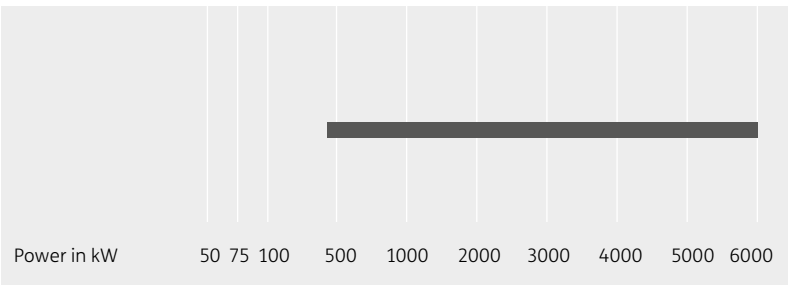
For detailed information please refer to data sheets.

Further information: www.semikron.com/stacks

Water-cooled IGBT

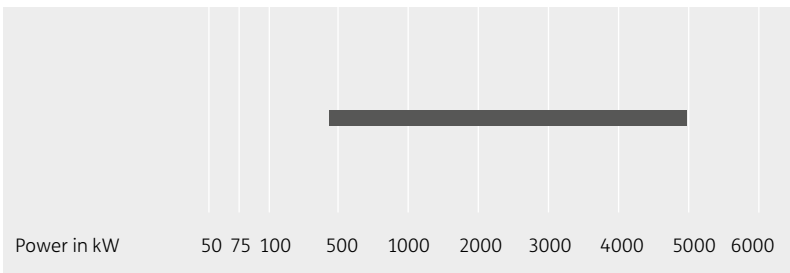
SEMISTACK®RE

- Synchronous wind generators
- Double-fed wind generators
- Solar inverters



SKiiPRACK®

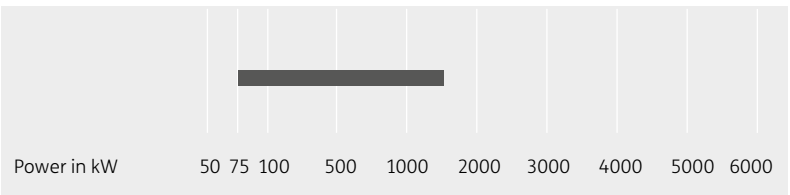
- Synchronous wind generators
- Double-fed wind generators
- High power AC drives



Air-cooled IGBT

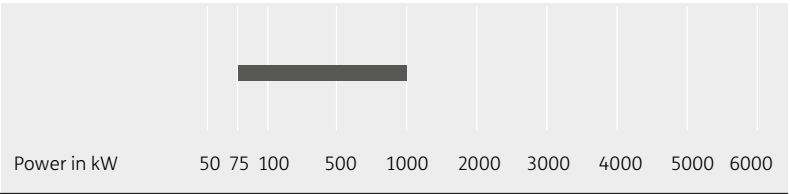
SEMIKUBE®

- Solar inverters
- Pump and compressor drives



SEMIKUBE® SlimLine

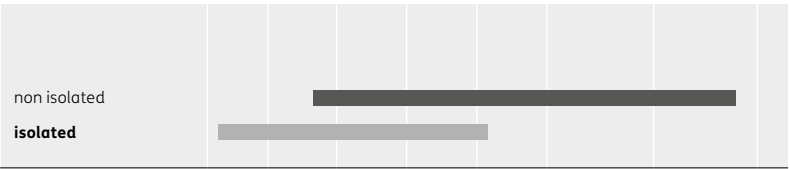
- Solar inverters
- AC drives and servos



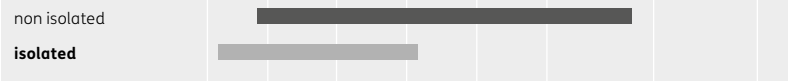
Diode/Thyristor

SEMISTACK®CLASSICS

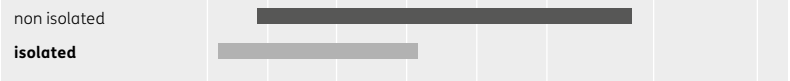
- B6U
3-phase uncontrolled rectifier



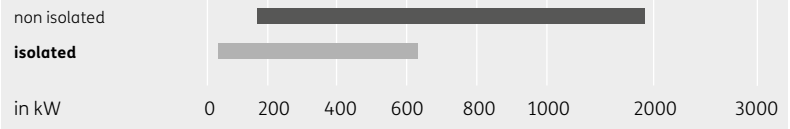
- B6HK
3-phase half controlled rectifier



- B6C
3-phase fully controlled rectifier



- W3C
3-phase reverse parallel thyristor converter



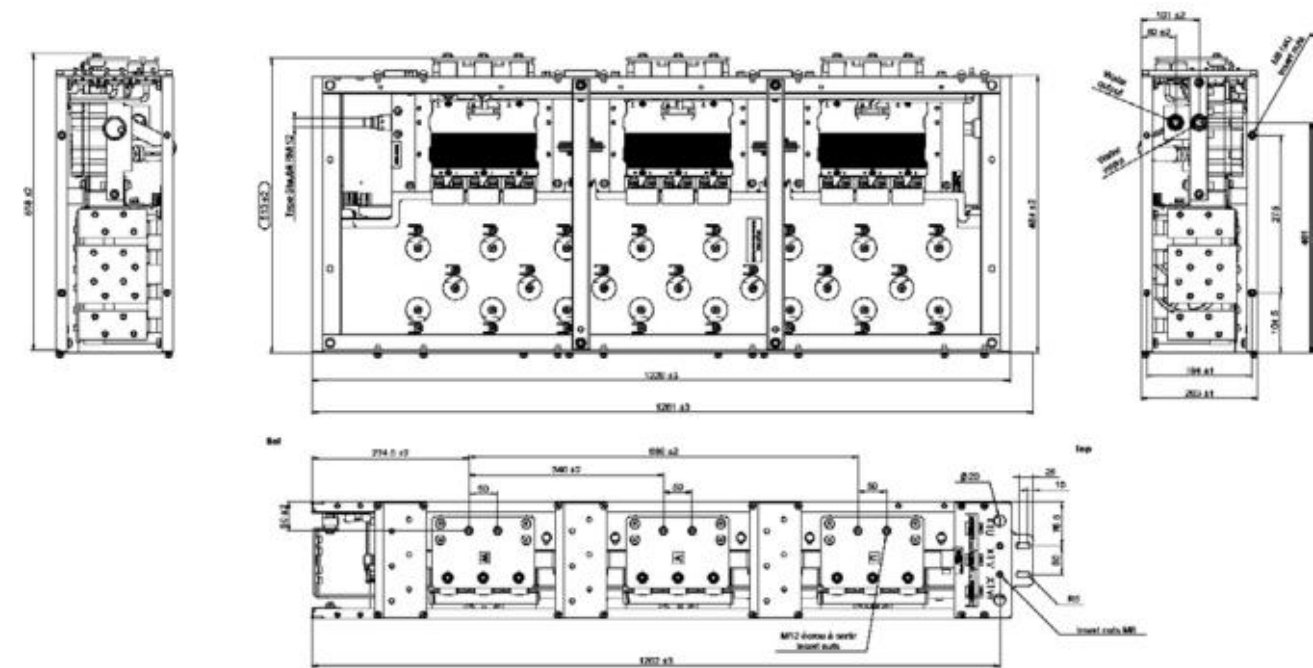
Stacks / SEMISTACK RE

Type								
	V _{Ac}	V _{Dc}	Current	Component Family	Cooling	Heatsink profile	Isolated	
	V	V	A					Topology
4-Quadrant converter								
SKS B2 120 GDD 69/11 - A11 MA PB	690	1100	1200	SKiiP 3	Water/Glycol	-	yes	
SKS B2 140 GDD 69/12 U - A11 MA PB	690	1250	1400	SKiiP 4	Water/Glycol	-	yes	
3-phase inverter								
SKS B1 090 GD 69/11 - MA PB	690	1100	900	SKiiP 3	Water/Glycol	-	yes	
SKS B2 100 GD 69/11 - MA PB	690	1100	1000	SKiiP 3	Water/Glycol	-	yes	
SKS B2 120 GD 69/11 - MA PB	690	1100	1200	SKiiP 3	Water/Glycol	-	yes	
SKS B2 140 GD 69/12 U - MA PB	690	1250	1400	SKiiP 4	Water/Glycol	-	yes	

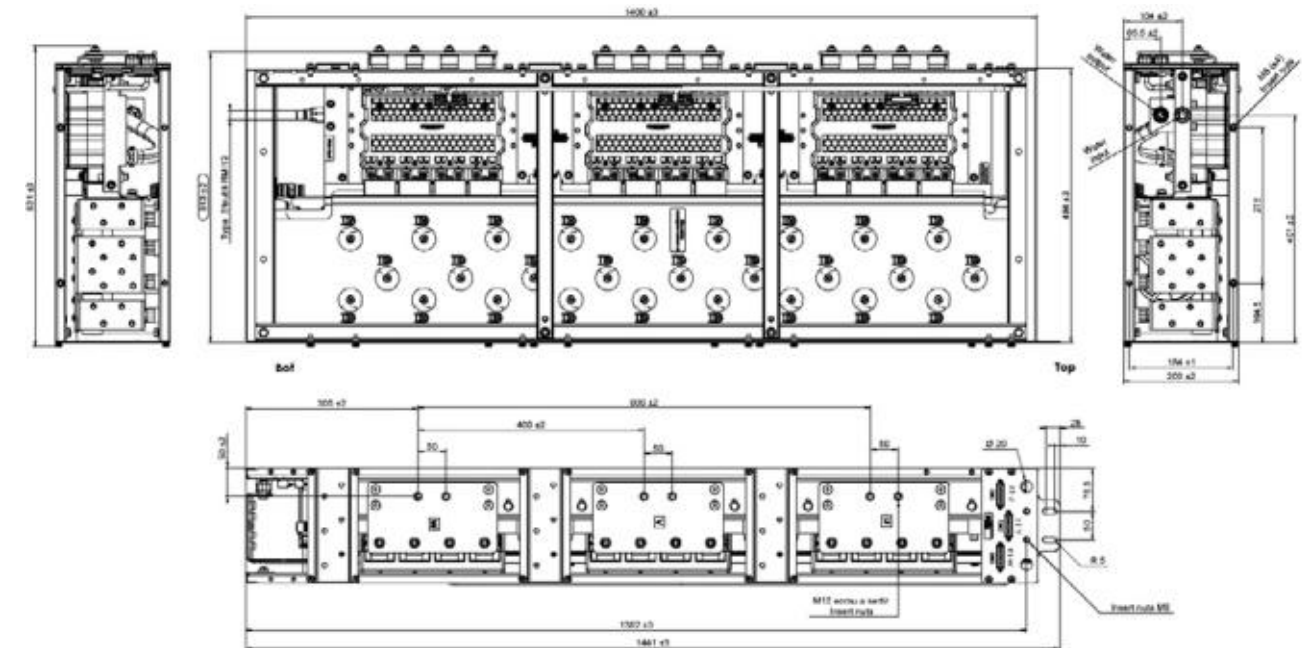
Stacks / SEMISTACK RE

Packages

SKS B1 090 GD 69/11 - MA PB



SKS B2 100 GD 69/11 - MA PB, SKS B2 120 GD 69/11 - MA PB, and SKS B2 140 GD 69/12 - MA PB



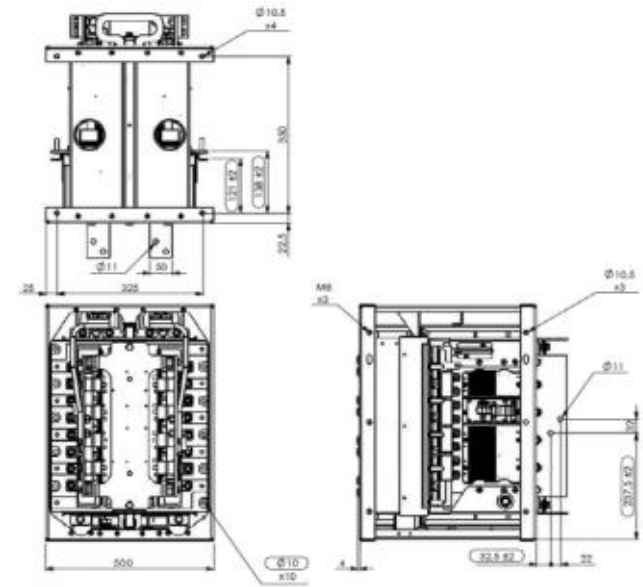
Dimensions in mm

Stacks / SKiiPRACK

Type									
	V _{Ac} V	V _{Dc} V	Current A	Component Family	Cooling	Heatsink profile	Isolated	Topology	
4-Quadrant converter									
SKS C 120 GDD 69/11 - A3A WA B1B	690	1100	1200	SKiiP 3	Water/Glycol	-	yes		
SKS C 240 GDD 69/11 - A6A MA B1C	690	1100	2400	SKiiP 3	Water/Glycol	-	yes		

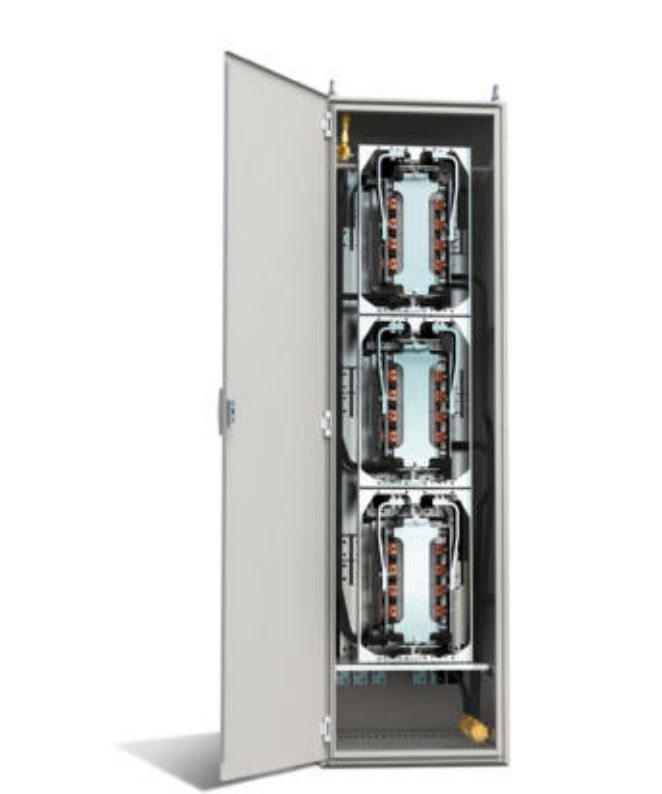
Packages

SKiiPRACK basic stack element, the CELL



Dimensions in mm

3-Cell vertical integration



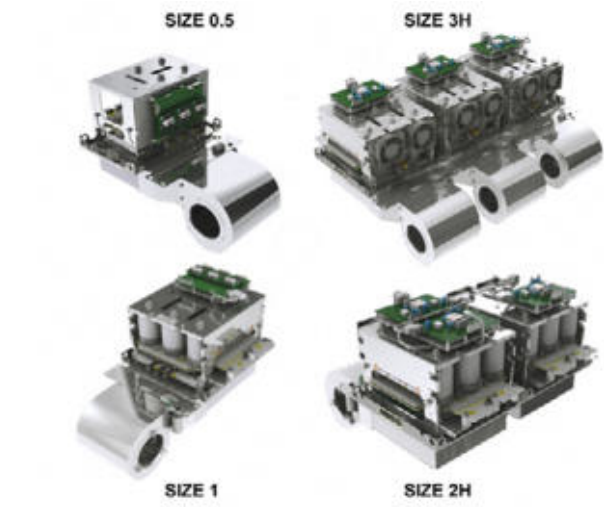
Stacks / SEMIKUBE

Type									
	V _{Ac} V	V _{Dc} V	Current A	Component Family	Cooling	Heatsink profile	Isolated	Topology	
3-phase inverter									
IGD-1-424-P1N4-DL-FA	460	900	200	SEMITRANS	Forced-air cooled	PX 308	yes		
IGD-2-424-P1N6-DH-FA	460	900	350	SEMITRANS	Forced-air cooled	PX 308	yes		
IGD-4-424-P1F7-BL-FA	460	900	750	SEMITRANS	Forced-air cooled	PX 308	yes		
IGD-8-326-E1F12-BH-FA	460	750	1230	SEMITRANS	Forced-air cooled	PX 308	yes		
IGD-8-426-E1F12-BH-FA	460	750	1470	SEMITRANS	Forced-air cooled	PX 308	yes		
IGD-8-424-P1F9-BH-FA	460	900	1470	SEMITRANS	Forced-air cooled	PX 308	yes		
IGD-8-474-P2F9-BI-FA 2)	690	1250	1300	SEMITRANS	Forced-air cooled	PX 308	yes		
3-phase rectifier and inverter									
IGDD6-1-326-D1616-E1N6-DL-FA	460	750	150	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes		
IGDD6-1-426-D1616-E1N6-DL-FA	460	750	180	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes		
IGDD6-2-326-D1616-E1F12-DH-FA	460	750	280	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes		
IGDD6-2-426-D1616-E1F12-DH-FA	460	750	330	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes		
IGDD6-4-326-D3816-E1F12-BL-FA	460	750	570	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes		
IGDD6-4-426-D3816-E1F12-BL-FA	460	750	680	SEMITRANS/SEMIPACK	Forced-air cooled	PX 308	yes		

Footnotes: 2) In production new

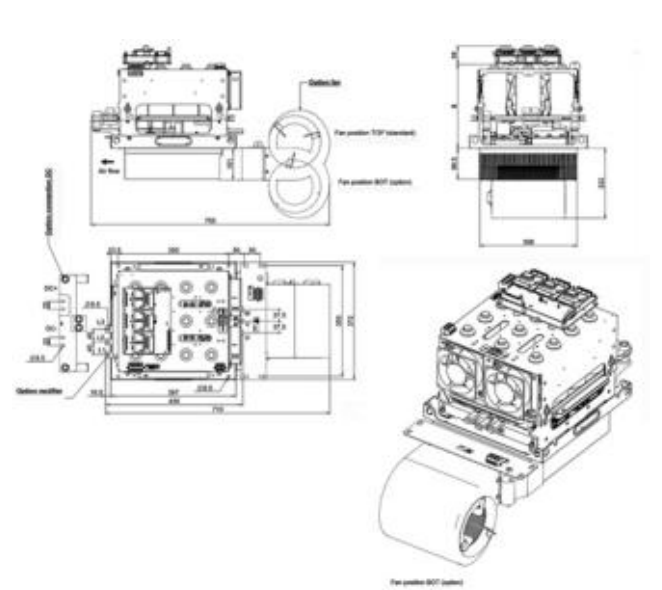
Packages

Frames



Dimensions in mm

Size 1



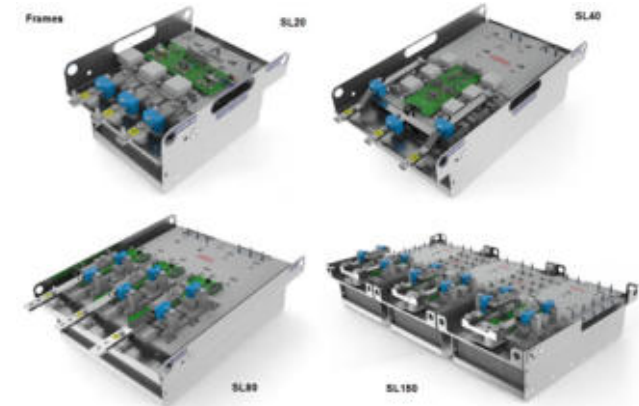
Stacks / SEMIKUBE SlimLine

Type								
	V _{Ac}	V _{Dc}	Current	Component Family	Cooling	Frame	Isolated	Topology
	V	V	A					
3-phase inverter								
SKS SL 20 GD 50/10 - E4 P1 G ²⁾	500	1000	230	SEMITRANS	Forced-air cooled	SL20	-	
SKS SL 40 GD 50/10 - E4 P1 G ²⁾	500	1000	440	SEMITRANS	Forced-air cooled	SL40	-	
SKS SL 80 GD 50/10 - E4 P1 G ²⁾	500	1000	750	SEMITRANS	Forced-air cooled	SL80	-	
SKS SL 150 GD 50/10 - E4 P1 G ²⁾	500	1000	1500	SEMITRANS	Forced-air cooled	SL150	-	
SKS SL 20 GD 50/10 - E4 P1 AF ²⁾	500	1000	230	SEMITRANS	Forced-air cooled	SL20	-	
SKS SL 40 GD 50/10 - E4 P1 AF ²⁾	500	1000	440	SEMITRANS	Forced-air cooled	SL40	-	
SKS SL 80 GD 50/10 - E4 P1 AF ²⁾	500	1000	750	SEMITRANS	Forced-air cooled	SL80	-	
SKS SL 150 GD 50/10 - E4 P1 AF ²⁾	500	1000	1500	SEMITRANS	Forced-air cooled	SL150	-	

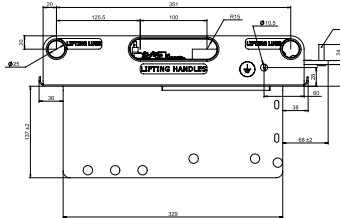
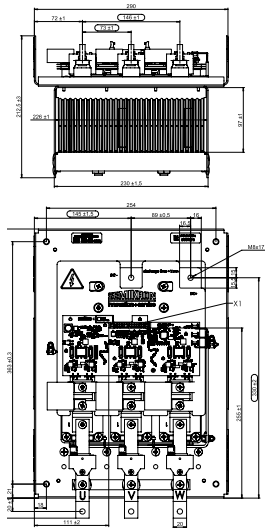
Footnotes: 2) In production new

Packages

Semikube SlimLine



SL 20



Dimensions in mm

Stacks / SEMISTACK CLASSICS

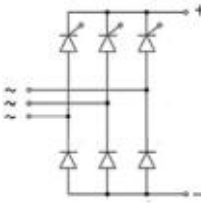
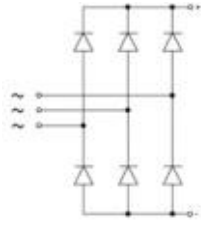
Type								
	V _{Ac}	V _{Dc}	DC Current	Component Family	Cooling	Heatsink profile	Isolated	Topology
	V	V	A					
3-phase fully-controlled thyristor bridge rectifier								
SKS 88N B6C 60 V16	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 88N B6C 60 V16 SU	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 180F B6C 120 V16	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 180F B6C 120 V16 SU	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 215N B6C 145 V16	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 215N B6C 145 V16 SU	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 250F B6C 170 V16	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 250F B6C 170 V16 SU	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 355N B6C 240 V16	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 355N B6C 240 V16 SU	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 365F B6C 245 V16	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 365F B6C 245 V16 SU	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 570F B6C 380 V16	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 570F B6C 380 V16 SU	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6C 430 V16	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6C 430 V16 SU	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 700N B6C 470 V16	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 700N B6C 470 V16 SU	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 845N B6C 570 V16	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 845N B6C 570 V16 SU	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 970F B6C 650 V16	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 970F B6C 650 V16 SU	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1000N B6C 670 V16	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1000N B6C 670 V16 SU	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1200F B6C 800 V16	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1200F B6C 800 V16 SU	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6C 1010 V16	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6C 1010 V16 SU	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1890F B6C 1270 V16	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 1890F B6C 1270 V16 ZU	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 2580F B6C 1730 V16	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
SKS 2580F B6C 1730 V16 ZU	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
SKSE 2580F B6C 1730 V16 ²⁾	500	670	2580	Capsules	Forced-air cooled	Z5/120	no	
SKSE 2580F B6C 1730 V16 ZU ²⁾	500	670	2580	Capsules	Forced-air cooled	Z5/120	no	
SKSE 1890F B6C 1270 V16 ZU ²⁾	500	670	1890	Capsules	Forced-air cooled	Z5/90	no	
SKSE 1890F B6C 1270 V16 ²⁾	500	670	1890	Capsules	Forced-air cooled	Z5/90	no	
SKSE 1500F B6C 1010 V16 SU ²⁾	500	670	1500	Capsules	Forced-air cooled	Z5/60	no	
SKSE 1500F B6C 1010 V16 ²⁾	500	670	1500	Capsules	Forced-air cooled	Z5/60	no	
SKSE 1200F B6C 800 V16 SU ²⁾	500	670	1200	Capsules	Forced-air cooled	Z5/60	no	
SKSE 1200F B6C 800 V16 ²⁾	500	670	1200	Capsules	Forced-air cooled	Z5/60	no	

3-phase half-controlled bridge rectifier

SKS 88N B6HK 60 V16	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 88N B6HK 60 V16 SU	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 180F B6HK 120 V16	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 180F B6HK 120 V16 SU	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 215N B6HK 145 V16	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 215N B6HK 145 V16 SU	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 250F B6HK 170 V16	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 250F B6HK 170 V16 SU	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 355N B6HK 240 V16	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 355N B6HK 240 V16 SU	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 365F B6HK 245 V16	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 365F B6HK 245 V16 SU	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 570F B6HK 380 V16	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 570F B6HK 380 V16 SU	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	

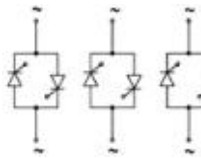
Footnotes: 2) In production new

Stacks / SEMISTACK CLASSICS

Type								Topology
	V _{Ac}	V _{Dc}	DC Current	Component Family	Cooling	Heatsink profile	Isolated	
	V	V	A					
3-phase half-controlled bridge rectifier								
SKS 640F B6HK 430 V16	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6HK 430 V16 SU	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 700N B6HK 470 V16	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 700N B6HK 470 V16 SU	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 845N B6HK 570 V16	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 845N B6HK 570 V16 SU	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 970F B6HK 650 V16	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 970F B6HK 650 V16 SU	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1000N B6HK 670 V16	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1000N B6HK 670 V16 SU	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1200F B6HK 800 V16	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1200F B6HK 800 V16 SU	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6HK 1010 V16	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6HK 1010 V16 SU	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1890F B6HK 1270 V16	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 1890F B6HK 1270 V16 ZU	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 2580F B6HK 1730 V16	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
SKS 2580F B6HK 1730 V16 ZU	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
3-phase uncontrolled bridge rectifier								
SKS 91N B6U 60 V16	500	670	91	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 91N B6U 60 V16 SU	500	670	91	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 185F B6U 125 V16	500	670	185	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 185F B6U 125 V16 SU	500	670	185	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 290F B6U 195 V16	500	670	290	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 290F B6U 195 V16 SU	500	670	290	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 425N B6U 285 V16	500	670	425	Stud devices	Natural cooled	P1/150	no	
SKS 425N B6U 285 V16 SU	500	670	425	Stud devices	Natural cooled	P1/150	no	
SKS 430F B6U 290 V16	500	670	430	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 430F B6U 290 V16 SU	500	670	430	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 535N B6U 360 V16	500	670	535	Stud devices	Natural cooled	P1/200	no	
SKS 535N B6U 360 V16 SU	500	670	535	Stud devices	Natural cooled	P1/200	no	
SKS 660F B6U 440 V16	500	670	660	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 660F B6U 440 V16 SU	500	670	660	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 850F B6U 570 V16	500	670	850	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 850F B6U 570 V16 SU	500	670	850	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 1185N B6U 795 V16	500	670	1185	Capsules	Natural cooled	P11/415	no	
SKS 1185N B6U 795 V16 SU	500	670	1185	Capsules	Natural cooled	P11/415	no	
SKS 1220F B6U 820 V16	500	670	1220	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1220F B6U 820 V16 SU	500	670	1220	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1630N B6U 1090 V16	500	670	1630	Capsules	Natural cooled	U3/515	no	
SKS 1630N B6U 1090 V16 ZU	500	670	1630	Capsules	Natural cooled	U3/515	no	
SKS 1910N B6U 1280 V16	500	670	1910	Capsules	Natural cooled	U3/515	no	
SKS 1910N B6U 1280 V16 ZU	500	670	1910	Capsules	Natural cooled	U3/515	no	
SKS 1950F B6U 1305 V16	500	670	1950	Capsules	Forced-air cooled	P17/130	no	
SKS 1950F B6U 1305 V16 ZU	500	670	1950	Capsules	Forced-air cooled	P17/130	no	
SKS 2300F B6U 1540 V16	500	670	2300	Capsules	Forced-air cooled	P18/180	no	
SKS 2300F B6U 1540 V16 ZU	500	670	2300	Capsules	Forced-air cooled	P18/180	no	
SKS 4015F B6U 2690 V16	500	670	4015	Capsules	Forced-air cooled	N4/250	no	
SKSE 2300F B6U 1540 V16 ZU ²⁾	500	670	2300	Capsules	Forced-air cooled	Z5/120	no	
SKSE 2300F B6U 1540 V16 ²⁾	500	670	2300	Capsules	Forced-air cooled	Z5/120	no	
SKSE 1950F B6U 1305 V16 ZU ²⁾	500	670	1950	Capsules	Forced-air cooled	Z5/90	no	
SKSE 1950F B6U 1305 V16 ²⁾	500	670	1950	Capsules	Forced-air cooled	Z5/90	no	

Footnotes: 2) In production new

Stacks / SEMISTACK CLASSICS

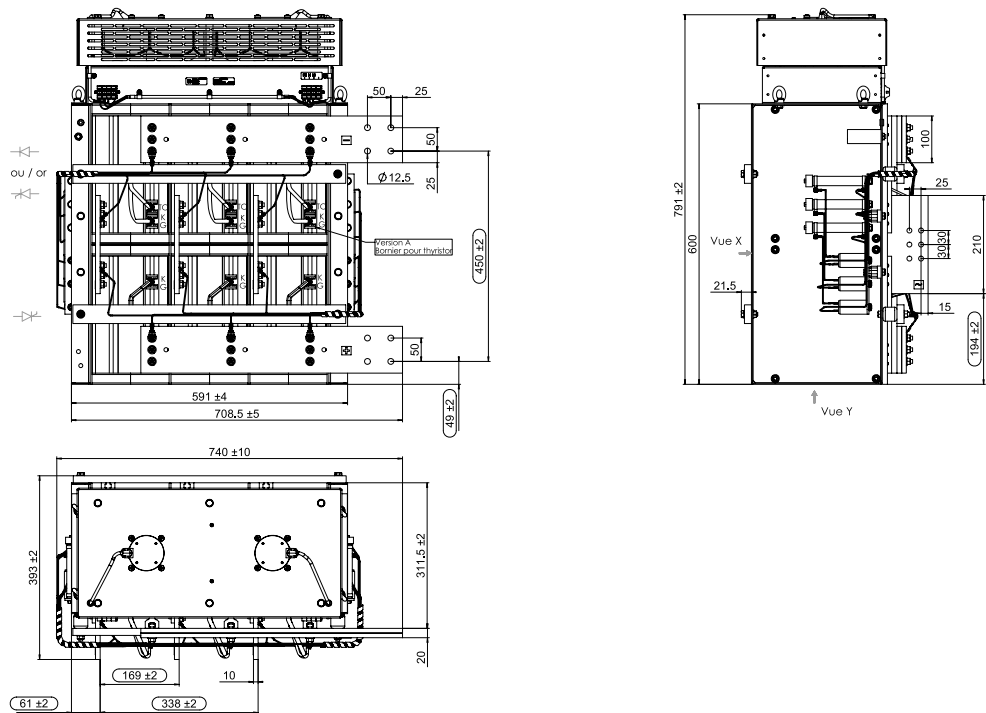
Type								Topology
	V _{Ac}	V _{Dc}	DC Current	Component Family	Cooling	Heatsink profile	Isolated	
	V	V	A					
3-phase reverse parallel thyristor converter								
SKS 67N W3C 60 V16	500	-	67	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 67N W3C 60 V16 SU	500	-	67	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 140F W3C 120 V16	500	-	140	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 140F W3C 120 V16 SU	500	-	140	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 170N W3C 150 V16	500	-	170	Stud devices	Natural cooled	P1/150	no	
SKS 170N W3C 150 V16 SU	500	-	170	Stud devices	Natural cooled	P1/150	no	
SKS 195F W3C 170 V16	500	-	195	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 195F W3C 170 V16 SU	500	-	195	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 275N W3C 240 V16	500	-	275	Stud devices	Natural cooled	P1/200	no	
SKS 275N W3C 240 V16 SU	500	-	275	Stud devices	Natural cooled	P1/200	no	
SKS 290F W3C 250 V16	500	-	290	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 290F W3C 250 V16 SU	500	-	290	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 450F W3C 390 V16	500	-	450	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 450F W3C 390 V16 SU	500	-	450	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 520F W3C 450 V16	500	-	520	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 520F W3C 450 V16 SU	500	-	520	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 545N W3C 470 V16	500	-	545	Capsules	Natural cooled	P11/415	no	
SKS 545N W3C 470 V16 SU	500	-	545	Capsules	Natural cooled	P11/415	no	
SKS 650N W3C 560 V16	500	-	650	Capsules	Natural cooled	U3/515	no	
SKS 650N W3C 560 V16 SU	500	-	650	Capsules	Natural cooled	U3/515	no	
SKS 760F W3C 660 V16	500	-	760	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 760F W3C 660 V16 SU	500	-	760	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 780N W3C 675 V16	500	-	780	Capsules	Natural cooled	U3/515	no	
SKS 780N W3C 675 V16 SU	500	-	780	Capsules	Natural cooled	U3/515	no	
SKS 950F W3C 825 V16	500	-	950	Capsules	Forced-air cooled	P17/130	no	
SKS 950F W3C 825 V16 SU	500	-	950	Capsules	Forced-air cooled	P17/130	no	
SKS 1180F W3C 1020 V16	500	-	1180	Capsules	Forced-air cooled	P17/130	no	
SKS 1180F W3C 1020 V16 SU	500	-	1180	Capsules	Forced-air cooled	P17/130	no	
SKS 1540F W3C 1335 V16	500	-	1540	Capsules	Forced-air cooled	P18/180	no	
SKS 1540F W3C 1335 V16 SU	500	-	1540	Capsules	Forced-air cooled	P18/180	no	
SKS 2150F W3C 1860 V16	500	-	2150	Capsules	Forced-air cooled	N4/250	no	
SKS 2150F W3C 1860 V16 ZU	500	-	2150	Capsules	Forced-air cooled	N4/250	no	

Footnotes: 2) In production new

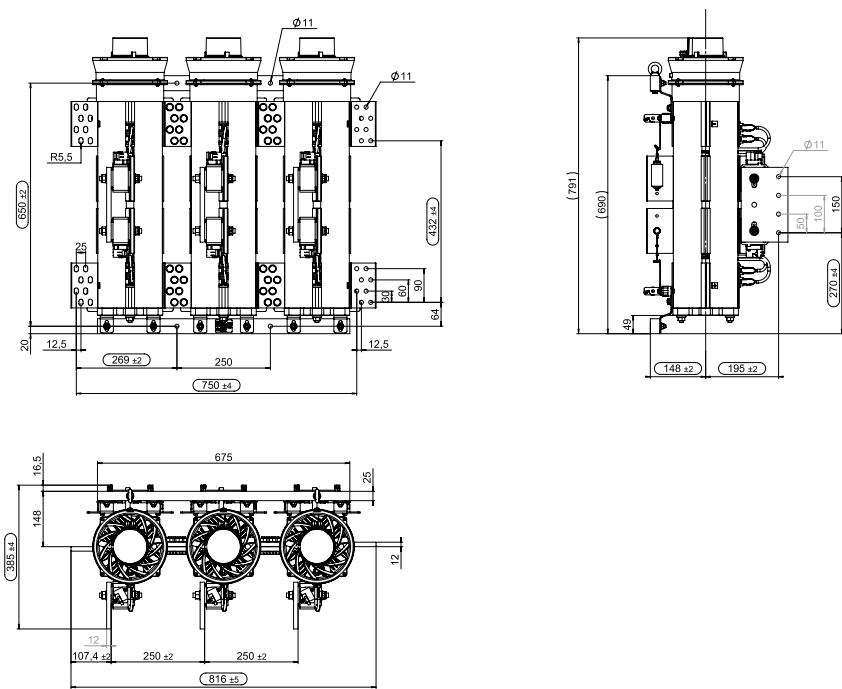
Stacks / SEMISTACK CLASSICS

Packages

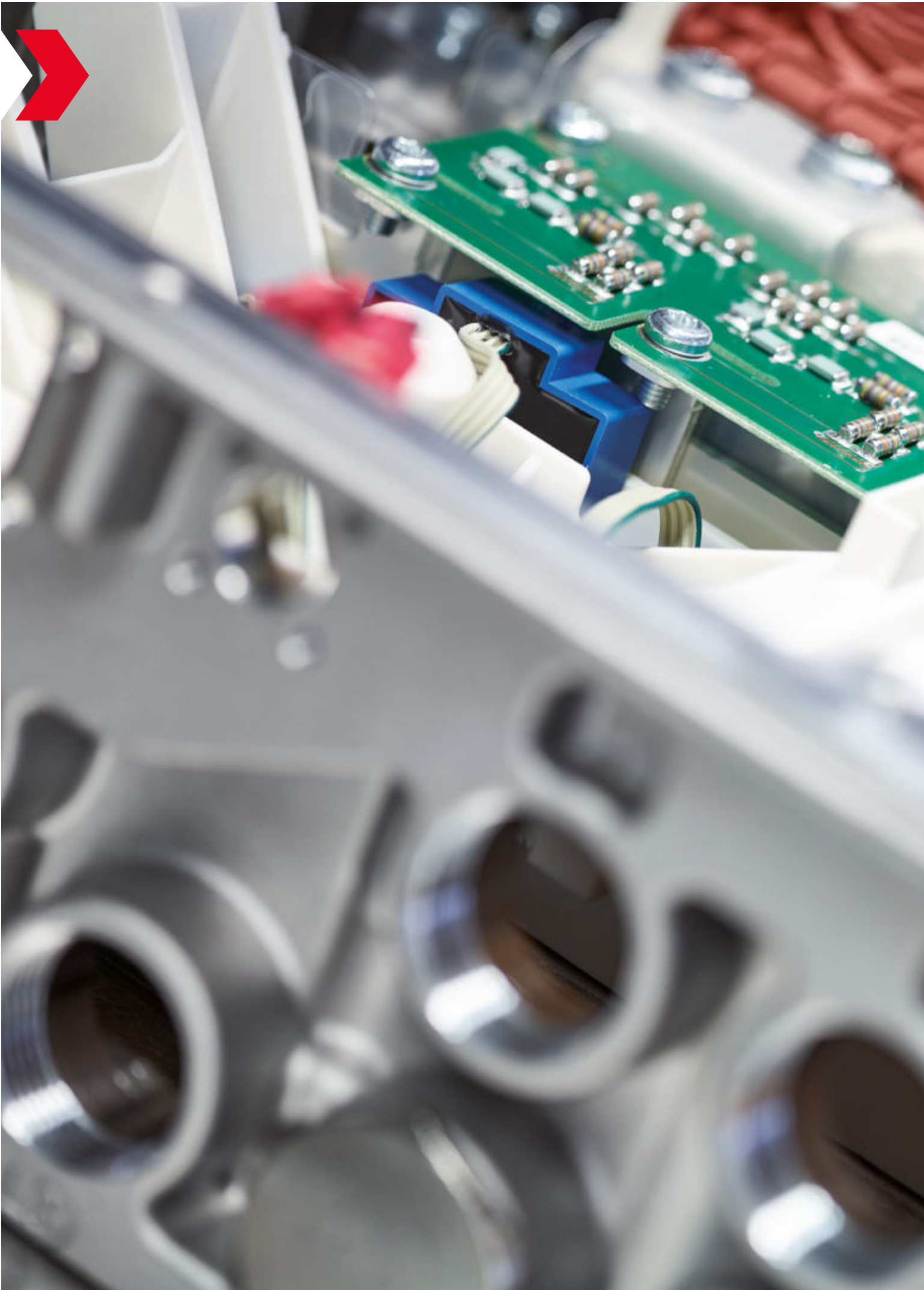
SKS



SKSE



Dimensions in mm



Systems

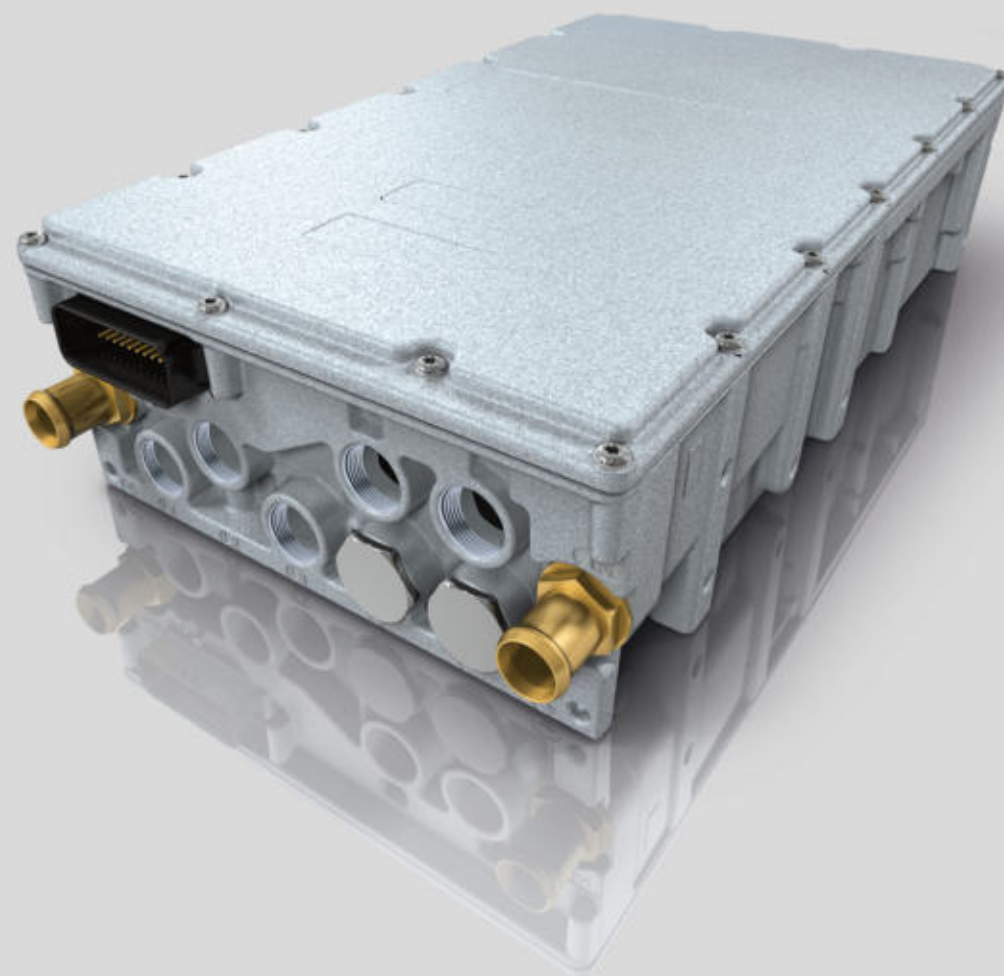
PAGE

SKAI®2 HV 188

SKAI®3 LV 188

5

SKAI® 2 HV
SKAI® 3 LV



Most Compact Power Electronic System “Off-the-shelf” for Electro-Mobility

SKAI®

Short facts

Suitable for battery voltages 24V up to 800V

Sintered power semiconductors

EMI compliant

“Off-the-shelf” versions with gate driver interface, vector control software, automotive power connections

Key features

Compact integration into IP67 enclosure

Voltage, current and temperature sensors

Gate driver with protection

IGBT/ MOSFET power semiconductors

Fully programmable digital signal processor

EMI filters

Versatile cooling system (liquid cooled, forced air cooled, base plate)

DC link capacitors

Motor control software

Applications

The SKAI “off-the-shelf” power electronic building block family has been introduced to cover a broad range of vehicle electrification applications. Examples are electric drivetrains with standardized motor/generator flanges to fit or retrofit the drives easily into existing vehicle designs. These types of drivetrains have been developed for many vehicle types, i.e. buses, light trucks, agriculture and construction machinery as well as marine applications or cars.

Benefits

The SKAI power electronic platform comprises highly integrated motor controllers which provide the ideal powertrain solution for mobile electric and hybrid applications.

Power densities of up to 20 kVA / liter bring about notable size reductions compared with other existing standard motor controller products. The systems are designed to operate with supply voltages of 24V to 800V and with output power ratings of up to 250 kVA. The IGBT-based SKAI 2 HV motor controller operates on sintered, 100% solder-free 600V or 1200V power semiconductors and it features polypropylene film DC-link capacitors. The MOS-based SKAI 3 LV motor controller uses established SkiIP technology with a very low-inductance connection to the DC-link capacitors, driver electronics, current, voltage and temperature sensors. It is integrated into a waterproof IP66 enclosure. The compact motor controllers can withstand high vibration amplitudes of up to 10g rms. SKAIware motor control software adds to the system function and finishes off this tried-and-tested package for the SKAI 2 HV nicely. SEMIKRON provides engineering services to support customers with the integration of SKAI 2 HV motor controller systems. Other available services include, for instance, lifetime estimation, field application support, individual parameterization of motor control software, and others.

Product range

Versatile SKAI 2 HV “off-the-shelf” versions are available. The SKAI 3 LV is available for supply voltages between 24V and 180V. Cooling methods are liquid, forced air cooling or base-plate. Various optional services also exist, such as end-of-line flashing of customer specific software, lifetime estimation based on application profile analysis, field application support, individual parameterization of motor control software and other services (on request).

Further information: www.semikron.com/skai



Abn

ЭйБиЭн

Tel.: +375 17 310 44 44

Tel. +375 44 592 00 86

Tel. +375 33 366 51 85

<https://www.abn.by>

info@abn.by

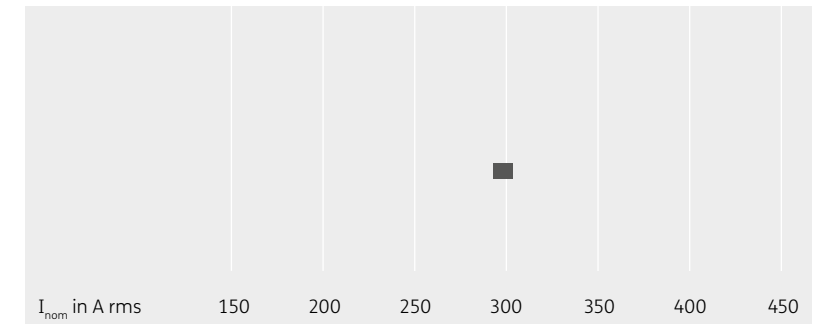
Systems – Ultra Compact Power Electronics System for Utility Vehicles

SEMIKRON's motor controllers are already fully equipped with current sensors, IGBT drivers, DC link capacitors and a fast processor (DSP). The systems are designed to operate with supply voltages of 24V to 800V and with output power ratings of up to 300kVA.

SKAI®2 HV IGBT Motor Controller



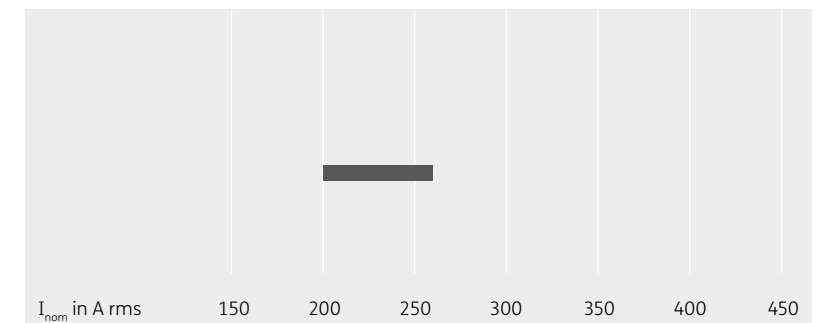
115V up to 800V



SKAI®3 LV MOSFET Sixpack Stack



24V up to 115V



SKAI

190

For detailed information please refer to data sheets.

Further information: www.semikron.com/systems

Systems / SKAI

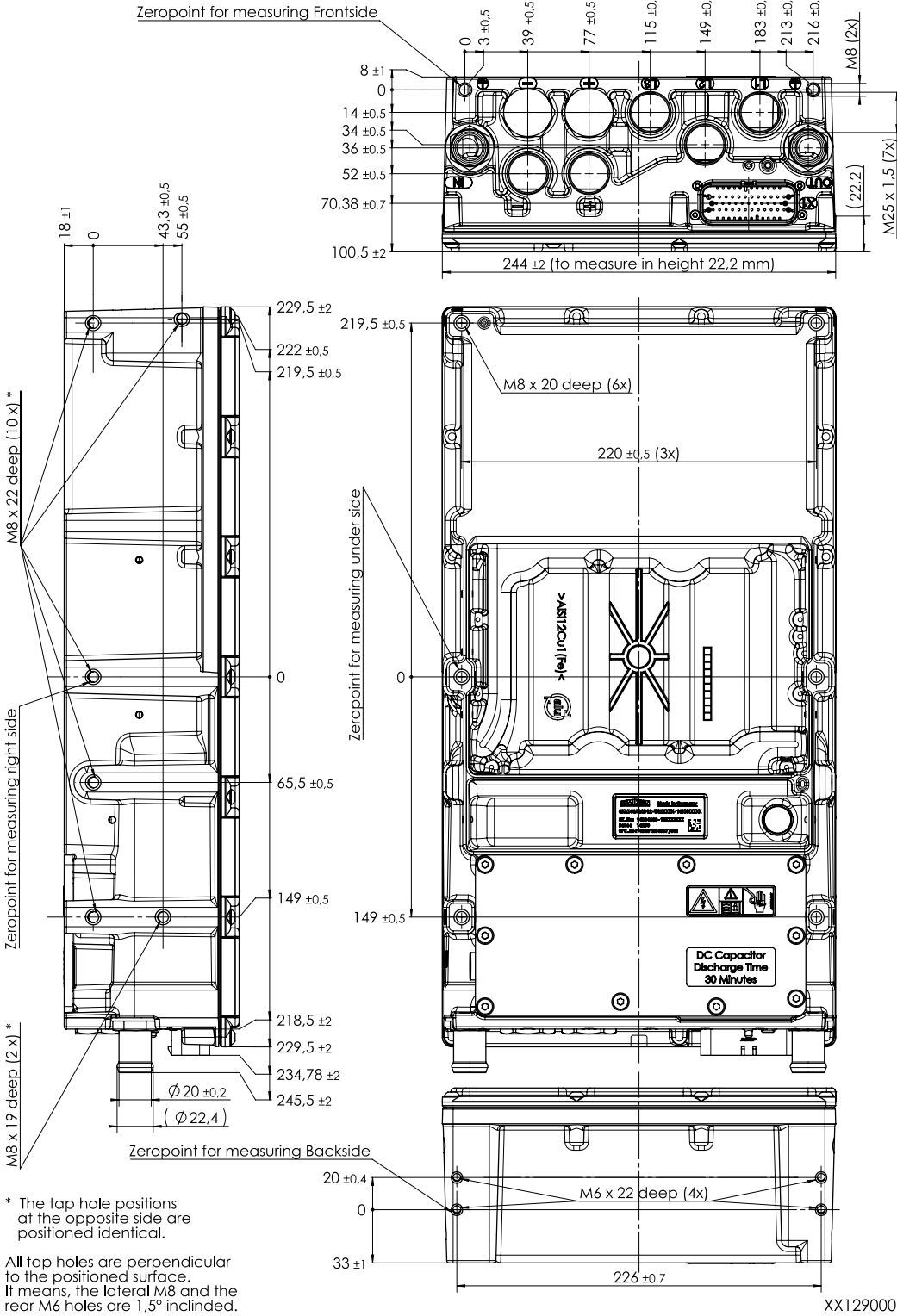
Type								
	$V_{\text{battery (max)}}$	I_{nom}	Topology	Cooling	DSP	Package	Topology	
	V	A _{rms}						
IGBT - Motor Controller								
SKAI 90 A2 GD06-WCI	450	300	3-Phase	Liquid	Yes	7		
SKAI 45 A2 GD12-WCI	800	300	3-Phase	Liquid	Yes	7		
SKAI 90 A2 GD06-WDI ³⁾	450	300	3-Phase	Liquid	No	7		
SKAI 45 A2 GD12-WDI	800	300	3-Phase	Liquid	No	7		
MOSFET - Motor Controller								
SKAI 41 A3 MD10-P ¹⁾	72	240	3-Phase	Baseplate	No	A P		
SKAI 41 E3 MD10-PE ¹⁾	72	240	3-Phase	Baseplate	No	E P		
SKAI 48 A3 MD15-P ¹⁾	120	230	3-Phase	Baseplate	No	A P		
SKAI 48 E3 MD15-PE ¹⁾	120	230	3-Phase	Baseplate	No	E P		

Footnotes: 1) Sample status / 3) Not for new designs

Systems / SKAI

Packages

7

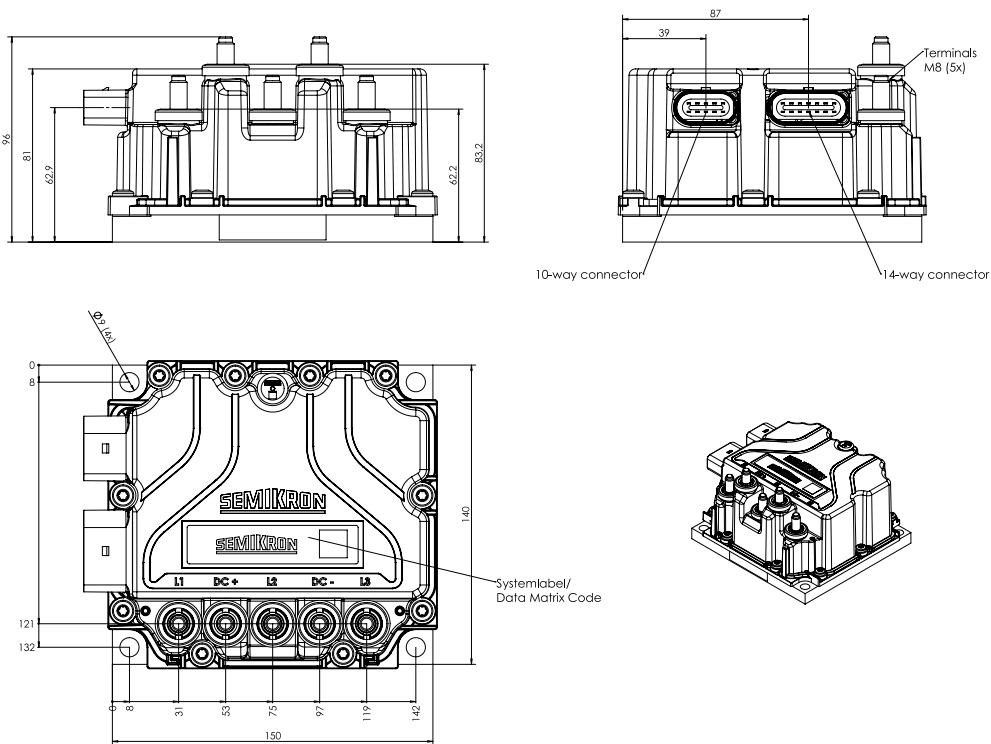


Dimensions in mm

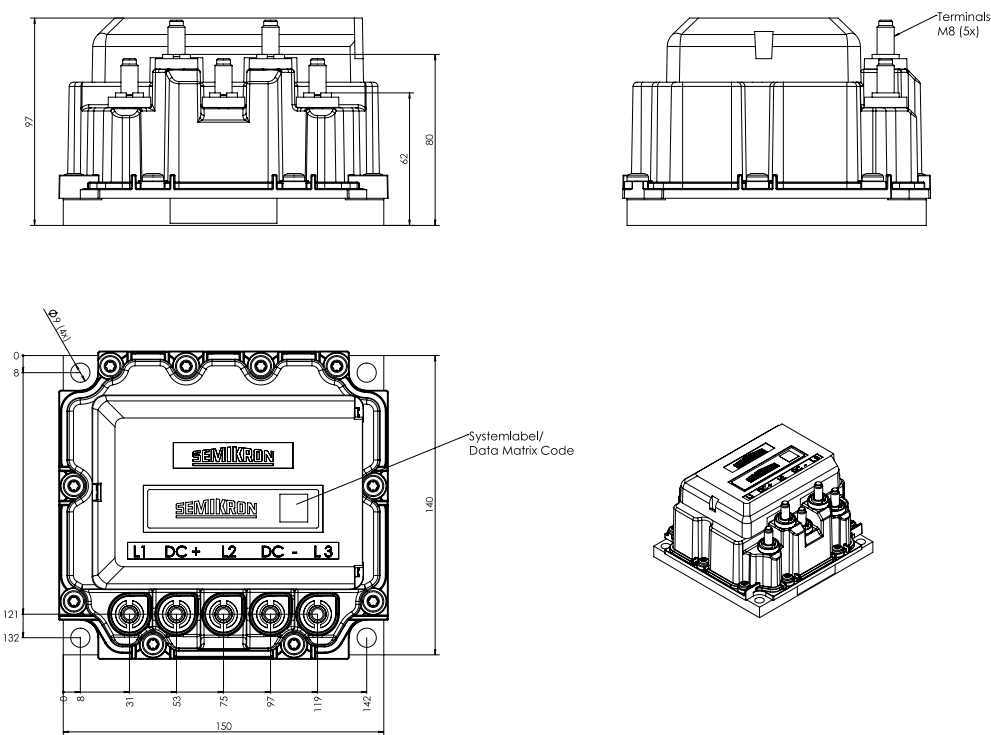
Systems / SKAI

Packages

A P



E P



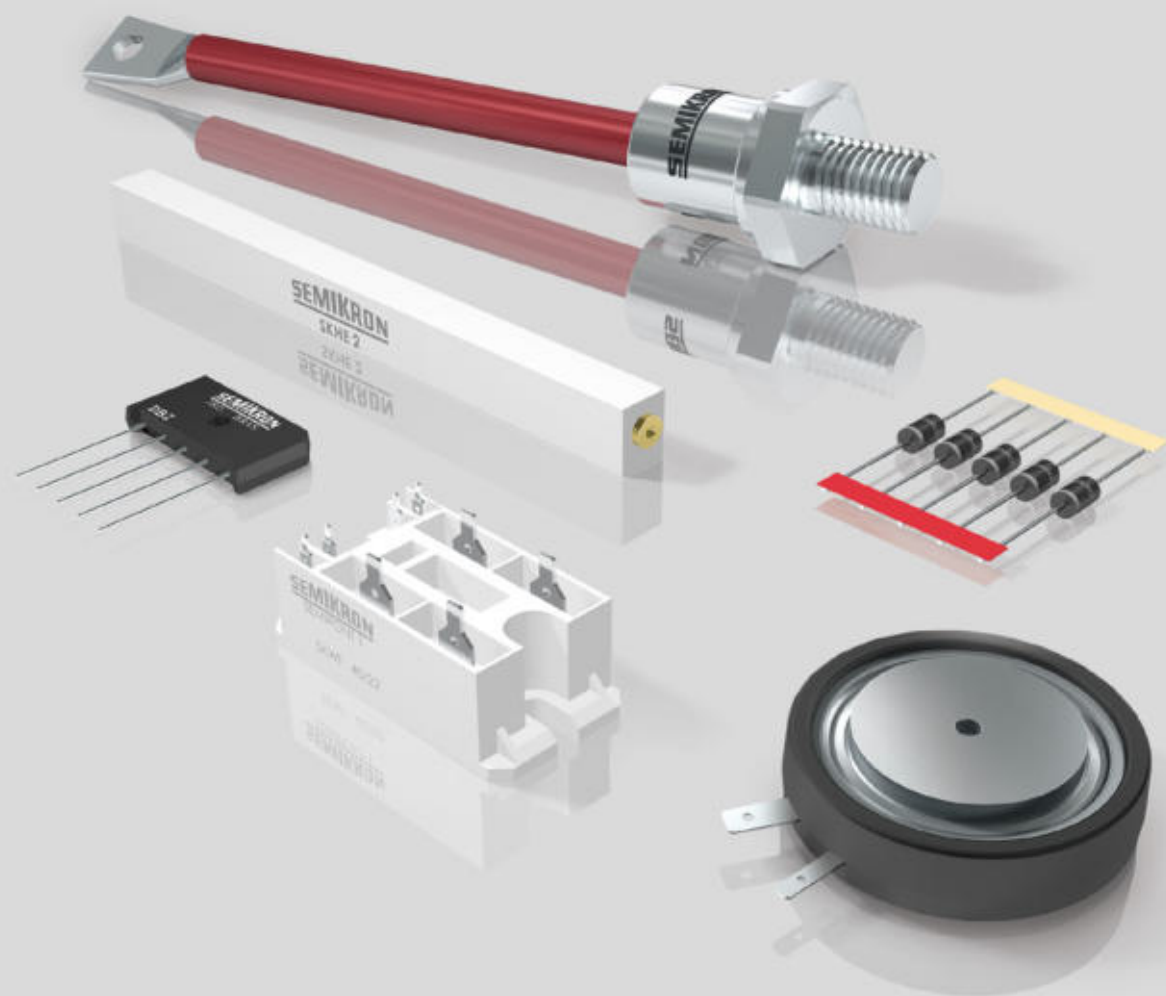
Dimensions in mm

Discretes

	PAGE
Discretes	198
Chips	210
Accessories	216

6

Discrete Diodes Discrete Thyristors Rectifier Bridges



Discrete Devices – Robust and Easy to Use

Discretes

Short facts

Discrete diodes and thyristors for low to high-power applications
Rectifier bridges for low to medium-power applications
Available in voltage classes from 200V to 8000V
Current ratings from 1A to 7500A
Wide range of case designs

Key features

Recommended for natural convection, forced air and water cooling
Compact case with high current capability
Stud and disc types: forward drop selections available for easy paralleling
Axial diodes for PCB mounting
Standard, avalanche and fast types

Discrete benefits

Discrete components are used in a wide variety of applications. Particular benefits are achieved whenever high current, uncommon topologies, natural cooling or resistance to harsh conditions are required.

The SEMIKRON portfolio includes axial leaded diodes of up to 6A, diodes and thyristors in screw fit (stud) and capsule housings from 7500A and 8000V for diodes to 1200A and 1800V for thyristors.

- Easy assembly
- Hermetic sealing
- Rugged construction

Rectifier bridge benefits

SEMIKRON rectifier bridges are the best solution in many applications where performance, space and fast production are paramount. Single or 3-phase topologies using diodes, thyristors and IGBTs in isolated compact cases are possible. Whether your preference is connection by solder, solderless spring or press-fit contacts, mechanical screw connections, fast-on or busbars, SEMIKRON has the right product for your needs.

Discrete applications

Key applications include welding machines, battery chargers, electroplating, soft starters, DC motor control, AC controllers (e.g. for temperature control), alternators and others. With sealed cases, discrete devices make sense for both natural convection and forced cooling, allowing for use in wider fields of application. With over 50 years of field experience and millions of units produced every year, the SEMIKRON portfolio provides options that are competitive, flexible and highly reliable.

Avalanche diodes

- No overvoltage suppressors needed
- Insensitive to short term reverse overloads
- High blocking voltages possible without static or dynamic voltage sharing topology

Rectifier bridge applications

Key applications include battery chargers, motor drive input rectifiers, power supplies, DC motor control, rectifiers with PFC, AC controllers, static switches (SKWT types) for natural convection or forced cooling.

Further information: www.semikron.com/discrete-diodes-thyristors
www.semikron.com/rectifier-bridges

Discretes

SEMIKRON offers discrete diodes in three major packaging styles; axial epoxy diodes for PCB mounting, stud screw-fit diodes that are suitable for applications such as welding, rotating rectifiers in brushless generators thanks to their robustness and easy assembly, as well as capsule (disc) diodes for high-power applications.

The line includes standard rectifiers with current ratings up to 7500A, fast rectifiers up to 140A, and avalanche rectifiers that allow for high voltage rectification of up to 8000V with single diodes and much more when connected in series. Typical applications: all-purpose rectifiers, battery chargers, welding equipment, rotating rectifiers for brushless generators, electroplating, free-wheeling diodes, high-voltage rectifiers, electrostatic filters, blocking diodes and others.

SEMIKRON's discrete thyristors are available as stud screw-fit types that are suitable for applications which require robustness and easy assembly, plus capsule (disc) types for high-power applications. The line also has phase control types for current ratings of up to 1200A, with blocking and reverse voltages of up to 1800V, covering the major market applications. Typical applications are soft-starters, resistance heating, static switches, battery chargers, welding equipment, static excitation and others.

Discrete diodes

HV Screw-Axial	200
Leaded	201
Stud Screw-Fit	202
Capsules	205

Discrete thyristors

Stud Screw-Fit	207
Capsules	208

For detailed information please refer to data sheets.

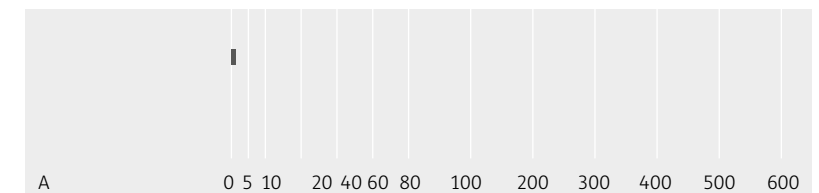
Further information

www.semikron.com/discrete-diodes
www.semikron.com/discrete-thyristors

Discrete Diodes

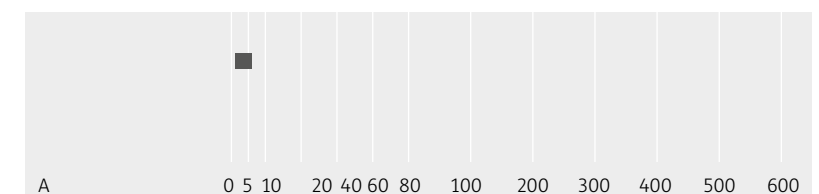
HV Screw-Axial

4800V up to 8000V



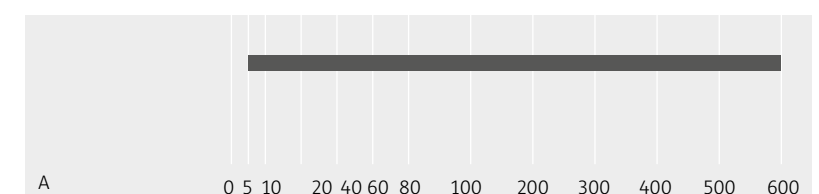
Leaded

100V up to 2000V



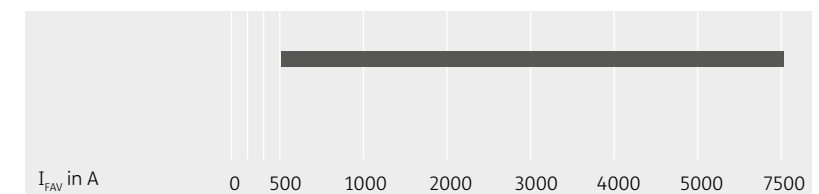
Stud Screw-Fit

400V up to 5000V



Capsules

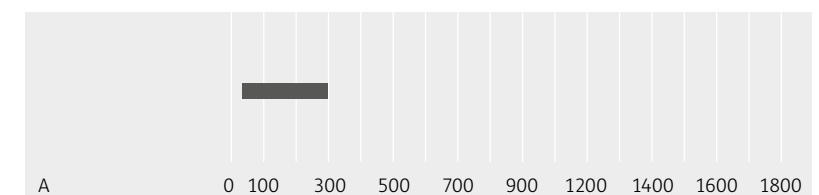
200V up to 2200V



Discrete Thyristors

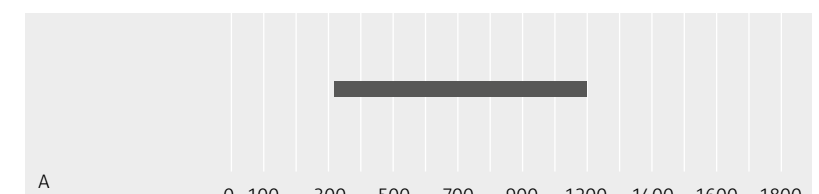
Stud Screw-Fit

400V up to 1800V



Capsules

400V up to 1800V

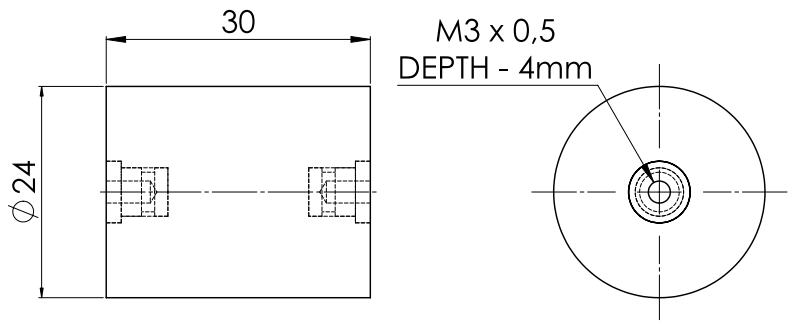


Discretes / Diodes / HV Screw Axial

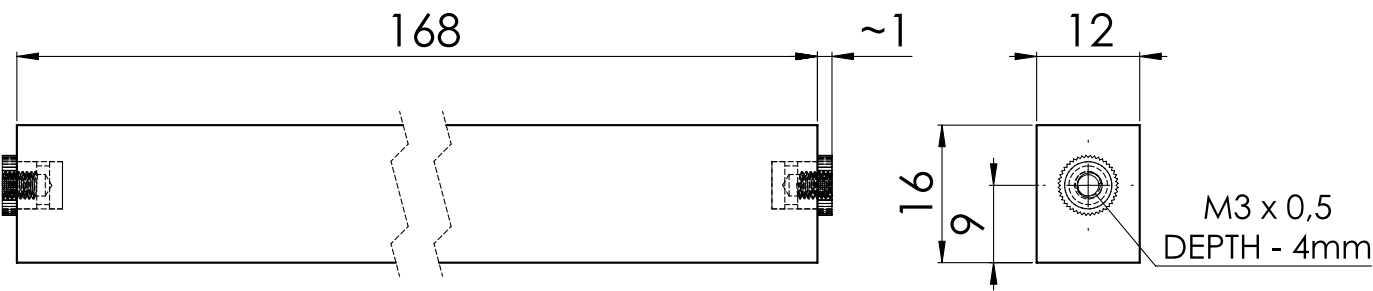
Type	Voltage (V)	I_{FAV} @ T_{oil}	T_{oil}	I_{FSM} @ $T_j=25^{\circ}C$	V_F	$R_{th(j-a)}$ per chip	T_j	Package	Topology
	V	A	°C	A	V	K/W	°C		
SKHE 2000/900-1,2	4800	1.5	75	135	3.60	21	-40 ... +150	SKHE 1	
SKHE 3500/1550-2,0	8000	2.5	75	270	6.70	8	-40 ... +150	SKHE 2	

Packages

SKHE 1



SKHE 2



Dimensions in mm

Discretes / Diodes / Leaded

Type	Voltage (V)	Current (A)	T_c	I_{FSM} @ $T_j=25^{\circ}C$	V_F	$R_{th(j-a)}$ per chip	T_j	Package	Topology
	V	A	°C	A	V	K/W	°C		
Standard recovery									
SK 1	1000-1600	1.45	85	60	1.50	85	-40 ... +150	E33	
SKN 2,5	400-1600	2.5	173	180	1.20	55	-40 ... +180	E5	
SK 3	400-1600	3	92	180	1.20	60	-40 ... +150	E34	
SKN 5	200-1600	5	169	190	1.25	25	-40 ... +180	E6	
SK 6 ²⁾	400-1600	6	46	375	1.10	55	-40 ... +150	SK6	

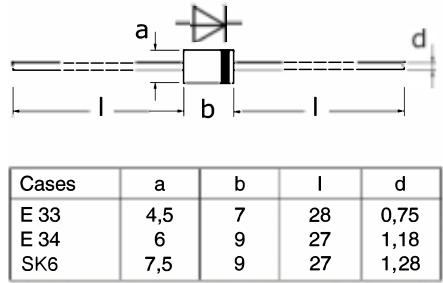
Avalanche

SKa1	1300-1700	1.45	85	60	1.50	85	-40 ... +150	E33	
SKNa2	1300-1700	2	175	180	1.20	2.5	-40 ... +150	E5	
SKa3	1300-2000	3	92	180	1.20	60	-40 ... +150	E34	
SKNa4	1300-1700	4	171	190	1.20	25	-40 ... +150	E6	
SKa 6 ²⁾	1300-2000	6	46	375	1.10	55	-40 ... +150	SK6	

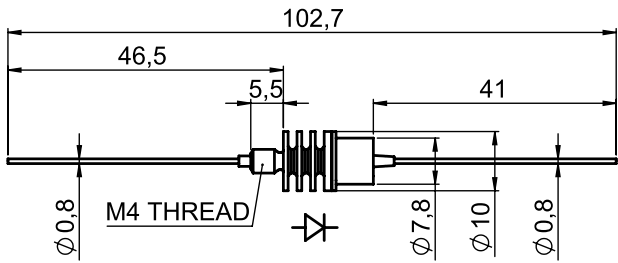
Footnotes: 2) In production new

Packages

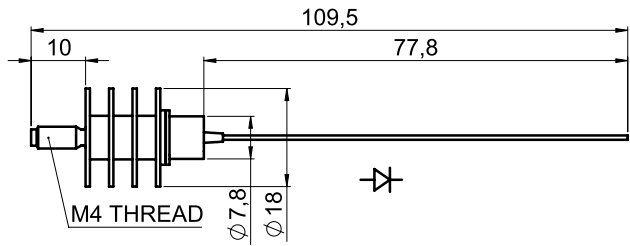
E33 / E34 / SK6



E5



E6



Dimensions in mm

Discretes / Diodes / Stud Screw Fit

Type										
	Voltage (V)	Current (A)	T _c	I _{FSM} @T _J =25°C	V _F	R _{th(j-c)} per chip	T _j	Package		Topology
	V	A	°C	A	V	K/W	°C			
Standard recovery										
SKN 20	400-1600	20	125	375	1.55	2	-40 ... +180	E9		
SKN 26	400-1600	25	100	375	1.55	2	-40 ... +180	E8		
SKN 45	400-1600	45	125	700	1.60	0.85	-40 ... +180	E12		
SKN 46	800-1600	45	125	700	1.60	0.85	-40 ... +180	E11		
SKN 70	400-1600	70	125	1150	1.50	0.55	-40 ... +180	E12		
SKN 71	400-1600	70	125	1150	1.50	0.55	-40 ... +180	E11		
SKN 86 ²⁾	800-1600	86	129	1500	1.20	0.4	-40 ... +180	E10		
SKN 94	200-1200	96	141	2000	1.20	0.35	-40 ... +180	E12		
SKN 96	200-1200	96	141	2000	1.20	0.35	-40 ... +180	E10		
SKN 100	400-1800	100	120	1750	1.55	0.45	-40 ... +180	E13		
SKN 130	400-1800	130	125	2500	1.50	0.35	-40 ... +180	E14		
SKN 152	200-1200	152	139	4500	1.40	0.22	-40 ... +180	DO-8		
SKN 240	400-1800	240	125	6000	1.40	0.2	-40 ... +180	E15		
SKN 262	2000-2800	262	115	6000	1.40	0.2	-40 ... +180	E45		
SKN 300	400-1600	300	124	6500	1.40	0.15	-40 ... +180	E15		
SKN 320	400-1600	320	125	9000	1.35	0.16	-40 ... +180	E16		
SKN 390	400-1600	390	117	9000	1.35	0.13	-40 ... +180	E15		
SKN 400	1800-3600	400	100	9000	1.45	0.11	-40 ... +160	E17		
SKN 600 ²⁾	400-1600	600	105	14000	1.33	0.1	-40 ... +180	E16		
SKR 20	400-1600	20	125	375	1.55	2	-40 ... +180	E9		
SKR 26	400-1600	25	100	375	1.55	2	-40 ... +180	E8		
SKR 45	400-1600	45	125	700	1.60	0.85	-40 ... +180	E12		
SKR 46	800-1600	45	125	700	1.60	0.85	-40 ... +180	E11		
SKR 70	400-1600	70	125	1150	1.50	0.55	-40 ... +180	E12		
SKR 71	400-1600	70	125	1150	1.50	0.55	-40 ... +180	E11		
SKR 86 ²⁾	800-1600	86	129	1500	1.20	0.4	-40 ... +180	E10		
SKR 94	200-1200	96	141	2000	1.20	0.35	-40 ... +180	E12		
SKR 96	200-1200	96	141	2000	1.20	0.35	-40 ... +180	E10		
SKR 100	400-1800	100	120	1750	1.55	0.45	-40 ... +180	E13		
SKR 130	400-1800	130	125	2500	1.50	0.35	-40 ... +180	E14		
SKR 152	200-1200	152	139	4500	1.40	0.22	-40 ... +180	DO-8		
SKR 240	400-1800	240	125	6000	1.40	0.2	-40 ... +180	E15		
SKR 262	2000-2800	262	115	6000	1.40	0.2	-40 ... +180	E45		
SKR 300	400-1600	300	124	6500	1.40	0.15	-40 ... +180	E15		
SKR 320	400-1600	320	125	9000	1.35	0.16	-40 ... +180	E16		
SKR 390	400-1600	390	117	9000	1.35	0.13	-40 ... +180	E15		
SKR 400	1800-3600	400	100	9000	1.45	0.11	-40 ... +160	E17		
SKR 600 ²⁾	400-1600	600	105	14000	1.33	0.1	-40 ... +180	E16		
Fast recovery										
SKN 2F17	400-1000	17	113	450	2.15	1.2	-40 ... +150	E7		
SKN 3F20	800-1200	20	104	375	2.15	1.2	-40 ... +150	E7		
SKN 2F50	400-1000	50	105	1100	1.80	0.5	-40 ... +150	E10		
SKN 60F	1200-1700	60	100	1400	1.75	0.5	-40 ... +150	E10		
SKN 135F	800-1200	135	100	2500	1.95	0.2	-40 ... +150	E14		
SKN 136F	800-1200	135	100	2500	1.95	0.2	-40 ... +150	E31		
SKN 140F	1200-1700	140	100	2500	1.80	0.2	-40 ... +150	E14		
SKN 141F	1200-1700	140	100	2500	1.80	0.2	-40 ... +150	E31		
SKR 2F17	400-1000	17	113	450	2.15	1.2	-40 ... +150	E7		
SKR 3F20	800-1200	20	104	375	2.15	1.2	-40 ... +150	E7		
SKR 2F50	400-1000	50	95	1100	1.80	0.5	-40 ... +150	E10		
SKR 60F	1200-1700	60	100	1400	1.75	0.5	-40 ... +150	E10		
SKR 135F	800-1200	135	100	2500	1.95	0.2	-40 ... +150	E14		
SKR 136F	800-1200	135	100	2500	1.95	0.2	-40 ... +150	E31		
SKR 140F	1200-1700	140	100	2500	1.80	0.2	-40 ... +150	E14		
Footnotes: 1) Sample status / 2) In production new										

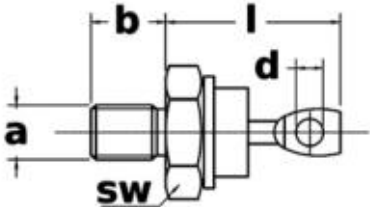
Footnotes: 1) Sample status / 2) In production new

Discretes / Diodes / Stud Screw Fit

Type									
	Voltage (V)	Current (A)	T _c	I _{FSM} @T _J =25°C	V _F	R _{th(j-c)} per chip	T _J	Package	
	V	A	°C	A	V	K/W	°C		Topology
Fast recovery									
SKR 141F	1200-1700	140	100	2500	1.80	0.2	-40 ... +150	E31	
Avalanche									
SKNa 20	1300-1700	20	93	375	1.55	2	-40 ... +150	E9	
SKNa 22	3600-5000	25	104	450	1.95	1	-40 ... +160	E42	
SKNa 26	1300-1700	26	69	375	1.55	2	-40 ... +150	E8	
SKNa 46	1400-2000	46	124	700	1.60	0.85	-40 ... +180	E11	
SKNa 47	3600-5000	45	106	700	1.80	0.6	-40 ... +160	E43	
SKNa 86 ¹⁾	1400-2000	86	129	1500	1.20	0.4	-40 ... +180	E10	
SKNa 102	3600-5000	125	80	1900	1.90	0.3	-40 ... +160	E44	
SKNa 202	3600-5000	200	80	3800	1.95	0.2	-40 ... +160	E45	
SKNa 402	3600-5000	400	88	7800	1.85	0.1	-40 ... +160	E46	
SKRa 26	1300-2000	26	69	375	1.55	2	-40 ... +150	E8	
SKRa 46	1400-2000	46	124	700	1.60	0.85	-40 ... +180	E11	
SKRa 86 ¹⁾	1400-2000	86	129	1500	1.20	0.4	-40 ... +180	E10	
Footnotes: 1) Sample status / 2) In production new									

Packages

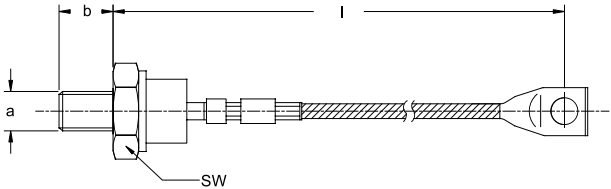
E7 / E8 / E10 / E11 / E31



Cases	a	b	d	l	sw
E 7	M 5	11	2,7	22	11
E 8	M 6	11	2,7	21,5	11
E 10	M 6	11	4	25	17
E 11	M 8	11	4	25,5	17
E 31	M 12	18	8,4	55	24

Dimensions in mm

E9 / E12 ... E17 / DO-8

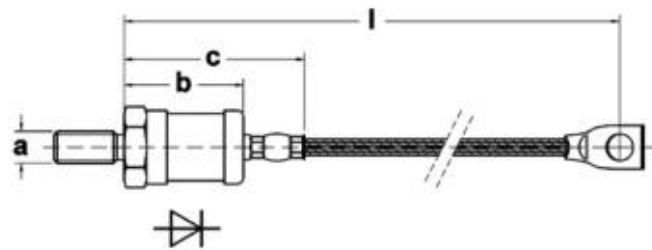


Cases	a	b	l	SW
E9	M6	11	130	11
E12	M8	11	135	17
E13	M12	18	165	24
E14	M12	18	165	24
E15	M16 x 1.5	20	190	32
E16, E17	M24 x 1.5	20	230	41
DO-8	3/8 - 24 UNF 2A	16	112	27

Discretes / Diodes / Stud Screw Fit

Packages

E 42 / E 43 / E 44 / E 45 / E 46



Cases	a	b	c	l
E 42	M 6	28.5	45	150
E 43	M 8	32	54	160
E 44	M 12	38	57	185
E 45	M 16 x 1,5	48	70	205
E 46	M 24 x 1,5	54	82	250

Dimensions in mm

Discretes / Diodes / Capsules

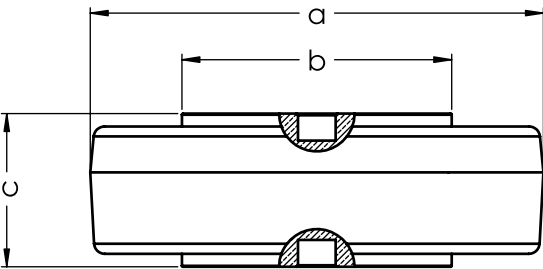
Type

	Voltage (V) V	Current (A) A	T _C °C	I _{FSM} @T _J =25°C A	V _F V	R _{th(j-a)} per chip K/W	T _J °C	Package	Topology
SKN 503 SG ¹⁾	400-2200	503	120	7000	1.50	0.075	-40 ... +180	E25	
SKN 1503 SG ¹⁾	400-2200	1503	91	19000	1.50	0.033	-40 ... +175	E26	
SKN 6000	200-600	6000	85	60000	1.30	0.012	-40 ... +180	E35	
SKN 7500/06 ¹⁾	600	7500	85	60000	1.12	0.009	-40 ... +180	E28	

Footnotes: 1) Sample status

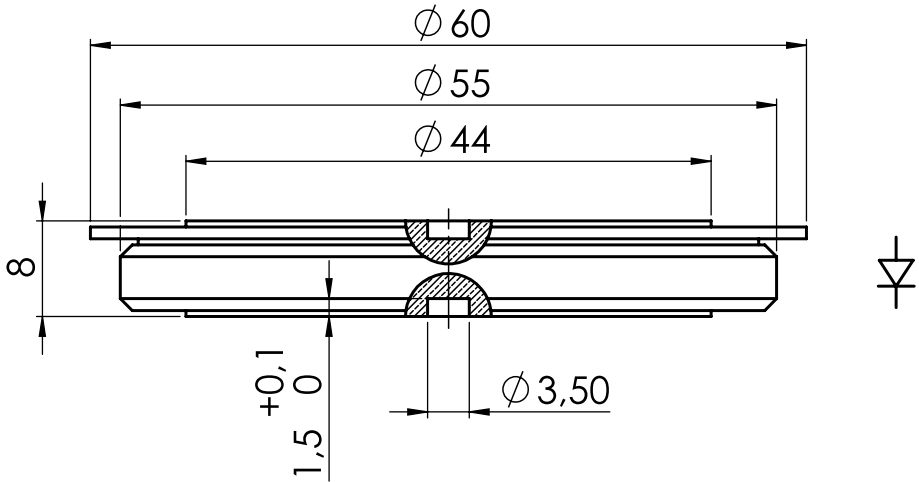
Packages

E25, E26, E27



Cases	a	b	c
E25	42	25	14,5
E26	58	36	26,5
E27	50	32	14,5

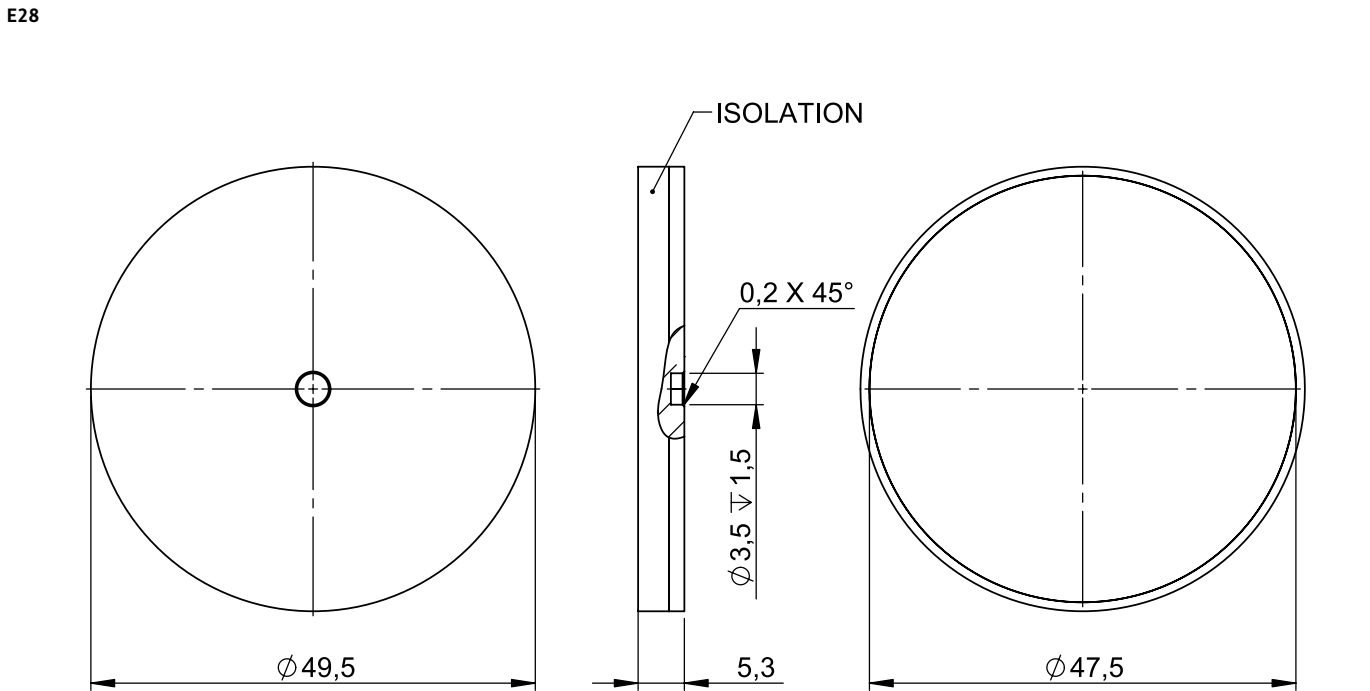
E35



Dimensions in mm

Discretes / Diodes / Capsules

Packages



Dimensions in mm

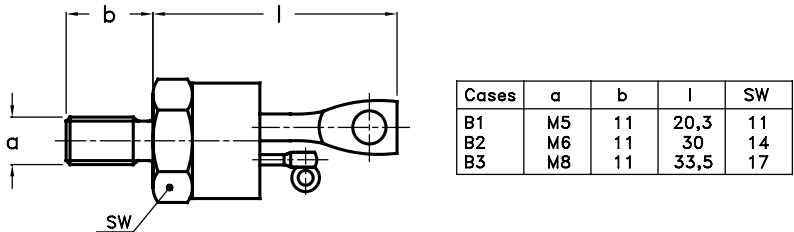
Discretes / Thyristors / Stud Screw Fit

Type

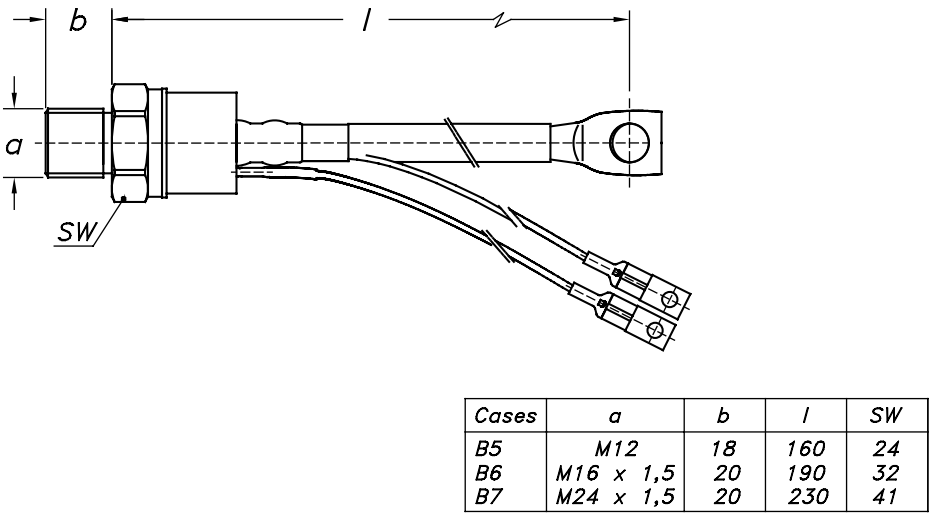
	Voltage (V)	Current (A)	T_c	I_{SM} @ $T_J = 25^\circ C$	V_T @ $I_T, T_J = 25^\circ C$	I_T @ V_T	$R_{th(j-a)}$ per chip	T_J	Package	Topology
	V	A	$^\circ C$	A	V	A	K/W	$^\circ C$		
SKT 10	600-1200	10	111	250	1.6	30	1.3	-40 ... +130	B1	
SKT 16	400-1800	16	104	370	2.4	75	0.9	-40 ... +130	B2	
SKT 24	400-1800	24	95	450	1.9	75	0.9	-40 ... +130	B2	
SKT 40	400-1800	40	80	700	1.95	120	0.66	-40 ... +130	B3	
SKT 50	600-1800	50	78	1050	1.8	120	0.6	-40 ... +130	B3	
SKT 55	400-1800	55	92	1300	1.8	200	0.47	-40 ... +130	B5	
SKT 80	600-1800	80	85	1700	2.25	300	0.28	-40 ... +130	B5	
SKT 100	400-1800	100	85	2000	1.75	300	0.28	-40 ... +130	B5	
SKT 130	400-1600	130	85	3500	2.25	500	0.18	-40 ... +130	B6	
SKT 160	400-1600	160	84	4300	1.75	500	0.18	-40 ... +130	B6	
SKT 250	400-1600	250	85	7000	1.65	800	0.123	-40 ... +130	B7	
SKT 300	400-1600	300	93	11000	1.45	800	0.096	-40 ... +130	B7	

Packages

B1 ... B3



B5 ... B7



Dimensions in mm

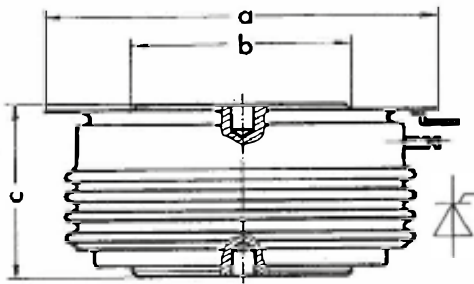
Discretes / Thyristors / Capsules

Type										
	Voltage (V)	Current (A)	T _c	I _{SM} @T _J =25°C	V _T @ I _p , T _J =25°C	I _T @V _T	R _{th(j-a)} per chip	T _J	Package	Topology
	V	A	°C	A	V	A	K/W	°C		
SKT 340	1200-1800	340	82	5700	1.9	1000	0.072	-40 ... +125	B8	
SKT 551	1200-1800	550	85	9000	1.65	1500	0.047	-40 ... +125	B11	
SKT 553 SG ²⁾	400-1800	554	85	9000	1.65	1500	0.045	-40 ... +125	B11b	
SKT 760	1200-1800	760	80	15000	1.65	2400	0.04	-40 ... +125	B10	
SKT 813 ²⁾	400-1800	855	85	15000	1.65	2400	0.03	-40 ... +125	B21	
SKT 883 ¹⁾	400-1800	890	85	19000	1.46	2400	0.032	-40 ... +125	B23	
SKT 1200	1200-1800	1200	85	30000	1.65	3600	0.021	-40 ... +125	B14	

Footnotes: 1) Sample status / 2) In production new

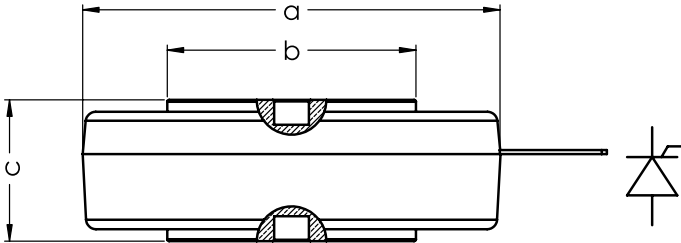
Packages

B8 ... B14



Cases	a	b	c
B 8	41	19	14
B 10	57,3	34	26
B 11	41	25	14
B 14	73	47	26

B11b, B21, B23



Cases	a	b	c
B11b	42	25	14,5
B21	50	32	14,5
B23	58	36	26,5

Dimensions in mm

Discretes / Chips

CAL (Controlled Axial Lifetime) freewheeling diodes are available in 600V / 650V, 1200V, and 1700V voltage classes with current ratings of up to 200A. Depending on the frequency of the target application, custom-designed switching properties are also available.

Rectifier diodes and thyristors are designed for the 1600V voltage class, covering a wide range of current ratings up to 770A, equivalent to a die size of more than 500mm². Variable configurations of the thyristor gate (corner vs. center gate) allow for optimised bond layout in the respective target design on the customer side. All the chips cover SEMIKRON's extensive module and system range, which means a proven history of outstanding performance and reliability. They are compatible with various connection and assembly technologies. Customers can benefit from the wealth and depth of application knowledge that the SEMIKRON engineering team has.

Freewheeling Diode CAL	212
Rectifier Diode	215
Thyristor	215

For detailed information please refer to data sheets.

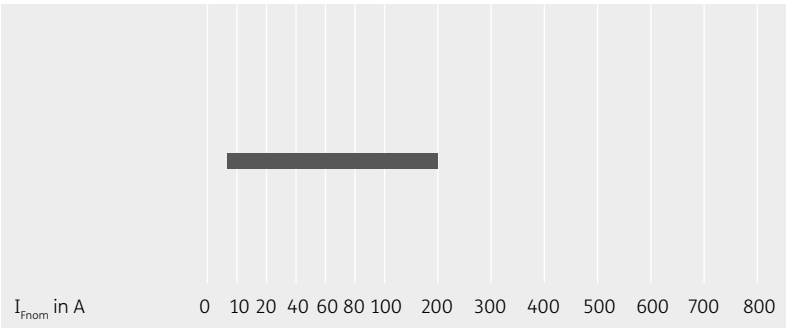
Further information: www.semikron.com/chips

Chips SEMICELL

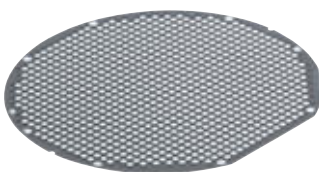
Freewheeling
Diode CAL



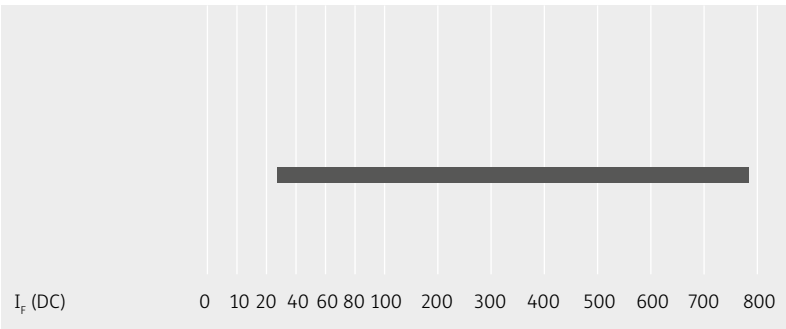
600V up to 1700V



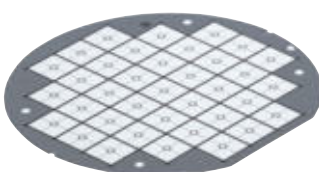
Rectifier
Diode



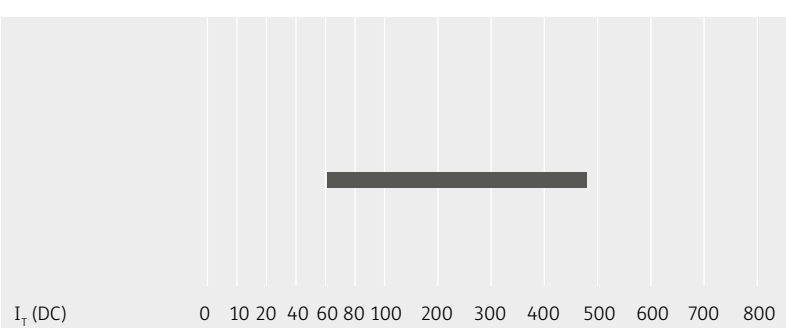
1600V



Thyristor



1600V



Discretes / Chips / SEMICELL

Type						
	V _{RRM}	I _F @T _J =150°C	I _{FSM} @T _J =150°C	V _F @T _J =25°C	I _F @ V _F T _J =25°C	Q _{rr} @T _J =125°C
	V	A	A	V	A	µC
600V - Freewheeling Diodes CAL I3 Fast						
SKCD 06 C 060 I3	600	15	80	1.35	8	1
SKCD 09 C 060 I3	600	20	100	1.35	13	1.46
SKCD 18 C 060 I3	600	30	200	1.35	25	1.98
SKCD 31 C 060 I3	600	50	440	1.35	50	3.3
SKCD 47 C 060 I3	600	80	720	1.35	85	6.2
SKCD 61 C 060 I3	600	100	1000	1.35	110	8.7
SKCD 81 C 060 I3	600	150	1260	1.35	155	11.5
SKCD 121 C 060 I3	600	210	2100	1.35	245	18
Type						
	V _{RRM}	I _F @T _J =175°C	I _{FSM} @T _J =150°C	V _F @T _J =25°C	I _F @ V _F T _J =25°C	Q _{rr} @T _J =150°C
	V	A	A	V	A	µC
600V - Freewheeling Diodes CAL High Density						
SKCD 04 C 060 I HD	600	10	65	1.23	4.7	1.3
SKCD 06 C 060 I HD	600	20	95	1.23	8	1.42
SKCD 09 C 060 I HD	600	30	160	1.23	13	2.4
SKCD 16 C 060 I HD	600	50	320	1.23	25	3.87
SKCD 24 C 060 I HD	600	75	395	1.23	41	6
SKCD 42 C 060 I HD	600	100	810	1.23	75	11.1
SKCD 61 C 060 I HD	600	150	1080	1.23	112	15.75
SKCD 81 C 060 I HD	600	200	1310	1.23	152	19.69
Type						
	V _{RRM}	I _F @T _J =175°C	I _{FSM} @T _J =150°C	V _F @T _J =25°C	I _F @ V _F T _J =25°C	E _{rr} @T _J =150°C
	V	A	A	V	A	mJ
650V - Freewheeling Diodes CAL I4 Fast						
SKCD 24 C 065 I4F	650	50	460	1.30	39	1.1
SKCD 42 C 065 I4F	650	100	680	1.30	73	2.2
SKCD 61 C 065 I4F	650	150	1100	1.30	109	3.8
SKCD 81 C 065 I4F	650	200	1290	1.30	148	5.8

Discretes / Chips / SEMICELL

Type						
	V _{RRM}	I _F @T _J =150°C	I _{FSM} @T _J =150°C	V _F @T _J =25°C	I _F @ V _F T _J =25°C	Q _{rr} @T _J =125°C
	V	A	A	V	A	µC
1200V - Freewheeling Diodes CAL I3 Fast						
SKCD 11 C 120 I3	1200	15	130	2.00	10	1.6
SKCD 18 C 120 I3	1200	25	200	2.00	15	3
SKCD 23 C 120 I3R	1200	30	270	2.00	25	3.8
SKCD 31 C 120 I3	1200	40	370	2.00	35	5.3
SKCD 47 C 120 I3	1200	55	600	2.00	55	7.5
SKCD 61 C 120 I3	1200	75	800	2.00	70	11
SKCD 81 C 120 I3	1200	100	1100	2.00	100	16.5
SKCD 121 C 120 I3	1200	150	1600	2.00	155	24
1200V - Freewheeling Diodes CAL High Density						
SKCD 06 C 120 I HD	1200	6	60	1.50	5	1.24
SKCD 11 C 120 I HD	1200	15	140	1.50	12	2.9
SKCD 14 C 120 I HD	1200	20	170	1.50	15	4
SKCD 18 C 120 I HD	1200	25	200	1.50	20	5
SKCD 31 C 120 I HD	1200	55	480	1.50	45	11
SKCD 47 C 120 I HD	1200	85	700	1.50	70	17.4
SKCD 61 C 120 I HD	1200	115	900	1.50	90	24.5
SKCD 81 C 120 I HD	1200	160	1150	1.50	130	34.4
Type						
	V _{RRM}	I _F @T _J =175°C	I _{FSM} @T _J =150°C	V _F @T _J =25°C	I _F @ V _F T _J =25°C	E _{rr} @T _J =150°C
	V	A	A	V	A	mJ
1200V - Freewheeling Diodes CAL I4 Fast						
SKCD 08 C 120 I4F	1200	8	36	2.33	8	0.4
SKCD 11 C 120 I4F	1200	15	65	2.38	15	0.6
SKCD 16 C 120 I4F	1200	25	100	2.41	25	1
SKCD 22 C 120 I4F	1200	35	170	2.30	35	1.6
SKCD 31 C 120 I4F	1200	50	270	2.22	50	2.6
SKCD 31 C 120 I4F R	1200	50	270	2.22	50	4.38
SKCD 46 C 120 I4F	1200	75	430	2.17	75	4.2
SKCD 46 C 120 I4F R	1200	75	430	2.17	75	4.2
SKCD 53 C 120 I4F	1200	100	550	2.20	100	5.4
SKCD 81 C 120 I4F	1200	150	900	2.14	150	8.7

Discretes / Chips / SEMICELL

Type						
	V_{RRM}	$I_F @ T_J = 150^{\circ}C$	$I_{FSM} @ T_J = 150^{\circ}C$	$V_F @ T_J = 25^{\circ}C$	$I_F @ V_F, T_J = 25^{\circ}C$	$Q_{rr} @ T_J = 125^{\circ}C$
	V	A	A	V	A	µC
1700V - Freewheeling Diodes CAL Fast						
SKCD 47 C 170 I	1700	55	550	2.05	55	15
SKCD 61 C 170 I	1700	75	720	2.05	75	24
1700V - Freewheeling Diodes CAL High Density						
SKCD 47 C 170 I HD	1700	75	650	1.73	75	25
SKCD 61 C 170 I HD	1700	100	710	1.73	100	35
SKCD 81 C 170 I HD	1700	150	1070	1.73	150	53.5

Type						
	V_{RRM}	$I_F @ T_J = 175^{\circ}C$	$I_{FSM} @ T_J = 150^{\circ}C$	$V_F @ T_J = 25^{\circ}C$	$I_F @ V_F, T_J = 25^{\circ}C$	$E_{rr} @ T_J = 150^{\circ}C$
	V	A	A	V	A	mJ
1700V - Freewheeling Diodes CAL I4 Fast						
SKCD 28 C 170 I4F	1700	40	280	1.71	23	12
SKCD 46 C 170 I4F	1700	75	450	1.71	43	17
SKCD 56 C 170 I4F	1700	100	580	1.71	57	22.2
SKCD 81 C 170 I4F	1700	150	860	1.71	89	31.5

Discretes / Chips / SEMICELL

Type						
	V_{RRM}	T_{Jmax}	$I_{F(DC)} @ T_{Jmax}$	$I_{F(AV)} @ T_{Jmax}$	$I_{FSM} @ T_J = 150^{\circ}C$	$V_F @ T_J = 25^{\circ}C$
	V	°C	A	A	A	V
1600V - Rectifier - Standard						
SKR 3,5 Qu bond ⁶⁾	1600	150	25	18	200	1.00
SKR 4,2 Qu bond ⁶⁾	1600	150	35	28	270	1.00
SKR 4,8 Qu bond ⁶⁾	1600	150	45	35	350	1.00
SKR 5,6 Qu bond ⁶⁾	1600	150	50	40	490	1.00
SKR 6,2 Qu bond ⁶⁾	1600	150	65	50	600	1.00
SKR 7,0 Qu bond ⁶⁾	1600	150	75	60	890	1.00
SKR 8,9 Qu bond ⁶⁾	1600	150	140	110	1380	1.00
SKR 10,3 Qu bond ⁶⁾	1600	150	170	135	1650	1.00
SKR 12,4 Qu bond ⁶⁾	1600	150	235	190	2300	1.00
SKR 15,2 Qu bond ⁶⁾	1600	150	330	270	3800	1.00
SKR 16,3 x 18,2 Qu bond ⁶⁾	1600	150	365	305	5100	1.00
SKN 18,2 Qu bond ⁶⁾	1600	150	380	318	5500	1.00
SKN 22,4 Qu bond ⁶⁾	1600	150	770	634	9450	1.00
1600V - Rectifier - PEP						
SKR012XP16B1F	1600	175	35	26	200	0.97
SKR018XP16B1F	1600	175	50	38	270	0.97
SKR023XP16B1F	1600	175	63	48	350	0.97
SKR031XP16B1F	1600	175	85	64	490	0.97
SKR106XP16B1F	1600	175	290	220	1650	0.97
SKR231XP16B1T	1600	175	665	510	4200	0.97
SKR297XP16B1T	1600	175	840	640	5100	0.97

Footnotes: 6) solderable top metallization on request

Type						
	V_{RRM}, V_{DRM}	$I_{T(DC)} @ T_J = 130^{\circ}C$	$I_{FSM} @ T_J = 130^{\circ}C$	$V_{GT} @ T_J = 25^{\circ}C$	$I_{GT} @ T_J = 25^{\circ}C$	$t_q @ T_J = 130^{\circ}C$
	V	A	A	V	A	µs
1600V - Thyristor Central Gate						
SKT 8,9 Qu ZG bond ⁶⁾	1600	105	1000	1.65	100	150
SKT 10,3 Qu ZG bond ⁶⁾	1600	125	1250	1.65	100	150
SKT 12,4 Qu ZG bond ⁶⁾	1600	165	1800	1.65	100	150
SKT 13,5 Qu ZG bond ⁶⁾	1600	185	2300	1.65	100	135
SKT 15,2 Qu ZG bond ⁶⁾	1600	215	3200	1.65	100	150
SKT 18,2 Qu ZG bond ⁶⁾	1600	250	5000	1.65	100	150
SKT 24,3 Qu ZG bond SG ⁶⁾	1600	480	8200	1.65	150	150
1600V - Thyristor Corner Gate						
SKT 5,6 Qu RG bond ⁶⁾	1600	60	280	1.65	100	150
SKT 7,0 Qu RG bond ⁶⁾	1600	75	450	1.65	100	150
SKT 8,9 Qu RG bond ⁶⁾	1600	105	1000	1.65	100	150
SKT 10,3 Qu RG bond ⁶⁾	1600	125	1250	1.65	100	150
SKT 12,4 Qu RG bond ⁶⁾	1600	165	1800	1.65	100	150

Footnotes: 6) solderable top metallization on request

Accessories

Heatsinks / Fans

SEMIKRON offers a wide range of heat sinks including forced and natural air cooling. The heatsinks are available for capsules, insulated base modules or IPMs.

SEMIKRON offers a broad range of axial, centrifugal and radial fans for different inverter designs.

Heatsinks	218
Fans	220

For detailed information please refer to data sheets.

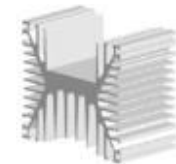
Further information
www.semikron.com/heatsinks
www.semikron.com/fans

Heatsinks

Forced air-cooled



Natural cooled



Fans

Axial



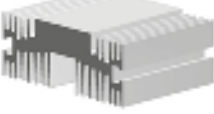
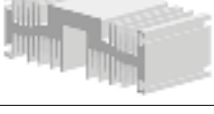
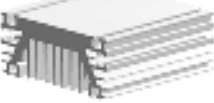
Centrifugal



Radial

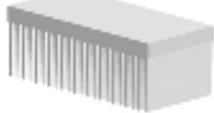
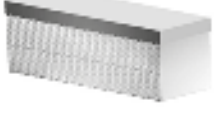
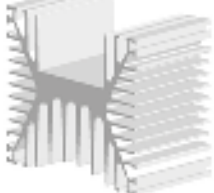


Accessories / Heatsinks

Type							
	Suitable for	R_{thsa} natural cooling	R_{thsa} forced air cooling	Weight	Weight		Produkt Picture
		K/W	K/W	kg	kg/m		
Forced-air cooled							
N 4	Capsules	-	0.04	6.3	25.1		
P 11	Capsules	0.2	0.05	3.8	15		
P 17	Capsules	0.45	0.12	1.5	10.6		
P 18	Capsules	0.37	0.08	1.6	12.2		
P 8 ⁹⁾	Capsules	0.35	0.07	1.7	9.6		
P 8,5 ⁹⁾	Capsules	0.3	0.08	1.5	9.5		
P 9 ⁹⁾	Capsules	0.21	0.06	4.1	17.8		
U 3	Capsules	0.14	0.06	7.1	23.7		
P 21 ⁹⁾	Isolated base modules	-	0.02	4.1	40.8		
R 4A	Isolated base modules	1.4	0.38	0.6	-		

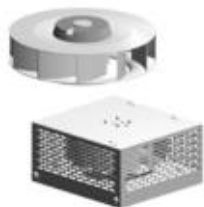
Footnotes: 9) Non standard item, available on request only, typical minimum batch quantities of 60 pieces will apply

Accessories / Heatsinks

Type							
	Suitable for	R_{thsa} natural cooling	R_{thsa} forced air cooling	Weight	Weight		Produkt Picture
		K/W	K/W	kg	kg/m		
Forced-air cooled							
P 16	SKiiP or modules	-	0.06	1.3	23.5		
Px 308 ⁹⁾	SKiiP or modules	-	0.013	2	12.2		
P 1	Studs or modules	0.7	0.4	0.8	11.3		
P 3	Isolated base modules	0.45	0.14	0.7	17.6		
Natural cooled							
P 4 ⁹⁾	Stud device	0.27	-	4.1	20.6		

Footnotes: 9) Non standard item, available on request only, typical minimum batch quantities of 60 pieces will apply

Accessories / Fans

Type								
	V_{in}	f	V_{air}/t	P_{max}	T_{Amax}	Weight	Noise	
	V	Hz	m³/h	W	°C	kg	dB	Produkt Picture
Axial Fans								
SKF 3-230-01	230	50 / 60	150 / 174	15 / 14	70	0.55	37 / 41	
SKF RE-024-02	24	-	500	90	75	0.43	76	
SKF SR-024-01	24	-	56	3.6	70	0.085	43	
SKF 9-230-01	230	50 / 60	375 / 440	24 / 26	70	1	54 / 60	
Centrifugal Fans								
SKF 17A-230-11	230	50 / 60	850 / 930	110 / 120	70	2	74	
SKF 17B-230-12	230	50 / 60	1175 / 1300	230	70	6.1	73 / 76	
SKF N4-230-03 ²⁾	230	-	1500 / 1700	250 / 390	80 / 80	3.1	76 / 78	
Radial Fans								
SKF 16A-230-01	230	50 / 60	630 / 590	130 / 140	60 / 50	3.3	59	
SKF 16P-230-01	230	50 / 60	1125	165	60	3.9	-	
SKF 16B-230-01	230	50 / 60	640 / 580	167 / 191	70 / 50	3.75	58 / 57	
SKF 16A-230-11	230	50 / 60	630 / 590	130 / 140	60 / 50	3.3	59	

Footnotes: 2) In production new

INFORMATION

Service & Contact





Technical Seminars at SEMIKRON

SEMIKRON develops innovative power electronics products for space saving, energy efficient electronic systems. Our power modules are the heart of modern, energy efficient motor drives and industrial automation systems. But that's not all – our products are also paving the way for reduced global energy consumption in the areas of power supplies, the production of renewable energy and electric commercial vehicles. Our success is based on close cooperation and technical dialogue between our application engineers, product managers and our customers.

This close partnership is also reflected in our practical range of technical seminars and roadmap workshops which cover all the relevant topics in our product scope and application areas. You are cordially invited to any of our seminars and workshops.

Examples of topics at our technical seminars

- SiC chips and their application-specific advantages
- Three level topology - topology, protection concepts, application areas
- Reliability and service life of power modules
- Loss calculation, thermal resistance, module dimensioning
- IGBT driver topologies
- Parallel connection of power modules
- Simulation tool SEMISEL
- Typical problems in inverter design
- Motor drives – topologies, challenges, trends
- Solar inverters – topologies, challenges, trends
- UPS inverters – topologies, challenges, trends
- Wind inverters – topologies, challenges, trends
- Fault analysis of power semiconductors

Further information: www.semikron.com/technical-seminars

Technologies

Single Sided Sintering Technology

Single Sided Sintering (SSS) technology utilises a highly reliable silver sinter layer to connect the chip to the ceramic substrate (DBC), replacing the standard solder layer.



Double Sided Sintering Technology

Double Sided Sintering Technology

In Double Sided Sintering technology (DSS) two sinter layers are used: the chip is sintered to the DBC and a flex layer is sintered on top of the chip. The flex layer replaces the wire bonds, resulting in maximum reliability and current capability.



Direct Pressed Die Technology™

Direct Pressed Die Technology™

Direct Pressed Die (DPD) technology includes a Double Sided Sintered (DSS) chip on a ceramic substrate that is pressed onto the heatsink by a defined force directly on top of the chip. This optimises reliability and thermal resistance, combined with flexibility with regard to cooling and integration in standard power modules.



SKiN® Technology inside

SKiN® Technology

SKiN technology is based on Double Sided Sintering. It also integrates the heatsink using a third sinter layer. SKiN technology is free of bond wires, thermal grease and solder, combining maximum reliability with minimum thermal resistance.

SPRiNG Technology

SPRiNG technology utilises springs to establish the contacts to the PCB. It is the best choice for ultra fast assembly and when field reliability in harsh environments is critical.

SKiIP® Technology

Semikron's SKiIP technology utilises spring loaded mechanical and electrical contacts and features a compact and durable module construction.

Press-Fit Technology

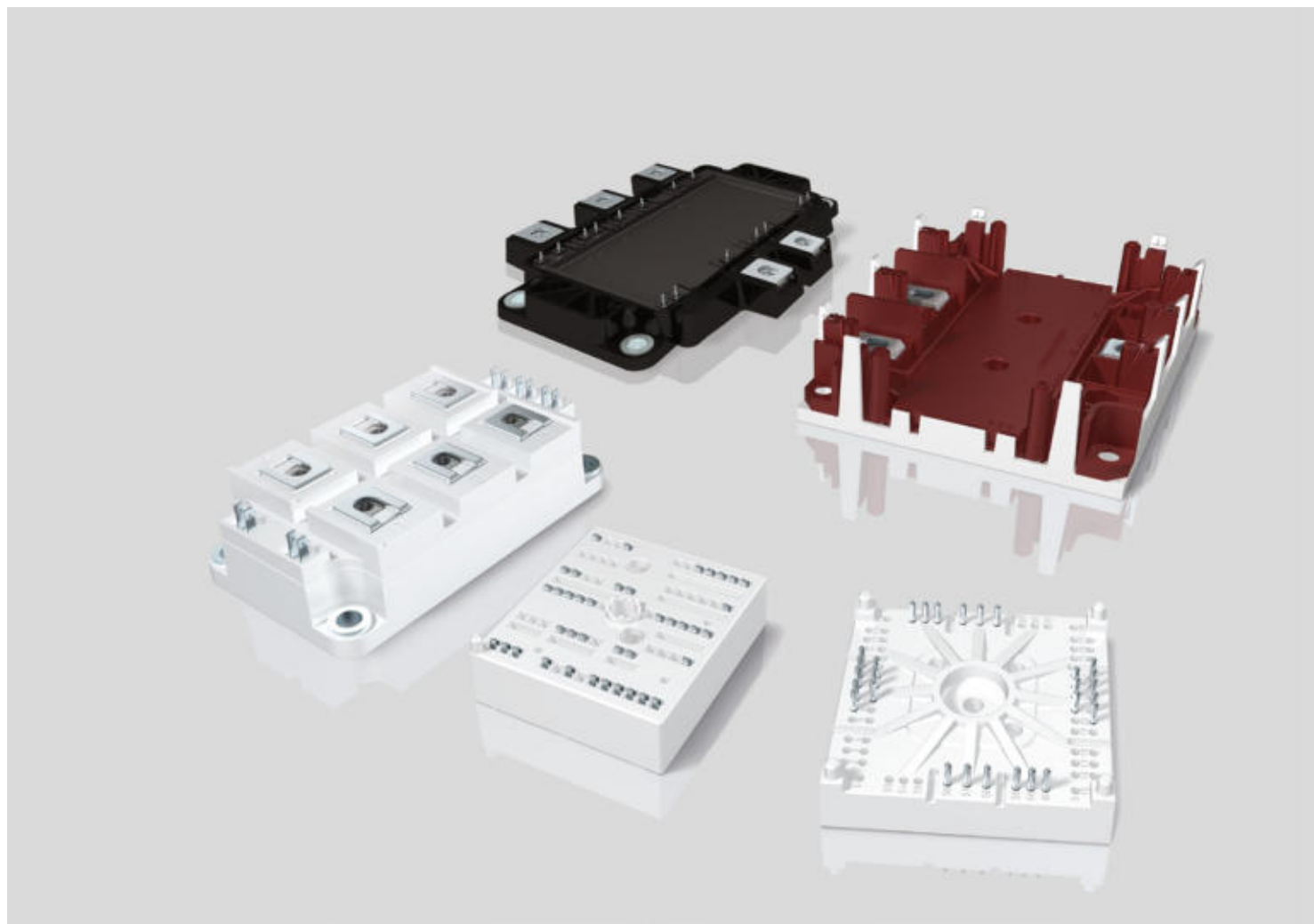
Alternative concept to solder for module to PCB assembly press-fit pins ensure a reliable connection in a solder-free production process.

SOLDER Technology

The tried and tested interface for power modules. Solder pins are a robust interface that are used in a wide range of applications worldwide. Solder processes are widely used and easy to implement.

SCREW Technology

The standard interface to the power terminals for medium and high-power modules. Easy to use and robust power interface to AC and DC terminals.



Product Sample Request

Product sample service at a click

The development of prototypes is more precise and faster if power electronics modules are integrated during the design-in phase.

As of now, you can request samples for electronic design online from SEMIKRON. This is available during this project phase and gives you quick and easy access to our samples with no obligation. Depending on the design, application and the size of the project, we also offer this service free of charge.

Three steps to getting your SEMIKRON sample

- **Initial contact** Fill in the sample order request form
- **Consultation** Response from SEMIKRON within 24 hours
- **Dispatch** SEMIKRON sends the sample without lengthy waits

Further information: www.semikron.com



Тел.: +375 17 310 44 44

ЭйБиЭн

Tel.: +375 44 592 00 86
Tel. +375 33 366 51 85
<https://www.abn.by>
info@abn.by

www.semikron.com



SemiSel Simulation Free Support for Your Converter Design

Applications

SemiSel is the SEMIKRON online calculation and simulation tool for losses, temperatures and optimal choice of power electronic components (www.semikron.com). The days when a module was purchased solely on the basis of its nominal current are over. Today, increased product diversity in the field of power semiconductors calls for comparisons beyond the information contained in data sheets. Only a comparison under application-oriented conditions, such as voltage level, switching frequency or cooling conditions, can demonstrate differences in the performance of the devices available. Miniaturisation combined with higher power densities makes it essential to have information on device losses and temperatures to be able to specify requirements for a cooling system at an early stage of product development.

Benefits

In proper topology design the risk arising from variations in both component and electrical topology parameters ought to be considered. These facts are only a few of the many points that need to be considered when developing a power electronics system. And this is where efficient support is provided by SemiSel to enabling developers to make the right decision. SemiSel is still the most comprehensive free tool of its kind that can be used to investigate different power electronic topologies under different operating conditions.

This tool has been available online since 2001, and it has been continually improved and expanded since its introduction. It provides a good compromise between user-friendliness, applications and speed. The calculation functions range from product proposal for nominal operating conditions to drivers and heat sink specifications and product selections for specific overload conditions and complex calculations, such as complete load cycles that take into account temperature cycling problems.



Available in German, English, Chinese and Japanese

Application Manual Power Semiconductors

IGBTs and MOSFETs integrated in power modules are the key components of power electronic topologies today and are continuously finding their way into new fields of application. This goes hand in hand with the ever increasing call for line rectifier diodes and thyristors as a cost effective way of connecting the topologies to the power grid. The aim of the application manual is to provide users with support in selecting and using such devices.

The manual contains basic background knowledge on semi-conductors in order to enable a better understanding of application possibilities and limits. More in-depth explanations are given on packaging and assembly technologies, because of the major influence they have on module properties and limitations in field applications. The manual also includes statements on reliability data, life cycle analyses and key test processes.

The Application Manual also explains the structure of datasheets and provides notes to help users better understand datasheet parameters. The Application Manual contains detailed application-related information on electrical configuration under important operating conditions, driver and protection elements for semiconductors, thermal dimensioning and cooling, tips on parallel and series connection, assembly tips for optimised power layouts with regard to parasitic elements and the requirements arising from specific ambient conditions.

This book is written for users and provides help with component selection and design-in work. It couples a wealth of experience with detailed practical knowledge, the result being a vast pool of information which up till now has been spread across various individual articles or in the minds of experts only. The second revised edition was published in 2015.

Further information: www.semikron.com/application-manual

Abbreviations

Acronym	English
E_{off}	Energy dissipation during turn-off
E_{on}	Energy dissipation during turn-on
E_{rr}	Energy dissipation during reverse recovery (diode)
f	Operating frequency
f_{max}	Maximum frequency
I_C	Continuous collector current
I_{Cnom}	Nominal collector current
I_D	Direct output current (of a rectifier connection)
I_D	Continuous drain current (MOSFET)
I_F	Forward current (actual value)
I_{FAV}	Mean forward current
I_{FSM}	Surge forward current
I_{GT}	Minimum guaranteed gate trigger current
$I_{outPEAK}$	Output peak current (driver)
$I_{overload}$	Overload current for a specified time
i_T	On-State current (instantaneous value)
I_{TAV}	Mean on-state current
I_{TSM}	Surge on-state curren
$Q_{out/pulse}$	Output charge per pulse (Driver)
Q_{rr}	Reverse recovery charge
$R_{DS(on)}$	Drain-source on-resistance (MOSFET)
r_T	On-state slope resistance, forward slope resistance (Thyristor)

Acronym	English
$R_{th(c-s)}$	Thermal resistance case to heat sink
$R_{th(j-a)}$	Thermal resistance junction to ambient
$R_{th(j-c)}$	Thermal resistance junction to case
$R_{th(j-s)}$	Thermal resistance junction to sink
$R_{th(s-a)}$	Thermal resistance heat sink to ambient
T_c	Case temperature
T_j	Junction temperature
t_q	Circuit commutated turn-off time (thyristor)
T_s	Heatsink temperature
V_{air}/t	Air flow
V_{CE}	Collector-emitter voltage
V_{CEsat}	Collector-emitter saturation voltage
V_{DRM}	Repetitive peak off-state voltage
V_{DS}	Drain-source voltage
V_F	Forward voltage
$V_{G(off)}$	Turn-off gate voltage level (driver)
$V_{G(on)}$	Turn-on gate voltage level (driver)
V_{GT}	Gate trigger voltage
V_{in}	Input voltage
$V_{isol(IO)}$	Isolation test voltage (r.m.s. /1 min.) input-output (driver)
V_{RRM}	Repetitive peak reverse voltage
V_T	On-state voltage (Thyristor)
W	Weight

Applications



Motor Drives

Converters for all types of electric motors utilized in industry. SEMIKRON power semiconductors help to maximize efficiency in any 2 or 4-quadrant drive or servo.



Wind Energy

With power semiconductors in the converters or in the drives controlling blade pitch. Almost one in three wind turbines in the world is fitted with SEMIKRON power modules.



Solar Energy

With focus on cost and efficiency in photo voltaic systems, SEMIKRON has products that cover the entire spectrum from micro inverters and medium-power multi string to megawatt central inverters.



Power Quality

PFC, AVC and UPS systems ensure a clean reliable mains supply is kept available to critical applications. SEMIKRON power modules are at the heart of critical power systems.



Process and Medical Power Supplies

In electrotechnology and medical diagnostics, power semiconductors at the mains input facilitate and improve processes and save energy.



Urban Transport Equipment

Electrical transportation applications demand high reliability of the drive systems with their cyclic operating profile and the continuous auxiliary supplies over years of operation.



Car Charger Stations

EV charging based on DC-transmission to the electric vehicle needs especially powerful semiconductor modules. Reliable and efficient SEMIKRON power modules drive the distance-range of e-mobility.



Energy Storage

For integration of renewable energy sources into the grid, high-performance energy storage systems are essential to ensure permanent grid stability. SEMIKRON offers a variety of power modules that are ideally suited for this application.

Applications Electric & Electrified Vehicles



Light Duty Vehicles

Power electronics form the heart of any electric vehicle. SEMIKRON's solder-free semiconductor modules and systems are particularly well suited to the robust needs of today's vehicles.



Battery Vehicles

Battery driven vehicles, mostly for material handling such as fork lifters, require maximum availability. SEMIKRON's SKAI LV systems are the ideal solution for this application.



Heavy Duty Vehicles

For heavy duty vehicle applications such as hybrid and all-electric trucks and buses, SEMIKRON offers a broad portfolio, from highly reliable modules and IPMs to highly integrated SKAI HV systems.



SEMIKRON Online Shop

Delivering expert support

Our specialty lies in the delivery of expert support to small and medium-sized enterprises by offering them the following services:

Technical & sales support

- Reply within 24 hours
- Multilingual sales and support
- Design-in-support directly from manufacturers' specialists

Worldwide shipping

- Fast shipping to more than 100 countries
- Low-volume purchases also possible
- Shipping directly from manufacturer's warehouse
- Over 600 conventional SCRs, IGBT modules, bridge rectifiers and IPMs in stock

Transparency & efficiency

- Transparent price breakdowns online
- Updated information
- Instant quotes using the online quotation tool

Cross reference search

Find a fully compatible SEMIKRON device for any other brand:
shop.semikron.com/en/Cross-Reference-Search/



Visit us at
shop.semikron.com



We are close
to our customers



Contact Africa

SEMIKRON Online Shop Global Direct Sales

Online
Shop

SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
---	---

South Africa

Distributor

Semiconductor Solutions Route 21, Corporate Park, Cnr Regency/Sovereign Streets 0062 Irene, Centurion South Africa	Phone : +27 12 345 6060 Phone alternative : +27 82 820 8653 Fax : +27 12 345 6070 E-mail sales : neels.krieg@semiconduct.co.za www.semiconduct.co.za
---	--

Contact Asia

SEMIKRON Online Shop China Direct Sales

Online
Shop

Zhuhai SindoPower Electronics Company Limited Unit 3, Ground Floor, 2#, Manufacturing Centre , No. 1 Software Road 519080 Zhuhai, Guangdong China	Phone : +86 756 3396 619 Fax : +86 756 3396 677 E-mail : sales.cn@semikron.com shop.semikron.cn
--	--

China

Main site

SEMIKRON Electronics (Zhu Hai) Co. Ltd. Unit 1, Ground Floor, 2#, Unit 2,4,5,7, Ground Floor, 5#, Manufacturing Centre, No. 1 Software Road 519080 Zhuhai, Guangdong China	Phone : +86 756 3396 707 Fax : +86 756 3396 773 E-mail sales : sales.zhuhai@semikron.com E-mail jobs : jobs.skc@semikron.com www.semikron.com
---	---

Branch
office

SEMIKRON Shanghai Room 1603, Building A, Greenland Riverside International Center, No.596 Middle Longhua Road, Xuhui District 200032 Shanghai China	Phone : +86 21 5436 2988 Fax : +86 21 5436 3998 E-mail sales : sales.shanghai@semikron.com E-mail jobs : jobs.skc@semikron.com www.semikron.com
---	---

Branch
office

SEMIKRON Beijing Room 1603, Building A, Chengjian Plaza, No. 18 Beitapingzhuang Road, Haidian District 100088 Beijing China	Phone : +86 10 8225 5398 Fax : +86 10 8225 5836 E-mail sales : sales.beijing@semikron.com E-mail jobs : jobs.skc@semikron.com www.semikron.com
--	--

Branch
office

SEMIKRON Shenzhen Room 13C, Golden Century, No. 6033 ShenNan Road, Futian District 518040 Shenzhen China	Phone : +86 755 8256 2866 Fax : +86 755 8345 8937 E-mail sales : sales.shenzhen@semikron.com E-mail jobs : jobs.skc@semikron.com www.semikron.com
---	---

Distributor

HK China Group Limited (East) News Road, Futian District, East Wing, 1 Electric Razor Information Building, 1717-1721, Room 1717, East Block 510800 Shenzhen China	Phone : + 86 755 8373 3223 Fax : +86 755 8373 3798 E-mail : hongkongchina_sz@163.com
--	--

Distributor

Semcor (Qingdao) Electronic Co., Ltd. No. 192 Zhuzhou Rd., Hi-Tech Park Qingdao China	Phone : +86 532 8870 1773 Fax : +86 532 8870 1478 E-mail : luying.zhang@semcor.com.cn
---	---

Distributor

Weltronics Component Limited Rm 611-622, 6/F., Chang Ping Commercial Bldg., 99 Hong Hua Road, Futian Free Trade Zone 518038 Shenzhen China	Phone : +86 755 8348 0330 Fax : +86 755 8348 0105 E-mail : market@weltronics.com
---	--

Contact Asia

Online Shop	SEMIKRON Online Shop Global Direct Sales	
	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
Main site	Hong Kong SAR of China	
	SEMIKRON (HONG KONG) CO. Ltd. Unit 403A, 4th Floor, Golden Centre, 188 Des Voeux Road Central Hong Kong SAR of China	Phone : +852 3426 3366 Fax : +852 3426 3399 E-mail sales : sales.skhk@semikron.com E-mail jobs : jobs.skc@semikron.com www.semikron.com
Distributor	Crypson Electronics (HK) Co. Ltd 11/F, Wang Cheong Enterprises, Centre, 69 Chai Wan Kok St Tsuen Wan Hong Kong SAR of China	Phone : 010 65189830 205 Fax : 010 656447 1582
Distributor	FREEMAN Industrial Supplies Co. Flat C,10/F, China Fen Hin, Building, 5 Cheung Yue Street Cheung Sha Wan, Kowloon Hong Kong SAR of China	Phone : +852 2365 3231 Fax : +852 2365 0476 E-mail : may_mhwong@yahoo.com.hk
Distributor	Richardson RFPD Hong Kong Limited 20th Floor, Tower 2, 88 Container Port Road, Ever Gain Plaza, Kwai Chung Kwai Tsing Hong Kong SAR of China	Phone : + 86 755 8294 3736

Contact Asia

Online Shop	SEMIKRON Online Shop Global Direct Sales	
	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
Main site	India	
	SEMIKRON Electronics Private Limited EL 148, TTC Industrial Area, MIDC Electronics Zone, Mahape 400710, Navi Mumbai India	Phone : +91 22 2762 8600 Fax : +91 22 2762 8641 45 E-mail sales: sales.skind@semikron.com E-mail jobs: jobs.skind@semikron.com www.semikron.com
Distributor	Airmaster Rectifiers Pvt. Ltd. G78, Triveni Commercial Complex, Sheikh Sarai Phase - 1 110017 New Delhi India	Phone : +91 11 4131 5934 Fax : + 49 11 2386 1508 E-mail : office@airmasterindia.com E-mail alternative ajaykanwar@airmasterindia.com
Distributor	Ghosh & Co. 171/C, Lenin Sarani 700013 Kolkata India	Phone : +91 33 2212 8727 Fax : +91 33 2212 8727 E-mail : debasis_ghosh@vsnl.net
Distributor	INNOVA ENTERPRISES Sr No-81, Plot No-3/2, Nda Khadakwasla Road, Shivane 411023 Pune India	Phone : +91 20 2529 0077 Phone alternative : +91 20 2529 1177 Fax : +91 20 2529 2188 E-mail : sales_innova@vsnl.net
Distributor	Premier Controls 122, 1st Floor, Valluvar Kottam High Rd 600034 Chennai India	Phone : +91 44 2825 8882 Fax : +91 44 2827 4307 E-mail : premiercontrols@hotmail.com
Distributor	Rectifier House (India) Pvt. Limited 101, 1st Floor, Munani Trade Centre, near Model CO-OP Bank, Waliv Phata 401208 Mumbai India	Phone : +91 99 3059 6249 Fax : +91 22 2386 1262 E-mail : info@rectifier.in
Distributor	S.V. ELECTRONICS 135, 1st Floor, Archana Arcade, Behind Hotel Ramakrishna 500025 Secunderabad India	Phone : +91 40 2782 1970 Phone alternative : +91 40 2782 1971 Fax : +91 40 2782 3696 E-mail : anil@svelectro.in
Distributor	V V ELECTROTECH 113, Saffron Complex, Fatehgunj Circle, Fatehgunj, 390002 Vadodara India	Phone : +91 265 278 6781 Phone alternative : +91 265 278 8438 Fax : +91 265 278 8438 E-mail : sales@vvelectrotech.com

Contact Asia

SEMIKRON Online Shop Global Direct Sales

Online Shop	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
Japan		
Main site	SEMIKRON K. K. Sarugakucho Kikuhide Bldg. 4F, 2-8-4 Sarugakucho, Chiyodaku 101-0064 Tokyo Japan	Phone : +81 3 6895 1396 Fax : +81 3 6895 5078 E-mail sales : sales.skj@semikron.com E-mail jobs : jobs.skj@semikron.com www.semikron.com
Main site	SEMIKRON Osaka branch office Daitaku17 bldg 6F, 4-13-22 Nishi-Nakajima, Yodogawa-ku, 532-0011 Osaka Japan	Phone : +81 6 6305 3299 Fax : +81 6 6305 3560 www.semikron.com
Distributor	NADEX CO., LTD. 9-27 Furuwatari-cho, Naka-ku, Nagoya City, Aichi 460-8338 Nagoya Japan	Phone : +81 5 2322 3511 Fax : +81 5 2332 4324
Distributor	TOKYO ELECTRON DEVICE LIMITED Yokohama East Square 1-4, Kinko-cho, Kanagawa-ku, Yokohama City, Kanagawa 221-0056 Yokohama Japan	Phone : +81 4 5443 4000 Fax : +81 4 5443 4050
Distributor	EICH Corporation 5F, KDX Nishi Shinjuku Bldg., 7-22-45, Nishi Shinjuku, Shinjuku-ku 160-0023 Tokyo Japan	Phone : +81 3 5348 7716 Fax : +81 3 5348 4145
Distributor	KTL Corporation 9F, Yamatane Building · 1-2-21, Ecchujima · Koto-ku 135-0044 Tokyo Japan	Phone : +81 3 5639 1102 Fax : +81 3 5639 1156
Distributor	Kenden Corporation Mita 43MT Building, 3-13-16 Mita, Minato-ku 108-0073 Tokyo Japan	Phone : +81 3 3769 5311 Fax : +81 3 3769 5333

SEMIKRON Online Shop Global Direct Sales

Online Shop	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
South Korea		
Main site	SEMIKRON Co. Ltd. 9, Sosam-ro 36beon-gil, Sosa-gu, Bucheon-si 14701 Gyeonggi-do South Korea	Phone : +82 323 462 830 Fax : +82 323 462 834 E-mail sales : Sales.skkor@semikron.com E-mail jobs : jobs.skkor@semikron.com www.semikron.com
Distributor	RAON Device 202,2nd Floor, 29-22, Wolgot Haean-ro, Si-Heung -si, Gyeonggi-do South Korea	Phone : +82 505 306 3079 Fax : +82 505 309 3079 E-mail : Justin.Song@Raon-Device.com
Distributor	Wintech-W Co., Ltd 1417, 90, Gyeongin-ro 53gil, Guro-gu, Seoul South Korea	Phone : +82 226 837 240 Fax : +82 226 837 241 E-mail : kdu@wintechw.co.kr www.wintechw.co.kr
Distributor	Dong-San Electronics A-117, 9-10, Seojeon-ro 38beon-gil, Busan gin-gu, Busan South Korea	Phone : +82 518 049 133 Fax : +82 518 187 400 E-mail : dsc9133@hanmail.net
Distributor	CS Component GA-4303, Jungang Circulation Comlex Guro-2-dong, Guro-guo, Seoul South Korea	Phone : +82 266 794 630~1 Fax : +82 226 860 291 E-mail : art21-j@icscom.co.kr
Taiwan		
Main site	SEMIKRON (HONG KONG) CO. Ltd. Taiwan Representative Office 8F, No. 32 Guang-zhou Street, Wanhua Dist. 108 Taipei City Taiwan	Phone : +886 930 347 711 Fax : +886 282 820 403 E-mail : DavidTJ.Lee@semikron.com www.semikron.com

Contact Australia & New Zealand

Online Shop	SEMIKRON Online Shop Global Direct Sales	
	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
Main site	Australia & New Zealand	
	SEMIKRON Pty. Ltd. 8/15 Ricketts Road Mount Waverley VIC 3149 Melbourne Australia	Phone : +61 385 615 600 E-mail : Jaison.Jacob@semikron.com E-mail jobs : jobs.skaus@semikron.com www.semikron.com

Contact Europe

Online Shop	SEMIKRON Online Shop Global Direct Sales	
	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
Main site	Austria	
	SEMIKRON Gleichrichterelemente Ges.m.b.H. Hirschstettner Strasse 19-21 (Stg.I/EG-OE1) 1220 Wien Austria	Phone : +43 158 6365 80 Fax : +43 158 6365 832 E-mail sales : sales.ska@semikron.com E-mail jobs : jobs.ska@semikron.com www.semikron.com
Main site	Belgium	
	<i>Flemish-speaking</i> SEMIKRON Linie 502 7325 DZ Apeldoorn Netherlands	Phone : +31 555 295 295 Fax : +31 555 295 290 E-mail sales : sales.sknl@semikron.com E-mail jobs : jobs.sknl@semikron.com www.semikron.com
Main site	<i>French-speaking</i> SEMIKRON S.A.R.L 130 route de Cormeilles, BP 70 78501 Sartrouville Cedex France	Phone : +33 130 868 000 Fax : +33 139 151 083 E-mail sales : sales.skf@semikron.com E-mail jobs : jobs.skf@semikron.com www.semikron.com
Main site	Czech Republic	
	SEMIKRON s.r.o. Teslova 3 30100 Plzen Czech Republic	Phone : +420 378 051 400 Fax : +420 378 051 401 E-mail sales : sales.skczech@semikron.com www.semikron.com
Distributor	Semic Trade, s.r.o. Volutová 2521/18, Praha 5 158 00 Prague Czech Republic	Phone : +420 251 551 204 E-mail : semic@semic.cz
Main site	Denmark	
	SEMIKRON AB Östra Köpmangatan 18 44430 Stenungsund Sweden	Phone : +46 303 816 16 Fax : +46 303 816 31 E-mail sales : sales.sks@semikron.com E-mail jobs : jobs.sksf@semikron.com www.semikron.com
Main site	France	
	SEMIKRON S.A.R.L 130 route de Cormeilles, BP 70 78501 Sartrouville Cedex France	Phone : +33 130 868 000 Fax : +33 139 151 083 E-mail sales : sales.skf@semikron.com E-mail jobs : jobs.skf@semikron.com www.semikron.com
Distributor	FGET.sa ZI Mi-Plaine 17, rue de Genève, BP 354 69746 Genas Cedex France	Phone : +33 472 796 415 Fax : +33 472 796 410 E-mail : info@fget.fr www.fget.fr
Distributor	DIRECT SA ZAC de la vente Olivier 960 rue du Noyer des Bouttières 76800 Saint-Etienne-du-Rouvray France	Phone : +33 232 102 343 www.direct.fr

Contact Europe

Online Shop	SEMIKRON Online Shop Global Direct Sales	
	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
Main site	Germany	
	SEMIKRON Elektronik GmbH & Co. KG / SEMIKRON INTERNATIONAL GmbH Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 0 Phone sales : +49 911 6559 6663 Phone purchase : +49 911 6559 6767 Phone jobs : +49 911 6559 460 Fax : +49 911 6559 262 E-mail sales : sales@semikron.com E-mail jobs : jobangebote@semikron.com www.semikron.com
Technical Offices	SEMIKRON, Technisches Büro Südwest, Karlsruhe Dipl.-Ing. (FH) Thomas Birnbreier Guntherstr. 1 76297 Stutensee Germany	Phone : +49 724 4720 819 Phone alternative : +49 160 8830 497 Fax : +49 724 4720 824 E-mail : thomas.birnbreier@semikron.com www.semikron.com
Technical Offices	SEMIKRON, Technisches Büro Solutions Solar, Mannheim Dipl.-Ing. Walter Schmidt Carl-Orff-Str. 9 69488 Birkenau-Herrenwiese Germany	Phone : +49 620 1393 090 Phone alternative : +49 171 3000 289 Fax : +49 911 6559 775 97 E-mail : walter.schmidt@semikron.com www.semikron.com
Technical Offices	SEMIKRON, Technisches Büro West-Mitte, Wiesbaden Jörg Jung Schönbornstr. 4 65439 Flörsheim Deutschland	Phone : +49 614 5540 708 Phone alternativ : +49 160 8986 557 Fax : +49 911 6559 775 61 E-mail : joerg.jung@semikron.com www.semikron.com
Technical Offices	SEMIKRON, Technisches Büro Norddeutschland Dipl.-Physiker Martin Boing Stadtlohner Str. 8 48691 Vreden Deutschland	Phone : +49 911 6559 6200 Phone alternativ : +49 176 3008 6200 Fax : +49 911 6559 776200 E-mail : martin.boing@semikron.com www.semikron.com
Distributor	Arrow Central Europe GmbH Frankfurter Straße 211 63263 Neu-Isenburg Deutschland	Phone : +49 6102 5030 0 Fax : +49 6102 5030 8455

Main site	Italy	
	SEMIKRON S.r.l. Via Laurentina km 24,200 00071 Pomezia (Rome) Italy	Phone : +39 069 114 241 Fax : +39 069 1142 4711 E-mail sales : sales.ski@semikron.com E-mail jobs : jobs.ski@semikron.com www.semikron.com
Main site	SEMIKRON S.r.l. Via Mecenate 76/22 20138 Milano Italy	Phone : +39 0250 1130 Fax : +39 0691 1424 711 E-mail sales : SKI-Sales-Milano@semikron.com E-mail jobs : jobs.ski@semikron.com www.semikron.com
Distributor	Bongiorno Srl Via Galvani 9 35030 Rubano PD Italy	Phone : +39 049 8974 236 Phone alternative : +39 049 8974 588 Fax : +39 049 8974240 E-mail : info@bongiornocomponenti.it
Distributor	TOTEM ELECTRO SRL Viale Lombardia 66 20131 Milano Italy	Phone : +39 02 2885 111 Fax : +39 02 2885 1150 E-mail : totem@totemelectro.com
Main site	Netherlands	
	SEMIKRON B.V. Linie 502 7325 DZ Apeldoorn Netherlands	Phone : +31 555 295 295 Fax : +31 555 295 290 E-mail sales : sales.sknl@semikron.com E-mail jobs : jobs.sknl@semikron.com www.semikron.com
Main site	Poland	
	SEMIKRON Sp. z o.o. ul. Pozaryskiego 28 04-703 Warszawa Poland	Phone : +48 226 157 984 Fax : +48 226 133 887 E-mail sales : sales.skpl@semikron.com E-mail jobs : jobs.skpl@semikron.com www.semikron.com
Main site	Russia	
	Semikron Ltd. Gabrichevskogo Str. 5; Building 1 125367 Moscow Russia	Phone : +7 812 2329 825 Fax : +7 812 2329 825 E-mail : info@semikron.spb.ru E-mail jobs : jobs.skru@semikron.com www.semikron.com
Technical Office	SEMIKRON Ltd. B. Pushkarskaya 41 197101 Sankt Petersburg Russia	Phone : +7 812 2329 825 Fax : +7 812 2329 825 E-mail : info@semikron.spb.ru E-mail jobs : jobs.skru@semikron.com www.semikron.com
Distributor	COMPEL JSC 1/2 Derbenevskaya Str., Bldg. 1 115114 Moscow Russia	Phone : +7 495 234 7762 Fax : +7 495 234 7763 E-mail : msk@compel.ru www.compel.ru
Distributor	Corporation IP Ltd. 131, Plakhotnogo Str. 630136 Novosibirsk Russia	Phone : +8 800 555 3361 E-mail : sales@iphold.ru www.iphold.ru
Distributor	PTElectronics LCC Prospect Engels, d. 71 194214 St. Petersburg Russia	Phone : +7 812 324 6350 Fax : +7 812 324 6611 E-mail : semicond@ptelectronics.ru https://ptelectronics.ru/
Distributor	Serbia	
	VREMEPLOV d.o.o. Vidikovacki Venac 104g, Lokal 75 11137 Beograd Serbia	Phone : +381 11 265 3685 Fax : +381 11 265 3618 E-mail : zoran@vremeplov.co.yu
Main site	Slovakia	
	SEMIKRON s.r.o. Steruská ul. 3 92203 Vrbové Slovakia	Phone : +420 378 051 400 Fax : +420 378 051 401 E-mail sales : sales.sksk@semikron.com E-mail jobs : job.sksk@semikron.com www.semikron.com

Contact Europe

Online Shop	SEMIKRON Online Shop Global Direct Sales	
	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
Distributor	Slovenia	
	ALMA Electronic d.o.o. Leskoscova Cesta 6 1000 Ljubljana Slovenia	Phone : +386 1 256 1381 Fax : +386 12 256 3870 E-mail : prodaja@almaelectronic.com
Main site	Spain	
	SEMIKRON ELECTRONICS S.L.U. C/ de la Ciencia, 35, Nave 3 8850 Gavá Spain	Phone : +34 936 335 890 Fax : +34 936 333 065 E-mail sales : sales.ske@semikron.com E-mail jobs : jobs.ske@semikron.com www.semikron.com
Main site	Sweden	
	SEMIKRON OY Taivaltie 5 01610 Vantaa Finland	Phone : +358 103 217 950 Fax : +358 9870 1308 E-mail sales : sales.skfin@semikron.com E-mail jobs : jobs.skse@semikron.com www.semikron.com
Main site	Switzerland	
	SEMIKRON AG Rugenparkstrasse 7 3800 Interlaken Switzerland	Phone : +41 449 141 333 Fax : +41 449 141 330 E-mail sales : sales.skch@semikron.com E-mail jobs : sales.skch@semikron.com www.semikron.com
Main site	Turkey	
	SEMIKRON Esentepe Mah. Milangaz cad. no.77, Dumankaya Vizyon Rezidans, A1-Blok Daire 46 34870 Kartal/Istanbul Turkey	Phone : +90 216 5115 046 Phone alternative : +90 532 5088 500 Fax : +90 216 5115 846 E-mail : halim.ozmen@semikron.com www.semikron.com
Distributor	ELSE ELEKTRIK MAKINA SANAYI VE TICARET A.S. Cihangir Mah. Kargaci Sok. No:5, Avcılar TR-34310 Istanbul Turkey	Phone : +90 212 422 6670 Fax : +90 212 422 6679 E-mail : aysekocak@else.com.tr
Distributor	Ukraine	
	TECHNOSERVICEDRIVE LTD. Peremogy ave 56, of.335 03057 Kiev Ukraine	Phone : +380 44 366 2462 Phone alternative : +380 44 458 4766 E-mail : tsdrive@ukr.net www.semismart.com.ua
Distributor	INCOMTECH-PROJECT LTD. Hertsenastr. 17-25, Office # 9 04050 Kiev Ukraine	Phone : +380 44 230 0181 Phone alternative : +380 44 230 0186 E-mail : semikron@i-p.net.ua www.i-p.com.ua
Main site	United Kingdom	
	SEMIKRON Ltd. 9 Harforde Court, John Tate Road, Foxholes Business Park SG13 7NW Hertford United Kingdom	Phone : +44 199 2584 677 Fax : +44 199 2503 837 E-mail sales : sales.skuk@semikron.com E-mail jobs : jobs.skuk@semikron.com www.semikron.com
Distributor	RS Components Ltd. Weldon Industrial Estate Birchington Road NN17 9RS Corby United Kingdom	Phone : +44 153 6201 201

Contact North America

Online Shop	SEMIKRON Online Shop Global Direct Sales	
	SEMIKRON Elektronik GmbH & Co. KG Sigmundstr. 200 90431 Nuremberg Germany	Phone : +49 911 6559 6663 Fax : +49 911 3091 9771 00 E-mail : sales@semikron.com shop.semikron.com
Main site	Canada	
	SEMIKRON Inc. 11 Executive Drive NH 03051 Hudson United States	Phone : +1 603 8838 102 Fax : +1 603 8838 021 E-mail : sales.skusa@semikron.com www.semikron.com
Main site	Mexico	
	SEMIKRON DE MEXICO S.A. de C.V. Ave Morelos No. 28, Col. Parque Industrial Naucalpan de Juárez C.P. 53470 Estado de México Mexico	Phone : +52 555 3001 151 Phone alternative : +52 555 3007 922 Fax : +52 555 3000 364 E-mail sales : sales.skmex@semikron.com www.semikron.com
Main site	United States	
	SEMIKRON Inc. 11 Executive Drive NH 03051 Hudson United States	Phone : +1 603 8838 102 Fax : +1 603 8838 021 E-mail sales : sales.skusa@semikron.com E-mail jobs : jobs.skusa@semikron.com www.semikron.com
Technical Offices	NORTH EAST USA / Eastern Canada (ME, NH, VT, MA, CT, RI, NJ, DE, EASTERN MD, EASTERN NY, EASTERN PA, CANADA: QUEBEC PROVINCE) SEMIKRON, Regional Sales Office Tom Rantala United States	Phone : +1 603 8838 773 Phone alternative : +1 603 9307 834 Fax : +1 603 8838 021 E-mail : tom.rantala@semikron.com www.semikron.com
Technical Offices	CENTRAL USA (IL, MN, WI, ND, SD, NE, IA, MO, JOHN, DEERE[OLD PHOENIX INT'L], ROCKWELL) SEMIKRON, Regional Sales Office Robert Falk United States	Phone : +1 262 4704 242 Phone alternative : +1 603 8839 051 Fax : +1 603 8838 021 E-mail : robert.falk@semikron.com www.semikron.com
Technical Offices	WESTERN USA (UT, WY, ID, MT, NV, AZ, CA, WA, OR, CANADA: BRITISH COLUMBIA, ALBERTA, MANITOBA, SASKATCHEWAN) SEMIKRON, Regional Sales Office Kevin Monohan United States	Phone : +1 425 7375 060 Phone alternative : +1 425 6368 025 Fax : +1 603 8838 021 E-mail : kevin.monohan@semikron.com www.semikron.com
Technical Offices	MIDWEST USA (MI, IN, OH, KY, W.VA, ONTARIO CANADA, WESTERN NY, WESTERN MD, WESTERN PA, TN, V, NC) SEMIKRON, Regional Sales Office Andy Camardo United States	Phone : +1 603 8839 096 Phone alternative : +1 216 4968 580 E-mail : andy.camardo@semikron.com www.semikron.com
Technical Offices	SOUTH USA (TX, OK, AR, LA, KS, NM, CO, MEXICO, MS, AL, GA, FL, SC) SEMIKRON, Regional Sales Office Emiliano Meza United States	Phone : +1 940 231 3491 Phone alternative : +1 603 883 1533 Fax : +1 603 8838 021 E-mail : emiliano.meza@semikron.com www.semikron.com
Distributor	Richardson RFPD 1950 S. Batavia Avenue, Suite 100 60134 Geneva United States	Phone : +1 630 208 2437 E-mail : kjohnson@rell.com

Contact South America

SEMIKRON Online Shop
Global Direct Sales

Online Shop	SEMIKRON Semicondutores Ltda. Av. Inocência Seráfico, 6300 06366-900 Carapicuíba - São Paulo Brazil	Phone : +55 11 4186 9500 Fax : +55 11 4186 3567 E-mail : SKBR-Sales@semikron.com shop.semikron.com
-------------	---	---

Argentina

Distributor	DINATECNICA S.A Blanco Encalada 35, Villa Martelli 1603 - Buenos Aires Argentina	Phone: + 54 11 4709-0069 Fax: + 54 11 5181-8273 E-mail: ftallarico@dinatecnica.com.ar
-------------	--	---

Brazil

Main site	SEMIKRON Semicondutores Ltda. Av. Inocência Seráfico, 6300 06366-900 Carapicuíba - São Paulo Brazil	Phone : +55 11 4186 9500 Fax : +55 11 4186 3567 E-mail sales : SKBR-Sales@semikron.com www.semikron.com
-----------	---	--

Chile

Main site	SEMIKRON Semicondutores Ltda. Av. Inocência Seráfico, 6300 06366-900 Carapicuíba - São Paulo Brazil	Phone : +55 11 4186 9500 Fax : +55 11 4186 3567 E-mail sales : SKBR-Sales@semikron.com www.semikron.com
-----------	---	--

Colombia

Distributor	SEMIKRON Semicondutores Ltda. Av. Inocência Seráfico, 6300 06366-900 Carapicuíba - São Paulo Brazil	Phone : +55 11 4186 9500 Fax : +55 11 4186 3567 E-mail sales : SKBR-Sales@semikron.com www.semikron.com
-------------	---	--

Ecuador

Main site	SEMIKRON Semicondutores Ltda. Av. Inocência Seráfico, 6300 06366-900 Carapicuíba - São Paulo Brazil	Phone : +55 11 4186 9500 Fax : +55 11 4186 3567 E-mail : SKBR-Sales@semikron.com shop.semikron.com
-----------	---	---

Peru

Distributor	SEMIKRON Semicondutores Ltda. Av. Inocência Seráfico, 6300 06366-900 Carapicuíba - São Paulo Brazil	Phone : +55 11 4186 9500 Fax : +55 11 4186 3567 E-mail : SKBR-Sales@semikron.com shop.semikron.com
-------------	---	---

Uruguay

Distributor	SEMIKRON Semicondutores Ltda. Av. Inocência Seráfico, 6300 06366-900 Carapicuíba - São Paulo Brazil	Phone : +55 11 4186 9500 Fax : +55 11 4186 3567 E-mail : SKBR-Sales@semikron.com shop.semikron.com
-------------	---	---

Venezuela

Main site	SEMIKRON Semicondutores Ltda. Av. Inocência Seráfico, 6300 06366-900 Carapicuíba - São Paulo Brazil	Phone : +55 11 4186 9500 Fax : +55 11 4186 3567 E-mail : SKBR-Sales@semikron.com shop.semikron.com
-----------	---	---

Welcome to the World
of Power Electronics



Image film and further information
on a wide range of products
www.semikron.com/video/image

Note

All data and information referred to in this data book are based on the best of our knowledge and state-of-the-art technology available at the time of printing and are intended to be used for information purposes only. Component specifications are not to be considered a guarantee of component characteristics. The use of SEMIKRON products in life-support appliances and systems is subject to prior specification and written approval by SEMIKRON. All product specifications and terms of delivery are subject to change. For updates of our datasheets as well as information on our latest products, please refer to www.semikron.com. Sales and delivery of SEMIKRON products are subject to our "General Terms and Conditions of Sale". Please refer to www.semikron.com for applicable power semiconductor standards. Reproduction permission may be granted on request on condition that the source is cited. Modifications to any and all data published by SEMIKRON are expressly prohibited. All product specifications and promotion statements apply to SEMIKRON International GmbH and all SEMIKRON companies within the SEMIKRON group.

For reasons of readability, separate gender-specific nouns are not used in the text.
The text nonetheless always refers to all genders.

Printed in Germany © by SEMIKRON International GmbH, 05/2019
man Weishart Photography; additional: Stockfotos from fotolia, istockfoto, shutterstock and getty images.



We are close to our customers

www.semikron.com/contact



shop.semikron.com



www.youtube.com/c/semikron



de.linkedin.com/company/semikron

SEMIKRON INTERNATIONAL GmbH

Sigmundstrasse 200
90431 Nuremberg, Germany
Tel: +49 911 6559 6663
Fax: +49 911 6559 262
sales@semikron.com

www.semikron.com
shop.semikron.com



< BACK TO COVER

Interactive Surfaces for Document Navigation

1. Basic marks
2. Chapter marks
3. Content
4. Turn the page

Link to the SEMIKRON Homepage

5. Web-addresses
6. Online-shop icon 

